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Microcircuit Device Reliability

MEMORY/DIGITAL LSI

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Microcircuit Device Reliability

MEMORY/DIGITAL LSI

Winter 1981/82

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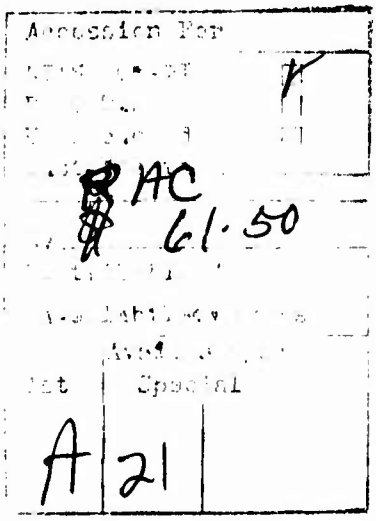

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This book contains data on memory and digital LSI device failure rates. The raw data is presented as well as a series of summaries designed to bring out the salient points. Where possible, graphical aids are used to depict the data. Comparison of predicted with observed failure rates is given, predictions being carried out to MIL-HDBK-217C. This book includes a new section on failure analysis results not included in previous editions.

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PREFACE

This is one of a series of annual data publications dealing with microcircuit reliability which includes hybrid, linear and interface, memory and LSI devices, as well as digital SSI/MSI components. Other volumes specifically treat discrete semiconductors (including optoelectronic and microwave) and nonelectronic components.

Each document contains analyzed reliability information in addition to the detailed presentation of field data and failure analysis results. This information aids in determining device fallout rates and the operational test and field reliability characteristics of devices. Life test results and their relationship to field experience as well as observed vs. MIL-HDBK-217C predicted failure rates can be reviewed. The relative risks of screening decisions may also be examined. Additionally, information is available to form the foundation for failure mode effects and criticality analyses (FMECA). Through the data presented, these publications are intended to actively complement such documents as MIL-STD-883B and MIL-HDBK-217C. The user is cautioned that the data contained herein may not be used in lieu of other contractually cited references.

The tables and graphs are printed directly from the Reliability Analysis Center's computerized data base using programs developed by the programming staff.

The authors were given valuable assistance by a number of RAC staff, including the following: Reduction and Summarization--Bernie Radigan, Don Rash and Mike Rossi; Data Collection--Irv Krulac and Jim Carey; Software--Ed Szwedo, Steve Kelly and Vi Winstanly; Computations--Tom Ballou; Typing, Technical Illustration, and Editing--Sue Ziankoski, Kimberly Strong, and Helen Downing.

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INTRODUCTION

This book provides failure data on memory and LSI microcircuits. The data for this publication was collected and reduced from government and industry reports by the Reliability Analysis Center (RAC). The purpose of this book is to present objective data in clear and unbiased format for widespread usage.

Section 1 describes the basic statistical methods used in evaluating the life and field data, which compose the tables and plots.

Section 2 contains field and life test data categorized by device function (e.g., RAM, ROM, etc.) and by technology (e.g., CMOS, TTL, etc.). A number of parameters defining the component and the application in which it was used are also listed. Comparisons between the observed failure rates and those predicted by MIL-HDBK-217C are also given, both numerically and graphically.

Section 3 contains the detailed information from which Section 2 was derived, listed by device function, manufacturer and by alphanumeric part number.

The final two sections (4 and 5) are concerned with the failure event record structure and the summarization of failure analysis results. The failure event records contain detailed information on specific devices whose failures have been verified and on which failure analysis has been performed. Each failure event record reveals the particular device and test characteristics, as well as associated stress values and other failure information (failure mode, failure defect cause, etc.). These detailed records are then summarized to obtain failure distributions which reveal the nature of failure trends by operation type. The distribution summaries form the basis of Section 4, while the detailed records from which they were derived are included in Section 5.

The data in this book can be used in part selection and in failure rate estimation. Analysis of the data provides information about the relative effect of various factors on reliability. Thus the relative merits of design alternatives in terms of reliability may be evaluated and quantified.

Additional information not contained in this book may be obtained by contacting the Reliability Analysis Center directly.

The field data reported in this book are provided to enhance but not replace the information contained in MIL-HDBK-217C. **As with other RAC publications, the data should not be used in lieu of other contractually cited references and specifications.**

MICROCIRCUIT DEVICE RELIABILITY
MEMORY/DIGITAL LSI DATA

Section 1

STATISTICAL TECHNIQUES

STATISTICAL TECHNIQUES

The objective of this databook is to present failure data in clear and unbiased format. Basic statistical estimation and inference is used to obtain estimates of failure rates and to construct confidence intervals; these methods are described below. The graphical format used in comparing observations to predictions is also described.

Point Estimate of the Failure Rate

In order to properly estimate a failure rate it is necessary to include survival data with failure data. Thus every attempt is made to secure such information on operating time for components which have not failed as well as the times to failure (TTF) for those components which did fail. In a life test this information is straightforward to obtain and is readily analyzed using estimation techniques applicable to censored data (Ref. 2). However, for field data, practical constraints make retrieval of survival data more difficult and much data has to be rejected for want of such information.

It is likely that a higher than desirable level of noise is inherent in the data summarized in this book, and this is caused by the physical problems of accurately assessing operational hours from flight logs, maintenance records and elapsed time indicators. This problem can be reduced by taking large enough samples of data and assessing the resultant variability. Thus, the point estimate of the failure rate should be expressed with some measure of its variability; this is detailed later.

The point estimate of the failure rate is given by the maximum likelihood estimator (MLE)

$$\hat{\lambda} = f/t$$

where

$\hat{\lambda}$ is the MLE

t is the total number of part hours including survival data

f is the number of failures observed in the sample

$\hat{\lambda}$ is expressed in terms of failures per million hours for convenience

Confidence Intervals on the Estimated Failure Rate

Any parameter estimated from data will be subject to sampling errors and therefore such an estimate may or may not equal the true population parameter. It is therefore of little use to derive an estimate without some measure of its confidence.

A confidence interval may be constructed about a parameter estimate derived from data. The confidence may be specified in advance. In this book, the confidence is set at 0.6 so that 60% confidence intervals are presented. The width of these intervals depends on the test time and the number of failures observed.

In order to derive confidence intervals, the distribution of the data must be determined or at least assumed. The exponential distribution of time to failure is assumed, and under this assumption it may be shown (e.g., Ref. 1) that the following identities apply. (Certain assumptions are made as to the censoring of the data.)

$$\lambda^* = \frac{\chi_2^2\,(f+1),\ \alpha/2}{2t}$$

$$\lambda_{**} = \frac{\chi^2 2f,\ 1-\alpha/2}{2t}$$

where

λ^* is the upper confidence limit

λ_{**} is the lower confidence limit

and where

- f is the number of failures observed
- t is the total number of part hours in which the failures occured
- $\chi^2_{a,b}$ is the chi-squared statistic which may be evaluated from tables with "a" degrees of freedom at the "b^{th}" percentile
- $1-\alpha$ is the confidence (so 100 $(1-\alpha)$% is the confidence expressed as a percentage)

Thus, $(\lambda_{**}, \lambda^*)$ is a 100 $(1-\alpha)$% confidence interval for the estimated failure rate λ under the stated assumptions.

Some records may consist of only survival data; that is, no failures occurred. In such cases, where there are enough test hours (>5 x 10^5) the upper confidence limit on the failure rate is included in the summary tables.

The intervals given in the tables contained in this book are computer generated using a numerical approximation of the above formula. For $f > 30$ the error induced by the approximation is negligible. As f becomes smaller, the error may tend to show in the third significant figure.

The Exponential Assumption

The most popular probability density function in reliability theory is the exponential distribution given by $f(t) = \lambda e^{-\lambda t}$ where λ is the failure rate and t is time in part hours (which may or may not be real time). The reason this distribution is so often used is due to its mathematical simplicity and the fact that in many cases it is found valid for physical reasons.

For microelectronics, after burn-in and screening, a constant or decreasing hazard rate model would appear to be the most likely contender.

Empirically, it is difficult to fit a model because of shortages of data in each category and because in many cases there is more than one failure in a record (that is, the time of each individual failure is not always known although information in the form of "f failure in t part hours" is available). Some work has been done on the goodness of fit of the exponential model for data of this type and is reported in Reference 3. In summary, the exponential hypothesis is not rejected by sample data sets presented in this book although it has not been possible to adequately check all the data.

Residual Plot

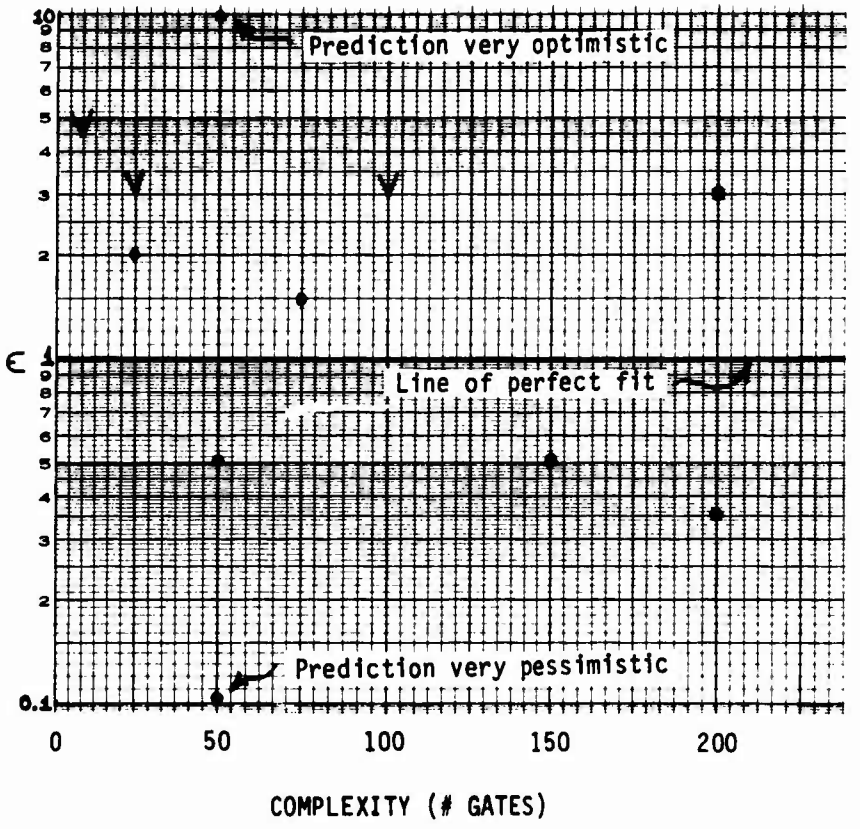
In order to present a comparison of observed failure rates to those predicted by MIL-HDBK-217C, a graphical method is used. A residual plot is convenient; that is, the residual error left in the data after the (prediction) model has been fitted. Since the MIL-HDBK-217C model is multiplicative and since errors are magnitude-dependent, a transformation is first necessary. A suitable transformation which gives normally distributed residuals is given by:

$$\epsilon = \log_{10} (\lambda_o/\lambda_p)$$

where

λ_o is the observed failure rate
λ_p is the predicted failure rate
ϵ is the residual

Values of ϵ are then plotted against some independent variable as in Figure 1. The residual plots then show both the performance of the MIL-HDBK-217C model with the data presented and also the overall variability in the data. It should be noted that the plotted points in many cases represent more than one failure and hence will be less than the variability of the TTF data by a factor of $\sqrt{n}$ (where n is the number



Graph of $\in$ against complexity for hypothetical data.

$$\in = \frac{\text{Observed failure rate}}{\text{Predicted failure rate}}$$ and is

plotted on a logarithmic scale.

"V" represents an upper confidence limit (60%) from data for which there were no failures.

FIGURE 1: EXAMPLE OF A RESIDUAL RATIO PLOT WITH COMPLEXITY AS INDEPENDENT VARIABLE

of failures per point). Some "funnelling" in Figure 17 shows this, although there is a fair amount of noise. Note that the perfect model fit is at $\epsilon = 1$.

Figure 1 is an example of a residual plot. The rest of the plots are computer generated and are identical in format to the example (though they have no grid lines).

The figures are arranged according to the following table.

Figure No.	Data Shown	Independent Variable
2	RAMs	Complexity
3	Microprocessors	
4	Shift Registers	
5	RAMs	Screen Class
6	Microprocessors	
7	Shift Registers	
8	RAMs	Application Environment
9	Microprocessors	
10	Shift Register	
11	RAMs	Number of Failures Per Record
12	Microprocessors	
13	Shift Registers	
14	All memories (i.e., RAMS, ROMs, PROMS, EPROMs, etc.)	Complexity
15		Screen Class
16		Application Environment
17		Number of Failures Per Record

Clearly there is some bias in certain plots which may be due to inadequacies of MIL-HDBK-217C or to sampling bias.

Other conclusions from the plots may be drawn as needed and are self-explanatory.

MICROCIRCUIT DEVICE RELIABILITY
MEMORY/DIGITAL LSI DATA

Section 2

MEMORY/DIGITAL LSI SUMMARIZED DATA

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Field Data

The following tables of field data are summarized from Section 3, Detailed Listings. Table 1 is a generic summary of Tables 2 through 6.

The data was collected from both military and commercial sources and consists of part level failure information from equipments operating under a variety of different environments.

The sample of data collected is not a truly random sample because more data is available in certain groups than others. For example, there is more data from the Ground, Fixed and Ground, Benign environments (computer rooms, offices and factories) than any others. Care should be exercised in any analysis of the data to acknowledge such inherent bias. The sample bias will also of course apply to a number of other factors such as screen level and temperature which may or may not be correlated with environment.

Minimum qualification for data used in estimation of failure rate and/or confidence intervals is set by the following guidelines:

1. 0 failures with at least 500,000 accumulated device hours
   1 failure with at least 250,000 accumulated device hours
   2 failures with at least 125,000 accumulated device hours

2. The device must have had an applied power/voltage stress.

TABLE 1: LSI-MEMORY GENERIC FIELD DATA

DEVICE TYPE	TECHNOLOGY	DEVICE HOURS	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
ROM	BIPOLAR	5.42E+ 7	4	.04	.07	.12
	MOS	4.91E+ 8	248	.48	.51	.53
RAM	BIPOLAR	1.97E+ 9	307	.15	.16	.16
	MOS	4.20E+ 9	1449	.34	.34	.35
PROM	BIPOLAR	8.85E+ 8	572	.62	.65	.67
	MOS	4.66E+ 6	1	.04	.21	.65
MICRO PROCESSOR	MOS	2.90E+ 8	188	.61	.65	.69

TABLE 2 : RANDOM ACCESS MEMORY (RAM) FIELD TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
16	ECL	GBC	D-1	PDIP	2.98E+ 7	[2]	3	.05	.10	.19
	TTL	GT	B-1	HDIP	1.44E+ 6	[3]	0	-*-	-*-	1.15
64	CMOS	GBC	D-1	PDIP	7.16E+ 6	[4]	1	.03	.14	.42
	TTL	GT	B-1	HDIP	9.44E+ 5	[5]	0	-*-	-*-	1.75
		GBC	D-1	PDIP	1.52E+ 8	[6]	38	.22	.25	.29
		AUF	B-1	HFPK	6.27E+ 5	[7]	0	-*-	-*-	2.64
		AUF	B-1	HDIP	1.04E+ 6	[8]	0	-*-	-*-	1.59
	STTL	NS	S-2	HDIP	1.41E+ 6	[9]	0	-*-	-*-	1.17
		GBC	D-1	PDIP	9.97E+ 7	[10]	34	.29	.34	.40
	LTTL	GBC	D-1	PDIP	1.16E+ 6	[11]	3	1.33	2.60	4.81
256	ECL	GBC	D	HDIP	5.50E+ 7	[12]	8	.10	.15	.21
	STAT-PMOS	NSS	B-1	HDIP	2.60E+ 6	[13]	0	-*-	-*-	.64
		GT	B-1	HDIP	7.22E+ 5	[14]	0	-*-	-*-	2.29
	STTL	GF	B-1	HDIP	8.67E+ 5	[15]	0	-*-	-*-	1.91
		GBC	D	HDIP	1.77E+ 6	[16]	6	2.21	3.39	5.14
1 K	CMOS	GF	D	HDIP	8.33E+ 5	[17]	0	-*-	-*-	1.99
	DYN-PMOS	GT	B-1	HDIP	1.22E+ 6	[18]	0	-*-	-*-	1.36
		GBC	D	HDIP	3.00E+ 7	[19]	10	.24	.33	.46
	STAT-NMOS	GF	D-1	PDIP	4.48E+ 6	[20]	4	.51	.89	1.51
		GBC	D-1	PDIP	1.50E+ 8	[21]	2	<.015	<.015	.03
		GBC	X	PDIP	1.69E+ 7	[22]	7	.28	.41	.61
4 K	DYN-NMOS	GF	D	PDIP	1.08E+ 7	[23]	1	.02	.09	.28
		GF	D	HDIP	4.09E+ 7	[24]	21	.42	.51	.63
		GF	D-1	PDIP	9.61E+ 6	[25]	2	.08	.21	.45
		GBC	D	HDIP	9.77E+ 8	[26]	242	.23	.25	.26
		GBC	X	PDIP	9.26E+ 6	[27]	4	.25	.43	.73
		GBC	X	HDIP	2.18E+ 9	[28]	940	.42	.43	.44
	STAT-NMOS	GP	X	PDIP	8.54E+ 7	[29]	594	6.71	6.95	7.20
16 K	DYN-NMOS	GF	D	HDIP	1.90E+ 6	[30]	0	-*-	-*-	.87
		GBC	D	HDIP	1.71E+ 8	[31]	38	.19	.22	.26

TABLE 3 : PROGRAMMABLE READ ONLY MEMORY (PROM) FIELD TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
256	ECL	GBC	D	HDIP	4.52E+ 5		0	-*-	-*-	-*-
512	TTL	AIU	C-1	HFPK	4.51E+ 5		0	-*-	-*-	-*-
		AUF	C-1	HFPK	1.53E+ 6	[32]	0	-*-	-*-	1.08
1 K	STTL	GBC	D-1	PDIP	6.99E+ 5	[33]	0	-*-	-*-	2.37
2 K	PMOS (UV)	GT	B-1	HDIP	8.27E+ 5	[34]	0	-*-	-*-	2.00
		GBC	D	HDIP	5.88E+ 5	[35]	0	-*-	-*-	2.82
4 K	STTL	AUT	B-1	HDIP	5.09E+ 5	[36]	0	-*-	-*-	3.25
8 K	NMOS (UV)	GBC	D	HDIP	2.80E+ 6	[37]	1	.07	.36	1.09

TABLE 4 : MICRO PROCESSOR FIELD TEST DATA

COMPLEXITY (GATES)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
759	DYN-PMOS	GF	D	HDIP	1.76E+ 7	[38]	14	.62	.80	1.03
1100	DYN-NMOS	GBC	D	HDIP	8.64E+ 6	[39]	4	.27	.46	.78
		GBC	D-1	PDIP	3.28E+ 7	[40]	38	1.00	1.16	1.35
1300	DYN-NMOS	GBC	D	HDIP	1.66E+ 7	[41]	13	.60	.78	1.03
		GBC	D-1	PDIP	5.65E+ 6	[42]	0	-*-	-*-	.29
2067	DYN-NMOS	GBC	D-1	PDIP	1.54E+ 7	[43]	11	.53	.71	.96
2833	DYN-NMOS	GBC	D-1	PDIP	6.46E+ 6	[44]	8	.86	1.24	1.77
3000	DYN-NMOS	GBC	D	HDIP	3.60E+ 6	[45]	5	.86	1.39	2.21
		GBC	D-1	PDIP	4.02E+ 6	[46]	7	1.18	1.74	2.56

TABLE 5: SHIFT REGISTERS FIELD TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
8	TTL	GBC	D-1	PDIP	7.28E+ 7	[47]	9	.09	.12	.17
12	LTTL	GBC	D-1	PDIP	3.77E+ 6	[48]	0	-*-	-*-	.44
16	TTL	AIU	C-1	HFPK	2.89E+ 6	[49]	0	-*-	-*-	.57
		GT	B-1	HDIP	7.64E+ 5	[50]	0	-*-	-*-	2.17
		GBC	D-1	PDIP	2.04E+ 7	[51]	0	-*-	-*-	.08
		AUF	C-1	HFPK	9.59E+ 6	[52]	10	.76	1.04	1.43
	LTTL	GBC	D-1	PDIP	1.27E+ 8	[53]	18	.11	.14	.18
128	DYN-PMOS	GF	B-1	HCAN	2.77E+ 6	[54]	0	-*-	-*-	.60
160	STAT-PMOS	GBC	D	HCAN	1.23E+ 6	[55]	0	-*-	-*-	1.35
200	DYN-PMOS	GBC	D	HCAN	2.98E+ 6	[56]	0	-*-	-*-	.56
1 K	DYN-PMOS	NSS	B-1	HCAN	1.43E+ 7	[57]	0	-*-	-*-	.12
		GB	D	HCAN	1.61E+ 8	[58]	47	.26	.29	.33
		GT	B-1	HCAN	5.00E+ 5		0	-*-	-*-	-*-
		GBC	D	HCAN	5.10E+ 6	[59]	2	.16	.39	.85
		GBC	D	HDIP	7.10E+ 6	[60]	0	-*-	-*-	.23
2 K	DYN-PMOS	AIT	D	HFPK	1.95E+ 6	[61]	26	11.12	13.35	16.06

TABLE 6 : PROGRAMABLE ARRAY FIELD TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
8	TTL	GBC	D-1	PDIP	2.58E+ 6	[62]	0	-*-	-*-	.64

Comparison with MIL-HDBK-217C Predictions

The field failure rates presented in the preceding tables are now compared to predictions using MIL-HDBK-217C (Reference 4).

Graphical comparisons are provided using the residual plotting method described in Residual Plot of Section 1.

Abbreviations

The following abbreviations are used in the tables in this book.

Operational Type

HTTL	High Speed, Transistor-Transistor Logic
LSTTL	Low Power Schottky, Transistor-Transistor Logic
STTL	Schottky, Transistor-Transistor Logic
LTTL	Low Power, Transistor-Transistor Logic
TTL	Transistor-Transistor Logic
ECL	Emitter Coupled Logic
IIL	Integrated Injection Logic
CMOS	Complementary, Metal Oxide Semiconductor
MNOS	Metal Nitride Oxide Semiconductor
NMOS	N-Channel, Metal Oxide Semiconductor
PMOS	P-Channel, Metal Oxide Semiconductor

Application Environment

AI	Airborne, Inhabited
AIF	Airborne, Inhabited, Fighter
AIT	Airborne, Inhabited, Transport
AU	Airborne, Uninhabited
AUF	Airborne, Uninhabited, Fighter
AUT	Airborne, Uninhabited, Transport

Applications Environment (Cont'd)

GB	Ground, Benign
GBC	Ground, Benign, Commercial (commercial environmentally controlled conditions)
GF	Ground, Fixed
GM	Ground, Mobile, Inhabited
GMU	Ground, Mobile, Uninhabited
GP	Ground, Portable (able to be hand carried)
GT	Ground, Transportable (carried by vehicle)
MGB	Missile, Ground, Benign
ML	Missile Launch and Flight
N.A.	Not Applicable (part level testing)
NS	Naval, Sheltered
NSS	Naval, Submarine Usage
NU	Naval, Unsheltered
SF	Space, Flight
SL	Satellite Launch
SPL	Spacecraft Launch and Flight

TABLE 7: LSI/MEMORY DEVICES OBSERVED AND MIL-HDBK-217C PREDICTED FAILURE RATES

DEVICE TYPE	REFERENCE NUMBER	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	FAILURE RATE (/10E+06 HOURS) POINT ESTIMATE	FAILURE RATE (/10E+06 HOURS) UPPER 80% LIMIT	MIL-HDBK-217C PREDICTED
ROM	1	-*-	-*-	1.51	3.89
RAM	2	.05	.10	.19	0.57
	3	-*-	-*-	1.15	0.09
	4	.03	.14	.42	0.73
	5	-*-	-*-	1.75	0.13
	6	.22	.25	.29	0.48
	7	-*-	-*-	2.64	0.22
	8	-*-	-*-	1.59	0.25
	9	-*-	-*-	1.17	0.03
	10	.29	.34	.40	0.51
	11	1.33	2.60	4.81	0.51
	12	.10	.15	.21	0.37
	13	-*-	-*-	.64	0.19
	14	-*-	-*-	2.29	0.18
	15	-*-	-*-	1.91	0.18
	16	2.21	3.39	5.14	0.40
	17	-*-	-*-	1.99	6.38
	18	-*-	-*-	1.36	0.23
	19	.24	.33	.46	0.34
	20	.51	.89	1.51	13.09
	21	<.015	<.015	.03	2.62
	22	.28	.41	.61	2.62
	23	.02	.09	.28	9.52
	24	.42	.51	.63	3.13
	25	.08	.21	.45	19.05
	26	.23	.25	.26	1.03
	27	.25	.43	.73	3.81
	28	.42	.43	.44	2.05
	29	6.71	6.95	7.20	67.67
	30	-*-	-*-	.87	6.50
	31	.19	.22	.26	2.57

TABLE 7: LSI/MEMORY DEVICES OBSERVED AND MIL-HDBK-217C PREDICTED FAILURE RATES (Cont'd)

DEVICE TYPE	REFERENCE NUMBER	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT	MIL-HDBK-217C PREDICTED
PROM	32	-*-	-*-	1.08	1.25
	33	-*-	-*-	2.37	0.40
	34	-*-	-*-	2.00	0.25
	35	-*-	-*-	2.82	0.38
	36	-*-	-*-	3.25	0.35
	37	.07	.36	1.09	1.07
MICRO PROCESSOR	38	.62	.80	1.03	0.92
	39	.27	.46	.78	0.82
	40	1.00	1.16	1.35	2.50
	41	.60	.78	1.03	0.84
	42	-*-	-*-	.29	2.61
	43	.53	.71	.96	4.47
	44	.86	1.24	1.77	4.98
	45	.86	1.39	2.21	1.20
	46	1.18	1.74	2.56	5.08
SHIFT REGISTERS	47	.09	.12	.17	0.61
	48	-*-	-*-	.44	0.86
	49	-*-	-*-	.57	0.62
	50	-*-	-*-	2.17	0.09
	51	-*-	-*-	.08	0.31
	52	.76	1.04	1.43	0.68
	53	.11	.14	.18	0.32
	54	-*-	-*-	.60	0.05
	55	-*-	-*-	1.35	0.15
	56	-*-	-*-	.56	0.12
	57	-*-	-*-	.12	0.27
	58	.26	.29	.33	0.35
	59	.16	.39	.85	0.35
	60	-*-	-*-	.23	0.42
	61	11.12	13.35	16.06	2.39
PROGRAMABLE ARRAY	62	-*-	-*-	.64	0.37

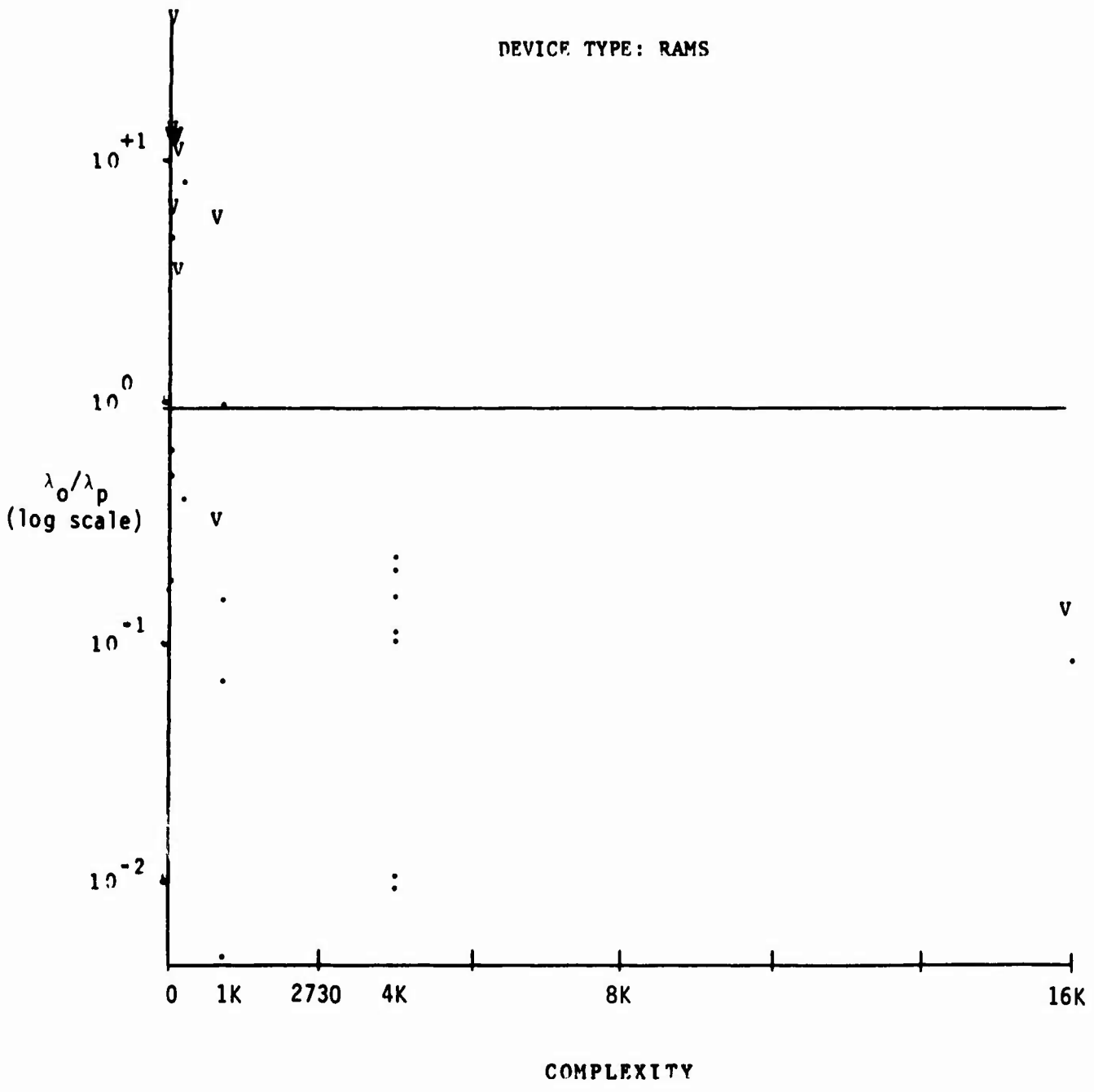


FIGURE 2: RATIO PLOT: RAMS

DEVICE TYPE: MICROPROCESSORS

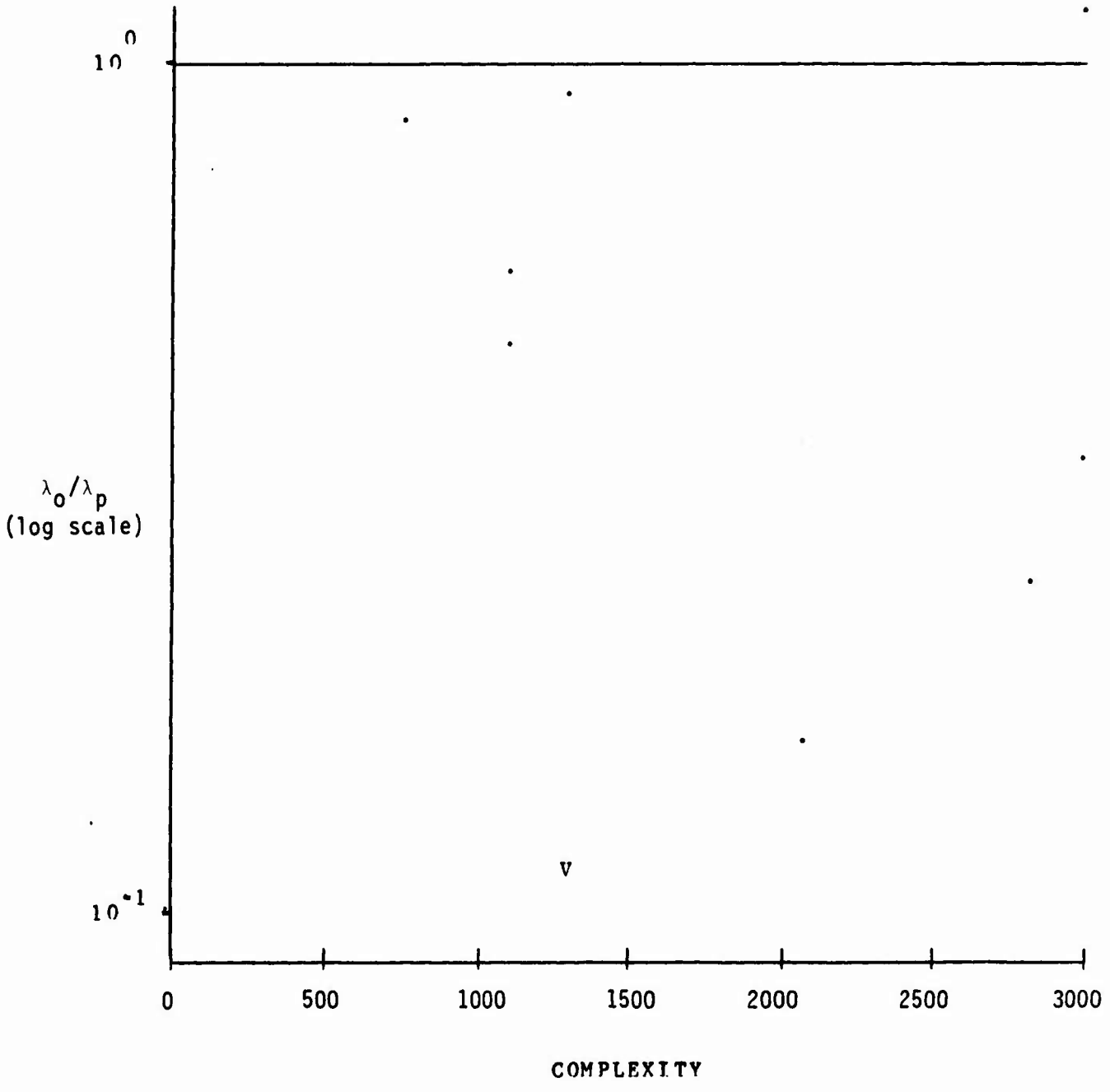


FIGURE 3: RATIO PLOT: MICROPROCESSORS

DEVICE TYPE: SHIFT REGISTERS

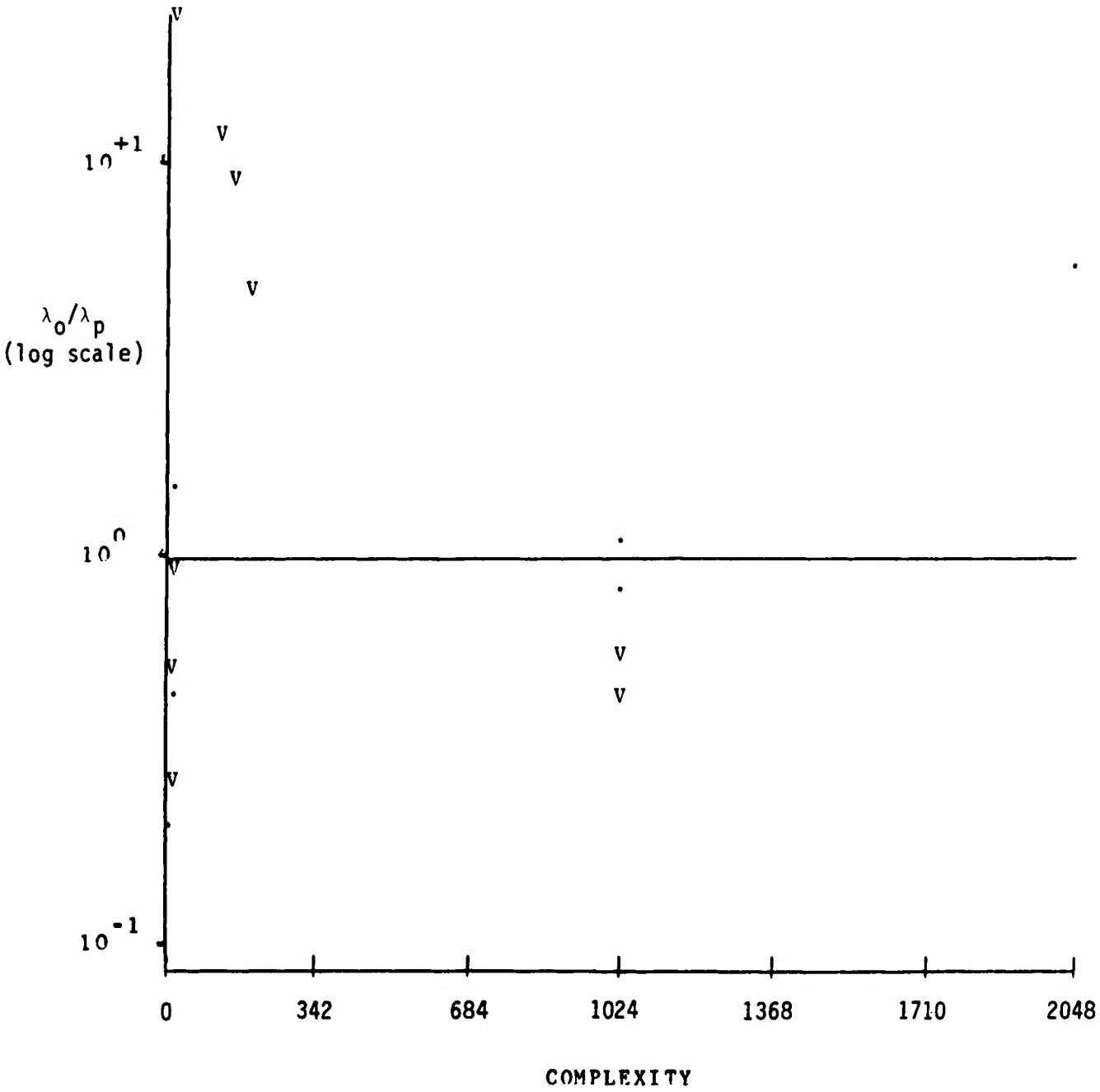


FIGURE 4: RATIO PLOT: SHIFT REGISTERS

DEVICE TYPE: RAMS

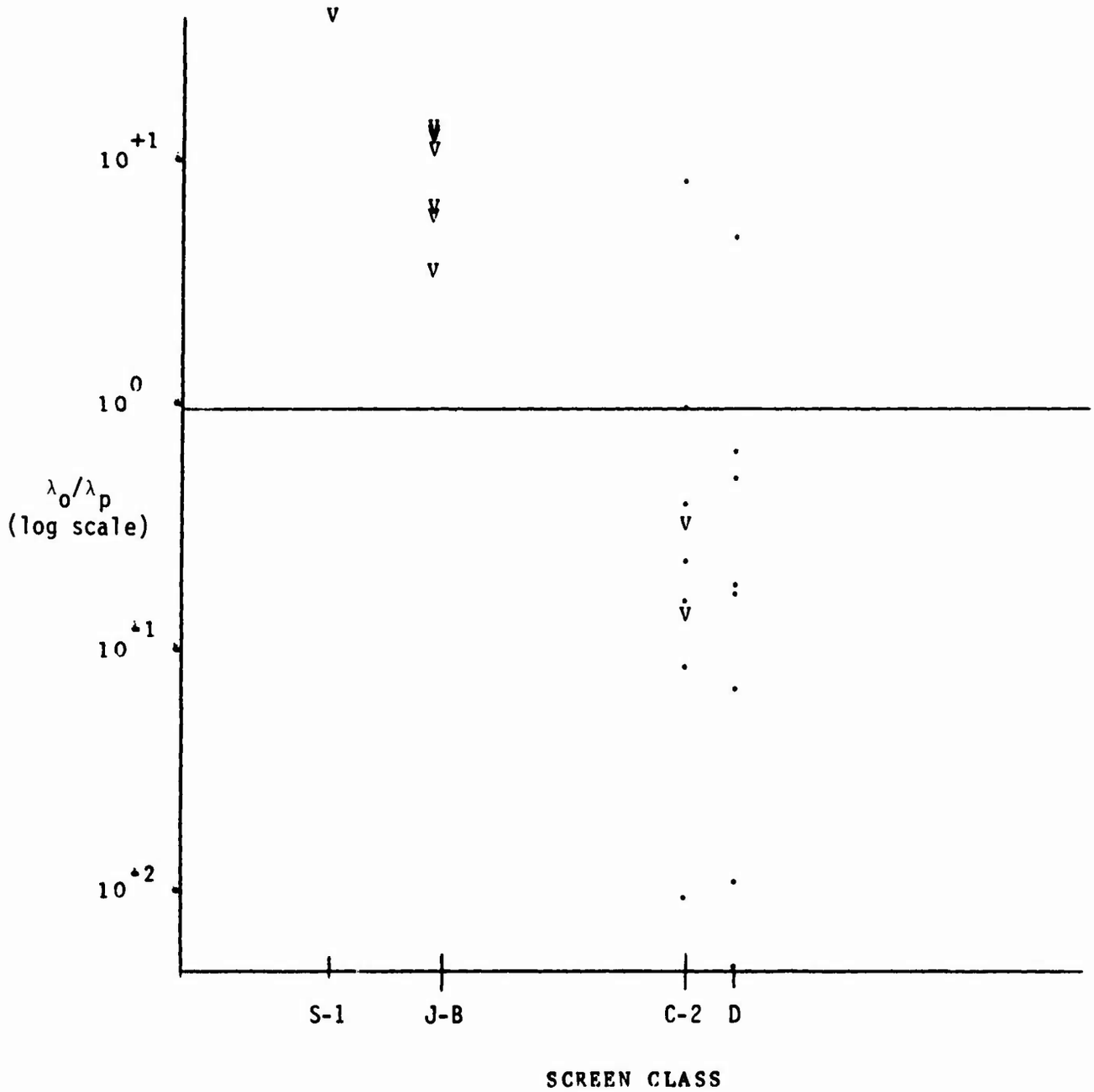


FIGURE 5: RATIO PLOT: RAMS

DEVICE TYPE: MICROPROCESSORS

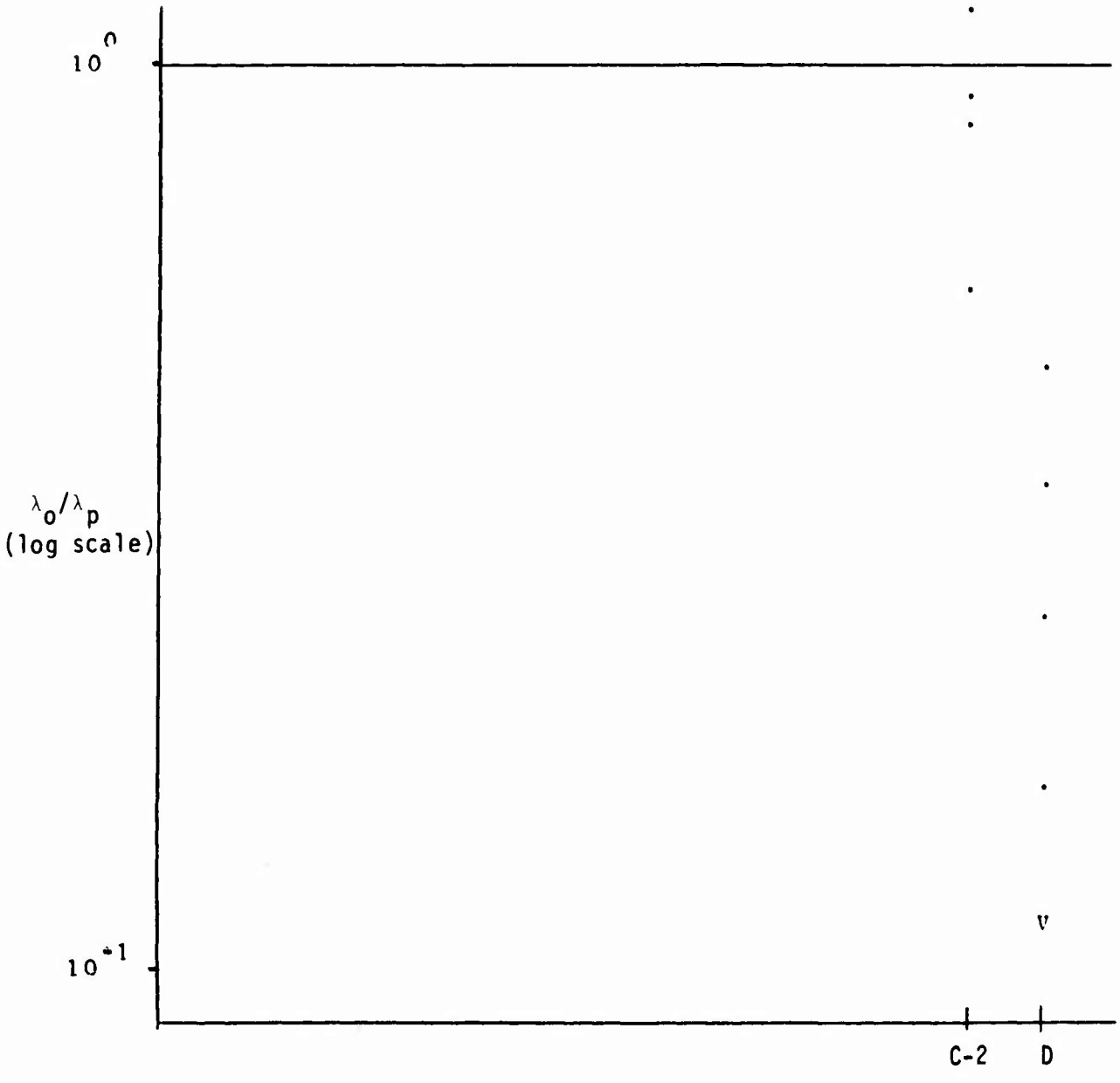


FIGURE 6: RATIO PLOT: MICROPROCESSORS

DEVICE TYPE: SHIFT REGISTERS

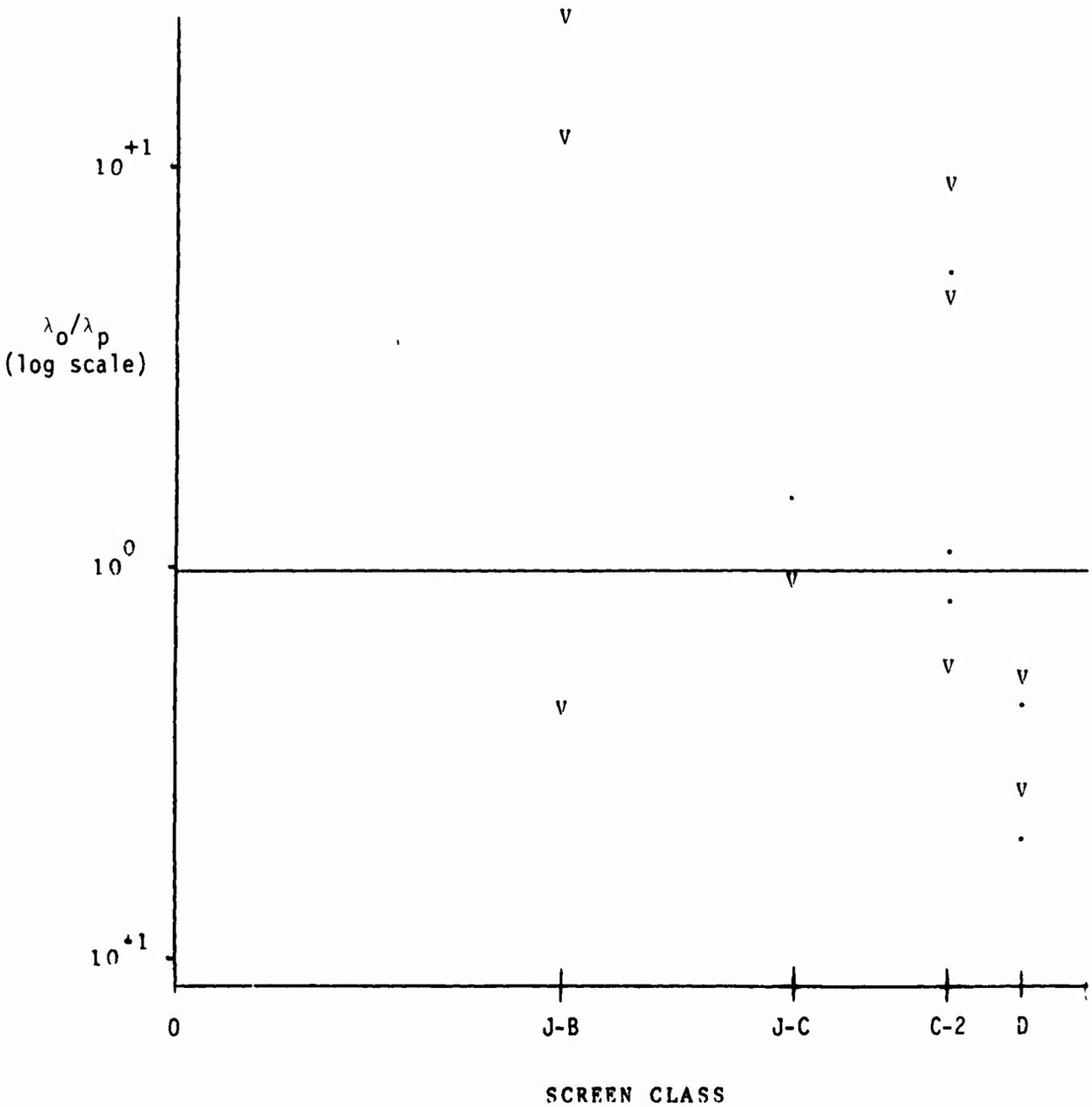


FIGURE 7: RATIO PLOT: SHIFT REGISTERS

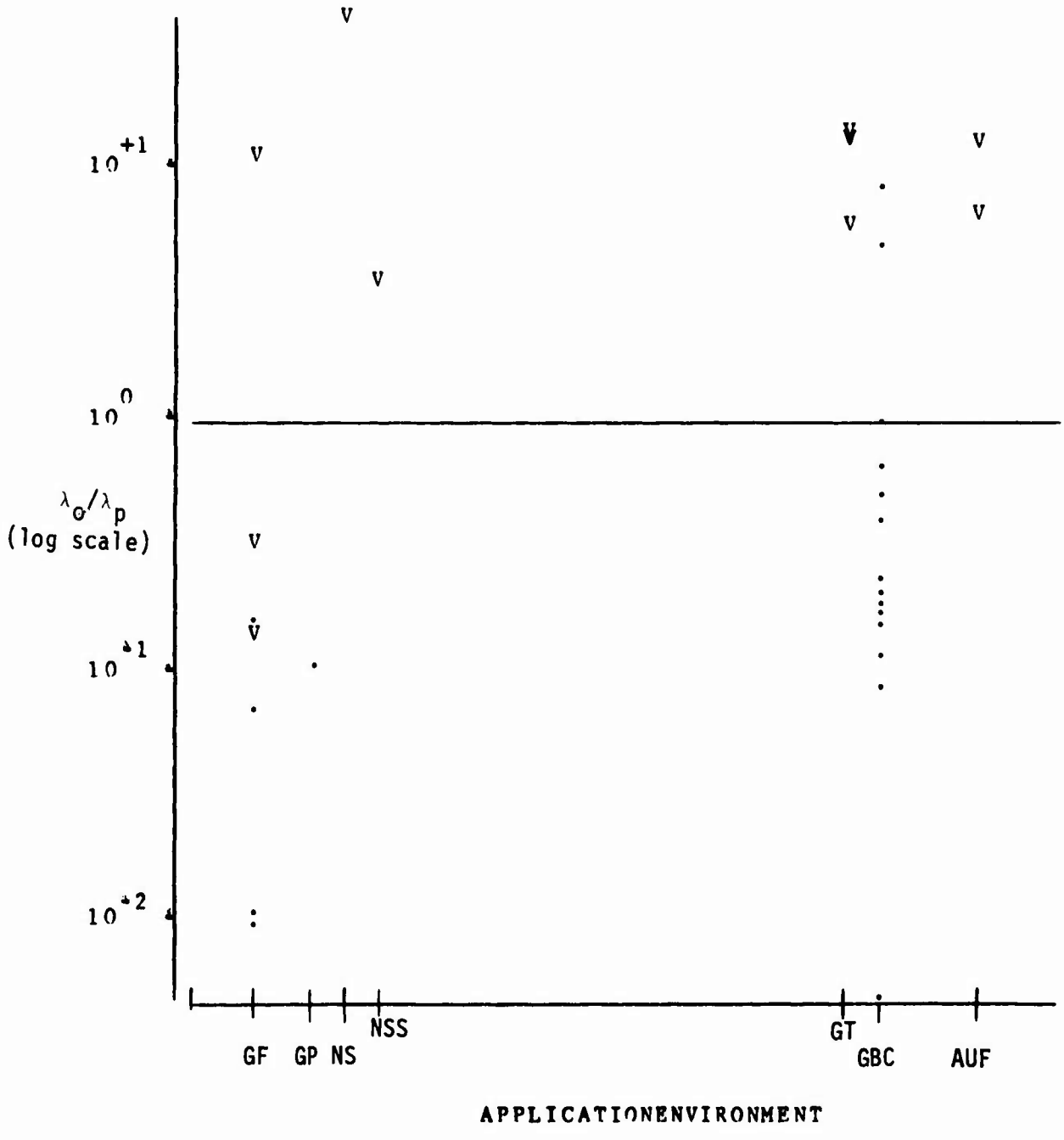


FIGURE 8: RATIO PLOT: RAMS

DEVICE TYPE: MICROPROCESSORS

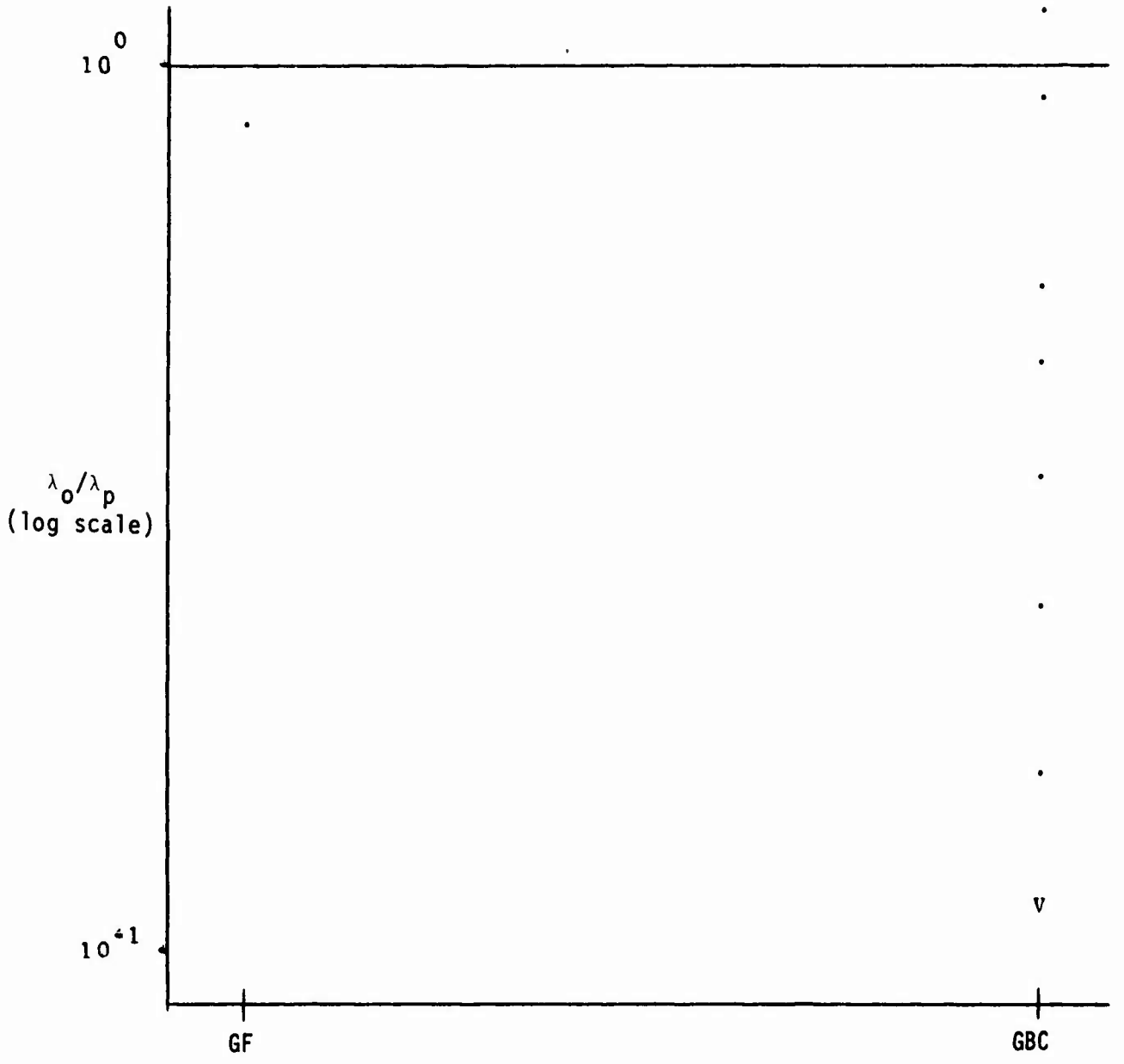


FIGURE 9: RATIO PLOT: MICROPROCESSORS

DEVICE TYPE: SHIFT REGISTERS

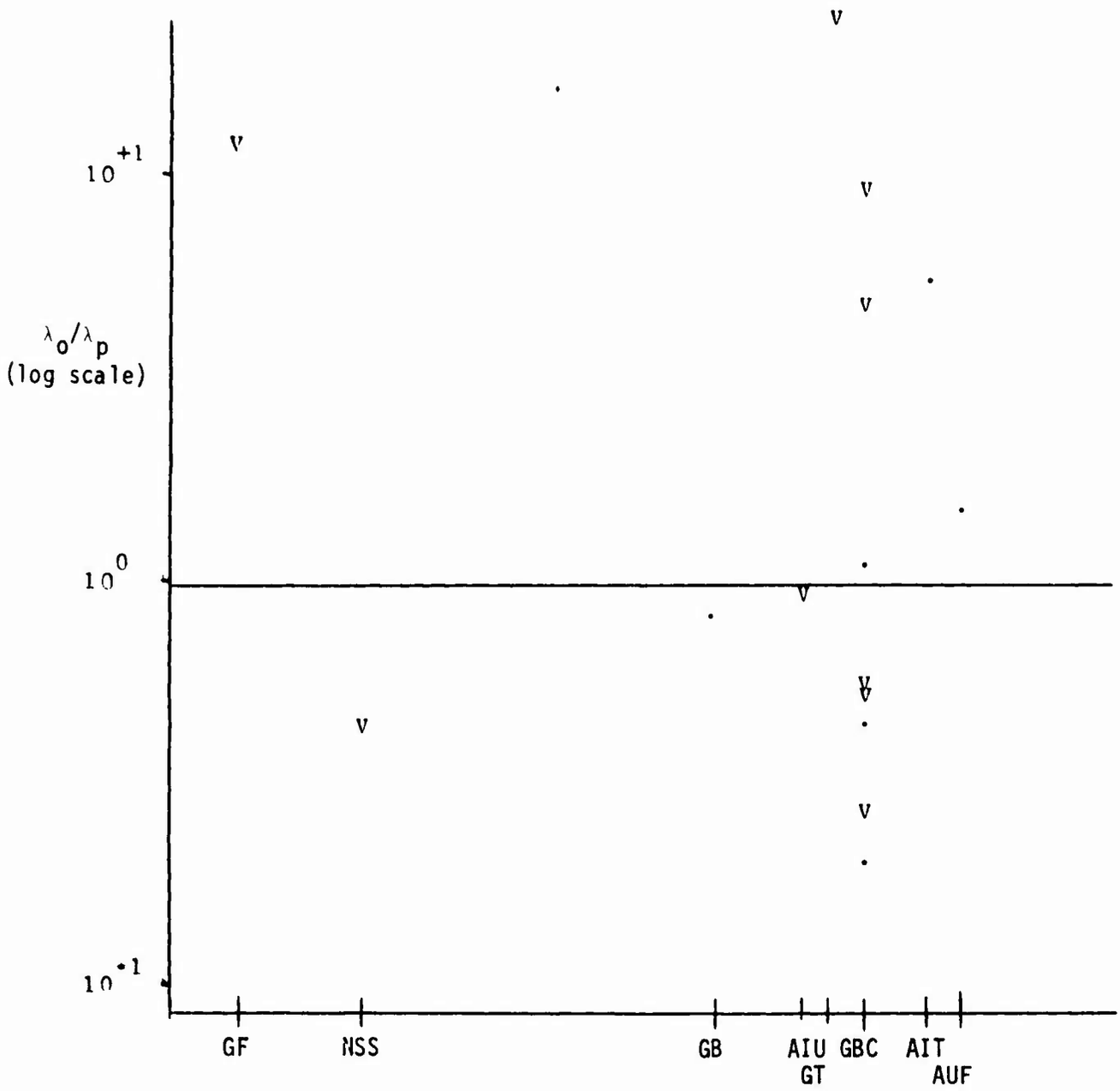


FIGURE 10: RATIO PLOT: SHIFT REGISTERS

DEVICE TYPE: RAMS

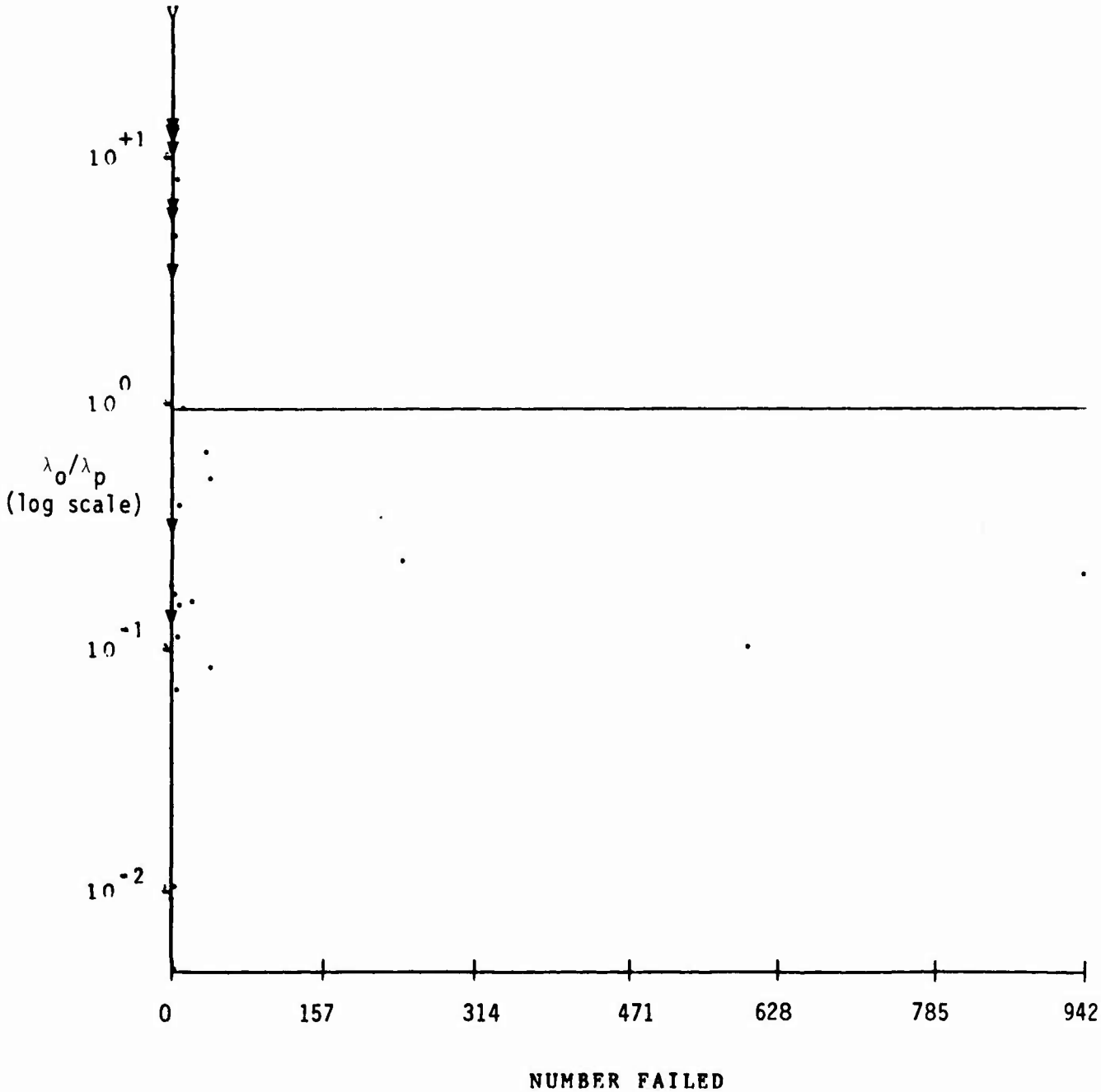


FIGURE 11: RATIO PLOT: RAMS

DEVICE TYPE: MICROPROCESSORS

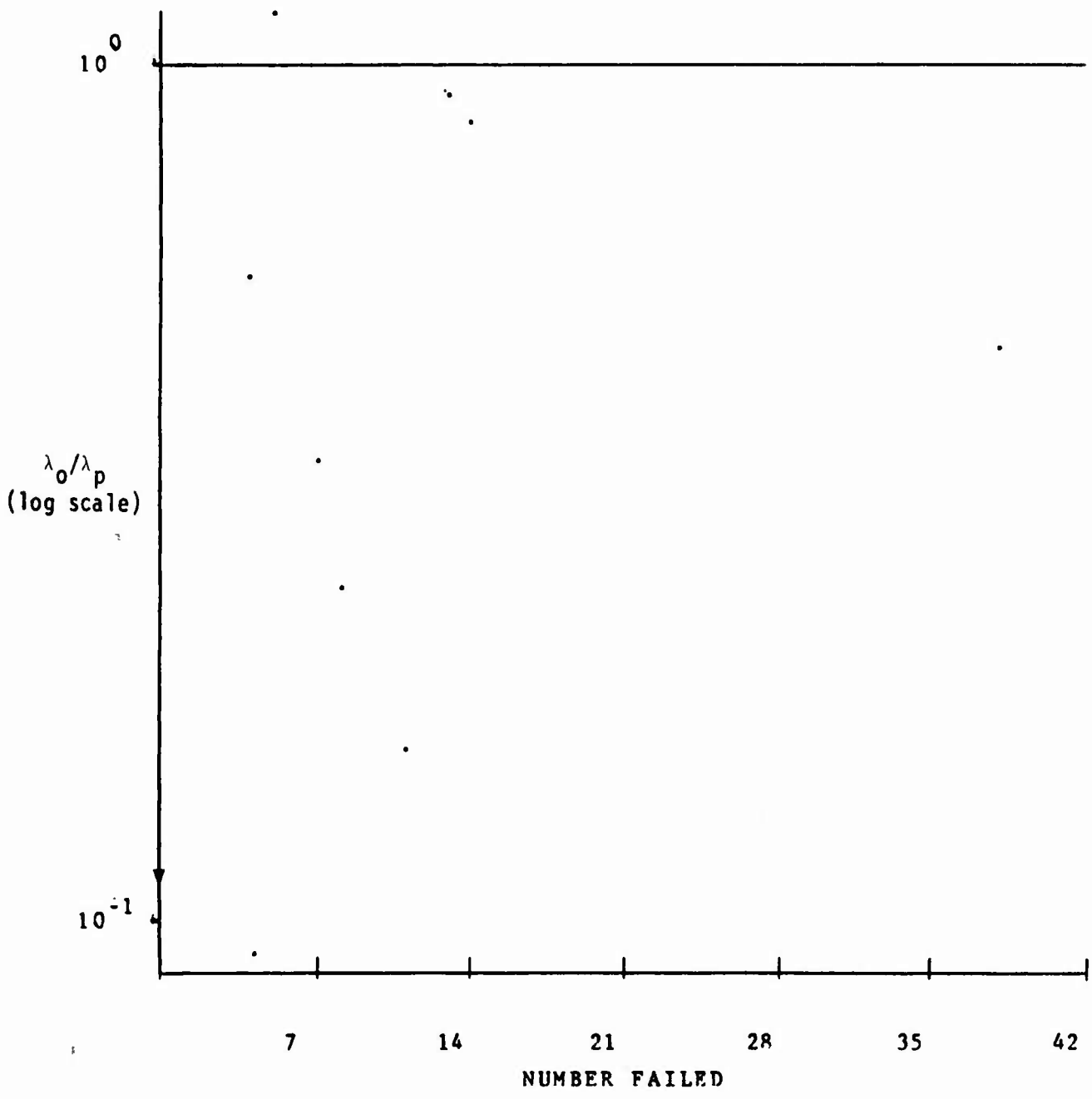


FIGURE 12: RATIO PLOT: MICROPROCESSORS

DEVICE TYPE: SHIFT REGISTERS

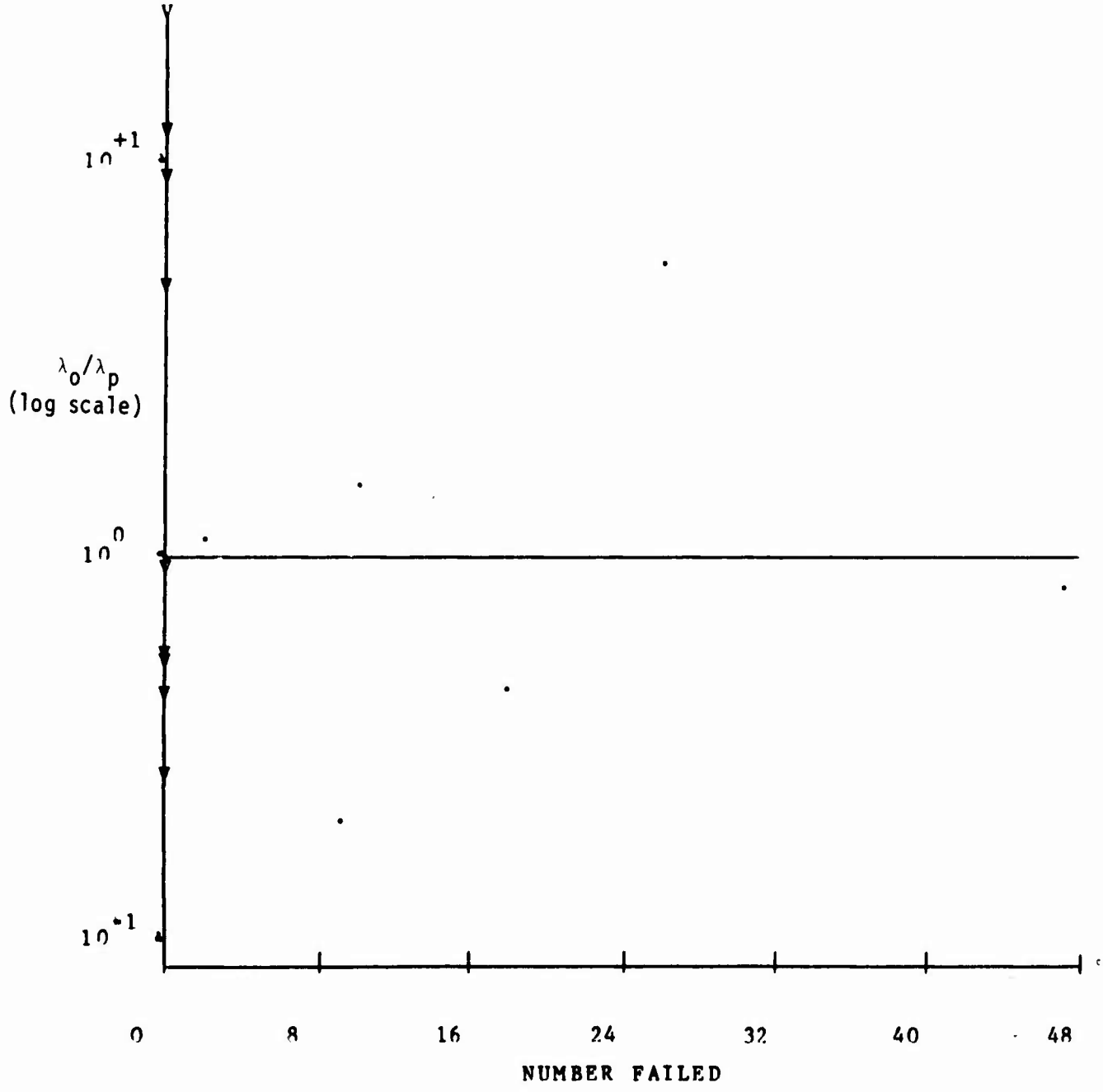


FIGURE 13: RATIO PLOT: SHIFT REGISTERS

FUNCTIONAL GROUP: MEMORY

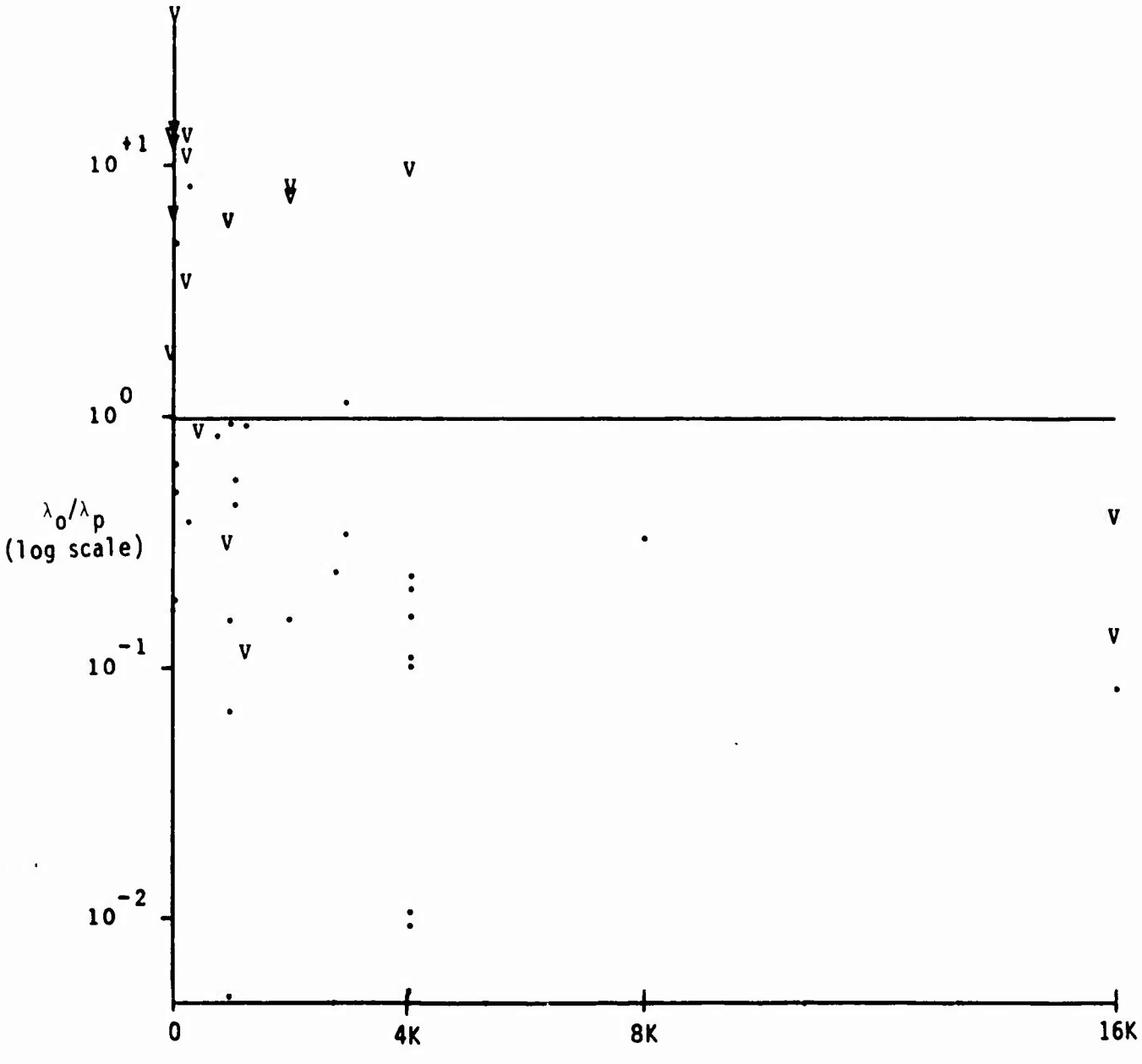


FIGURE 14: RATIO PLOT: MEMORY

FUNCTIONAL GROUP: MEMORY

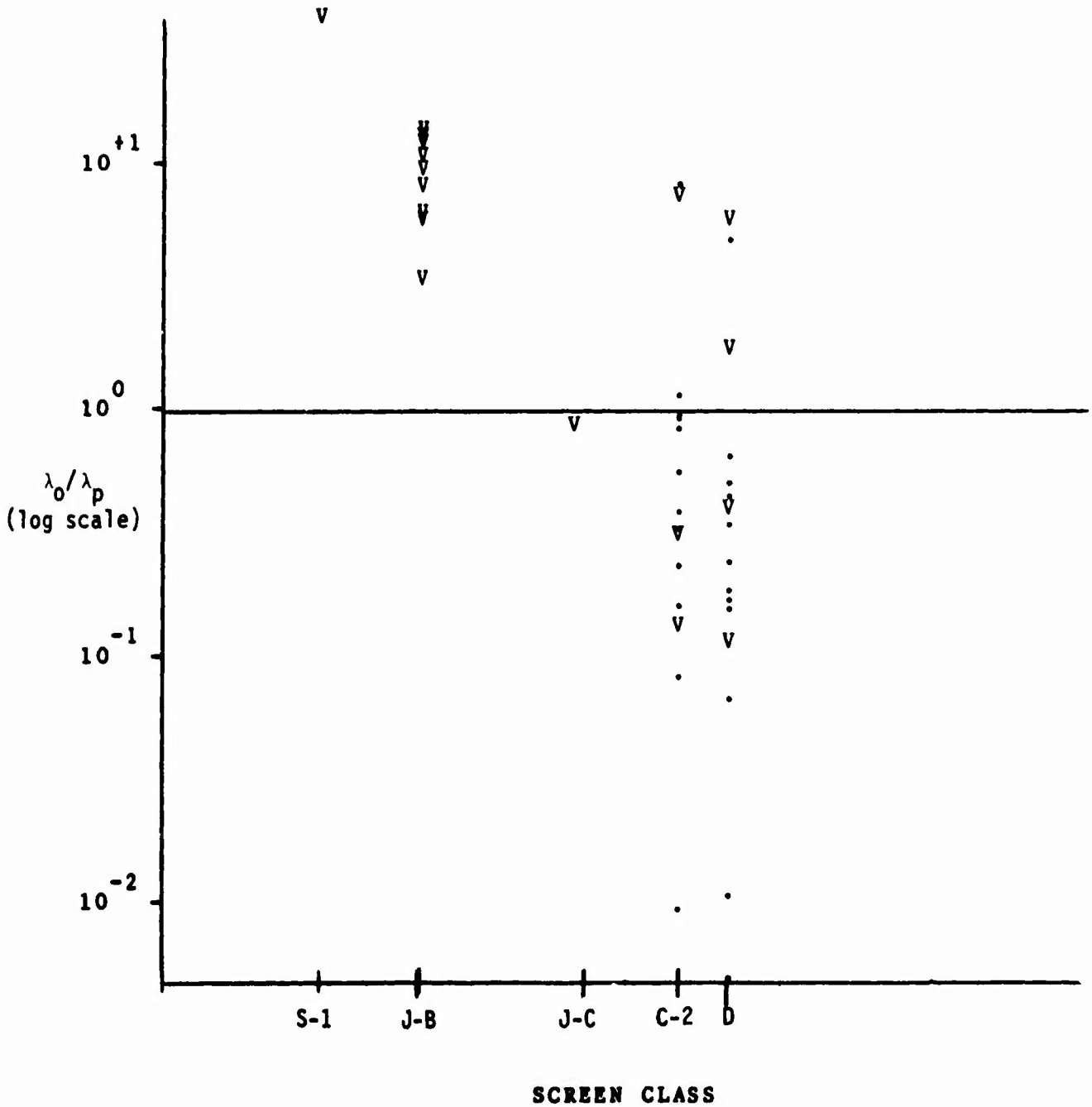
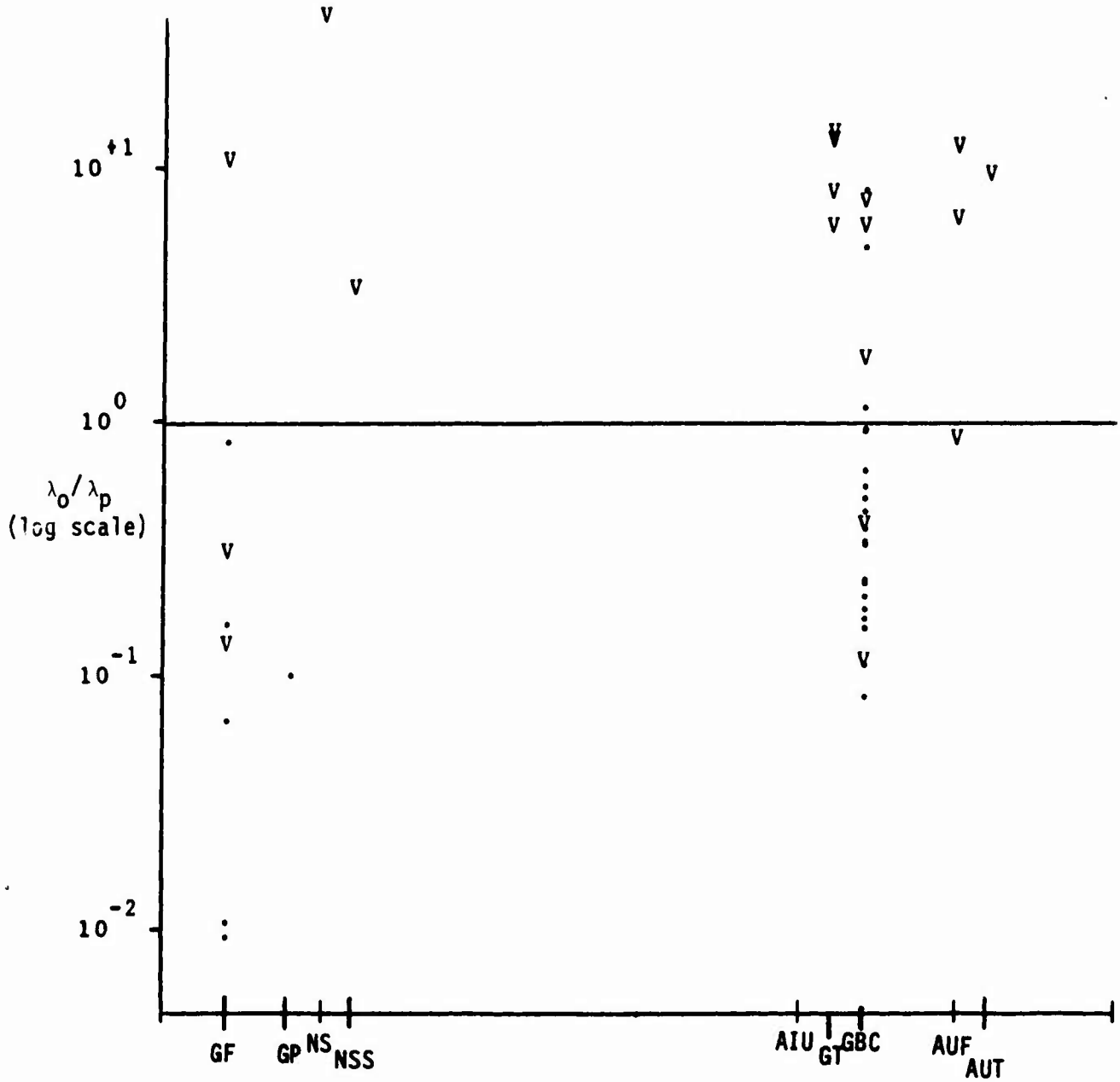


FIGURE 15: RATIO PLOT: MEMORY

FUNCTIONAL GROUP: MEMORY



APPLICATION ENVIRONMENT

FIGURE 16: RATIO PLOT: MEMORY

FUNCTIONAL GROUP: MEMORY

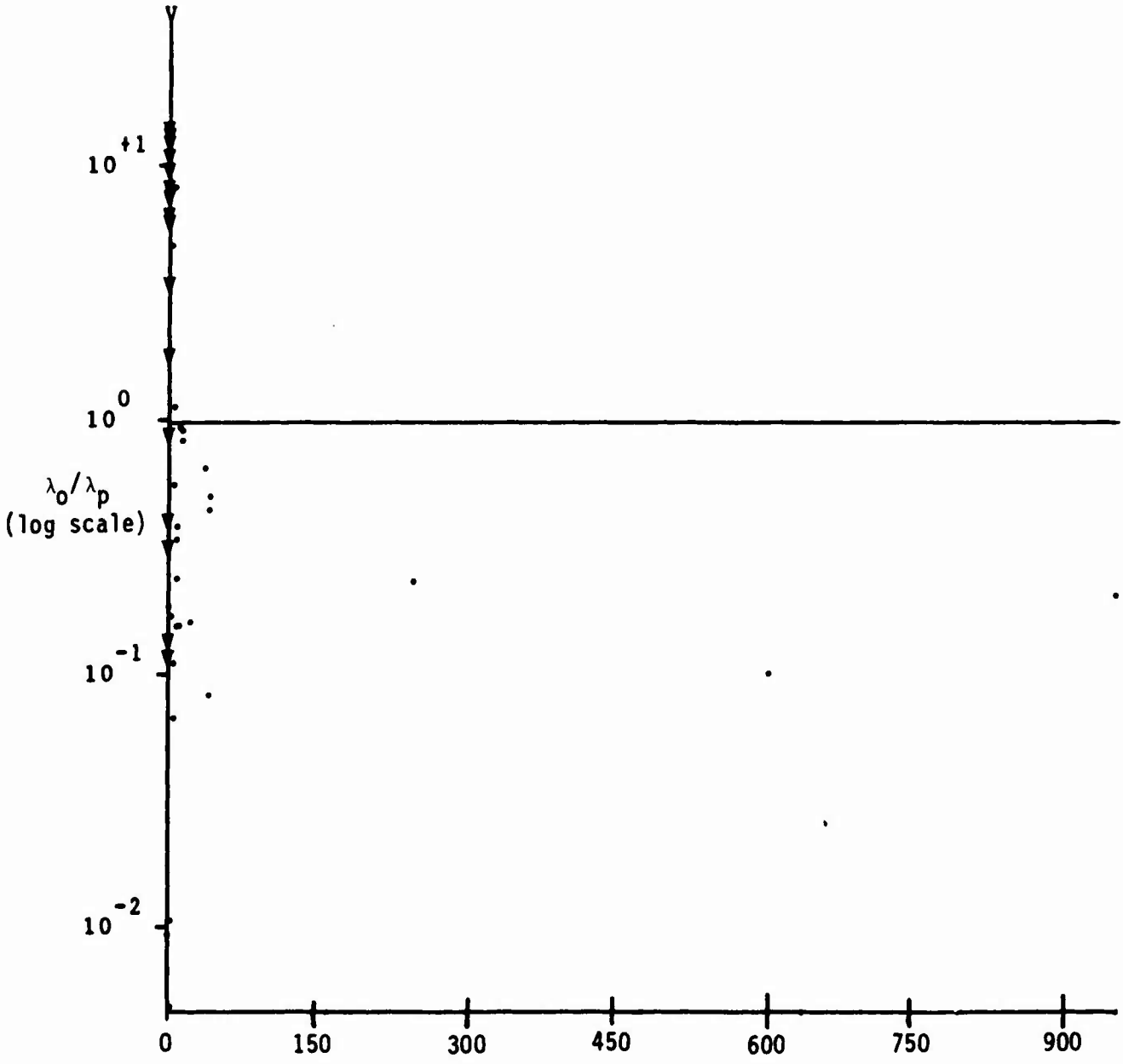


FIGURE 17: RATIO PLOT: MEMORY

Life Test Data

Tables 8 through 12 in this section consist of life test results and are presented to indicate the effects of temperature and bias configurations on the reliability of various device types. The results were generally obtained from either lot sample device qualification testing or production monitoring testing. The first table presents a condensed summary of the rest.

A detailed description of device level tests is available from the Reliability Analysis Center's document "Microcircuit Screening Effectiveness," catalogue no. TRS-1, by H.C. Rickers. Details on this publication may be obtained by contacting the Reliability Analysis Center directly.

TABLE 8 : READ ONLY MEMORY (ROM) LIFE TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	TEST TYPE	TEMPERATURE CENTIGRADE	PACKAGE	DEVICE HOURS	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
2 K	STAT-PMOS	OP DYN	70	PDIP	9.30E+ 5	1	.21	1.08	3.27
8 K	STAT-PMOS	OP DYN	125	HQIP	8.44E+ 5	0	-*-	-*-	1.96
	STAT-NMOS	OP DYN	125	HDIP	8.20E+ 5	8	6.81	9.75	13.92
16 K	STAT-NMOS	OP DYN	100	PDIP	4.67E+ 5	0	-*-	-*-	-*-

TABLE 9 : RANDOM ACCESS MEMORY (RAM) LIFE TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	TEST TYPE	TEMPERATURE CENTIGRADE	PACKAGE	DEVICE HOURS	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
256	CMOS	OP DYN	125	HDIP	1.02E+ 6	2	.80	1.96	4.24
	STTL	STGLIFE	150	HDIP	4.10E+ 5	0	-*-	-*-	-*-
		OP DYN	125	HDIP	4.38E+ 5	0	-*-	-*-	-*-
1 K	ECL	OP CNST	100	PDIP	1.25E+ 6	1	.16	.80	2.44
			125	HDIP	1.53E+ 6	0	-*-	-*-	1.09
	CMOS	OP DYN	125	HDIP	1.70E+ 6	2	.48	1.18	2.55
	DYN-PMOS	STGLIFE	150	PDIP	5.05E+ 5	0	-*-	-*-	3.28
		OP DYN	125	HQIP	4.40E+ 5	0	-*-	-*-	-*-
	STAT-PMOS	OP CNST	125	HDIP	9.70E+ 5	0	-*-	-*-	1.71
	STAT-NMOS	STGLIFE	150	PDIP	1.16E+ 6	0	-*-	-*-	1.43
			150	HDIP	9.35E+ 5	0	-*-	-*-	1.77
		OP DYN	50	HDIP	1.87E+ 7	16	.67	.85	1.09
			70	HDIP	8.27E+ 5	1	.24	1.21	3.68
			85	PDIP	1.33E+ 6	0	-*-	-*-	1.25
			85	HDIP	8.75E+ 5	0	-*-	-*-	1.89
			92	HDIP	6.97E+ 5	8	8.01	11.48	16.39
			125	PDIP	1.21E+ 6	2	.68	1.66	3.59
			125	HDIP	9.48E+ 6	5	.33	.53	.84
		REVBIAS	125	HDIP	1.20E+ 6	0	-*-	-*-	1.38
	STTL	OP CNST	100	PDIP	1.58E+ 6	1	.13	.63	1.92
			125	HDIP	1.36E+ 7	6	.29	.44	.67
		OP DYN	125	HDIP	4.18E+ 5	9	15.40	21.53	30.04
		REVBIAS	125	HDIP	4.91E+ 5	0	-*-	-*-	-*-
4 K	DYN-NMOS	STGLIFE	150	HDIP	4.59E+ 5	0	-*-	-*-	-*-
			250	HDIP	6.35E+ 5	2	1.28	3.15	6.80
		OP CNST	70	HDIP	5.55E+ 6	2	.15	.36	.78
		OP DYN	- 10	HDIP	1.16E+ 6	0	-*-	-*-	1.43
			25	HDIP	9.62E+ 6	12	.94	1.25	1.66
			70	HDIP	8.08E+ 5	0	-*-	-*-	2.05
			125	PDIP	1.42E+ 6	0	-*-	-*-	1.17
			125	HDIP	1.77E+ 7	15	.66	.85	1.09
		REVBIAS	150	HDIP	1.08E+ 6	2	.75	1.86	4.01
	STAT-NMOS	OP DYN	100	PDIP	1.49E+ 6	0	-*-	-*-	1.11
			125	HDIP	8.51E+ 6	0	-*-	-*-	.19
16 K	DYN-NMOS	OP DYN	125	HDIP	5.63E+ 6	101	16.42	17.93	19.60

TABLE 10: PROGRAMMABLE READ ONLY MEMORY (PROM) LIFE TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	TEST TYPE	TEMPERATURE CENTIGRADE	PACKAGE	DEVICE HOURS	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
256	TTL	OP CNST	125	HDIP	4.31E+ 5	0	-*-	-*-	-*-
		OP DYN	125	HDIP	7.21E+ 5	0	-*-	-*-	2.30
512	TTL	OP CNST	125	HDIP	8.34E+ 5	4	2.75	4.79	8.10
1 K	TTL	OP DYN	125	HDIP	1.02E+ 6	0	-*-	-*-	1.63
		REVBIAS	125	HDIP	5.58E+ 5	0	-*-	-*-	2.97
	STTL	STGLIFE	150	HDIP	5.94E+ 5	0	-*-	-*-	2.79
		OP DYN	100	PDIP	4.82E+ 5	0	-*-	-*-	-*-
			125	PDIP	2.51E+ 6	1	.08	.40	1.21
			125	HDIP	3.22E+ 6	2	.25	.62	1.34
2 K	PMOS (UV)	OP DYN	125	HDIP	4.51E+ 5	0	-*-	-*-	-*-
		REVBIAS	125	HDIP	4.70E+ 5	6	8.32	12.78	19.41
	STTL	OP CNST	25	PDIP	4.70E+ 5	0	-*-	-*-	-*-
			70	PDIP	4.74E+ 5	0	-*-	-*-	-*-
			100	PDIP	6.55E+ 5	0	-*-	-*-	2.53
		OP DYN	100	PDIP	1.79E+ 6	2	.46	1.12	2.42
			125	PDIP	7.21E+ 5	0	-*-	-*-	2.30
			125	HDIP	8.97E+ 6	0	-*-	-*-	.18
		REVBIAS	125	HDIP	7.52E+ 5	0	-*-	-*-	2.20
4 K	STTL	OP DYN	125	PDIP	7.48E+ 5	1	.26	1.34	4.06
			125	HDIP	7.87E+ 6	10	.93	1.27	1.74
8 K	NMOS (UV)	STGLIFE	250	HDIP	5.82E+ 5	33	48.32	56.72	66.72
		OP DYN	160	HDIP	7.22E+ 5	0	-*-	-*-	2.29
	STTL	OP DYN	125	HDIP	6.82E+ 5	4	3.37	5.86	9.91

TABLE 11: MICRO PROCESSOR LIFE TEST DATA

COMPLEXITY (GATES)	TECHNOLOGY	TEST TYPE	TEMPERATURE CENTIGRADE	PACKAGE	DEVICE HOURS	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
759	DYN-PMOS	OP DYN	70	HDIP	9.30E+ 5	1	.21	1.08	3.27
1500	DYN-NMOS	OP DYN	125	HDIP	5.88E+ 5	1	.34	1.70	5.17
		REVBIAS	70	HDIP	5.06E+ 6	0	-*-	-*-	.33

TABLE 12: READ ONLY MEMORY (ROM) FIELD TEST DATA

COMPLEXITY (BITS)	TECHNOLOGY	APPLICATION ENVIRONMENT	SCREEN CLASS	PACKAGE	DEVICE HOURS	REF. NO.	NUMBER FAILED	FAILURE RATE (/10E+06 HOURS) LOWER 20% LIMIT	POINT ESTIMATE	UPPER 80% LIMIT
8 K	TTL	AUF	B-1	HDIP	4.19E+ 5		0	-*-	-*-	-*-
16 K	DYN-NMOS	GBC	D-1	PDIP	1.10E+ 6	[1]	0	-*-	-*-	1.51

MICROCIRCUIT DEVICE RELIABILITY
MEMORY/DIGITAL LSI DATA

Section 3

DETAILED DATA LISTINGS

USER GUIDE

The description given below defines the format and codes of this section. The circled numbers shown on the tabulation form below refer to the explanatory text which follows.

MANUFACTURER ① DEVICE FUNCTION ②

OPERATIONAL TYPE ③ BASIC TECHNOLOGY ④ NUMBER OF BITS ⑤ 512

⑥ PART NO.	⑦ SCR. CLS	⑧ PKG	⑨ #PINS	⑩ TMP RNG	⑪ TEST TYPE	⑫ SOURCE	⑬ TEST DATE	⑬ STRESS LEVEL	⑭ ENV	⑮ PART HRS.	⑯ #TEST	⑰ #FAIL	⑱ MFEF
512	C-2	NHDIP	24	M	CNST	LIFE	4/79	125C	N/R	1.91E 05	276	0	
					LIFE	LIFE	4/79	150C	N/R	9.20E 04	70	0	

① MANUFACTURER. Denotes the manufacturer of the tested devices. Manufacturers are arranged alphabetically within each operation type. The term "various" is used to indicate parts produced by two or more manufacturers. This term is often used where second sourcing of equipment level parts occurs.

② DEVICE FUNCTION. This section is subdivided by the following device function categories: RAMs, ROMs, PROMs, shift registers, microprocessors, and arrays.

③ OPERATIONAL TYPE. This indicates the further classification of "Basic Technology" into CMOS, ECL, IIL, NMOS (static and dynamic), PMOS (static and dynamic), TTL, HTTL, LTTL, LSTTL, and STTL.

④ BASIC TECHNOLOGY. Categories within this heading are bipolar and MOS.

⑤ NUMBER OF BITS. The complexity of the memory-oriented devices is given by the "Number of Bits" entry. For the microprocessor and digital devices the gate count is used.

⑥ PART NO. These are listings of the device part number, neglecting package and temperature rating suffixes. Part numbers are arranged in left-hand justified numerical order. Thus, a sequence of the following part numbers is possible: 54157, 8080, 821, 9900.

⑦ SCR CLASS. Screen class is listed in order of decreasing quality within each part number category. These screening codes are the same basic form as found in MIL-HDBK-217C with some variations.

JS	38510, Class S
S-1	883 Method 5004, Screen Class S
JB	38510, Class B
B-1	883 Method 5004, Screen Class B
B-2	Class B, vendor or user equivalent
JC	38510, Class C
C-1	883 Method 5004, Screen Class C
C-2	Class C, vendor or user equivalent
D	Hermetic pkg., no screening beyond normal Q.C.
D-1	Plastic pkg., no screening beyond normal Q.C.
S/R	See Remarks. Device quality defined in item ㉔ REMARKS
JAN	38510, Screen Class not reported
883	883, probably Method 5004, Screen Class not reported

⑧ PKG. These entries indicate the package construction.

Package Prefixes:

H	Hermetic
NH	Non-Hermetic

Package Type:

CAN	Metal Can
DIP	Dual In-Line Package
FPK	Flat Package
QIP	Quad In-Line Package
LLP	Leadless Package
CC	Chip Carrier
INL	In-Line Package

⑨ # PINS. The number of pins per package.

⑩ TMP RNG. The rated operation temperature range coded by letter: M = Military, C = Commercial, I = Industrial.

⑪ TEST TYPE. Test types within the specific mode of testing are listed below.

EM	Electrical Measurements
OP CNST	Constant Operation Life Test
OP DYN	Dynamic Operation Life Test
OPERATE	Operational Equipment
REVBIAS	Reverse Bias Life Test
RHRB	Humidity Test with Reverse Bias
STG LIFE	High Temperature Storage Life (Non-operating)
TCVPC	Temperature Cycle, Vibration and Power Cycle

⑫ SOURCE. Defines the mode of testing according to the following:

BRN	Short Term Part Level Burn-In (<250 use)
CHK	Equipment Checkout
EBRN	Environmental and Burn-In Test
EVN	Environmental Test
FIELD	Field Data (In-service use)
LIFE	Laboratory Life Test
RELDEM	Reliability Demonstration
RELPRO	Production Reliability Test

⑬ TEST DATA. Indicates the reported end of device test.

⑭ STRESS LEVEL. Defines the magnitude and type of stress exerted during test using the following abbreviations:

ATMOS	Pressure Measure in Atmospheres
AXES	As defined in MIL-STD-883A
C	Degrees Centigrade

Stress Level (Cont'd)

CY	Number of Cycles
DEG	Degrees
E	Each
FLUOR	Fluorocarbon
G	Gravitational Constant
GMS	Grams
GMS/MSQ	Grams Per Square Meter
HE	Helium
HZ	Hertz
K	1000
MIN	Minutes
MINOIL	Mineral Oil (Ethylene Glycol)
MSEC	Milliseconds
OZ	Ounces
PSIA	Pounds Per Square Inch (Gauge = 15 at sea level)
RADIS	Radioisotope
RH	Relative Humidity
SEC	Second
V. CYC	Voltage Cycle (Followed by the percent of rated voltage applied)
X	Times (magnification)

(15) ENV. Application environment abbreviations are based on those used in MIL-HBK-217C and are defined as follows:

AI	Airborne, Inhabited, Carrier Unknown
AIF	Airborne, Inhabited, Fighter
AIT	Airborne, Inhabited, Transport
AU	Airborne, Uninhabited
AUF	Airborne, Uninhabited, Fighter
AUT	Airborne, Uninhabited, Transport
GB	Ground, Benign
GBC	Ground, Benign Commercial

Environment Abbreviations (Cont'd)

GF	Ground, Fixed
GM	Ground, Mobile
GT	Ground, Transportable (carried by vehicle)
N/R	Not Reported or Not Applicable

⑯ PART HRS. The number of part hours undergone by the devices under test (in total).

⑰ # TEST. The number of devices put on test.

⑱ # FAIL. The number of devices which failed during test.

⑲ MFEF #. Microcircuit failure event file. This number refers to the relevant file number of the failure event section.

MOTOROLA SEMI — BCD

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14553	D	NHDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.16E 05	67	0	
					N/R	FIELD	5/78	40C	GBC	9.75E 04	75	0	
					N/R	FIELD	4/79	40C	GBC	2.93E 05	225	0	
					N/R	FIELD	4/80	40C	GBC	2.57E 05	198	0	
					N/R	FIELD	4/81	40C	GBC	7.12E 05	274	0	

VARIOUS — BINARY

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	JB/BI	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	8.76E 05	64	0	
					N/R	FIELD	1/79	25C	GF	1.37E 05	10	0	
					N/R	FIELD	1/79	25C	GF	3.83E 05	28	0	
					N/R	FIELD	7/79	25C	GF	1.21E 05	28	0	
					N/R	FIELD	7/79	25C	GF	2.76E 05	64	0	
					N/R	FIELD	7/79	25C	GF	4.32E 04	10	0	
					N/R	FIELD	8/80	25C	GF	1.01E 05	10	0	
					N/R	FIELD	8/80	25C	GF	2.82E 05	28	0	
					N/R	FIELD	8/80	25C	GF	6.45E 05	64	0	
N/R		NHDIP	16	M	N/R	FIELD	1/79	25C	GF	8.76E 05	64	0	
					N/R	FIELD	1/79	25C	GF	1.09E 05	8	0	
					N/R	FIELD	1/79	25C	GF	3.56E 05	26	0	
					N/R	FIELD	7/79	25C	GF	1.12E 05	26	0	
					N/R	FIELD	7/79	25C	GF	2.76E 05	64	0	
					N/R	FIELD	7/79	25C	GF	3.46E 04	8	0	
					N/R	FIELD	8/80	25C	GF	2.62E 05	26	0	
					N/R	FIELD	8/80	25C	GF	6.45E 05	64	0	
					N/R	FIELD	8/80	25C	GF	8.06E 04	8	0	

INTEL — BUS DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8238	D	NHDIP	28	C	OPERATE	CHECK	10/77	025C	GBC	4.40E 02	1	0	
8238		NHDIP	28	C	OP DYN	BDLIFE	5/77	25C	N/R	2.47E 04	21	0	
					OP DYN	BDLIFE	5/77	55C	N/R	1.43E 04	21	0	
					OP DYN	BDLIFE	5/77	70C	N/R	2.00E 04	21	0	

ADVANCED MICRO DEVICES — CLOCK DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8224	D-1	HDIP	16	C	N/R	FIELD	5/78	40C	GBC	5.98E 04	46	0	
					N/R	FIELD	4/79	40C	GBC	1.43E 06	1102	3	
					N/R	FIELD	4/80	40C	GBC	2.40E 06	1845	5	
					N/R	FIELD	4/81	40C	GBC	4.26E 06	1637	2	

SIGNETICS — CLOCK DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3207A	D	NHDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	3.30L 04	33	0	
					EM						33	0	
3207A	D-1	HDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	4.10E 04	41	0	
					EM						41	1	

VARIOUS — CLOCK DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3207A	D	NHDIP	16	C	N/R	FIELD	5/77	40C	GBC	3.49E 06	700	0	

INTEL — CONTENT ADDRS

N-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8259	D	NHDIP	28	C	OPERATE	CHECK	10/77	025C	GBC	4.40E 02	1	0	

FAIRCHILD SEMI — COUNTER

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9408	D	NHDIP	40	N/R	OP DYN	LIFE	5/77	125C	N/R	3.50E 04	35	0	
					EM						35	0	
					REVBIAS	LIFE	5/77	125C	N/R	3.50E 04	35	0	

FAIRCHILD SEMI — COUNTER

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9408	D	NHDIP	40	N/R	EM	LIFE	5/77		N/R		35	0	
					RHRB	LIFE	5/78	125C	N/R	7.90E 04	41	0	
					EM						41	0	
					OP DYN	LIFE	5/78	125C	N/R	1.50E 04	36	0	
					EM						36	0	
					OP DYN	LIFE	5/78	125C	N/R	3.50E 04	35	0	
					EM						35	0	
					REVBIAS	LIFE	5/78	125C	N/R	3.50E 04	35	0	
					EM						35	0	
					OP DYN	LIFE	5/78	125C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/78	125C	N/R	8.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/78	125C	N/R	5.87E 04	40	1	
					EM						39	0	
					RHRB	LIFE	5/78	125C	N/R	3.60E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/78	125C	N/R	2.70E 04	27	0	
					EM						27	0	
					TEMPCYC	ENV	5/78	-065C 150C	N/R		42	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 1 AXIS			42	0	
								1 MIN E					
					FINE LK			HE 5.E-8			42	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			42	0	
								3X					
								90PSIG					
					EM						42	0	
					MECHSHK	ENV	5/78	1.5KG .5MSEC	N/R		42	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			42	0	
								20G					
								3 AXES					
					CNSTACC			30KG 1 AXIS			42	0	
								1 MIN E					
					FINE LK			HE 5.E-8			42	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			42	0	
								3X					
								90PSIG					
					EM						42	0	
					THRMSHK	ENV	5/78	-055C 125C	N/R		42	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			42	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			42	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			42	0	
								3X					
								90PSIG					
					EM						42	0	
					OP DYN	LIFE	5/79	125C	N/R	2.00E 04	40	0	
					EM						40	0	
					OP CNST	LIFE	5/79	125C	N/R	7.20E 04	36	0	
					EM						36	0	
					OP CNST	LIFE	5/79	125C	N/R	5.40E 04	27	0	
					EM						27	0	

SIGNETICS — GENERATOR

ECL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10160	D	NHDIP	16	1	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

SIGNETICS — GENERATOR

IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8X01	D-1	HDIP	14	N/R	N/R	FIELD	4/79	40C	GBC	5.73E 06	4408	0	
					N/R	FIELD	4/80	40C	GBC	5.73E 06	4404	1	
					N/R	FIELD	4/81	40C	GBC	1.26E 07	4842	0	

MOTOROLA SEMI — GENERATOR

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14411	D-1	HDIP	24	1	N/R	FIELD	5/77	40C	GBC	2.73E 04	18	0	
					N/R	FIELD	5/78	40C	GBC	3.54E 05	272	0	
					N/R	FIELD	4/79	40C	GBC	6.75E 05	519	0	
					N/R	FIELD	4/80	40C	GBC	2.20E 06	1696	0	
					N/R	FIELD	4/81	40C	GBC	6.25E 06	2403	0	

INTEL — LATCH

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3212	D-1	HDIP	24	C	OPERATE	CHECK	10/77	025C	GBC	4.40E 02	1	0	

MONOLITHIC MEMORIES — MEMORY

TTL — BIPOLAR — NUMBER OF BITS 320

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
57402J	D	NHDIP	16	M	PAR EXC	LIFE	10/81	125C	N/R	9.40E 04	94	0	

MONOLITHIC MEMORIES — MEMORY

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
57401	D	NHDIP	16	M	OP DYN	LIFE	1/79	125C	N/R	1.58E 05	95	0	
					EM			25C			95	0	
					PAR EXC	LIFE	10/81	125C	N/R	5.00E 04	50	0	
67401		NHDIP	16	C	OP DYN	LIFE	1/79	125C	N/R	1.93E 05	144	0	
					EM			25C			144	0	

TEXAS INSTRUMENTS — MEMORY

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S225	D-1	HDIP	20	C	N/R	FIELD	2/78	25C	GBC	1.66E 04	3	0	
					N/R	FIELD	6/78	25C	GBC	8.64E 03	3	0	

FAIRCHILD SEMI — MEMORY

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9403	D-1	HDIP	24	N/R	OP CNST	LIFE	5/77	100C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/77	100C	N/R	4.80E 04	48	0	
					EM						48	0	
					RHRB	LIFE	5/78	85C	N/R	2.35E 04	47	0	
					EM						47	0	
					OP CNST	LIFE	5/78	100C	N/R	8.14E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/78	100C	N/R	4.80E 04	48	0	
					EM						48	0	
					RHRB	LIFE	5/78	85C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/78	100C	N/R	7.99E 04	48	1	
					EM						47	0	
					RHRB	LIFE	5/78	85C	N/R	4.80E 04	48	0	
					EM						48	0	
					THRMSHK	ENV	5/78	-055C 125C 15CY	N/R		25	0	

FAIRCHILD SEMI — MEMORY

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
9403	D-1	HDIP	24	N/R	TEMPCYC	ENV	5/78	-065C 150C 10CY	N/R		25	0	
					MOIST						25	0	
					EM						25	0	
					THRMSHK	ENV	5/78	-055C 125C 1000CY LIQUID	N/R		25	0	
					EM						25	1	
					OP CNST	LIFE	5/79	100C	N/R	2.40E 04	46	0	
					EM						48	0	
					RHRB	LIFE	5/79	85C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	100C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	100C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	100C	N/R	9.60E 04	48	0	
					EM						48	0	
					RHRB	LIFE	5/79	85C	N/R	9.42E 04	48	1	
					EM						47	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		84	0	
					TEMPCYC			-065C 150C 10CY			84	0	
					MOIST			-010C 065C 98%RH			84	0	
					FINE LK			HE 5.E-6 60 MIN 30 MIN			84	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			84	0	
					EM						84	0	
					THRMSHK	ENV	8/79	-055C 125C 1000CY LIQUID	N/R		67	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			67	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			67	0	
					EM						67	0	
					OP CNST	LIFE	12/79	100C	N/R	1.44E 05	72	0	
					EM						72	0	
					OP CNST	LIFE	12/79	100C	N/R	1.80E 04	16	0	
					EM						18	0	
					RHRB	LIFE	12/79	85C	N/R	1.00E 04	10	0	
					EM						10	0	
					OP CNST	LIFE	12/79	125C	N/R	7.20E 04	48	0	
					EM						48	0	
					RHRB	LIFE	12/79	85C	N/R	9.60E 04	48	0	
					EM						48	0	
					RHRB	LIFE	12/79	85C	N/R	9.50E 04	47	0	
					EM						47	0	
9403	D	NHDIP	24	N/R	OP CNST	LIFE	5/78	125C	N/R	8.20E 04	82	0	
					EM						82	0	
					TEMPCYC	ENV	5/78	-065C 150C 10CY	N/R		22	0	
					CNSTACC			30KG 1 AXIS 1 MIN E			22	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			22	0	

FAIRCHILD SEMI — MEMORY

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9403	D	MIDIP	24	M/R	GROSSLK	ENV	5/78	FLUOR 125C	M/R		22	0	
								3X					
								90PSIG					
					EM						22	1	
					TEMPCYC	ENV	5/78	-065C 150C	M/R		30	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 1 AXIS			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								90PSIG					
					EM						30	0	
					TEMPCYC	ENV	5/78	-065C 150C	M/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 1 AXIS			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM						25	0	
					MECHSHK	ENV	5/78	1.5KG .5MSEC	M/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 1 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM						25	0	
					THRMSHK	ENV	5/78	-055C 125C	M/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	1	
								3X					
								90PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	M/R		21	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			21	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			21	0	
								1 MIN E					
					FINE LK			HE 5.E-8			21	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — MEMORY

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9403	D	NHDIP	24	N/R	GROSSLK	ENV	6/79	FLUOR 125C	N/R		21	0	
								3X					
								60PSIG					
					EM						21	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		19	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			19	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			19	0	
								98%RH					
					FINE LK			HE 5.E-8			19	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			19	0	
								3X					
								60PSIG					
					EM						19	0	
9403A	D-1	HDIP	24	C	OP CNST	LIFE	12/79	100C	N/R	3.27E 04	16	1	2386
					EM						15	0	
					RHRB	LIFE	12/79	85C	N/R	3.47E 04	16	0	
					EM						16	0	
9410	D	NHDIP	18	N/R	OP CNST	LIFE	5/78	100C	N/R	3.60E 04	24	0	
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					

FAIRCHILD SEMI — MEMORY

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9410	D	NHDIP	18	N/R	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

ADVANCED MICRO DEVICES — MEMORY

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2841	D	NHDIP	16	M	VIS INS	ENV	1/77	3X	N/R		25	0	
								10X					
					S&D EM						25	0	
					BAKE	ENV	1/77	150C	N/R	5.52E 02	23	0	
					TEMPCYC			-065C 150C			23	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								90PSIG					
					X-RAY						23	0	
					EM						23	0	
					TEMPCYC	ENV	1/77	-065C 150C	N/R		8	0	
								50CY					
								10/10DT					
					FINE LK			HE 5.E-8			8	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			8	0	
								3X					
								90PSIG					
					EM						8	0	
					N/R	LIFE	1/77	125C	N/R	3.00E 04	15	0	
					S&D EM						15	0	
	B-2				PAR EXC	LIFE	6/80	150C	N/R	1.66E 04	83	0	

ADVANCED MICRO DEVICES — MEMORY

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
2841	D	NHDIP	16	M	EM	LIFE	6/80	150C	N/R		83	0	

NITRON — MEMORY

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	4.45E 04	1855	0	
					TEMPCYC			-065C 150C			1855	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			1855	0	
								1 MIN E					
					FINE LK			HE 5.E-7			1855	6	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			1855	1	
								3X					
								90PSIG					
					FNCT EM			085C			1848	213	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.03E 05	1206	0	
					S&F EM			85C			1206	8	
					STAT EM			-35C			1206	2	
					FNCT EM			25C			1206	17	
					VIS INS						1206	3	
					REVBIAS	BRN	2/78	125C	N/R	6.05E 03	36	0	
					S&F EM			85C			36	0	
					STAT EM			-35C			36	1	
					FNCT EM			25C			36	0	
					VIS INS						36	0	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	0	
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	4.65E 04	1938	0	
					TEMPCYC			-065C 150C			1938	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			1938	0	
								1 MIN E					
					FINE LK			HE 5.E-7			1938	5	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			1938	2	
								3X					
								90PSIG					
					FNCT EM			085C			1931	181	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.21E 05	1315	0	
					S&F EM			85C			1315	12	
					STAT EM			-35C			1315	11	
					FNCT EM			25C			1315	15	
					VIS INS						1315	4	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	1	

VARIOUS — MEMORY

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2841/3341	D-1	HDIP	16	C	VIS INS	EBRN	3/78		N/R		1515	0	
					TEMPCYC			-055C 125C			1515	0	
								10CY					
					REVBIAS			125C		2.42E 05	1515	0	
					S&F EM			070C			1515	13	2481
													2482
													2483
2841/3341	D	NHDIP	16	C	VIS INS	EBRN	3/78		N/R		10534	0	
					TEMPCYC			-055C 125C			10534	0	
								10CY					
					REVBIAS			125C		1.69E 06	10534	0	
					S&F EM			070C			10534	91	2468
													2469
													2470

ADVANCED MICRO DEVICES — MEMORY

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2812	B-2	NHDIP	28	M	PAR EXC	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	1	

MOTOROLA SEMI — MODEM

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6860	NONE	DIP	24	C	OP DYN	LIFE	11/77	125C	N/R	7.30E 04	76	0	
					EM						76	4	

MOTOROLA SEMI — MODEM

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14412	D-1	HDIP	16	I	N/R	FIELD	4/79	40C	GBC	3.25E 04	25	0	
					N/R	FIELD	4/80	40C	GBC	3.98E 05	306	0	
					N/R	FIELD	4/81	40C	GBC	8.87E 05	341	0	

HARRIS SEMI — MULTIPLEXER

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5508A/509A	C-2	NHDIP	16	M	OP CNST	LIFE	4/79	125C	N/R	7.20E 04	72	0	

MOTOROLA SEMI — N/R

N/R — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
68XX	D-1	HDIP	24	C	TEMPCYC	LIFE	4/78	:- 65C	N/R		56	1	
					FNCT EM			25C			55	0	
68XX		HDIP	40	C	TEMPCYC	LIFE	4/78	:- 65C	N/R		20	0	
					FNCT EM			25C			20	0	
6800/6820		HDIP	40	C	RHOC	LIFE	4/78	85C	N/R	2.60E 04	35	0	
					SDF EM						35	0	
					RHOC	LIFE	4/78	85C	N/R	2.64E 05	262	4	
					SDF EM						258	3	
					RHOC	LIFE	4/78	85C	N/R	3.43E 04	17	0	
					SDF EM						17	0	
					RHOC	LIFE	4/78	85C	N/R	5.14E 04	17	1	
					SDF EM						16	0	

MOTOROLA SEMI — PERIPHERAL

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6828/8507	D-1	HDIP	24	C	N/R	FIELD	4/79	40C	GBC	4.42E 04	34	0	
					N/R	FIELD	4/80	40C	GBC	2.46E 05	189	0	
					N/R	FIELD	4/81	40C	GBC	8.14E 05	313	0	

MOTOROLA SEMI — PERIPHERAL

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6580	NONE	DIP	24	C	OP DYN	LIFE	11/77	125C	N/R	2.46E 05	177	8	
					EM						177	8	
68A21	D-1	HDIP	40	C	N/R	FIELD	4/79	40C	GBC	3.90E 03	3	0	
					N/R	FIELD	4/80	40C	GBC	1.53E 05	118	0	
					N/R	FIELD	4/81	40C	GBC	1.87E 06	720	0	
68488/A/B488		HDIP	40	C	N/R	FIELD	4/79	40C	GBC	3.50E 05	269	0	
					N/R	FIELD	4/80	40C	GBC	1.02E 06	783	0	
					N/R	FIELD	4/81	40C	GBC	8.65E 06	3327	0	
68488/A/B488	D	NHDIP	40	C	N/R	FIELD	4/79	40C	GBC	1.83E 06	1410	0	
					N/R	FIELD	4/80	40C	GBC	5.28E 06	4062	0	
					N/R	FIELD	4/81	40C	GBC	1.32E 07	5071	0	

MOTOROLA SEMI — PERIPHERAL

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6850	D	NHDIP	24	C	N/R	FIELD	4/79	40C	GBC	5.98E 04	46	0	

VARIOUS — PERIPHERAL

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6850	D	NHDIP	24	C	N/R	FIELD	4/79	40C	GBC	6.81E 05	524	0	
					N/R	FIELD	4/80	40C	GBC	2.56E 06	1969	1	
					N/R	FIELD	4/81	40C	GBC	7.06E 06	2714	2	

ZILOG — PERIPHERAL

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80S10	D-1	HDIP	40	C	PAR EXC	LIFE	3/80	125C	N/R	3.96E 05	182	0	
					EM						182	1	2399

RCA — PERIPHERAL

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1852	D	NHDIP	24	M	N/R	FIELD	6/78		GF	4.26E 05	42	42	
					N/R	FIELD	6/78		GF	6.12E 04	6	6	
	B-2				N/R	FIELD	3/80		GF	6.65E 05	42	1	
					N/R	FIELD	3/80		GF	9.50E 04	6	0	

FAIRCHILD SEMI — PROGRAM

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9406	D	NHDIP	24	C	OP CNST	LIFE	12/79	125C	N/R	8.00E 03	8	0	
					EM						8	0	

NATIONAL SEMI — PROGRAMMABLE

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6575	D-1	HDIP	24	C	N/R	FIELD	4/79	40C	GBC	5.66E 05	437	0	
					N/R	FIELD	4/80	40C	GBC	2.01E 06	1545	0	

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93458	D	NHDIP	28	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		14	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			14	0	
								1 MIN E					
					FINE LK			HE 5.E-8			14	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			14	0	
								3X					
								60PSIG					
					EM						14	0	
93458		NHDIP	28	M	OP DYN	LIFE	5/79	125C	N/R	3.60E 04	36	0	
					EM						36	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93458	D	NHDIP	28	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	1	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-055C 125C	N/R		35	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			35	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93458	D	NHDIP	28	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		35	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			35	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93459		NHDIP	28	M	OP DYN	LIFE	5/79	125C	N/R	5.60E 04	28	0	
					EM						28	0	
					OP DYN	LIFE	5/79	125C	N/R	6.00E 04	30	0	
					EM						30	0	
					OP DYN	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93459	D	NHDIP	28	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		35	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			35	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		36	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			36	0	
								1 MIN E					
					FINE LK			HE 5.E-8			36	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			36	0	
								3X					
								60PSIG					
					EM						36	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93459	D	NHDIP	28	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		36	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			36	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			36	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			36	0	
								3X					
								60PSIG					
					EM						36	0	
93459		NHFPK	28	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		35	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			35	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93459	D	NHFPK	28	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

SIGNETICS — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S101	D	NHDIP	28	N/R	OP DYN	LIFE	11/77	125C	N/R	5.30E 04	53	0	
					EM						53	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

FAIRCHILD SEMI — PROGRAMMABLE

SCHOTTKY IIL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9406	D-1	HDIP	24	N/R	THRMSHK	ENV	5/78	-055C 125C	N/R		25	0	
								15CY					
					TEMPCYC			-065C 150C			25	0	
								10CY					
					EM						25	1	682
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

NATIONAL SEMI — PROGRAMMABLE

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5307	D-1	HDIP	14	C	N/R	FIELD	4/79	40C	GBC	4.07E 05	313	0	
					N/R	FIELD	4/80	40C	GBC	5.60E 05	431	0	

MOTOROLA SEMI — PROGRAMMABLE

N-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6840	D-1	HDIP	28	C	OP DYN	LIFE	4/78	125C	N/R	1.66E 04	33	0	
					SDF EM						33	0	
6840	NONE	DIP	28	C	OP DYN	LIFE	11/77	125C	N/R	1.02E 05	145	0	
					EM						145	0	
6840	D	NHDIP	28	C	OP DYN	LIFE	4/78	125C	N/R	1.13E 05	112	0	
					SDF EM						112	0	

FAIRCHILD SEMI — PROGRAMMABLE

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4702	X	HDIP	16	I	N/R	FIELD	2/78	25C	GBC	1.91E 05	17	0	
					N/R	FIELD	6/78	25C	GBC	4.90E 04	17	0	

INTEL — PROM

N/R — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M3605A/25A	D	NHDIP	18	M	BURN-IN	BRN	6/80	25C	N/R	1.70E 05	3536	0	
					EM			25C			3536	9	2532
													2533
													2534
													2535
													2536
					OP DYN	LIFE	6/80	125C	N/R	4.43E 05	2653	0	
					EM			25C			2635	1	2609
					OP DYN			125C		3.80E 05	1145	0	
					EM			25C			1145	0	
					OP DYN			125C		5.73E 05	1145	0	
					EM			25C			1145	0	
					REVBIAS	LIFE	6/80	150C	N/R	1.06E 05	211	0	
					EM			25C			211	0	
					REVBIAS			150C		1.06E 05	211	0	
					EM			25C			211	0	
					BAKE	LIFE	6/80	250C	N/R	3.44E 04	205	0	

INTEL PROM

N/R BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M3605A/25A	D	NHDIP	18	M	EM	LIFE	6/80	25C	N/R		205	0	
					BAKE			250C		6.81E 04	205	0	
					EM			25C			205	0	
					TEMPCYC	ENV	6/80	-055C 125C	N/R		205	0	
								200 CYC					
					EM			025C			205	1	

INTEL PROM

N/R BIPOLAR NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M3628A	D	NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	2.53E 04	528	0	
					EM			25C			528	0	
					OP DYN	LIFE	6/80	125C	N/R	8.87E 04	528	0	
					EM			25C			528	0	
					OP DYN			125C		9.89E 04	298	0	
					EM			25C			298	0	
					OP DYN			125C		1.49E 05	298	0	
					EM			25C			298	1	2610
					OP DYN			125C		2.97E 05	297	0	
					EM			25C			297	0	
					REVBIAS	LIFE	6/80	150C	N/R	7.50E 04	150	0	
					EM			25C			150	0	
					REVBIAS			150C		7.50E 04	150	0	
					EM			25C			150	0	
					BAKE	LIFE	6/80	250C	N/R	3.60E 03	75	0	
					EM			25C			75	0	
					BAKE			250C		9.00E 03	75	0	
					EM			25C			75	0	
					BAKE			250C		2.49E 04	75	0	
					EM			25C			75	0	

INTEL PROM

N/R BIPOLAR NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M3636	D	NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	2.03E 05	4228	0	
					EM			25C			4228	4	
					OP DYN	LIFE	6/80	125C	N/R	5.21E 05	3103	0	
	•				EM			25C			3103	0	
					OP DYN			125C		5.64E 05	1698	0	
					EM			25C			1698	0	
					OP DYN			125C		7.23E 05	1446	0	
					EM			25C			1446	0	
					REVBIAS	LIFE	6/80	150C	N/R	1.86E 05	371	0	
					EM			25C			371	0	
					REVBIAS			150C		1.59E 05	317	0	
					EM			25C			317	0	
					BAKE	LIFE	6/80	250C	N/R	4.03E 04	240	0	
					EM			25C			240	0	
					BAKE			250C		7.27E 04	219	0	

INTEL — PROM

N/R — BIPOLAR — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
H3636	D	NHDIP	24	M	EM	LIFE	6/80	25C	N/R		219	0	
					TEMPCYC	ENV	6/80	-055C 125C 200 CYC	N/R		150	0	
					EM			025C			150	0	
					BURN-IN	BRN	3/80		N/R	1.89E 05	3938	0	
					EM						3938	4	3123
					BAKE	LIFE	3/80	250C	N/R	1.30E 05	260	0	
					EM						260	0	
					TEMPCYC	ENV	3/80	-055C 150C 200 CY	N/R		180	0	
					EM						180	0	
					REVBIAS	LIFE	3/80	150C	N/R	3.71E 05	371	1	3181
					EM						370	2	
					REVBIAS	LIFE	3/80	150C	N/R	4.15E 04	83	0	
					EM						83	0	

HARRIS SEMI — PROM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8256	C-2	NHDIP	16	N/R	OP DYN	LIFE	4/79	125C	N/R	7.21E 05	556	0	
					STGLIFE	LIFE	4/79		N/R	2.20E 04	22	0	

INTERSIL — PROM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5610M	B-2	NHDIP	16	M	OPERATE	RELDEM	12/77		AIU	2.50E 04	775	0	

SIGNETICS — PROM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8223	D-1	HDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	6.10E 04	30	0	
					EM						30	0	
					OP DYN	LIFE	11/77	85C	N/R	4.30E 04	43	0	
					EM						43	0	
					OP DYN	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	0	
					OP DYN	LIFE	11/77	85C	N/R	8.50E 04	85	0	
					EM						85	0	
					OP DYN	LIFE	11/77	125C	N/R	4.20E 04	42	0	

SIGNETICS — PROM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8223	D-1	HDIP	16	C	EM	LIFE	11/77		N/R		42	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.00E 04	40	0	
					EM						40	0	
					REVBIAS	LIFE	11/77	125C	N/R	5.00E 04	25	0	
					EM						25	0	

HARRIS SEMI — PROM

TTL — BIPOLAR — NUMBER OF BITS 512

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
512	C-2	NHDIP	24	M	OP CNST	LIFE	4/79	125C	N/R	1.91E 05	276	0	
					STGLIFE	LIFE	4/79	150C	N/R	9.20E 04	70	0	

VARIOUS — PROM

TTL — BIPOLAR — NUMBER OF BITS 512

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
512	D	NHFPK	24	M	TCVPC	RELPRO	1/77	-054C 071C 17CY 1.3G50% 23HZ 8.3%	AUF	1.54E 03	12	0	
					TCVPC	RELPRO	1/77	-054C 071C 17CY 1.3G50% 23HZ 8.3%	AUF	8.22E 03	64	0	
	C-1				N/R	FIELD	9/78		AUF	1.20E 06	1056	0	
					N/R	FIELD	9/78		AUF	2.56E 05	198	0	
					N/R	FIELD	9/79		AIU	3.80E 05	1056	0	
					N/R	FIELD	9/79		AIU	7.13E 04	198	0	
512		NH	24	N/R	N/R	FIELD	12/79	25C	NS	3.03E 04	6	0	

FAIRCHILD SEMI — PROM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93416	D	NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/77	125C	N/R	4.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/77	125C	N/R	5.60E 04	28	0	
					EM						28	0	
					OP DYN	LIFE	5/77	125C	N/R	5.10E 04	51	0	
					EM						51	0	
					REVBIAS	LIFE	5/77	- 25C	N/R	1.32E 05	66	0	

FAIRCHILD SEMI — PROM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93416	D	NHDIP	16	M	EM	LIFE	5/77		N/R		66	0	
					REVBIAS	LIFE	5/77	-25C	N/R	2.00E 04	10	0	
					EM						10	0	
93416		NHDIP	16	M	REVBIAS	LIFE	5/77	-25C	N/R	5.00E 04	50	0	
					EM						50	0	
93416		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	5.00E 04	50	0	
					EM						50	0	
					REVBIAS	LIFE	5/77	-25C	N/R	1.00E 05	100	0	
					EM						100	0	
					REVBIAS	LIFE	5/77	125C	N/R	1.13E 05	113	0	
					EM						113	1	
93426		NHDIP	16	M	REVBIAS	LIFE	5/77	125C	N/R	9.00E 04	50	0	
					EM						50	0	

MONOLITHIC MEMORIES — PROM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5300	D	NHDIP	16	M	OP CNST	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
					OP DYN	LIFE	1/79	125C	N/R	9.10E 04	91	0	
					EM			25C			91	0	
					PAR EXC	LIFE	10/81	125C	N/R	7.70E 04	77	0	
5300	B-2	NHDIP	16	M	OPERATE	RELDEM	12/77		AIU	1.95E 04	605	0	
	B-1				N/R	RELDEM	7/78	025C	GT	7.38E 03	21	0	
5300	D	NHFPK	16	M	PAR EXC	LIFE	10/81	125C	N/R	9.50E 04	95	0	
5301		NHDIP	16	M	OP CNST	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
					OP DYN	LIFE	1/79	125C	N/R	5.20E 04	52	0	
					EM			25C			52	0	

VARIOUS — PROM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	NONE	DIP	0	C	N/R	FIELD	12/77	39C	GBC	7.93E 07	99999	571	
					N/R						63921	0	
N/R	D	NHDIP	16	C	ACCLFOD	LIFE	9/78	200C	N/R	6.00E 04	20	5	
					S&F EM			120C			20	0	
					ACCLFOD	LIFE	9/78	250C	N/R	7.00E 03	10	1	
					S&F EM			25C			10	1	
					ACCLFOD	LIFE	9/78	250C	N/R	2.50E 03	10	1	
					S&F EM			25C			10	0	
					OP DYN	LIFE	9/78	150C	N/R	1.00E 04	20	0	
					S&F EM			25C			20	0	
1024/5623	B-2	NHFPK	16	M	OPERATE	CHECK	3/78	025C	AIT	6.98E 02	26	0	
					OPERATE	CHECK	3/78	025C	AIT	8.99E 03	143	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	4.82E 02	26	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	5.06E 02	143	0	
					OPERATE	CHECK	3/78	025C	AIT	4.74E 03	26	0	
					OPERATE	CHECK	3/78	025C	AIT	2.27E 04	143	0	

VARIOUS PROM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1024/5623	B-2	NHFPK	16	M	TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	4.75E 03	26	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	2.47E 04	143	0	

MONOLITHIC MEMORIES PROM

TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5305	D	NHDIP	16	M	OP DYN	LIFE	1/79	125C	N/R	1.05E 05	105	0	
					EM			25C			105	0	
5305		NHFPK	16	M	OP CNST	LIFE	1/79	85C	N/R	7.70E 04	77	0	
					EM			25C			77	0	
5306		NHDIP	16	M	OP CNST	LIFE	1/79	125C	N/R	1.22E 05	122	0	
					EM			25C			122	0	
					OP DYN	LIFE	1/79	125C	N/R	1.22E 05	122	0	
					EM			25C			122	1	
					PAR EXC	LIFE	10/81	125C	N/R	1.99E 05	199	0	

VARIOUS PROM

TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2048/5624	B-2	NHFPK	16	M	OPERATE	CHECK	3/78	025C	AIT	3.49E 03	130	0	
					OPERATE	CHECK	3/78	025C	AIT	4.09E 04	650	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	2.41E 03	130	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	2.30E 03	650	0	
					OPERATE	CHECK	3/78	025C	AIT	2.37E 04	130	0	
					OPERATE	CHECK	3/78	025C	AIT	1.03E 05	650	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	2.38E 04	130	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	1.12E 05	650	0	

MONOLITHIC MEMORIES — PROM

TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5340	B-1	NHDIP	24	M	STAT EM	EBRN	9/77	025C	N/R		21	0	
					BAKE			125C		1.01E 03	21	0	
					TEMPCYC			-065C 125C			21	0	
								10CY					
								15/15DT					
					HERMETC						21	0	
					STAT EM			025C			21	1	
					BURN-IN			125C		5.81E 03	20	0	
					DYN LM			025C			20	0	
					X-RAY						20	10	
					VIS INS						10	0	
	D				STAT EM	EBRN	9/77	025C	N/R		5	0	
					BAKE			125C		2.40E 02	5	0	
					TEMPCYC			-065C 125C			5	0	
								10CY					
								15/15DT					
					HERMETC						5	0	
					STAT EM			025C			5	1	
					BURN-IN			125C		9.60E 02	4	0	
					DYN EM			025C			4	0	
					X-RAY						4	0	
					VIS INS						4	0	
					OP DYN	LIFE	1/79	125C	N/R	8.50E 04	85	0	
					LM			25C			85	0	

VARIOUS — PROM

TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	OP DYN	LIFE	9/78	150C	N/k	2.90E 04	29	3	
					S&F EM			25C			29	5	
					OP DYN	BRN	9/78	150C	N/R	2.40E 03	12	0	
					S&F EM			25C			12	0	
N/R		NHDIP	24	C	OP DYN	LIFE	9/78	150C	N/R	3.20E 04	16	1	
					S&F EM			25C			16	0	

NATIONAL SEMI — PROM

TTL — BIPOLAR — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8581	JB/B1	NHDIP	40	C	N/R	FIELD	1/79	25C	GF	1.37E 04	1	0	
					N/R	FIELD	7/79	25C	GF	4.32E 03	1	0	
					N/R	FIELD	8/80	25C	GF	1.01E 04	1	0	

FAIRCHILD SEMI — PROM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10416	D	NHSQR	18	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		29	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
10416/100416		NHDIP	16	M	OP DYN	LIFE	5/79	125C	N/R	1.74E 05	87	0	
					EM						87	0	
					OP DYN	LIFE	5/79	125C	N/R	1.34E 05	76	0	
					EM						76	0	
					OP DYN	LIFE	5/79	125C	N/R	3.52E 04	20	0	
					EM						20	0	

INTEL — PROM

N-STAT — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2708	D	NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	3.93E 06	81897	0	
					EM			25C			81897	217	2537
													2538
													2539
													2540
													2541
													2542
													2543
													2544
													2545
													2546
					OP DYN	LIFE	6/80	125C	N/R	3.90E 06	18913	0	
					EM			25C			18913	19	2611
													2612
													2613
													2614
					OP DYN			125C		1.70E 06	5111	0	
					EM			25C			5111	12	2615
													2616
					OP DYN			125C		2.57E 06	5132	0	
					EM			25C			5132	5	2617
													2618
													2619
													2620
					OP DYN			125C		1.20E 05	120	0	
					EM			25C			120	0	
					REVBIAS	LIFE	6/80	150C	N/R	7.29E 04	434	0	
					EM			25C			434	1	2643
					REVBIAS			150C		1.41E 05	424	0	
					EM			25C			424	0	
					REVBIAS			150C		2.11E 05	421	0	
					EM			25C			421	0	
					BAKE	LIFE	6/80	250C	N/R	6.54E 04	1363	0	
					EM			25C			1363	9	2682
													2683
					BAKE			250C		1.44E 06	12032	0	
					EM			25C			12032	90	2684

INTEL — PROM

N-STAT — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N2708	D	NHDIP	24	M	EM	LIFE	6/80	25C	N/R		12032	90	2685
													2686
													2687
					BAKE			250C		3.78E 06	11399	0	
					EM			25C			11399	32	2686
													2689
													2690
					OP DYN	LIFE	6/80	-10C	N/R	4.60E 04	92	0	
					EM			25C			92	0	
					OP DYN			-10C		4.60E 04	92	0	
					EM			25C			92	0	
					TEMPCYC	ENV	6/80	-055C 125C	N/R		76	0	
								200 CYC					
					EM			025C			76	0	

VARIOUS — PROM

S/R TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	2.74E 04	2	0	
					N/R	FIELD	7/79	25C	GF	8.64E 03	2	0	
					N/R	FIELD	8/80	25C	GF	2.02E 04	2	0	

VARIOUS — PROM

S/R TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	2.60E 05	19	0	
					N/R	FIELD	1/79	25C	GF	6.84E 04	5	0	
					N/R	FIELD	1/79	25C	GF	2.60E 05	19	0	
					N/R	FIELD	7/79	25C	GF	8.21E 04	19	0	
					N/R	FIELD	7/79	25C	GF	8.21E 04	19	0	
					N/R	FIELD	7/79	25C	GF	2.16E 04	5	0	
	JB/B1				N/R	FIELD	8/80	25C	GF	1.92E 05	19	0	
					N/R	FIELD	8/80	25C	GF	1.92E 05	19	0	
					N/R	FIELD	8/80	25C	GF	5.04E 04	5	0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7602/03	C-2	NHDIP	16	N/R	OP DYN	LIFE	4/79	125C	N/R	1.08E 05	108	0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7602/03	C-2	HDIP	16	C	RHRB	LIFE	7/79	85C	N/R	9.00E 04	72	0	
					EM						72	0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5330	D	NHDIP	16	M	PAR EXC	LIFE	10/61	125C	N/R	7.70E 04	77	0	
5331		NHDIP	16	M	OP DYN	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
					PAR EXC	LIFE	10/81	125C	N/R	1.54E 05	154	0	
6330		NHDIP	16	C	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	
6331		NHDIP	16	C	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	

NATIONAL SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S188	D-1	HDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	6.05E 04	60	0	
					EM						60	0	
					OP DYN	LIFE	12/78	125C	N/R	4.03E 04	40	0	
					EM						40	0	

SIGNETICS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S23	D-1	HDIP	16	N/R	OP DYN	LIFE	11/77	85C	N/R	3.60E 04	36	0	
					EM						36	0	
82S23	D	NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S288	B-1	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	6.24E 04	6	0	
					N/R	FIELD	2/78	25C	GBC	4.99E 04	9	0	
					N/R	FIELD	6/78	25C	GBC	1.73E 04	6	0	
					N/R	FIELD	6/78	25C	GBC	2.59E 04	9	0	

ADVANCED MICRO DEVICES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
27S20	B-2	NHDIP	16	M	REVBIAS	LIFE	6/80	125C	N/R	7.70E 04	77	0	
					EM			125C			77	0	
27S21		NHDIP	16	M	REVBIAS	LIFE	6/80	125C	N/R	1.68E 05	168	0	
					EM			125C			168	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93417	D-1	DIP	16		RHRB	LIFE	5/77	85C	N/R	2.20E 04	11	0	
					EM						11	0	
					RHRB	LIFE	5/77	85C	N/R	3.80E 04	19	0	
					EM						19	0	
					OP DYN	LIFE	5/79	100C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP DYN	LIFE	5/79	100C	N/R	8.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/79	100C	N/R	4.00E 04	20	0	
					EM						20	0	
					RHRB	LIFE	5/79	85C	N/R	2.20E 04	11	0	
					EM						11	0	
					RHRB	LIFE	5/79	85C	N/R	6.84E 03	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	6.80E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/79	85C	N/R	8.20E 04	41	0	
					EM						41	0	
					RHRB	LIFE	5/79	85C	N/R	5.40E 04	27	0	
					EM						27	0	
					RHRB	LIFE	5/79	85C	N/R	5.80E 04	29	0	
					EM						29	0	
					RHRB	LIFE	5/79	85C	N/R	7.00E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/79	85C	N/R	5.80E 04	29	0	
					EM						29	0	
					RHRB	LIFE	5/79	85C	N/R	7.60E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	85C	N/R	7.60E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	85C	N/R	1.24E 05	31	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.		#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:93417	:01	16	:C	EM	LIFE	5/79		N/R		31	0	
				RHRB	LIFE	5/79	85C	N/R	7.40E 04	37	0	
				EM						37	0	
				RHRB	LIFE	5/79	85C	N/R	1.99E 05	99	1	
				EM						98	0	
				RHRB	LIFE	5/79	85C	N/R	7.40E 04	37	0	
				EM						37	0	
				RHRB	LIFE	5/79	85C	N/R	2.70E 04	18	0	
				EM						18	0	
				RHRB	LIFE	5/79	85C	N/R	4.50E 04	45	0	
				EM						45	0	
				RHRB	LIFE	5/79	85C	N/R	8.40E 04	42	0	
				EM						42	0	
				RHRB	LIFE	5/79	85C	N/R	8.00E 04	40	0	
				EM						40	0	
				RHRB	LIFE	5/79	85C	N/R	1.26E 05	42	0	
				EM						42	0	
				RHRB	LIFE	5/79	85C	N/R	7.40E 04	37	0	
				EM						37	0	
				THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
							15CY					
							LIQUID					
				TEMPCYC			-065C 150C			25	0	
							10CY					
							10/10DT					
				FINE LK			HE 5.E-8			25	0	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			25	0	
							3X					
							60PSIG					
				EM						25	0	
				THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
							1000CY					
							LIQUID					
				FINE LK			HE 5.E-8			50	0	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			50	0	
							3X					
							60PSIG					
				EM						50	0	
				AUTOCLV	ENV	8/79	15PSIG121C	N/R		25	1	
							500HRS					
				EM						24	0	
				RHRB	LIFE	12/79	85C	N/R	9.20E 04	92	0	
				EM						92	0	
				RHRB	LIFE	12/79	85C	N/R	3.75E 04	25	0	
				EM						25	0	
				RHRB	LIFE	12/79	85C	N/R	3.50E 04	35	0	
				EM						35	0	
:93417	:D	:NHDIP	16	:M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		24	0	
							6 AXES					
							5 BLOS					
				VBVRFQ			20HZ 2KHZ			24	0	
							20G					
							3 AXES					
				CNSTACC			30KG 6 AXES			24	0	
							1 MIN E					
				HERMETC						24	0	
				THRMSHK	ENV	5/77	-055C 125C	N/R		24	0	
							15CY					
							LIQUID					
				TEMPCYC			-065C 150C			24	0	
							10CY					
							10/10DT					
				HERMETC						24	0	
				OP DYN	LIFE	5/77	125C	N/R	4.95E 04	33	0	
				EM						33	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
93417	D	NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	1.28E 05	64	0	
					EM						64	0	
					OP DYN	LIFE	5/77	125C	N/R	1.80E 05	90	0	
					EM						90	0	
					OP DYN	LIFE	5/77	125C	N/R	1.19E 05	119	0	
					EM						119	0	
93417		NHFPK	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		16	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			16	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			16	0	
								1 MIN E					
					HERMETC						16	0	
93417		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	5.20E 04	52	0	
					EM						52	0	
93417		NHDIP	16	M	MECHSHK	ENV	8/79	1.5G .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					OP DYN	LIFE	12/79	125C	N/R	3.50E 04	35	0	
					EM						35	0	
93427		NHFPK	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL.	MFEF #
93427	D	HDIPPK	16	M	HERMETC	ENV	5/77		N/R		25	0	
					THRMSHK	ENV	5/77	:-055C 125C	N/R		25	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			25	0	
								:10CY					
								:10/10DT					
					MOIST			:-010C 065C			25	0	
								:98%RH					
					HERMETC						25	0	
					THRMSHK	ENV	5/77	:-055C 125C	N/R		25	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			25	0	
								:10CY					
								:10/10DT					
					CNSTACC			:6 AXES			25	0	
								:1 MIN E					
					HERMETC						25	0	
93427		HHDIP	16	M	OP DYN	LIFE	5/77	: 125C	N/R	5.20E 04	26	0	
					EM						26	0	
					OP DYN	LIFE	5/77	: 125C	N/R	6.60E 04	66	0	
					EM						66	1	
					OP DYN	LIFE	5/79	: 125C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	: 125C	N/R	8.00E 04	80	0	
					EM						80	0	
					TEMPCYC	ENV	8/79	:-065C 150C	N/R		16	0	
								:10CY					
								:10/10DT					
					CNSTACC			:30KG 6 AXES			16	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			16	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			16	0	
								:3X					
								:60PSIG					
					EM						16	0	
93427	D-1	HDIP	16	C	RHRB	LIFE	5/77	: 85C	N/R	3.40E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/77	: 85C	N/R	6.80E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/77	: 85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/77	: 85C	N/R	5.80E 04	29	0	
					EM						29	0	
					OP DYN	LIFE	5/79	: 100C	N/R	4.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	: 100C	N/R	3.00E 04	15	0	
					EM						15	0	
					OP DYN	LIFE	5/79	: 100C	N/R	9.20E 04	46	0	
					EM						46	0	
					RHRB	LIFE	5/79	: 85C	N/R	7.60E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	: 85C	N/R	3.00E 04	15	0	
					EM						15	0	
					RHRB	LIFE	5/79	: 85C	N/R	2.82E 04	14	1	
					EM						13	0	
					RHRB	LIFE	5/79	: 85C	N/R	7.00E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	: 85C	N/R	8.00E 04	40	0	
					EM						40	0	
					RHRB	LIFE	5/79	: 85C	N/R	7.00E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	: 85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/79	: 85C	N/R	7.50E 04	37	0	
					EM						37	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL.	MFEF #
93427	D-1	HDIP	16	C	RHRB	LIFE	12/79	85C	N/R	2.90E 04	29	0	
					EM						29	0	
					OP DYN	LIFE	12/79	125C	N/R	5.42E 04	37	1	2391
					EM						36	0	
					RHRB	LIFE	12/79	85C	N/R	2.90E 04	29	0	
					EM						29	0	
					RHRB	LIFE	12/79	85C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	12/79	85C	N/R	7.50E 03	5	0	
					EM						5	0	
					RHRB	LIFE	12/79	85C	N/R	3.80E 04	38	0	
					EM						38	0	
93427	D	NHDIP	16	M	OP DYN	LIFE	5/79	125C	N/R	1.56E 05	78	0	
					EM						78	0	
	D-1				FREEZE	LIFE	5/79	-10C	N/R	3.10E 04	31	0	
					EM						31	0	
					FREEZE	LIFE	5/79	-10C	N/R	1.00E 05	50	0	
					EM						50	0	
	D				CNSTACC	ENV	6/79	30KG 6 AXES	N/R		47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		35	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			35	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93427	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		51	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			51	0	
								1 MIN E					
					FINE LK			HE 5.E-8			51	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			51	0	
								3X					
								60PSIG					
					EM						51	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		15	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			15	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								60PSIG					
					EM						15	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93427	D	NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7610/11	C-2	NHDIP	16	N/R	OP DYN	LIFE	4/79	125C	N/R	1.80E 05	180	0	

INTEL — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3601	D-1	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	3.33E 04	6	0	
					N/R	FIELD	2/78	25C	GBC	5.04E 05	50	0	
					N/R	FIELD	6/78	25C	GBC	1.73E 04	6	0	
					N/R	FIELD	6/78	25C	GBC	1.44E 05	50	0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
53S140	D-1	HDIP	16	M	HUMLIFE	LIFE	10/81	85C	N/R	3.80E 04	38	0	
					TEMPCYC	ENV	10/81	000C +100C	N/R		38	0	
								100CY					
					HIPRESS	LIFE	10/81	0C	N/R	6.38E 03	38	1	
53S141	D	NHDIP	16	M	PAR EXC	LIFE	10/81	125C	N/R	1.46E 05	146	0	
5300		NHDIP	16	M	OP CNST	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
5300	D-1	HDIP	16	M	OP DYN	LIFE	1/79	125C	N/R	7.50E 04	75	0	
					EM			25C			75	0	
5301	D	NHDIP	20	M	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	
63S140	D-1	HDIP	16	C	OP DYN	LIFE	1/79	125C	N/R	9.50E 04	95	0	
					EM			25C			95	0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
63S140	D-1	HDIP	16	C	PAR EXC	LIFE	10/81	125C	N/R	1.14E 05	114	0	
					HUMLIFE	LIFE	10/81	85C	N/R	7.60E 04	76	1	3703
					TEMPCYC	ENV	10/81	000C +100C 100CY	N/R		114	0	
					HIPRESS	LIFE	10/81	0C	N/R	1.92E 04	114	2	3706
63S140	D	NHDIP	16	C	PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	
63S141	D-1	HDIP	16	C	PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	
					HUMLIFE	LIFE	10/81	85C	N/R	3.80E 04	38	0	
					TEMPCYC	ENV	10/81	000C +100C 100CY	N/R		38	0	
					HIPRESS	LIFE	10/81	0C	N/R	6.38E 03	38	0	
6301		HDIP	16	C	OP DYN	LIFE	1/79	125C	N/R	5.00E 04	50	0	
					EM			25C			50	0	

NATIONAL SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S287	D-1	HDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	1	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	3.63E 05	180	0	
					EM						180	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	5.47E 05	264	0	
					EM						264	3	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	1.69E 05	84	0	
					EM						84	1	
					OP DYN	LIFE	12/78	125C	N/R	1.13E 05	56	0	
					EM						56	0	
					OP DYN	LIFE	12/78	125C	N/R	8.57E 04	85	0	
					EM						85	1	
					OP DYN	LIFE	12/78	125C	N/R	4.54E 04	45	0	
					EM						45	0	
					OP DYN	LIFE	12/78	125C	N/R	4.54E 04	45	0	
					EM						45	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	6.05E 04	60	0	
					EM						60	3	
					OP DYN	LIFE	12/78	125C	N/R	6.80E 04	45	0	
					EM						45	1	
					OP DYN	LIFE	12/78	125C	N/R	3.02E 04	30	0	
					EM						30	1	
					OP DYN	LIFE	12/78	125C	N/R	9.07E 04	45	0	
					EM						45	0	
					OP DYN	LIFE	12/78	125C	N/R	1.01E 05	50	0	
					EM						50	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	

NATIONAL SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S287	D-1	HDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	1	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	1	
					OP DYN	LIFE	12/78	125C	N/R	3.02E 04	30	0	
					EM						30	0	
74S287	D	NHDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	8.06E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	12/78	125C	N/R	1.39E 05	138	0	
					EM						138	1	
					OP DYN	LIFE	12/78	125C	N/R	2.52E 04	25	0	
					EM						25	0	
74S387		NHDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	5.44E 04	27	0	
					EM						27	0	
74S387	D-1	HDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	1.80E 05	119	0	
					EM						119	2	

SIGNETICS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S126	D	NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					STGL LIFE	LIFE	11/77	150C	N/R	6.60E 04	65	0	
					EM						65	0	
82S126		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	6.30E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	85C	N/R	1.92E 05	95	0	
					EM						95	0	
					STGL LIFE	LIFE	11/77	150C	N/R	6.60E 04	22	0	
					EM						22	0	
					STGL LIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGL LIFE	LIFE	11/77	150C	N/R	1.94E 05	96	0	
					EM						96	2	
82S129		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	8.60E 04	86	0	
					EM						86	0	
					STGL LIFE	LIFE	11/77	150C	N/R	4.30E 04	43	0	
					EM						43	0	
82S129		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	7.50E 04	25	0	
					EM						25	1	
					STGL LIFE	LIFE	11/77	150C	N/R	7.20E 04	24	0	
					EM						24	0	

VARIOUS PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	16	C	OP DYN	LIFE	9/78	150C	N/R	5.25E 03	10	0	
					S&F EM			25C			10	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93436	D	NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	6.80E 04	34	0	
					EM						34	0	
93436		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	1.90E 05	95	0	
					EM						95	0	
					OP DYN	LIFE	5/77	125C	N/R	1.68E 05	84	0	
					EM						84	0	
					OP DYN	LIFE	5/77	125C	N/R	4.40E 04	22	0	
					EM						22	0	
					OP DYN	LIFE	5/77	125C	N/R	9.90E 04	99	0	
					EM						99	0	
					OP DYN	LIFE	5/77	125C	N/R	3.54E 05	177	0	
					EM						177	0	
					OP DYN	LIFE	5/77	125C	N/R	7.78E 05	389	0	
					EM						389	1	
					OP DYN	LIFE	5/77	125C	N/R	1.70E 05	85	0	
					EM						85	0	
					OP DYN	LIFE	5/77	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					REVBIAS	LIFE	5/77	125C	N/R	3.76E 05	188	0	
					EM						188	0	
					OP DYN	LIFE	5/79	125C	N/R	1.11E 05	111	0	
					EM						111	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		157	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			157	0	
								1 MIN E					
					FINE LK			HE 5.E-8			157	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			157	0	
								3X					
								60PSIG					
					EM						157	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		20	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
93436	D-1	HDIP	16	C	RHRB	LIFE	5/77	85C	N/R	6.16E 05	88	0	
					EM						88	0	
					RHRB	LIFE	5/77	85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/77	85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/77	85C	N/R	1.50E 05	75	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93436	D-1	HDIP	16	C	EM	LIFE	5/77		N/R		75	0	
					RHRB	LIFE	5/77	85C	N/R	1.80E 05	90	0	
					EM						90	0	
					RHRB	LIFE	5/77	85C	N/R	6.60E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	5/77	100C	N/R	2.68E 05	134	0	
					EM						134	1	
					OP CNST	LIFE	5/77	100C	N/R	1.96E 05	98	0	
					EM						98	0	
					RHRB	LIFE	5/79	85C	N/R	3.93E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	3.00E 04	20	0	
					EM						20	0	
					RHRB	LIFE	5/79	85C	N/R	6.40E 04	32	0	
					EM						32	0	
					OP DYN	LIFE	5/79	100C	N/R	1.25E 05	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	100C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	100C	N/R	5.87E 04	30	0	
					EM						30	0	
					OP DYN	LIFE	5/79	100C	N/R	4.80E 04	32	0	
					EM						32	0	
					OP DYN	LIFE	5/79	100C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	100C	N/R	2.00E 04	20	0	
					EM						20	0	
					RHRB	LIFE	5/79	85C	N/R	6.19E 05	88	3	
					EM						85	0	
					RHRB	LIFE	5/79	85C	N/R	7.29E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	2.68E 05	88	0	
					EM						88	0	
					RHRB	LIFE	5/79	85C	N/R	5.40E 04	27	0	
					EM						27	0	
					RHRB	LIFE	5/79	85C	N/R	3.40E 04	17	0	
					EM						17	0	
					RHRB	LIFE	5/79	85C	N/R	5.55E 04	37	0	
					EM						37	0	
					RHRB	LIFE	5/79	85C	N/R	3.80E 04	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	9.00E 04	45	0	
					EM						45	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	38	1	
					EM						37	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		13	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			13	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			13	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			13	0	
								3X					
								60PSIG					
					EM						13	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93436	D-1	HDIP	16	C	AUTOCLV	ENV	8/79	15PSIG121C 500HRS	N/R		20	0	
					EM						20	0	
					OP DYN	LIFE	12/79	100C	N/R	1.60E 04	32	0	
					EM						32	0	
					OP DYN	LIFE	12/79	100C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	12/79	100C	N/R	1.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	12/79	125C	N/R	1.46E 05	73	0	
					EM						73	0	
					OP DYN	LIFE	12/79	125C	N/R	1.89E 05	126	0	
					EM						126	0	
					RHRB	LIFE	12/79	85C	N/R	1.07E 04	25	0	
					EM						25	0	
					RHRB	LIFE	12/79	85C	N/R	1.00E 04	20	0	
					EM						20	0	
					RHRB	LIFE	12/79	85C	N/R	2.34E 04	20	0	
					EM						20	0	
					RHRB	LIFE	12/79	85C	N/R	1.60E 04	19	0	
					EM						19	0	
					RHRB	LIFE	12/79	85C	N/R	6.40E 04	32	0	
					EM						32	0	
					RHRB	LIFE	12/79	85C	N/R	6.40E 04	32	0	
					EM						32	0	
					RHRB	LIFE	12/79	85C	N/R	5.20E 04	26	0	
					EM						26	0	
					RHRB	LIFE	12/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	12/79	85C	N/R	3.40E 04	34	0	
					EM						34	1	2393
93436	D	NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	1.08E 05	54	0	
					EM						54	0	
					OP DYN	LIFE	5/77	125C	N/R	5.20E 04	52	0	
					EM						52	0	
93436		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	9.40E 04	47	0	
					EM						47	0	
					OP DYN	LIFE	5/77	125C	N/R	2.06E 05	103	0	
					EM						103	0	
					OP DYN	LIFE	5/77	125C	N/R	1.14E 05	57	0	
					EM						57	0	
	D-1				FREEZE	LIFE	5/79	- 10C	N/R	5.00E 04	50	0	
					EM						50	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.50E 04	25	0	
					EM						25	0	
93436	D	NHDIP	24	M	OP DYN	LIFE	5/77	125C	N/R	1.98E 05	99	0	
					EM						99	0	
93436		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	2.06E 05	103	0	
					EM						103	0	
93436		NHDIP	16	M	OP DYN	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					OP DYN	LIFE	5/79	125C	N/R	1.98E 05	99	0	
					EM						99	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		25	0	
					VBVRFQ			20HZ 2KHZ 20G			25	0	
					CNSTACC			30KG 6 AXES 1 MIN E			25	0	
					FINE LK			HE 5.E-8 60 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93436	D	NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		27	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			27	0	
								3X					
								60PSIG					
					EM						27	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
	D-1				RHRB	LIFE	12/79	85C	N/R	1.62E 05	81	0	
					EM						81	0	
93446		HDIP	16	C	FREEZE	LIFE	5/77	- 50C	N/R	5.00E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/77	85C	N/R	7.40E 04	37	0	
					EM						37	0	
					RHRB	LIFE	5/77	85C	N/R	7.80E 04	39	1	
					EM						39	1	
					RHRB	LIFE	5/77	85C	N/R	5.25E 05	105	0	
					EM						105	0	
					RHRB	LIFE	5/77	85C	N/R	5.00E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/77	85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/77	85C	N/R	1.94E 05	130	0	
					EM						130	1	
					OP CNST	LIFE	5/77	75C	N/R	1.08E 05	54	0	
					EM						54	0	
					OP CNST	LIFE	5/77	100C	N/R	1.91E 05	127	0	
					EM						127	0	
					RHRB	LIFE	5/79	85C	N/R	5.00E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	5.00E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	2.40E 04	16	0	
					EM						16	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	4.95E 04	33	0	
					EM						33	0	
					RHRB	LIFE	5/79	85C	N/R	5.25E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	85C	N/R	4.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/79	100C	N/R	2.00E 05	101	1	
					EM						101	0	
					OP DYN	LIFE	5/79	100C	N/R	3.80E 04	19	0	
					EM						19	0	
					OP DYN	LIFE	5/79	100C	N/R	1.00E 05	50	0	
					EM						50	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D-1	HDIP	16	C	OP DYN	LIFE	5/79	100C	N/R	1.08E 05	54	0	
					EM						54	0	
					OP DYN	LIFE	5/79	100C	N/R	6.51E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	100C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	100C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	100C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	100C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	100C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	100C	N/R	8.41E 04	43	0	
					EM						43	0	
					OP DYN	LIFE	5/79	100C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	100C	N/R	3.80E 04	19	0	
					EM						19	0	
					OP DYN	LIFE	5/79	100C	N/R	3.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	100C	N/R	2.50E 04	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	100C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	LIFE	5/79	100C	N/R	3.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP DYN	LIFE	5/79	100C	N/R	6.02E 04	31	1	
					EM						31	0	
					RHRB	LIFE	5/79	85C	N/R	2.00E 05	40	0	
					EM						40	0	
					RHRB	LIFE	5/79	85C	N/R	1.26E 06	105	8	
					EM						97	0	
					RHRB	LIFE	5/79	85C	N/R	1.09E 06	129	1	
					EM						128	0	
					RHRB	LIFE	5/79	85C	N/R	2.00E 05	100	0	
					EM						100	0	
					RHRB	LIFE	5/79		N/R	4.00E 04	20	0	
					EM			0C			20	0	
					RHRB	LIFE	5/79	85C	N/R	6.80E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/79	85C	N/R	3.80E 04	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	1.14E 05	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	1.38E 05	23	0	
					EM						23	0	
					RHRB	LIFE	5/79	85C	N/R	6.60E 04	33	0	
					EM						33	0	
					RHRB	LIFE	5/79	85C	N/R	6.80E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/79	85C	N/R	8.80E 04	44	0	
					EM						44	0	
					RHRB	LIFE	5/79	85C	N/R	8.02E 04	37	0	
					EM						37	0	
					RHRB	LIFE	5/79	85C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	9.82E 04	49	1	
					EM			0C			48	0	
					RHRB	LIFE	5/79	85C	N/R	2.55E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	85C	N/R	7.00E 04	35	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D-1	HDIP	16	C	EM	LIFE	5/79		N/R		35	0	
					RHRB	LIFE	5/79	85C	N/R	6.20E 04	31	0	
					EM						31	0	
					RHRB	LIFE	5/79	85C	N/R	7.80E 04	39	0	
					EM						39	0	
					RHRB	LIFE	5/79	85C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	5.40E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	7.20E 04	36	0	
					EM						36	0	
					RHRB	LIFE	5/79	85C	N/R	2.98E 05	149	0	
					EM						149	0	
					RHRB	LIFE	5/79	85C	N/R	7.80E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	85C	N/R	1.75E 05	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	85C	N/R	6.80E 04	34	0	
					EM						34	0	
					RHRB	LIFE	5/79	85C	N/R	7.60E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	85C	N/R	7.60E 04	38	0	
					EM						38	0	
					RHRB	LIFE	5/79	85C	N/R	4.20E 04	21	0	
					EM						21	0	
					RHRB	LIFE	5/79	85C	N/R	6.40E 04	32	0	
					EM						32	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		20	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			20	0	
					MOIST			-010C 065C 98%RH			20	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			20	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			20	0	
					EM						20	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		25	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			25	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C 1000CY LIQUID	N/R		25	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	
					AUTOCLV	ENV	8/79	15PSIG121C 500HRS	N/R		29	0	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D-1	HDIP	16	C	EM	FNV	8/79		N/R		29	0	
					AUTOCLV	ENV	8/79	15PSIG121C 500HRS	N/R		109	0	
					EM						109	0	
					OP DYN	LIFE	12/79	100C	N/R	5.40E 04	54	0	
					EM						54	0	
					OP DYN	LIFE	12/79	125C	N/R	1.12E 05	56	0	
					EM						56	0	
					OP DYN	LIFE	12/79	125C	N/R	1.24E 05	62	0	
					EM						62	0	
					OP DYN	LIFE	12/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	12/79	85C	N/R	1.65E 04	33	0	
					EM						33	0	
					RHRB	LIFE	12/79	85C	N/R	1.75E 04	35	0	
					EM						35	0	
					RHRB	LIFE	12/79	85C	N/R	4.00E 04	40	0	
					EM						40	0	
					RHRB	LIFE	12/79	85C	N/R	1.32E 05	66	0	
					EM						66	0	
					RHRB	LIFE	12/79	85C	N/R	9.90E 04	50	1	2392
					EM						49	0	
93446	D	NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	9.80E 04	49	0	
					EM						49	0	
93446		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	8.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/77	125C	N/R	5.80E 04	29	0	
					EM						29	0	
					OP DYN	LIFE	5/79	125C	N/R	7.00E 04	35	0	
					EM						35	0	
					OP DYN	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					OP DYN	LIFE	5/79	125C	N/R	5.60E 05	280	0	
					EM						280	0	
					OP DYN	LIFE	5/79	125C	N/R	4.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/79	125C	N/R	4.60E 04	23	0	
					EM						23	0	
					OP DYN	LIFE	5/79	125C	N/R	1.66E 05	83	0	
					EM						83	0	
					OP DYN	LIFE	5/79	125C	N/R	7.70E 04	77	0	
					EM						77	0	
					OP DYN	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
	D-1				FREEZE	LIFE	5/79	- 10C	N/R	3.50E 04	35	0	
					EM						35	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.46E 04	24	0	
					EM						24	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.56E 04	25	0	
					EM						25	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.40E 04	24	0	
					EM						24	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.50E 04	25	0	
					EM						25	0	
					FREEZE	LIFE	5/79	- 10C	N/R	2.50E 04	25	0	
					EM						25	0	
	D				OP DYN	LIFE	5 79	125C	N/R	1.88E 05	94	0	
					EM						94	0	
					OP DYN	LIFE	5/79	125C	N/R	1.92E 05	96	0	
					EM						96	0	
					OP DYN	LIFE	5/79	125C	N/R	1.04E 05	52	0	
					EM						52	0	
					OP DYN	LIFE	5/79	125C	N/R	6.80E 04	34	0	
					EM						34	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		23	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	NHDIP	16	M	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		23	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	
93446		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	2.08E 05	104	0	
					EM						104	0	
					OP DYN	LIFE	5/77	125C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP DYN	LIFE	5/79	125C	N/R	2.88E 05	144	0	
					EM						144	0	
					OP LIFE	LIFE	5/79	125C	N/R	7.80E 04	78	0	
					EM						78	0	
					OP DYN	LIFE	5/79	125C	N/R	2.44E 05	122	0	
					EM						122	0	
					OP DYN	LIFE	5/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	125C	N/R	1.64E 05	82	0	
					EM						82	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		29	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			29	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		20	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					THRMSHK	ENV	8/79	-055 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					OP DYN	LIFE	12/79	125C	N/R	2.19E 05	101	0	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	NHDIP	16	M	EM	LIFE	12/79		N/R		101	0	
93446		NHDIP	16	M	OP DYN	LIFE	5/77	125C	N/R	8.40E 04	42	0	
					EM						42	0	
93446		NHDIP	16	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								10 CCY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		47	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			47	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		100	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			100	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			100	0	
								1 MIN E					
					FINE LK			HE 5.E-8			100	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			100	0	
								3X					
								60PSIG					
					EM						100	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		12	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			12	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			12	0	
								1 MIN E					
					FINE LK			HE 5.E-8			12	0	
								60 MIN					
								30 MIN					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	MDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		12	0	
								3X					
								60PSIG					
					EM						12	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		10	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			100	0	
								1 MIN E					
					FINE LK			HE 5.E-8			100	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			100	0	
								3X					
								60PSIG					
					EM						100	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		27	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			27	0	
								3X					
								60PSIG					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	NHDIP	16	M	EM	ENV	8/79		N/R		27	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		12	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			12	0	
								1 MIN E					
					FINE LK			HE 5.E-8			12	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			12	0	
								3X					
								60PSIG					
					EM						12	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		27	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			27	0	
								3X					
								60PSIG					
					EM						27	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		10	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			10	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			10	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			10	0	
								3X					
								60PSIG					
					EM						10	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		44	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			44	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			44	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			44	0	
								3X					
								60PSIG					
					EM						44	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		34	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			34	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			34	0	
								98%RH					
					FINE LK			HE 5.E-8			34	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			34	0	
								3X					
								60PSIG					
					EM						34	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		45	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			45	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			45	0	
								98%RH					
					FINE LK			HE 5.E-8			45	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			45	0	
								3X					
								60PSIG					
					EM						45	0	
					OP DYN	LIFE	12/79	125C	N/R	5.61E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	12/79	125C	N/R	1.60E 05	96	0	
					EM						96	0	
					OP DYN	LIFE	12/79	125C	N/R	7.34E 04	44	0	
					EM						44	0	
					OP DYN	LIFE	12/79	125C	N/R	1.09E 05	93	0	
					EM						93	0	
93446		NHDIP	16	M	OP DYN	LIFE	5/79	125C	N/R	8.80E 04	44	0	
					EM						44	0	
					OP DYN	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93446	D	NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:93446	:D	:NHDIP	16	:M	: FINE LK	: ENV	: 8/79	:HE 5.E-8	: N/R		: 20	: 0	
								:60 MIN					
								:30 MIN					
					: GROSSLK			:FLUOR 125C			: 20	: 0	
								:3X					
								:60PSIG					
					: FN			:			: 20	: 0	
					: OP DYN	: LIFE	: 12/79	: 10C	: N/R	: 9.50E 04	: 95	: 0	
					: EM			:			: 95	: 0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2048	:B-1	:NHDIP	16	:M	: N/R	: FIELD	: 10/80	:	: AUT	: 2.55E 05	: 60	: 0	
:7620/21	:C-2	:NHDIP	16	:N/R	: OP DYN	: LIFE	: 4/79	: 125C	: N/R	: 9.50E 04	: 95	: 0	
:7620/21A	:	:NHDIP	16	:M	: OP DYN	: LIFE	: 7/79	:- 40C	: N/R	: 1.44E 05	: 144	: 1	
					: EM			:			: 143	: 0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:53S241	:D	:NHDIP	16	:M	: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 1.25E 05	: 75	: 0	
:53S241	:D-1	:HDIP	16	:M	: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 7.50E 04	: 75	: 0	
					: HUMLIFE	: LIFE	: 10/81	: 85C	: N/R	: 7.60E 04	: 76	: 0	
					: TEMPCYC	: ENV	: 10/81	:000C +100C	: N/R		: 38	: 0	
								:100CY					
					: HIPRESS	: LIFE	: 10/81	: 0C	: N/R	: 6.38E 03	: 38	: 0	
:5306	:	:HDIP	16	:M	: OP DYN	: LIFE	: 1/79	: 85C	: N/R	: 3.15E 05	: 210	: 0	
					: EM			: 25C			: 210	: 0	
:5306	:D	:NHDIP	16	:M	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 1.77E 05	: 177	: 0	
					: EM			: 25C			: 177	: 0	
					: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 9.00E 04	: 90	: 0	
:5306	:	:NHFPK	16	:M	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 1.05E 05	: 105	: 0	
					: EM			: 25C			: 105	: 0	
:63S240	:D-1	:HDIP	16	:C	: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 1.14E 05	: 114	: 0	
					: HUMLIFE	: LIFE	: 10/81	: 85C	: N/R	: 7.60E 04	: 76	: 0	
					: TEMPCYC	: ENV	: 10/81	:000C +100C	: N/R		: 76	: 0	
								:100CY					
					: HIPRESS	: LIFE	: 10/81	: 0C	: N/R	: 1.28E 04	: 76	: 0	
:63S241	:D	:NHDIP	16	:C	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 2.50E 04	: 25	: 0	
					: EM			: 25C			: 25	: 0	
					: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 3.80E 04	: 38	: 0	
:63S241	:D-1	:HDIP	16	:C	: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 8.80E 04	: 88	: 1	: 3698
:6306	:D	:NHDIP	16	:C	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 4.50E 04	: 45	: 0	
					: EM			: 25C			: 45	: 0	
:6306	:D-1	:HDIP	16	:C	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 5.00E 04	: 50	: 0	
					: EM			: 25C			: 50	: 0	
:6309	:D	:NHDIP	20	:C	: PAR EXC	: LIFE	: 10/81	: 125C	: N/R	: 3.40E 04	: 34	: 0	
:6335	:	:NHDIP	24	:C	: OP DYN	: LIFE	: 1/79	: 125C	: N/R	: 4.50E 04	: 45	: 0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6335	D	NHDIP	24	C	EM	LIFE	1/79	25C	N/R		45	0	
					PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	

SIGNETICS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S130	D	NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGL LIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
82S131		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	7.80E 04	77	0	
					EM						77	0	
					STGL LIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	1	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93438	D	NHFPK	24	M	THRMSHK	ENV	5/77	-055C 125C	N/R		24	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			24	0	
								10CY					
								10/10DT					
					HERMETC						24	0	
93438		NHDIP	24	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					HERMETC						25	0	
					OP DYN	LIFE	5/77	125C	N/R	4.20E 04	42	0	
					EM						42	0	
					OP DYN	LIFE	5/77	125C	N/R	1.20E 05	60	0	
					EM						60	0	
					OP DYN	LIFE	5/77	125C	N/R	1.36E 05	68	0	
					EM						68	1	
					OP DYN	LIFE	5/77	125C	N/R	2.36E 05	118	0	
					EM						118	0	
					OP DYN	LIFE	5/77	125C	N/R	7.40E 04	37	0	
					EM						37	0	
					OP DYN	LIFE	5/77	125C	N/R	1.86E 05	93	0	
					EM						93	0	
					OP DYN	LIFE	5/77	125C	N/R	9.00E 04	45	0	
					EM						45	1	
					OP DYN	LIFE	5/79	125C	N/R	2.34E 04	28	0	

FAIRCHILD SEMI PROM

SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93438	D	NHDIP	24	M	EM	LIFE	5/79		N/R		28	0	
					OP DYN	LIFE	5/79	125C	N/R	1.68E 05	84	0	
					EM						84	0	
					OP DYN	LIFE	5/79	125C	N/R	5.60E 04	56	0	
					EM						56	0	
					OP DYN	LIFE	5/79	125C	N/R	7.82E 04	40	1	
					EM						40	0	
					OP DYN	LIFE	5/79	125C	N/R	1.41E 05	75	1	
					EM						75	0	
					OP DYN	LIFE	5/79	125C	N/R	1.76E 05	88	0	
					EM						88	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C 1000CY LIQUID	N/R		178	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			178	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			178	0	
					EM						178	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		25	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			25	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		50	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			50	0	
					MOIST			-010C 065C 98%RH			50	0	
					FINE LK			HE 5.E-9 60 MIN 30 MIN			50	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			50	0	
					EM						50	0	
					OP DYN	LIFE	12/79	125C	N/R	3.26E 04	24	0	
					EM						24	0	
93438	D-1	HDIP	24	C	OP CNST	LIFE	5/77	100C	N/R	8.00E 04	40	0	
					EM						40	0	
					OP CNST	LIFE	5/77	100C	N/R	4.40E 04	22	0	
					EM						22	0	
					OP CNST	LIFE	5/77	100C	N/R	7.40E 04	37	0	
					EM						37	0	
					OP DYN	LIFE	5/79	100C	N/R	4.20E 04	21	0	
					EM						21	0	
					AUTOCLV	ENV	8/79	15PSIG121C 500HRS	N/R		10	0	
					EM						10	0	
					OP DYN	LIFE	12/79	125C	N/R	1.20E 05	72	0	
					EM						72	0	
					OP DYN	LIFE	12/79	125C	N/R	2.25E 04	45	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS *4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93438	D-1	HDIP	24	C	EM	LIFE	12/79		N/R		45	0	
					OP DYN	LIFE	12/79	125C	N/R	3.97E 04	80	1	2390
					FM						79	0	
					RHRB	LIFE	12/79	85C	N/R	3.00E 04	20	0	
					EM						20	0	
					RHRB	LIFE	12/79	85C	N/R	5.26E 04	45	0	
					EM						45	0	
93438	D	NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	5.40E 04	27	0	
					EM						27	0	
					OP DYN	LIFE	5/79	125C	N/R	5.58E 04	78	0	
					EM						78	0	
					OP DYN	LIFE	5/79	125C	N/R	1.43E 05	95	0	
					EM						95	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93438	D	NHDIP	24	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93438	D	NHDIP	24	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP DYN	LIFE	12/79	125C	N/R	5.22E 04	25	1	2389
					EM						25	0	
					OP DYN	LIFE	12/79	125C	N/R	2.34E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	12/79	125C	N/R	3.50E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	12/79	125C	N/R	1.97E 04	40	1	2387
					EM						39	0	
93448	D-1	HDIP	24	C	OP DYN	LIFE	5/79	100C	N/R	3.80E 04	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	5.00E 04	25	0	
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	1	

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D-1	HDIP	24	C	OP DYN	LIFE	12/79	125C	N/R	8.18E 04	70	0	
					EM						70	0	
93448	D	NHDIP	24	M	MECHSHK	ENV	5/77	1.5KG .5MSEC 6 AXES	N/R		10	0	
								5 BLOS					
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			10	0	
					CNSTACC			30KG 6 AXES 1 MIN E			10	0	
					HERMETC						10	0	
					THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		7	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			7	0	
					HERMETC						7	0	
					THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		27	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			27	0	
					CNSTACC			30KG 6 AXES 1 MIN E			27	0	
					HERMETC						27	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC 6 AXES	N/R		28	0	
					VBVRFQ			5 BLOS 20HZ 2KHZ 20G 3 AXES			28	0	
					CNSTACC			30KG 6 AXES 1 MIN E			28	0	
					HERMETC						28	0	
					TEMPCYC	ENV	5/77	-065C 150C 10CY 10/10DT	N/R		19	0	
					CNSTACC			30KG 6 AXES 1 MIN E			19	0	
					HERMETC						19	0	
					OP DYN	LIFE	5/77	125C	N/R	4.60E 04	23	0	
					EM						23	0	
					OP DYN	LIFE	5/77	125C	N/R	9.40E 04	47	0	
					EM						47	0	
					OP DYN	LIFE	5/77	125C	N/R	1.76E 05	88	0	
					EM						88	0	
					OP DYN	LIFE	5/77	125C	N/R	1.74E 05	87	0	
					EM						87	0	
					OP DYN	LIFE	5/77	125C	N/R	9.40E 04	47	0	
					EM						47	0	
	X				TEMPCYC	ENV	3/78	-055C 125C 250CY 60/60DT	N/R		4	0	
					EM			025C			4	1	
	D				OP DYN	LIFE	5/79	125C	N/R	1.60E 05	80	0	
					EM						80	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	125C	N/R	3.35E 04	27	0	
					EM						27	0	
					OP DYN	LIFE	5/79	125C	N/R	5.60E 04	56	0	
					EM						56	0	
					OP DYN	LIFE	5/79	125C	N/R	2.77E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	5/79	125C	N/R	7.26E 04	93	1	
					EM						93	0	
					OP DYN	LIFE	5/79	125C	N/R	3.32E 04	68	1	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	EM	LIFE	5/79		N/R		68	0	
					OP DYN	LIFE	5/79	125C	N/R	4.20E 04	42	0	
					EM						42	0	
					OP DYN	LIFE	5/79	125C	N/R	8.40E 04	42	0	
					EM						42	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		31	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			31	0	
								1 MIN E					
					FINE LK			HE 5.E-8			31	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			31	0	
								3X					
								60PSIG					
					EM						31	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
93448		NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	125C	N/R	1.51E 05	76	1	
					EM						76	0	
					OP DYN	LIFE	5/79	125C	N/R	1.12E 05	112	0	
					EM						112	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	125C	N/R	1.12E 05	56	0	
					EM						56	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	4.70E 04	24	1	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		48	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			48	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			48	0	
								1 MIN E					
					FINE LK			HE 5.E-8			48	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		49	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			49	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			49	0	
								1 MIN E					
					FINE LK			HE 5.E-8			49	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			49	0	
								3X					
								60PSIG					
					EM						49	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

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SCHOTTKY TTL — BIPOLAR

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		35	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			35	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		19	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			19	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			19	0	
								1 MIN E					
					FINE LK			HE 5.E-8			19	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			19	0	
								3X					
								60PSIG					
					EM						19	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		23	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			23	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		25	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			25	0	
					CNSTACC			30KG 6 AXES 1 MIN E			25	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		50	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			50	0	
					CNSTACC			30KG 6 AXES 1 MIN E			50	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			50	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			50	0	
					EM						50	1	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		45	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			45	0	
					CNSTACC			30KG 6 AXES 1 MIN E			45	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			45	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			45	0	
					EM						45	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		50	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			50	0	
					CNSTACC			30KG 6 AXES 1 MIN E			50	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			50	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			50	0	
					EM						50	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		24	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			24	0	
					CNSTACC			30KG 6 AXES 1 MIN E			24	0	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		33	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			33	0	
								1 MIN E					
					FINE LK			HE 5.E-8			33	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			32	0	
								3X					
								60PSIG					
					EM						32	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	EM	ENV	8/79		N/R		50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		19	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			19	0	
								1 MIN E					
					FINE LK			HE 5.E-8			19	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			19	0	
								3X					
								60PSIG					
					EM						19	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		45	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			45	0	
								1 MIN E					
					FINE LK			"E 5.E-8			45	0	
								60 MIN					
								30 MIN					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MEF #
93448	D	MHDIP	24	N	GROSSLK	ENV	8/79	FLUOR 125C	N/R		45	0	
								3X					
								60PSIG					
					EM						45	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			49	0	
								3X					
								60PSIG					
					EM						49	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		200	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			200	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			200	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			200	0	
								3X					
								60PSIG					
					EM						200	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		37	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			37	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			37	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			37	0	
								3X					
								60PSIG					
					EM						37	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		19	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			19	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			19	0	
								98%RH					
					FINE LK			HE 5.E-8			19	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			19	0	
								3X					
								60PSIG					
					EM						19	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHDIP	24	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		34	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			34	0	
								20G					
								3 AXES					
					FINE LK			HE 5.E-8			34	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			34	0	
								3X					
								60PSIG					
					EM						34	0	
					OP DYN	LIFE	12/79	125C	N/R	2.13E 04	24	0	
					EM						24	0	
					OP DYN	LIFE	12/79	125C	N/R	4.03E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	12/79	10C	N/R	2.30E 04	23	0	
					EM						23	0	
93448		NHFPK	24	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		59	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			59	0	
								1 MIN E					
					FINE LK			HE 5.E-8			59	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			59	0	
								3X					
								60PSIG					
					EM						59	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		23	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		43	0	
								10CY					
								10/10DT					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHFPK	24	M	CNSTACC	ENV	8/79	30KG 6 AXES	N/R		43	0	
								1 MIN E					
					FINE LK			HE 5.E-8			43	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			42	0	
								3X					
								60PSIG					
					EM						42	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		195	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			195	0	
								1 MIN E					
					FINE LK			HE 5.E-8			195	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			195	0	
								3X					
								60PSIG					
					EM						195	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		104	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			104	0	
								1 MIN E					
					FINE LK			HE 5.E-8			104	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			104	1	
								3X					
								60PSIG					
					EM						103	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		39	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			39	0	
								1 MIN E					
					FINE LK			HE 5.E-8			39	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			39	0	
								3X					
								60PSIG					
					EM						39	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		60	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			60	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			60	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			60	0	
								3X					
								60PSIG					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93448	D	NHFPK	24	M	EM	ENV	8/79		N/R		60	0	
93452		NHDIP	18	M	THRMSHK	ENV	5/77	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					HERMETC						25	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		22	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			22	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			22	0	
								1 MIN E					
					HERMETC						22	0	
93452		NHDIP	18	M	OP DYN	LIFE	5/79	125C	N/R	1.05E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	5/79	125C	N/R	1.05E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	5/79	125C	N/R	1.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	125C	N/R	4.37E 04	30	1	
					EM						30	0	
					OP DYN	LIFE	5/79	125C	N/R	2.10E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	5/79	125C	N/R	2.10E 04	21	0	
					EM						21	0	
					OP DYN	LIFE	5/79	125C	N/R	1.05E 04	21	0	
					EM						21	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		59	0	
								1 MIN E					
					FINE LK			HE 5.E-8			59	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			58	0	
								3X					
								60PSIG					
					EM						58	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		21	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			21	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			21	0	
								1 MIN E					
					FINE LK			HE 5.E-8			21	0	
								60 MIN					
								30 MIN					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93452	D	NHDIP	18	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		21	0	
								3X					
								60PSIG					
					EM						21	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		120	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			120	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			120	0	
								1 MIN E					
					FINE LK			HE 5.E-8			120	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			120	0	
								3X					
								60PSIG					
					EM						120	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		70	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			70	0	
								1 MIN E					
					FINE LK			HE 5.E-8			70	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			69	0	
								3X					
								60PSIG					
					EM						69	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		200	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			200	0	
								1 MIN E					
					FINE LK			HE 5.E-8			200	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			200	0	
								3X					
								60PSIG					
					EM						200	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		23	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93452	D	NHDIP	18	M	TEMPCYC	ENV	8/79	:-065C 150C :10CY :10/10DT	N/R		25	0	
					CNSTACC			:30KG 6 AXES:1 MIN E			25	0	
					FINE LK			:HE 5.E-8 :60 MIN :30 MIN			25	0	
					GROSSLK			:FLUOR 125C :3X :60PSIG			25	0	
					EM			:			25	0	
					TEMPCYC	ENV	8/79	:-065C 150C :10CY :10/10DT	N/R		135	0	
					CNSTACC			:30KG 6 AXES:1 MIN E			135	0	
					FINE LK			:HE 5.E-8 :60 MIN :30 MIN			135	0	
					GROSSLK			:FLUOR 125C :3X :60PSIG			135	0	
					EM			:			135	0	
					THRMSHK	ENV	8/79	:-055C 125C :15CY :LIQUID	N/R		85	0	
					TEMPCYC			:-065C 150C :10CY :10/10DT			85	0	
					FINE LK			:HE 5.E-8 :60 MIN :30 MIN			85	0	
					GROSSLK			:FLUOR 125C :3X :60PSIG			85	0	
					EM			:			85	0	
					TEMPCYC	ENV	8/79	:-065C 150C :10CY :10/10DT	N/R		31	0	
					CNSTACC			:30KG 6 AXES:1 MIN E			31	0	
					FINE LK			:HE 5.E-8 :60 MIN :30 MIN			31	1	
					GROSSLK			:FLUOR 125C :3X :60PSIG			30	0	
					EM			:			30	0	
					THRMSHK	ENV	8/79	:-055C 125C :15CY :LIQUID	N/R		83	0	
					TEMPCYC			:-065C 150C :10CY :10/10DT			33	0	
					FINE LK			:HE 5.E-8 :60 MIN :30 MIN			83	0	
					GROSSLK			:FLUOR 125C :3X :60PSIG			83	0	
					EM			:			83	0	
					THRMSHK	ENV	8/79	:-055C 125C :15CY :LIQUID	N/R		25	0	
					TEMPCYC			:-065C 150C :10CY :10/10DT			25	0	

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93452	D	NHDIP	18	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		23	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			23	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		69	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			69	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			69	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			69	0	
								3X					
								60PSIG					
					EM						69	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP DYN	LIFE	12/79	125C	N/R	2.10E 04	21	0	
					EM						21	0	
93452		NHDIP	24	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93452		NHDIP	22	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93452	D	NHDIP	22	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93453		NHDIP	18	M	OP DYN	LIFE	5/77	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	125C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP DYN	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93453	D	NHDIP	18	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93453		NHDIP	18	M	OP DYN	LIFE	5/79	125C	N/R	6.35E 04	41	0	
					EM						41	0	
					OP DYN	LIFE	5/79	125C	N/R	7.20E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	5/79	125C	N/R	2.20E 04	22	0	
					EM						22	0	
					OP DYN	LIFE	5/79	125C	N/R	1.60E 04	16	0	
					EM						16	0	
					OP DYN	LIFE	5/79	125C	N/R	9.42E 04	48	1	
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		47	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			47	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					

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SCHOTTKY TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93453	D	NHDIP	18	M	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		111	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			111	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			111	0	
								1 MIN E					
					FINE LK			HE 5.E-8			111	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			111	0	
								3X					
								60PSIG					
					EM						111	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	1	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93453	D	NHDIP	18	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		54	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			54	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			54	0	
								1 MIN E					
					FINE LK			HE 5.E-8			54	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			53	0	
								3X					
								60PSIG					
					EM						53	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		15	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			15	0	
								1 MIN E					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								60PSIG					
					EM						15	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		48	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			48	0	
								1 MIN E					
					FINE LK			HE 5.E-8			48	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			48	0	
								3X					
								60PSIG					
					EM						48	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		91	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			91	0	
								1 MIN E					
					FINE LK			HE 5.E-8			91	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			91	0	
								3X					
								60PSIG					
					EM						91	0	

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
93453	D	NHDIP	18	M	TEMPCYC	ENV	8/79	:-065C 150C	N/R		50	0	
								:10CY					
								:10/10DT					
					CNSTACC			:30KG 6 AXES			50	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			50	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			50	0	
								:3X					
								:60PSIG					
					EM			:			50	0	
					TEMPCYC	ENV	8/79	:-065C 150C	N/R		50	0	
								:10CY					
								:10/10DT					
					CNSTACC			:30KG 6 AXES			50	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			50	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			50	0	
								:3X					
								:60PSIG					
					EM			:			50	0	
					TEMPCYC	ENV	8/79	:-065C 150C	N/R		27	0	
								:10CY					
								:10/10DT					
					CNSTACC			:30KG 6 AXES			27	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			27	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			27	0	
								:3X					
								:60PSIG					
					EM			:			27	0	
					THRMSHK	ENV	8/79	:-055C 125C	N/R		47	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			47	0	
								:10CY					
								:10/10DT					
					FINE LK			:HE 5.E-8			47	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			47	0	
								:3X					
								:60PSIG					
					EM			:			47	0	
					THRMSHK	ENV	8/79	:-055C 125C	N/R		24	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			24	0	
								:10CY					
								:10/10DT					
					FINE LK			:HE 5.E-8			24	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			24	0	
								:3X					
								:60PSIG					
					EM			:			24	0	
					THRMSHK	ENV	8/79	:-055C 125C	N/R		35	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			35	0	
								:10CY					
								:10/10DT					

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SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFLF #
93453	D	NHDIP	18	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		35	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			34	0	
								3X					
								60PSIG					
					EM						34	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP DYN	LIFE	12/79	125C	N/R	2.20E 04	22	0	
					EM						22	0	
					OP DYN	LIFE	12/79	125C	N/R	1.60E 04	16	0	
					EM						16	0	
93453	D-1	HDIP	18	C	OP LIFE	LIFE	5/79	125C	N/R	5.00E 03	5	0	
					EM						5	0	
					OP LIFE	LIFE	5/79	125C	N/R	3.45E 04	23	0	
					EM						23	0	
93453	D	NHFPK	22	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93453	D	NHFPK	22	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93453		NHFPK	18	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7640	X	NHDIP	24	M	TEMPCYC	ENV	3/78	-055C 125C	N/R		8	0	
								1000CY					
								60/60DT					
					EM			025C			8	0	
7640/41	C-2	NHDIP	24	N/R	OP DYN	LIFE	4/79	125C	N/R	9.50E 04	95	0	
7643A-2	B-1	NHDIP	18	M	N/R	FIELD	10/80		AUT	5.09E 05	120	0	
7647R	C-2	NHDIP	24	M	OP DYN	LIFE	7/79	125C	N/R	3.90E 05	102	0	
					EM						102	0	
7649		NHDIP	20	M	OP DYN	LIFE	7/79	125C	N/R	4.58E 05	163	0	
					EM						163	0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
53S440	D-1	HDIP	18	M	PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	
53S441	D	NHDIP	18	M	OP DYN	LIFE	1/79	125C	N/R	4.70E 04	47	0	
					EM			25C			47	0	
53S441	NONE		18	M	PAR EXC	LIFE	10/81	125C	N/R	9.80E 04	98	0	
5341	D	NHDIP	24	M	OP DYN	LIFE	1/79	125C	N/R	4.70E 04	47	0	
					EM			25C			47	0	
					PAR EXC	LIFE	10/81	125C	N/R	1.85E 05	185	0	
5341		NHDIP	24	M	OP CNST	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	1	
					OP DYN	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
5348		NHDIP	20	M	OP DYN	LIFE	1/79	125C	N/R	3.80E 04	38	0	
					EM			25C			38	0	
5349		NHDIP	20	M	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	
5353		NHDIP	18	M	OP DYN	LIFE	1/79	125C	N/R	2.44E 05	321	0	
					EM			25C			321	0	
					PAR EXC	LIFE	10/81	125C	N/R	3.14E 05	314	1	3695
5353		NHDIP	18	M	OP DYN	LIFE	1/79	125C	N/R	7.70E 04	154	0	
					EM			25C			154	0	
5353		NHFPK	18	M	OP DYN	LIFE	1/79	85C	N/R	5.60E 04	56	0	
					EM			25C			56	0	
6340		HDIP	24	C	OP DYN	LIFE	1/79	125C	N/R	7.00E 04	70	0	
					EM			25C			70	0	
6340		NHDIP	24	C	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	
6341		NHDIP	24	C	PAR EXC	LIFE	10/81	125C	N/R	3.60E 04	36	1	3697

NATIONAL SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S573	D-1	HDIP	18	C	OP DYN	LIFE	12/78	125C	N/R	9.68E 04	64	0	
					EM						64	0	
					OP DYN	LIFE	12/78	125C	N/R	6.05E 04	60	0	
					EM						60	1	
					OP DYN	LIFE	12/78	125C	N/R	1.56E 05	155	0	
					EM						155	4	
					OP DYN	LIFE	12/78	125C	N/R	1.01E 05	50	0	
					EM						50	1	
74S573	D	NHDIP	18	C	OP DYN	LIFE	12/78	125C	N/R	2.42E 04	16	0	
					EM						16	0	
					OP DYN	LIFE	12/78	125C	N/R	1.31E 06	1152	0	
					EM						1152	9	

SIGNETICS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S115	D	NHDIP	24	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.50E 04	45	0	
					EM						45	0	

SIGNETICS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S136	D	NHDIP	18	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3604/82S140	D	NHDIP	24	C	VIS INS	EBRN	3/78		N/R		297	0	
					TEMPCYC			-055C 125C			297	0	
								10CY					
					REVBIAS			125C		4.75E 04	297	0	
					S&F EM			070C			297	9	2471
													2472
													2473

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93450	D	NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	2.25E 04	12	0	
					EM						12	0	
					OP DYN	LIFE	5/79	125C	N/R	9.82E 04	49	1	
					EM						49	0	
					OP DYN	LIFE	5/79	125C	N/R	2.25E 04	12	0	
					EM						12	0	
93450		NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	3.80E 04	19	0	
					EM						19	0	
					OP DYN	LIFE	5/79	125C	N/R	3.80E 04	19	0	
					EM						19	0	
93450	D-1	HDIP	24	C	OP DYN	LIFE	5/79	100C	N/R	3.80E 04	19	0	
					EM						19	0	
					RHRB	LIFE	5/79	85C	N/R	3.40E 04	17	0	
					EM						17	0	
					RHRB	LIFE	5/79	85C	N/R	3.40E 04	17	0	
					EM						17	0	
93451	D	NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	4.31E 04	23	0	
					EM						23	0	
					OP DYN	LIFE	5/79	125C	N/R	7.20E 04	18	0	
					EM						18	0	
					OP DYN	LIFE	5/79	125C	N/R	4.31E 04	23	0	
					EM						23	0	
					OP DYN	LIFE	5/79	125C	N/R	7.20E 04	18	0	
					EM						18	0	
					OP CNST	LIFE	12/79	125C	N/R	1.80E 04	18	0	
					EM						18	0	
					OP CNST	LIFE	12/79	125C	N/R	2.10E 04	21	0	
					EM						21	0	
93451		NHDIP	24	M	OP DYN	LIFE	5/79	125C	N/R	3.00E 04	15	0	
					EM						15	0	

FAIRCHILD SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93451	D	NHDIP	24	M	OP CNST	LIFE	12/79	125C	N/R	1.50E 04	15	0	
					EM						15	0	
93451	D-1	HDIP	24	C	OP CNST	LIFE	12/79	125C	N/R	7.20E 04	48	0	
					EM						48	0	
					OP DYN	LIFE	12/79	125C	N/R	3.60E 04	24	0	
					EM						24	0	
					RHRB	LIFE	12/79	85C	N/R	3.60E 04	24	0	
					EM						24	0	

HARRIS SEMI — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	C-2	NHDIP	0	N/R	OP DYN	LIFE	4/79	125C	N/R	1.20E 04	24	0	
					OP DYN	LIFE	4/79	125C	N/R	1.85E 04	37	3	
7684/85/86/8		NHDIP	0	M	OP DYN	LIFE	7/79	125C	N/R	6.00E 04	60	0	
					EM						60	0	

MONOLITHIC MEMORIES — PROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5380	D	NHDIP	24	M	PAR EXC	LIFE	10/81	125C	N/R	3.00E 04	30	0	
5389		NHDIP	18	M	PAR EXC	LIFE	10/81	125C	N/R	5.00E 04	50	0	
6380		NHDIP	24	C	OP DYN	LIFE	1/79	125C	N/R	2.80E 04	28	0	
					EM			25C			28	1	
6381		NHDIP	24	C	OP DYN	LIFE	1/79	125C	N/R	8.40E 04	42	0	
					EM			25C			42	0	
6381		NHDIP	24	C	PAR EXC	LIFE	10/81	125C	N/R	1.59E 05	159	0	

ADVANCED MICRO DEVICES — PROM

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
27LS09	NONE	NHDIP	16	M	N/R	FIELD	5/77		AIT	3.06E 03	9	0	

MONOLITHIC MEMORIES — PROM

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
53LS141	D	NHDIP	16	M	PAR EXC	LIFE	10/81	125C	N/R	1.88E 05	94	0	

FAIRCHILD SEMI — PROM

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L451	D-1	HDIP	24	C	OP CNST	LIFE	12/79	125C	N/R	1.19E 04	15	0	
					EM						15	0	
					OP DYN	LIFE	12/79	125C	N/R	1.19E 04	15	0	
					EM						15	0	
93L451	D	NHDIP	24	M	OP CNST	LIFE	12/79	125C	N/R	4.74E 04	24	1	2334
					EM						23	0	
					OP DYN	LIFE	12/79	125C	N/R	4.74E 04	24	1	2388
					EM						23	0	
					OP DYN	LIFE	12/79	125C	N/R	2.10E 04	21	0	
					EM						21	0	

ADVANCED MICRO DEVICES — PROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1602	B-1	NHDIP	24	M	N/R	RELDEM	7/78	025C	GT	2.11E 03	6	0	

INTEL — PROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1702A	D	NHDIP	24	C	N/R	FIELD	12/77	25C	GBC	3.12E 05	30	0	
					N/R	FIELD	12/77	25C	GBC	2.69E 05	30	0	
					N/R	FIELD	12/77	25C	GBC	6.44E 03	2	0	

NATIONAL SEMI — PROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1702A	D	NHDIP	24	C	REVBIAS	LIFE	4/77	125C	N/R	1.20E 05	30	0	
					EM						30	0	
					REVBIAS	LIFE	4/77	125C	N/R	6.35E 04	42	0	
					EM						42	0	
					REVBIAS	LIFE	4/77	125C	N/R	1.34E 05	66	0	
					EM						66	1	
					REVBIAS	LIFE	4/77	125C	N/R	2.40E 04	24	0	
					EM						24	1	
					OP DYN	LIFE	4/77	125C	N/R	4.67E 04	23	0	
					EM						23	0	
					OP DYN	LIFE	4/77	125C	N/R	3.63E 05	179	0	
					EM						179	1	
					OP DYN	LIFE	4/77	125C	N/R	4.06E 04	20	0	
					EM						20	0	
					BAKE	LIFE	4/77	225C	N/R	3.52E 04	225	0	
					EM						225	0	

SIGNETICS — PROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1702A	D	NHDIP	24	C	OP DYN	LIFE	11/77	85C	N/R	9.40E 04	47	0	
					EM						47	1	
					REVBIAS	LIFE	11/77	150C	N/R	4.90E 04	49	0	
					EM						49	0	

VARIOUS — PROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	OP DYN	LIFE	9/78	150C	N/R	3.50E 04	10	4	
					FNCT EM			25C			10	0	
					OP DYN	LIFE	9/78	150C	N/R	6.00E 04	12	2	
					FNCT EM			25C			12	0	
					OP DYN	LIFE	9/78	150C	N/R	1.35E 04	9	0	
					FNCT EM			25C			9	0	
					STGLIFE	LIFE	9/78	150C	N/R	6.00E 04	25	1	
					FNCT EM			25C			25	0	

ADVANCED MICRO DEVICES — PROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2708	B-2	NHDIP	24	M	PAR EXC	BRN	6/80	150C	N/R	1.68E 04	84	0	
					EM			150C			84	0	

INTEL — PROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2708	D	NHDIP	24	I	N/R	FIELD	6/77	30C	GBC	2.80E 06	5700	1	
8708	B-1	NHDIP	24	I	TEMPCYC	RELDEM	11/77	000C 050C	NSS	1.06E 04	14	0	
								16CY					

MOTOROLA SEMI — PROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
68708	X	NHDIP	24	M	N/R	FIELD	2/78	25C	GBC	1.98E 05	20	0	
68708	D	NHDIP	24	C	HERMETC	ENV	10/77		N/R		50	0	
					SALTATM			035C 25GMS			50	0	
								NSQ					
								24 HRS					
					HERMETC						50	0	
					LEADFTG						50	0	
					TEMPCYC	ENV	10/77	-065C 150C	N/R		50	0	
								1000CY					
								10/10DT					
					HERMETC						50	0	
					MOIST	ENV	10/77	-010C 065C	N/R		50	0	
								98%RH					
					HERMETC						50	0	
					MECHSHK	ENV	10/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					HERMETC						50	0	
					SALTSPY	ENV	10/77	20HZ 2KHZ	N/R		50	0	
								20G					
								3 AXES					
					HERMETC						50	0	
					THRMSHK	ENV	10/77	-065C 150C	N/R		50	0	
								1000CY					
								LIQUID					
					HERMETC						50	0	
					BAKE	ENV	10/77	250C	N/R	1.03E 03	19	0	
					HERMETC						19	0	
					STGLIFE	LIFE	10/77	250C	N/R	4.44E 05	121	0	
					EM						121	6	
					OP DYN	LIFE	10/77	125C	N/R	2.24E 05	259	0	
					EM						259	2	

SIGNETICS PROM

N-STAT MOS NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2708	D	NHDIP	24	C	OP DYN	LIFE	11/77	125C	N/R	6.10E 04	61	0	
					EM						61	0	
					REVBIAS	LIFE	11/77	125C	N/R	3.10E 04	32	0	
					EM						32	0	

VARIOUS PROM

N-STAT MOS NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	ACCLFOD	LIFE	9/78	200C	N/R	2.10E 04	30	12	
					FNCT EM			25C			30	7	
					ACCLFOD	LIFE	9/78	200C	N/R	4.50E 04	15	1	
					FNCT EM			25C			15	0	
					OP DYN	LIFE	9/78	150C	N/R	4.00E 04	10	1	
					FNCT EM			25C			10	0	
					BAKE	ENV	9/78	250C	N/R	3.68E 03	23	7	
					FNCT EM			025C			23	4	
					STGLIFE	LIFE	9/78	250C	N/R	1.06E 04	25	3	
					FNCT EM			25C			22	7	
					STGLIFE	LIFE	9/78	250C	N/R	3.50E 04	25	8	
					FNCT EM			25C			25	2	
					STGLIFE	LIFE	9/78	250C	N/R	2.80E 04	20	1	
					FNCT EM			25C			20	6	
					STGLIFE	LIFE	9/78	150C	N/R	1.00E 05	20	4	
					FNCT EM			25C			20	0	
					STGLIFE	LIFE	9/78	250C	N/R	3.13E 04	25	1	
					FNCT EM			25C			25	0	
					STGLIFE	LIFE	9/78	250C	N/R	1.25E 04	25	11	
					FNCT EM			25C			25	5	
					STGLIFE	LIFE	9/78	250C	N/R	2.04E 04	24	9	
					FNCT EM			25C			24	4	

INTEL PROM

N-STAT MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2716	D	NHDIP	24	M	OP DYN	BRN	5/79	125C	N/R	1.12E 06	23387	0	
					EM						23387	85	1999
					OP DYN	LIFE	6/79	125C	N/R	1.75E 06	1753	8	2001
					EM						1745	1	2002
					OP DYN	LIFE	5/79	125C	N/R	1.80E 05	360	0	
					EM						360	2	2003
					OP DYN	LIFE	6/79	125C	N/R	2.10E 05	210	0	
					EM						210	0	
					OP DYN	BRN	5/79		N/R	1.12E 05	665	0	
					EM						665	1	2004
					OP DYN	LIFE	6/79	160C	N/R	6.02E 05	615	16	2005
													2006
					EM						599	1	
					OP DYN	LIFE	6/79	160C	N/R	3.62E 05	364	4	
					EM						360	0	

INTEL PROM

N-STAT MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2716	D	NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	4.19E 06	87286	0	
					EM			25C			87286	201	2547
													2548
													2549
													2550
													2551
													2552
													2553
													2554
													2555
													2556
													2557
													2558
					OP DYN	LIFE	6/80	125C	N/R	2.15E 06	12810	0	
					EM			25C			12810	16	2621
					OP DYN			125C		2.59E 06	7816	0	
					EM			25C			7816	25	2622
					OP DYN			125C		3.62E 06	7233	0	
					EM			25C			7233	18	2623
					OP DYN			125C		1.04E 05	104	0	
					EM			25C			104	0	
					REVBIAS	LIFE	6/80	150C	N/R	4.20E 04	250	0	
					EM			25C			250	1	2644
					REVBIAS			150C		8.27E 04	249	0	
					EM			25C			249	1	
					REVBIAS			150C		1.24E 05	248	0	
					EM			25C			248	0	
					BAKE	LIFE	6/80	250C	N/R	1.99E 05	4152	0	
					EM			25C			4152	71	2691
													2692
													2693
													2694
													2695
					BAKE			250C		6.94E 05	5782	0	
					EM			25C			5782	77	2696
													2697
													2698
					BAKE			250C		1.80E 06	5407	0	
					EM			25C			5704	75	2699
													2700
													2701
													2702
													2703
					BAKE			250C		1.39E 05	277	0	
					EM			25C			277	2	2704
					TEMPCYC	ENV	6/80	-055C 125C 200 CYC	N/R		100	0	
					EM			025C			100	0	

NATIONAL SEMI PROM

N-STAT MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2716	D	NHDIP	24	N/R	OP DYN	LIFE	12/78	125C	N/R	3.95E 05	392	0	
					EM						392	3	

VARIOUS PROM

N-STAT MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/K	D	NHDIP	24	C	OP DYN	LIFE	9/78	150C	N/R	5.10E 04	17	0	
					S&F EM			25C			17	0	
					STGLIFE	LIFE	9/78	250C	N/R	3.00E 04	20	0	
					S&F EM			25C			20	0	

INTEL PROM

N-STAT MOS NUMBER OF BITS 32K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2732	D	NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	5.87E 0?	12234	0	
					EM			25C			12234	7	2559
													2560
													2561
					OP DYN	LIFE	6/80	125C	N/R	1.61E 06	9567	0	
					EM			25C			9567	9	2624
													2625
													2626
					OP DYN			125C		5.32E 05	1601	0	
					EM			25C			1601	2	2627
													2628
					OP DYN			125C		6.51E 05	1301	0	
					EM			25C			1301	1	2629
					OP DYN			125C		4.67E 05	467	0	
					EM			25C			467	0	
					REVBIAS	LIFE	6/80	150C	N/R	6.52E 04	388	0	
					EM			25C			388	1	2645
					REVBIAS			150C		1.24E 05	387	0	
					EM			25C			387	1	2646
					REVBIAS			150C		1.49E 05	297	0	
					EM			25C			297	0	
					BAKE	LIFE	6/80	250C	N/R	2.71E 04	564	0	
					EM			25C			564	5	2705
					BAKE			250C		7.88E 04	657	0	
					EM			25C			657	5	2706
					BAKE			250C		1.66E 05	501	0	
					EM			25C			501	3	2708
					OP DYN	LIFE	6/80	- 10C	N/R	2.95E 04	59	0	
					EM			25C			59	0	
					OP DYN			- 10C		2.95E 04	59	0	
					EM			25C			59	0	
					TEMPCYC	ENV	6/80	-055C 125C 200 CYC	N/R		183	0	
					EM			025C			183	0	
M2732A		NHDIP	24	M	BURN-IN	BRN	6/80	25C	N/R	1.28E 05	2669	0	
					EM			25C			2669	4	2562
					OP DYN	LIFE	6/80	125C	N/R	3.80E 05	2261	0	
					EM			25C			2261	1	2630
					OP DYN			125C		3.38E 05	1017	0	
					EM			25C			1017	2	2631
					OP DYN			125C		5.08E 05	1015	0	
					EM			25C			1015	1	2632
					OP DYN			125C		2.01E 05	201	0	
					EM			25C			201	1	
					REVBIAS	LIFE	6/80	150C	N/R	5.02E 04	299	0	
					EM			25C			299	2	2647
													2648
					REVBIAS			150C		9.86E 04	297	0	
					EM			25C			297	1	2649
					REVBIAS			150C		7.55E 04	151	0	
					EM			25C			151	0	

INTEL — PROM

N-STAT — MOS — NUMBER OF BITS 32K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
H2732A	D	NHDIP	24	M	BAKE	LIFE	6/80	250C	N/R	2.55E 04	532	0	
					EM			25C			532	8	2707
					BAKE			250C		1.02E 04	425	0	
					EM			25C			425	0	
					BAKE			250C		2.82E 04	425	0	
					EM			25C			425	5	2708
													2709
					OP DYN	LIFE	6/80	-10C	N/R	5.00E 04	100	0	
					EM			25C			100	1	2710
					OP DYN			-10C		3.70E 04	74	0	
					EM			25C			74	0	
					TEMPCYC	ENV	6/80	-055C 125C	N/R		81	0	
								200 CYC					
					EM			025C			81	0	

FAIRCHILD SEMI — RAM

N-STAT — N/R — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	X	HDIP	22	C	N/R	FIELD	7/77		GP	8.54E 07	99999	596	
					N/R						99999	0	
					N/R						40002	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93403	B-1	NHDIP	16	M	N/R	FIELD	9/78		AUF	7.52E 05	660	0	
					N/R	FIELD	9/79		AUF	2.38E 05	660	0	
93410	D-1	HDIP	16	C	THRMSHK	ENV	5/77	-055C 125C	N/R		37	0	
								2000CY					
								LIQUID					
					HERMETC						37	0	
					RHRB	LIFE	5/77	85C	N/R	9.40E 04	47	0	
					EM						47	0	
					OP CNST	LIFE	5/77	100C	N/R	8.60E 04	43	0	
					EM						43	0	
					RHRB	LIFE	5/79	85C	N/R	1.12E 05	56	0	
					EM						56	0	
93410	D	NHDIP	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					HERMETC						50	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFR #
93410	D	NHDIP	16	N	TEMPCYC	ENV	5/77	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					HERMETC						50	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					HERMETC						50	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					HERMETC						25	1	
					TEMPCYC	ENV	5/77	-065C 150C	N/R		24	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					HERMETC						24	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		45	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			45	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			45	0	
								98%RH					
					HERMETC						45	0	
					OP CNST	LIFE	5/77	125C	N/R	1.00E 06	1000	0	
					EM						1000	0	
					OP CNST	LIFE	5/77	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/77	125C	N/R	2.77E 05	277	0	
					EM						277	1	
					OP CNST	LIFE	5/77	125C	N/R	4.18E 05	209	0	
					EM						209	0	
					GROSSLK	LIFE	5/79	125C	N/R	8.00E 03	8	0	
					EM						8	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		7	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			7	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			7	0	
								1 MIN E					
					FINE LK			HE 5.E-8			7	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			7	0	
								3X					
								60PSIG					
					EM						7	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93410	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/					
								30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		7	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			7	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			7	0	
								98%RH					
					FINE LK			HE 5.E-8			7	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			7	0	
								3X					
								60PSIG					
					EM						7	0	
93410		NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					HERMETC						25	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					HERMETC						24	0	
					SALT AM	ENV	5/77	035C 25GMS	N/R		22	0	
								MSQ					
								24 HRS					
					VIS INS						22	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93410	D	NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	1.66E 05	83	0	
					EM						83	0	
					OP CNST	LIFE	5/77	125C	N/R	8.10E 04	81	0	
					EM						81	0	
					OP CNST	LIFE	5/77	125C	N/R	9.60E 04	96	0	
					EM						96	0	
93410		NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		29	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					OP CNST	LIFE	12/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
93411	D-1	HDIP	16	C	THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								2000CY					
								LIQUID					
					HERMETC						50	0	
93411	D	NHDIP	16	M	SALTATM	ENV	5/77	035C 25GMS	N/R		15	0	
								MSQ					
								24 HRS					
					VIS INS						15	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					HERMETC						50	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					HERMETC						50	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			20	0	
								98%RH					
					HERMETC						20	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					HERMETC						20	0	
					OP CNST	LIFE	5/77	125C	N/R	5.20E 04	26	0	
					EM						26	0	
					OP CNST	LIFE	5/77	125C	N/R	5.34E 05	534	0	
					EM						534	1	
					OP CNST	LIFE	5/77	125C	N/R	3.63E 05	363	0	
					EM						363	1	
					OP CNST	LIFE	5/77	125C	N/R	1.78E 05	89	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93411	D	NHDIP	16	M	EM	LIFE	5/77		N/R		89	0	
					OP CNST	LIFE	5/77	125C	N/R	5.93E 05	593	0	
					EM						593	0	
					OP CNST	LIFE	5/77	125C	N/R	2.71E 05	271	0	
					EM						271	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	6.40E 04	32	0	
					EM						32	0	
93411		NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	7.10E 04	71	0	
					EM						71	0	
					OP CNST	LIFE	5/77	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					OP CNST	LIFE	5/77	125C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL.	MFEF #
93411	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C 3X 60PSIG	N/R		20	0	
					EM						20	0	
					TEMPCYC	ENV	8/79	-065C 150C 10CY 10/10DT	N/R		31	0	
					CNSTACC			30KG 6 AXES 1 MIN E			31	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			31	1	
					GROSSLK			FLUOR 125C 3X 60PSIG			30	0	
					EM						30	0	
93421	D-1	HDIP	16	C	OP CNST	LIFE	5/79	125C	N/R	1.80E 05	60	0	
					EM						60	0	
					OP CNST	LIFE	5/79	125C	N/R	1.77E 05	60	1	
					EM						59	0	
					RHRB	LIFE	5/79	85C	N/R	1.12E 05	56	0	
					EM						56	0	
					RHRB	LIFE	5/79	85C	N/R	1.06E 05	53	0	
					EM						53	0	
					RHRB	LIFE	5/79	85C	N/R	1.62E 05	54	0	
					EM						54	0	
93421	D	NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		25	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			25	0	
					HERMETC						25	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		25	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			25	0	
					CNSTACC			30KG 6 AXES 1 MIN E			25	0	
					HERMETC						25	0	
					OP CNST	LIFE	5/77	125C	N/R	2.06E 05	206	0	
					EM						206	0	
					OP CNST	LIFE	5/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					OP CNST	LIFE	5/77	125C	N/R	1.80E 05	90	0	
					EM						90	0	
					OP CNST	LIFE	5/77	125C	N/R	3.00E 05	300	0	
					EM						300	0	
					OP CNST	LIFE	5/77	125C	N/R	5.14E 05	257	0	
					EM						257	0	
					OP CNST	LIFE	5/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
	D-1				OP CNST	LIFE	5/79	1C	N/R	5.00E 04	50	0	
					EM						50	0	
93421	D	NHDIP	16	M	SALTATM	ENV	5/77	035C 25GMS MSQ 24 HRS	N/R		15	0	
					VIS INS						15	0	
					STGLIFE	LIFE	5/77	150C	N/R		60	0	
					EM						60	1	
					THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		18	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			18	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93421	D	NHDIP	16	M	MOIST	ENV	5/77	-010C 065C	N/R		18	0	
								98%RH					
					HERMETC						18	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		18	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			18	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			18	0	
								1 MIN E					
					HERMETC						18	0	
					OP CNST	LIFE	5/79	125C	N/R	2.80E 04	28	0	
					EM						28	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		26	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			26	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		36	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			36	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			36	0	
								98%RH					
					FINE LK			HE 5.E-8			36	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			36	0	
								3X					
								60PSIG					
					EM						36	0	
93421		NHFPK	16	M	OP CNST	LIFE	5/79	125C	N/R	1.67E 05	91	0	
					EM						91	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		61	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			61	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			61	0	
								1 MIN E					

FAIRCHILD SEMI — NAV

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	REF #
93421	D	NHFPK	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		61	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			61	0	
								3X					
								60PSIG					
					EM						61	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		68	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			68	0	
								1 MIN E					
					FINE LK			HE 5.E-8			68	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			67	0	
								3X					
								60PSIG					
					EM						67	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		80	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			80	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			80	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			80	0	
								3X					
								60PSIG					
					EM						80	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		21	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			21	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			21	0	
								98%RH					
					FINE LK			HE 5.E-8			21	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			21	0	
								3X					
								60PSIG					
					EM						21	0	
93421		NHDIP	16	M	OP CNST	LIFE	5/79	1C	N/R	5.00E 04	50	0	
					EM						50	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		69	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			69	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			69	0	
								1 MIN E					
					FINE LK			HE 5.E-8			69	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			69	1	
								3X					
								60PSIG					
					EM						68	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		27	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93421	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		27	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			27	0	
								3X					
								60PSIG					
					EM						27	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		72	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			72	0	
								1 MIN E					
					FINE LK			HE 5.E-8			72	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			72	0	
								3X					
								60PSIG					
					EM						72	0	
					THRASHK	ENV	8/79	-055C 125C	N/R		70	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			70	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			70	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			70	0	
								3X					
								60PSIG					
					EM						70	0	
93421		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	2.99E 05	150	1	
					EM						149	0	
					OP CNST	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
	D-1				OP CNST	BRN	5/80	125C	N/R	1.03E 06	6133	0	
					EM						6133	7	

NATIONAL SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7489	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.28E 04	6	0	
					N/R	FIELD	5/78	40C	GBC	1.69E 04	13	0	
					N/R	FIELD	4/79	40C	GBC	1.82E 04	14	0	
					N/R	FIELD	4/80	40C	GBC	2.73E 04	21	0	
					N/R	FIELD	4/81	40C	GBC	7.28E 04	28	0	

SIGNETICS — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8225	D-1	HDIP	16	N/R	OP DYN EM	LIFE	11/77	125C	N/R	4.60E 04	46 46	0 0	

TEXAS INSTRUMENTS — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7489	D-1	HDIP	16	C	OP CNST EM	BRN	5/80	125C	N/R	5.95E 04	354 354	0 3	

VARIOUS — RAM

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/K	B-1	NHFPK	16	M	N/R	FIELD	9/78		AUF	4.51E 05	396	0	
					N/R	FIELD	9/79		AUF	1.43E 05	396	0	
N/R		NHDIP	16	M	N/R	FIELD	9/78		AUF	3.76E 04	33	0	
					N/R	FIELD	9/79		AIU	1.19E 04	33	0	
7489	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	4.45E 06	1244	3	
					N/R	FIELD	5/78	40C	GBC	8.82E 06	6788	9	
					N/R	FIELD	4/80	40C	GBC	1.55E 07	11958	3	
					N/R	FIELD	4/81	40C	GBC	3.59E 07	13817	5	
7489/4064		HDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.30E 07	3253	2	
					N/R	FIELD	5/78	40C	GBC	1.02E 05	7874	6	
					N/R	FIELD	4/79	40C	GBC	1.57E 07	12055	6	
					N/R	FIELD	4/80	40C	GBC	1.89E 07	14557	3	
					N/R	FIELD	4/81	40C	GBC	3.90E 07	15007	1	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 576

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93419	D	NHDIP	28	M	THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		49	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			49	0	
					MOIST			-010C 065C 98%RH			49	0	
					HERMETC						49	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 576

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	REF #
93419	D	NHD1P	28	M	SALTATM	ENV	5/77	035C 25GMS	N/R		15	0	
								MSQ					
								24 HRS					
					VIS INS						15	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		49	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			49	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			49	0	
								1 MIN E					
					HERMETC						49	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		34	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			34	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			34	0	
								1 MIN E					
					HERMETC						34	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		34	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			34	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			34	0	
								98%RH					
					HERMETC						34	0	
					TEMPCYC	ENV	5/77	-065C 150C	N/R		38	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			38	0	
								1 MIN E					
					HERMETC						38	0	
					SALTATM	ENV	5/77	035C 25GMS	N/R		15	0	
								MSQ					
								24 HRS					
					VIS INS						15	0	
					OP CNST	LIFE	5/77	125C	N/R	9.20E 04	46	0	
					EM						46	0	
					OP CNST	LIFE	5/77	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	9.80E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/79	125C	N/R	1.04E 05	52	0	
					EM						52	0	
					OP CNST	LIFE	5/79	125C	N/R	2.40E 04	12	0	
					EM						12	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		4	0	
								6 AXES					
								5 BLOS					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 576

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NFEF #
93419	D	NHDIP	28	M	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		4	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			4	0	
								1 MIN E					
					FINE LK			HE 5.E-8			4	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			4	0	
								3X					
								60PSIG					
					EM						4	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		4	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 576

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93419	D	NHDIP	28	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		4	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			4	0	
								98%RH					
					FINE LK			HE 5.E-8			4	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			4	0	
								3X					
								60PSIG					
					EM						4	0	
					OP CNST	LIFE	12/79	125C	N/R	6.00E 03	6	0	
					EM						6	0	
					OP CNST	LIFE	12/79	125C	N/R	2.82E 05	141	0	
					EM						141	0	
					OP CNST	LIFE	12/79	125C	N/R	5.37E 04	46	0	
					EM						46	0	
					OP CNST	LIFE	12/79	125C	N/R	7.20E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	12/79	125C	N/R	5.37E 04	46	0	
					EM						46	0	
93419		NHDIP	28	N	OP CNST	LIFE	5/79	125C	N/R	6.20E 04	31	0	
					EM						31	0	
					OP CNST	LIFE	5/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP CNST	LIFE	5/79	125C	N/R	3.50E 04	35	0	
					EM						35	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	1	
					FINE LK	LIFE	12/79	125C	N/R	3.50E 04	35	0	
					EM						35	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93412	D	NHDIP	22	C	OP CNST	LIFE	12/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
93415		NHFPK	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		70	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			70	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			70	0	
								1 MIN E					
					HERMETC						70	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		69	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			69	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			69	0	
								98%RH					
					HERMETC						69	0	
					OP CNST	LIFE	5/77	125C	N/R	2.50E 04	25	0	
					EM						25	0	
	B-2				OPERATE	CHECK	3/78	025C	AIT	1.28E 05	2041	6	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	7.22E 03	2041	0	
					OPERATE	CHECK	3/78	025C	AIT	3.24E 05	2041	0	
					TCVPC	RELPRO	3/78	002C 045C	AIT	1.62E 05	2041	0	
								5CY 1.5G 79%					
								45HZ 22%					
	D				OP CNST	LIFE	5/79	125C	N/R	2.40E 05	120	0	
					EM						120	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHFPK	16	N	FINE LK	ENV	8/79	HE 5.E-8	N/R		30	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		34	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			34	0	
								1 MIN E					
					FINE LK			HE 5.E-8			34	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI RAD

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHFPK	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		34	0	
								3X					
								60PSIG					
					EM						34	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		24	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			24	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			24	0	
								98%RH					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — MAN

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415		NHFPK	16	M	GROSSLK	ENV	8/79	FLUOR 125C 3X 60PSIG	N/R		30	0	
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		34	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			34	0	
					MOIST			-010C 065C 98%RH			34	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			34	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			34	0	
					EM						34	0	
93415	D-1	HDIP	16	C	RHRB	LIFE	5/77	85C	N/R	1.76E 05	88	0	
					EM						88	0	
					RHRB	LIFE	5/77	85C	N/R	9.20E 04	46	0	
					EM						46	0	
					RHRB	LIFE	5/77	85C	N/R	3.24E 05	108	0	
					EM						108	0	
					RHRB	LIFE	5/77	85C	N/R	8.40E 04	56	0	
					EM						56	0	
					RHRB	LIFE	5/77	85C	N/R	5.10E 04	51	0	
					EM						51	0	
					OP CNST	LIFE	5/77	75C	N/R	9.00E 05	90	0	
					EM			75C			90	0	
					OP CNST	LIFE	5/77	125C	N/R	4.90E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/77	100C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/77	100C	N/R	2.60E 05	104	0	
					EM						104	0	
					OP CNST	LIFE	5/77	100C	N/R	1.88E 05	125	0	
					EM						125	0	
					OP CNST	LIFE	5/77	100C	N/R	1.93E 05	193	0	
					EM						193	0	
					OP CNST	LIFE	5/79	100C	N/R	4.65E 05	93	1	
					EM						92	0	
					OP CNST	LIFE	5/79	75C	N/R	3.49E 05	90	0	
					EM						90	0	
					OP CNST	LIFE	5/79	100C	N/R	3.64E 05	104	0	
					EM						104	0	
					OP CNST	LIFE	5/79	100C	N/R	6.25E 04	125	0	
					EM						125	0	
					OP CNST	LIFE	5/79	100C	N/R	1.93E 05	193	0	
					EM						193	0	
					OP CNST	LIFE	5/79	100C	N/R	2.36E 05	118	0	
					EM						118	0	
					OP CNST	LIFE	5/79	100C	N/R	1.92E 05	97	1	
					EM						96	0	
					OP CNST	LIFE	5/79	100C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP CNST	LIFE	5/79	125C	N/R	2.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	2.90E 05	145	0	
					EM						145	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	96	0	
					EM						96	0	
					OP CNST	LIFE	5/79	100C	N/R	4.22E 05	211	0	
					EM						211	0	
					OP CNST	LIFE	5/79	100C	N/R	1.50E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	1.30E 05	52	0	
					EM						52	0	

FAIRCHILD SEMI KAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
93415	D-1	HDIP	16	C	OP CNST	LIFE	5/79	100C	N/R	1.50E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	7.00E 04	28	0	
					EM						28	0	
					OP CNST	LIFE	5/79	125C	N/R	2.08E 05	52	0	
					EM						52	0	
					OP CNST	LIFE	5/79	100C	N/R	1.14E 05	38	0	
					EM						38	0	
					OP CNST	LIFE	5/79	125C	N/R	7.95E 04	53	0	
					EM						53	0	
					OP CNST	LIFE	5/79	100C	N/R	7.60E 04	38	0	
					EM						38	0	
					OP CNST	LIFE	5/79	100C	N/R	1.32E 05	44	0	
					EM						44	0	
					OP CNST	LIFE	5/79	125C	N/R	2.22E 05	112	1	
					EM						111	0	
					OP CNST	LIFE	5/79	100C	N/R	9.40E 04	47	0	
					EM						47	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	100C	N/R	7.00E 04	35	0	
					EM						35	0	
					OP CNST	LIFE	5/79	100C	N/R	9.82E 04	50	1	
					EM						49	0	
					OP CNST	LIFE	5/79	100C	N/R	7.40E 04	37	0	
					EM						37	0	
					OP CNST	LIFE	5/79	100C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	3.50E 04	35	0	
					EM						35	0	
					OP CNST	LIFE	5/79	125C	N/R	4.60E 04	23	0	
					EM						23	0	
					OP CNST	LIFE	5/79	100C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	100C	N/R	9.82E 04	50	1	
					EM						50	0	
					OP CNST	LIFE	5/79	100C	N/R	4.80E 04	32	0	
					EM						32	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	100C	N/R	6.75E 04	45	0	
					EM						45	0	
					OP CNST	LIFE	5/79	125C	N/R	2.50E 04	25	0	
					EM						25	0	
	NONE				OP CNST	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
	D-1				OP CNST	LIFE	5/79	100C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	4.95E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	1	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D-1	HD1P	16	C	EM	LIFE	5/79		N/R		24	0	
					OP CNST	LIFE	5/79	125C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	100C	N/R	5.36E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
	NONE				RHRB	LIFE	5/79	85C	N/R	2.00E 05	100	0	
					EM						100	0	
	D-1				RHRB	LIFE	5/79	85C	N/R	1.98E 05	100	1	
					EM						99	0	
					RHRB	LIFE	5/79	85C	N/R	1.08E 05	54	0	
					EM						54	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
	NONE				RHRB	LIFE	5/79	85C	N/R	7.00E 04	35	0	
					EM						35	0	
	D-1				RHRB	LIFE	5/79	85C	N/R	1.02E 05	49	0	
					EM						49	0	
					RHRB	LIFE	5/79	85C	N/R	4.50E 04	30	0	
					EM						30	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	6.90E 04	46	0	
					EM						46	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	9.82E 04	50	1	
					EM						49	0	
					RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	6.00E 04	40	0	
					EM						40	0	
	NONE				RHRB	LIFE	5/79	85C	N/R	6.75E 04	45	0	
					EM						45	0	
	D-1				RHRB	LIFE	5/79	85C	N/R	7.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					RHRB	LIFE	5/79	85C	N/R	3.75E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	3.75E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	2.90E 04	29	0	
					EM						29	0	
					RHRB	LIFE	5/79	85C	N/R	3.75E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	5.25E 04	35	0	
					EM						35	0	
					RHRB	LIFE	5/79	85C	N/R	4.60E 04	23	0	
					EM						23	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D-1	HD1P	16	C	GROSSLK	ENV	8/79	FLUOR 125C	N/R		25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		88	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			88	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			88	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			88	0	
								3X					
								60PSIG					
					EM						88	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		35	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			35	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		192	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			192	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			192	0	
								3X					
								60PSIG					
					EM						192	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					AUTOCLV	ENV	8/79	15PSIG121C	N/R		28	0	
								500HRS					
					EM						28	0	
					AUTOCLV	ENV	8/79	15PSIG121C	N/R		116	1	
								500HRS					
					EM						115	0	
					OP CNST	LIFE	12/79	100C	N/R	2.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	12/79	125C	N/R	3.50E 04	35	0	

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFR #
93415	D-1	HDIP	16	C	EM	LIFE	12/79		N/R		35	0	
					OP CNST	LIFE	12/79	125C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	12/79	125C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	1.60E 04	32	0	
					EM						32	0	
					OP CNST	LIFE	12/79	125C	N/R	2.25E 04	45	0	
					EM						45	0	
					OP CNST	LIFE	12/79	125C	N/R	2.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	12/79	125C	N/R	2.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	12/79	125C	N/R	1.65E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	12/79	125C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	1.20E 04	24	0	
					EM						24	0	
					OP CNST	LIFE	12/79	125C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	1.65E 05	100	1	2332
					EM						99	0	
					OP CNST	LIFE	12/79	125C	N/R	7.51E 04	45	0	
					EM						45	0	
					RHRB	LIFE	12/79	85C	N/R	2.30E 04	46	0	
					EM						46	0	
					RHRB	LIFE	12/79	85C	N/R	2.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	12/79	85C	N/R	2.25E 04	45	0	
					EM						45	0	
					RHRB	LIFE	12/79	85C	N/R	2.50E 04	50	0	
					EM						50	0	
					RHRB	LIFE	12/79	85C	N/R	1.25E 04	25	0	
					EM						25	0	
					RHRB	LIFE	12/79	85C	N/R	1.25E 04	25	0	
					EM						25	0	
					RHRB	LIFE	12/79	85C	N/R	2.90E 04	29	0	
					EM						29	0	
					RHRB	LIFE	12/79	85C	N/R	1.25E 04	25	0	
					EM						25	0	
					RHRB	LIFE	12/79	85C	N/R	1.75E 04	35	0	
					EM						35	0	
					RHRB	LIFE	12/79	85C	N/R	1.17E 05	100	0	
					EM						100	0	
93415	D	NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					HERMETC						50	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		29	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			29	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					HERMETC						29	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	TEMPCYC	ENV	5/77	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					HERMETC						30	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					HERMETC						50	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					HERMETC						50	0	
					SALTATM	ENV	5/77	035C 25GMS	N/R		21	0	
								MSQ					
								24 HRS					
					VIS INS						21	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		45	0	
								500CY					
					HERMETC						45	0	
					TEMPCYC	ENV	5/77	-065C 150C	N/R		31	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			31	0	
								1 MIN E					
					HERMETC						31	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		31	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			31	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			31	0	
								98%RH					
					HERMETC						31	1	
					VBVRFQ	ENV	5/77	20HZ 2KHZ	N/R		25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					HERMETC						25	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		105	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			105	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			105	0	
								98%RH					
					HERMETC						105	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		15	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			15	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			15	0	
								1 MIN E					
					HERMETC						15	0	

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TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		15	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			15	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			15	0	
								98%RH					
					HERMETC						15	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					HERMETC						30	1	
					THRMSHK	ENV	5/77	-055C 125C	N/R		48	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			48	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			48	0	
								98%RH					
					HERMETC						48	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		105	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			105	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			105	0	
								98%RH					
					HERMETC						105	0	
					OP CNST	LIFE	5/77	125C	N/R	9.80E 04	98	0	
					EM						98	0	
					OP CNST	LIFE	5/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					OP CNST	LIFE	5/77	125C	N/R	1.32E 05	132	0	
					EM						132	0	
					OP CNST	LIFE	5/77	125C	N/R	5.25E 04	35	0	
					EM						35	0	
					OP CNST	LIFE	5/77	125C	N/R	8.40E 04	56	0	
					EM						56	0	
					OP CNST	LIFE	5/77	125C	N/R	2.08E 05	208	0	
					EM						208	0	
					OP CNST	LIFE	5/77	125C	N/R	1.84E 05	184	0	
					EM						184	0	
					OP CNST	LIFE	5/77	125C	N/R	2.17E 05	217	0	
					EM						217	0	
					OP CNST	LIFE	5/77	125C	N/R	1.06E 06	532	0	
					EM						532	1	
					OP CNST	LIFE	5/77	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP CNST	LIFE	5/77	125C	N/R	1.32E 05	132	0	
					EM						132	0	
					OP CNST	LIFE	5/77	125C	N/R	1.54E 06	770	0	
					EM						770	0	
					OP CNST	LIFE	5/77	125C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP CNST	LIFE	5/77	125C	N/R	9.45E 04	63	0	
					EM						63	0	
					OP CNST	LIFE	5/77	125C	N/R	2.46E 05	123	0	
					EM						123	1	
					OP CNST	LIFE	5/77	125C	N/R	2.19E 05	146	0	
					EM						146	0	
					OP CNST	LIFE	5/77	125C	N/R	1.10E 05	73	0	

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NFEF #
93415	D	NHD1P	16	M	EM	LIFE	5/77		N/R		73	0	
					OP CNST	LIFE	5/77	125C	N/R	1.80E 04	9	0	
					EM						9	0	
					OP CNST	LIFE	5/77	125C	N/R	1.62E 05	108	0	
					EM						108	0	
					OP CNST	LIFE	5/77	125C	N/R	1.32E 05	132	0	
					EM						132	0	
					OP CNST	LIFE	5/79	125C	N/R	2.70E 04	27	0	
					EM						27	0	
					OP CNST	LIFE	5/79	125C	N/R	9.90E 04	99	0	
					EM						99	0	
					OP CNST	LIFE	5/79	125C	N/R	2.20E 04	22	0	
					EM						22	0	
					OP CNST	LIFE	5/79	125C	N/R	7.00E 03	7	0	
					EM						7	0	
					OP CNST	LIFE	5/79	125C	N/R	9.90E 04	99	0	
					EM						99	0	
					OP CNST	LIFE	5/79	25C	N/R	2.50E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	25C	N/R	2.50E 04	25	0	
					EM						25	0	
					OP DYN	LIFE	5/79	125C	N/R	2.88E 05	288	0	
					EM						288	0	
					OP CNST	LIFE	5/79	125C	N/R	1.09E 05	109	0	
					EM						109	0	
					OP CNST	LIFE	5/79	125C	N/R	5.86E 05	293	0	
					EM						293	0	
					OP CNST	LIFE	5/79	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					OP CNST	LIFE	5/79	125C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	2.34E 05	117	0	
					EM						117	0	
					OP CNST	LIFE	5/79	125C	N/R	1.24E 05	62	0	
					EM						62	0	
					OP CNST	LIFE	5/79	125C	N/R	1.66E 05	84	1	
					EM						83	0	
					OP CNST	LIFE	5/79	1C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	1C	N/R	1.00E 05	100	0	
					EM						100	0	
					OP CNST	LIFE	5/79	1C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	1C	N/R	2.50E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	1C	N/R	2.50E 04	25	0	
					EM						25	0	
	NONE				OP CNST	LIFE	5/79	1C	N/R	5.50E 04	55	0	
					EM						55	0	
	D				MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			49	0	
								3X					
								60PSIG					
					EM						49	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		66	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			66	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			66	0	
								1 MIN E					
					FINE LK			HE 5.E-8			66	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			66	0	
								3X					
								60PSIG					
					EM						66	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	1	
								3X					
								60PSIG					
					EM						29	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		20	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		20	0	
								10CY					
								10/10DT					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NFEF #
93415	D	NHDIP	16	M	CNSTACC	ENV	8/79	30KG 6 AXES	N/R		20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		65	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			65	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			65	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			65	0	
								3X					
								60PSIG					
					EM						65	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

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PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			50	0	
								98%RH					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		23	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			23	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			23	0	
								98%RH					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
93415		NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		22	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	TEMPCYC	ENV	5/77	-065C 150C	N/R		22	0	
								10CY					
								10/10DT					
					HERMETC						22	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		22	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			22	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			22	0	
								1 MIN E					
					HERMETC						22	0	
					SALTATM	ENV	5/77	035C 25GMS	N/R		38	0	
								MSQ					
								24 HRS					
					VIS INS						38	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		22	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			22	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			22	0	
								98%RH					
					HERMETC						22	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		23	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			23	0	
								20G					
								3 AXES					
					MOIST			-010C 065C			23	0	
								98%RH					
					HERMETC						23	0	
					STGLIFE	LIFE	5/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					TEMPCYC	ENV	5/77	-065C 150C	N/R		20	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					HERMETC						20	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		82	0	
					HERMETC						82	1	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					HERMETC						20	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			20	0	
								98%RH					
					HERMETC						20	0	
					OP CNST	LIFE	5/77	125C	N/R	1.73E 05	345	0	
					EM						345	1	
					OP CNST	LIFE	5/77	125C	N/R	2.34E 05	467	0	
					EM						467	1	
					OP CNST	LIFE	5/77	125C	N/R	1.01E 05	201	0	
					EM						201	0	

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TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
93415	D	NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	9.90E 04	198	0	
					EM						198	0	
					OP CNST	LIFE	5/77	125C	N/R	2.90E 05	145	0	
					EM						145	0	
					OP CNST	LIFE	5/77	125C	N/R	5.10E 04	51	0	
					EM						51	0	
					OP CNST	LIFE	5/77	125C	N/R	9.90E 04	66	0	
					EM						66	0	
					OP CNST	LIFE	5/79	125C	N/R	3.28E 05	164	0	
					EM						164	0	
					OP CNST	LIFE	5/79	125C	N/R	2.60E 05	130	0	
					EM						130	0	
					OP CNST	LIFE	5/79	125C	N/R	1.70E 05	85	0	
					EM						85	0	
					OP CNST	LIFE	5/79	125C	N/R	1.56E 05	78	0	
					EM						78	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		40	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			40	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			40	0	
								3X					
								60PSIG					
					EM						40	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		29	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			29	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

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TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		29	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			29	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			29	0	
								98%RH					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					OP CNST	LIFE	12/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	12/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
93415		NHFPK	24	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		88	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			88	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			88	0	
								1 MIN E					
					HERMETC						88	0	
93415		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	1.61E 05	81	1	
					EM						80	0	
					OP CNST	LIFE	5/79	125C	N/R	2.32E 05	116	0	
					EM						116	0	
					OP CNST	LIFE	5/79	125C	N/R	2.30E 05	115	0	
					EM						115	0	
					OP CNST	LIFE	5/79	125C	N/R	1.19E 05	58	0	
					EM						58	0	
					OP CNST	LIFE	5/79	125C	N/R	1.90E 05	96	1	
					EM						95	0	
					OP CNST	LIFE	5/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP CNST	LIFE	5/79	125C	N/R	2.42E 05	113	0	
					EM						113	0	
					OP CNST	LIFE	5/79	125C	N/R	1.98E 05	99	0	
					EM						99	0	
					OP CNST	LIFE	5/79	125C	N/R	2.18E 05	109	0	
					EM						109	0	
					OP CNST	LIFE	5/79	125C	N/R	1.16E 05	29	0	
					EM						29	0	
					OP CNST	LIFE	5/79	125C	N/R	5.85E 04	39	0	
					EM						39	0	

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TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	6.75E 04	45	0	
					EM						45	0	
					OP CNST	LIFE	5/79	125C	N/R	8.25E 04	55	0	
					EM						55	0	
					OP CNST	LIFE	5/79	125C	N/R	9.00E 04	60	0	
					EM						60	0	
					OP CNST	LIFE	5/79	125C	N/R	6.60E 04	44	0	
					EM						44	0	
					OP CNST	LIFE	5/79	125C	N/R	5.72E 04	39	1	
					EM						39	0	
					OP CNST	LIFE	5/79	1C	N/R	2.50E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	1C	N/R	3.30E 04	22	0	
					EM						22	0	
					OP CNST	LIFE	5/79	1C	N/R	3.75E 04	25	0	
					EM						25	0	
	NONE				OP CNST	LIFE	5/79	1C	N/R	3.75E 04	25	0	
					EM						25	0	
	D				OP CNST	LIFE	5/79	1C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	1C	N/R	3.75E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	1C	N/R	3.62E 04	25	1	
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		100	0	
								1 MIN E					
					FINE LK			HE 5.E-8			100	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			100	0	
								3X					
								60PSIG					
					EM						100	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 6 AXES	N/R		105	0	
								1 MIN E					
					FINE LK			HE 5.E-8			105	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			105	0	
								3X					
								60PSIG					
					EM						105	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		75	0	
								15CY					
								LIQUID					
					FINE LK			HE 5.E-8			75	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			75	0	
								3X					
								60PSIG					
					EM						75	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					

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TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		93	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			93	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			93	0	
								1 MIN E					
					FINE LK			HE 5.E-8			93	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			93	0	
								3X					
								60PSIG					
					EM						93	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		145	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			145	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			145	0	
								1 MIN E					
					FINE LK			HE 5.E-8			145	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			145	0	
								3X					
								60PSIG					
					EM						145	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		47	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			47	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		47	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			47	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		234	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			234	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			234	0	
								1 MIN E					
					FINE LK			HE 5.E-8			234	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			234	0	
								3X					
								60PSIG					
					EM						234	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		63	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			63	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			63	0	
								1 MIN E					
					FINE LK			HE 5.E-8			63	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			63	0	
								3X					
								60PSIG					
					EM						63	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	THRMSHK	ENV	8/79	-055C 125C	N/R		75	0	
								15CY					
								LIQUID					
					FINE LK			HE 5.E-8			75	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			75	0	
								3X					
								60PSIG					
					EM						75	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		81	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			81	0	
								1 MIN E					
					FINE LK			HE 5.E-8			81	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			80	0	
								3X					
								60PSIG					
					EM						80	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		47	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		150	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			150	0	
								1 MIN E					
					FINE LK			HE 5.E-8			150	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			150	0	
								3X					
								60PSIG					
					EM						150	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	EM	ENV	8/79		N/R		50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						2	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		26	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		224	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			224	0	
								1 MIN E					
					FINE LK			HE 5.E-8			224	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — KAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		224	0	
								3X					
								60PSIG					
					EM						224	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		63	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			63	0	
								1 MIN E					
					FINE LK			HE 5.E-8			63	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			63	0	
								3X					
								60PSIG					
					EM						63	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		31	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			31	0	
								1 MIN E					
					FINE LK			HE 5.E-8			31	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			31	0	
								3X					
								60PSIG					
					EM						31	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		58	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			58	0	
								1 MIN E					
					FINE LK			HE 5.E-8			58	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			58	0	
								3X					
								60PSIG					
					EM						58	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		24	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			24	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		45	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
93415	D	NHE1P	TEMPCYC	ENV	8/79	-065C 150C	N/R		45	0	
						10CY					
						10/10DT					
			FINE LK			HE 5.E-8			45	0	
						60 MIN					
						30 MIN					
			GROSSLK			FLUOR 125C			45	0	
						3X					
						60PSIG					
			EM						45	0	
			THRMSHK	ENV	8/79	-055C 125C	N/R		150	0	
						15CY					
						LIQUID					
			TEMPCYC			-065C 150C			150	0	
						10CY					
						10/10DT					
			FINE LK			HE 5.E-8			150	0	
						60 MIN					
						30 MIN					
			GROSSLK			FLUOR 125C			150	0	
						3X					
						60PSIG					
			EM						150	0	
			THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
						15CY					
						LIQUID					
			TEMPCYC			-065C 150C			50	0	
						10CY					
						10/10DT					
			FINE LK			HE 5.E-8			50	0	
						60 MIN					
						30 MIN					
			GROSSLK			FLUOR 125C			50	0	
						3X					
						60PSIG					
			EM						50	0	
			THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
						15CY					
						LIQUID					
			TEMPCYC			-065C 150C			25	0	
						10CY					
						10/10DT					
			FINE LK			HE 5.E-8			25	0	
						60 MIN					
						30 MIN					
			GROSSLK			FLUOR 125C			25	1	
						3X					
						60PSIG					
			EM						24	0	
			THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
						15CY					
						LIQUID					
			TEMPCYC			-065C 150C			25	0	
						10CY					
						10/10DT					
			FINE LK			HE 5.E-8			25	0	
						60 MIN					
						30 MIN					
			GROSSLK			FLUOR 125C			25	0	
						3X					
						60PSIG					
			EM						25	0	
			THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
						15CY					
						LIQUID					
			TEMPCYC			-065C 150C			25	0	
						10CY					
						10/10DT					

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		46	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			46	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			46	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			46	0	
								3X					
								60PSIG					
					EM						46	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		24	0	
								15CY					
								LIQUID					
					TEMPCYC			-065 150C			24	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		193	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			193	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			193	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			193	0	
								3X					
								60PSIG					
					EM						193	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		63	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			63	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			63	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NFEF #
93415	D	NHDIP	16	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		63	0	
								3X					
								60PSIG					
					EM						63	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		31	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			31	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			31	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			31	0	
								3X					
								60PSIG					
					EM						31	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM			0			25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		73	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			73	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			73	0	
								98%RH					
					FINE LK			HE 5.E-8			73	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			73	0	
								3X					
								60PSIG					
					EM						73	0	
					OP CNST	LIFE	12/79	125C	N/R	1.95E 04	39	0	
					EM						39	0	
					OP CNST	LIFE	12/79	125C	N/R	2.30E 04	46	0	
					EM						46	0	
					OP CNST	LIFE	12/79	125C	N/R	2.75E 04	55	0	
					EM						55	0	
					OP CNST	LIFE	12/79	125C	N/R	3.00E 04	60	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NFEF #
93415	D	NHDIP	16	M	EM	LIFE	12/79		N/R		60	0	
					OP CNST	LIFE	12/79	125C	N/R	2.20E 04	44	0	
					EM						44	0	
					OP CNST	LIFE	12/79	125C	N/R	1.90E 04	38	0	
					EM						38	0	
					OP CNST	LIFE	12/79	125C	N/R	1.09E 06	546	0	
					EM						546	0	
					OP CNST	LIFE	12/79	125C	N/R	9.62E 04	49	1	2330
					EM						48	0	
					OP CNST	LIFE	12/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP CNST	LIFE	12/79	125C	N/R	1.66E 05	88	0	
					EM						88	0	
					OP CNST	LIFE	12/79	125C	N/R	2.36E 05	109	0	
					EM						109	0	
					OP CNST	LIFE	12/79	1C	N/R	1.10E 04	22	0	
					EM						22	0	
					OP CNST	LIFE	12/79	1C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	1C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	1C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	1C	N/R	1.25E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	12/79	1C	N/R	1.20E 04	24	0	
					EM						24	0	
93415		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	8.25E 04	55	0	
					EM						55	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		44	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			44	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			44	0	
								1 MIN E					
					FINE LK			HE 5.E-8			44	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			44	0	
								3X					
								60PSIG					
					EM						44	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		44	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			44	0	
								1 MIN E					
					FINE LK			HE 5.E-8			44	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			44	0	
								3X					
								60PSIG					
					EM						44	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		44	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHDIP	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		44	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			44	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			44	0	
								3X					
								60PSIG					
					EM						44	0	
					OP CNST	LIFE	12/79	125C	N/R	2.75E 04	55	0	
					EM						55	0	
93415		NHDIP	18	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		91	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			91	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			91	0	
								1 MIN E					
					FINE LK			HE 5.E-8			91	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			91	0	
								3X					
								60PSIG					
					EM						91	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		92	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			92	0	
								1 MIN E					
					FINE LK			HE 5.E-8			92	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			91	0	
								3X					
								60PSIG					
					EM						91	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415	D	NHFPK	24	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		23	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			23	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	1	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		23	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			23	0	
								1 MIN E					
					FINE LK			HE 5.E-8			23	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			23	0	
								3X					
								60PSIG					
					EM						23	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		24	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			24	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			24	0	
								98%RH					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
93422		NHFPK	24	M	THRMSHK	ENV	5/77	-055C 125C	N/R		27	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			27	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			27	0	
								98%RH					
					HERMETC						27	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		27	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			27	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					HERMETC						27	0	
93422		NHDIP	22	M	THRMSHK	ENV	5/77	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			20	0	
								98%RH					
					HERMETC						20	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93422	D	NHDIP	22	M	MECHSHK	ENV	5/77	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		20	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			20	0	
					CNSTACC			30KG 6 AXES 1 MIN E			20	0	
					HERMETC						20	0	
					TEMPCYC	ENV	5/77	-065C 150C 10CY 10/10DT	N/R		20	0	
					CNSTACC			30KG 6 AXES 1 MIN E			20	0	
					HERMETC						20	0	
93425		NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C 15CY LIQUID	N/R		20	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			20	0	
					MOIST			-010C 065C 98%RH			20	0	
					HERMETC						20	0	
					OP CNST	LIFE	5/77	125C	N/R	4.29E 05	286	0	
					EM						286	1	
					OP CNST	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	4.12E 05	206	0	
					EM						206	0	
					OP CNST	LIFE	5/79	125C	N/R	1.16E 05	58	0	
					EM						58	0	
					OP CNST	LIFE	5/79	125C	N/R	1.20E 05	61	1	
					EM						60	0	
93425		NHFPK	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		15	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			15	0	
					CNSTACC			30KG 6 AXES 1 MIN E			15	0	
					HERMETC						15	0	
93425		NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	3.26E 05	217	0	
					EM						217	1	
					OP CNST	LIFE	5/77	125C	N/R	9.60E 04	96	0	
					EM						96	0	
					OP CNST	LIFE	5/77	125C	N/R	8.80E 04	88	0	
					EM						88	0	
					OP CNST	LIFE	5/79	125C	N/R	1.50E 05	76	1	
					EM						75	0	
93425		NHFPK	16	M	MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		31	0	
					VBVRFQ			20HZ 2KHZ 20G 3 AXES			31	0	
					CNSTACC			30KG 6 AXES 1 MIN E			31	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			31	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			31	0	
					EM						31	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC 6 AXES 5 BLOS	N/R		29	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93425	D	NHFPK	16	M	VBVRFQ	ENV	8/79	20HZ 2KHZ	N/R		29	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			29	0	
								3X					
								60PSIG					
					EM						29	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					OP CNST	LIFE	12/79	125C	N/R	1.90E 05	95	0	
					EM						95	0	
93425		NHDIP	16	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		28	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93425	D	NHDIP	16	M	CNSTACC	ENV	8/79	30KG 6 AXES	N/R		28	0	
								1 MIN E					
					FINE LK			HE 5.E-8			28	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			28	0	
								3X					
								60PSIG					
					EM						28	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					OP CNST	LIFE	12/79	125C	N/R	1.94E 05	97	0	
					EM						97	0	
					OP CNST	LIFE	12/79	125C	N/R	5.00E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	12/79	150C	N/R	3.70E 05	185	0	
					EM						185	0	
					OP CNST	LIFE	12/79	125C	N/R	2.28E 05	106	1	2331
					EM						105	0	
					OP CNST	LIFE	12/79	125C	N/R	1.12E 05	96	0	
					EM						96	0	
					OP CNST	LIFE	12/79	150C	N/R	1.57E 05	96	0	
					EM						96	0	
					OP CNST	LIFE	12/79	125C	N/R	5.49E 04	47	0	
					EM						47	0	
					OP CNST	LIFE	12/79	125C	N/R	1.75E 05	105	0	
					EM						105	0	
					OP CNST	LIFE	12/79	125C	N/R	8.18E 04	70	0	
					EM						70	0	
					OP CNST	LIFE	12/79	150C	N/R	8.06E 04	69	0	
					EM						69	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93425	D	NHDIP	16	M	OP CNST	LIFE	12/79	1C	N/R	5.84E 04	50	0	
					EM						50	0	
93425	D-1	HDIP	16	C	OP CNST	LIFE	5/79	125C	N/R	1.50E 05	75	0	
					EM						75	0	
					OP CNST	LIFE	5/79	100C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP CNST	LIFE	5/79	100C	N/R	1.35E 05	54	0	
					EM						54	0	
					OP CNST	LIFE	5/79	100C	N/R	5.00E 04	25	0	
					EM						25	0	
					RHRB	LIFE	5/79	85C	N/R	1.48E 05	70	1	
					EM						69	0	
					RHRB	LIFE	5/79	85C	N/R	5.00E 04	25	0	
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C 1000CY 10/10DT	N/R		243	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			243	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			243	0	
					EM						243	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		75	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			75	0	
					MOIST			-010C 065C 98%RH			75	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			75	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			75	0	
					EM						75	0	
					THRMSHK	ENV	8/79	-055C 125C 15CY LIQUID	N/R		25	0	
					TEMPCYC			-065C 150C 10CY 10/10DT			25	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			25	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			25	0	
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C 1000CY LIQUID	N/R		105	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			105	0	
					GROSSLK			FLUOR 125C 3X 60PSIG			105	0	
					EM						105	0	
					THRMSHK	ENV	8/79	-055C 125C 1000CY LIQUID	N/R		243	0	
					FINE LK			HE 5.E-8 60 MIN 30 MIN			243	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93425	D-1	HDIP	16	C	GROSSLK	ENV	8/79	FLUOR 125C	N/R		243	0	
								3X					
								60PSIG					
					EM						243	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	1.56E 05	78	0	
					EM						78	0	

VARIOUS — RAM

TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93415/93425A	D-1	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	4.51E 06	480	1	
					N/R	FIELD	6/78	25C	GBC	1.38E 06	480	3	
93425A		HDIP	16	C	N/R	FIELD	2/78	25C	GBC	2.80E 06	270	0	
					N/R	FIELD	2/78	25C	GBC	4.82E 05	87	0	
					N/R	FIELD	6/78	25C	GBC	7.78E 05	270	0	
					N/R	FIELD	6/78	25C	GBC	2.51E 05	87	0	

FAIRCHILD SEMI — RAM

TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93471	D	NHDIP	18	M	OP CNST	LIFE	5/79	125C	N/R	8.20E 04	42	0	
					EM						42	0	
					OP CNST	LIFE	5/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	1.36E 05	69	0	
					EM						68	0	
					OP CNST	LIFE	5/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
					OP CNST	LIFE	5/79	125C	N/R	1.01E 05	67	0	
					EM						67	0	
					OP CNST	LIFE	5/79	125C	N/R	7.50E 04	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	4.92E 04	30	1	
					EM						29	0	
					OP CNST	LIFE	5/79	125C	N/R	4.80E 04	24	0	
					EM						24	0	
					OP CNST	LIFE	5/79	200C	N/R	5.00E 03	10	0	
					EM						10	0	
					OP CNST	LIFE	5/79	125C	N/R	6.50E 04	65	0	

FAIRCHILD SEMI RAM

TTL BIPOLAR NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
93471	D	NHDIP	18	M	EM	LIFE	5/79		N/R		65	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	1.92E 05	96	0	
					EM						96	0	
					OP CNST	LIFE	5/79	125C	N/R	2.32E 05	232	0	
					EM						232	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		100	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			100	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			100	0	
								3X					
								60PSIG					
					EM						100	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		27	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			27	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		17	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			17	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			17	0	
								98%RH					
					FINE LK			HE 5.E-8			17	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			17	0	
								3X					
								60PSIG					
					EM						17	0	
					OP CNST	LIFE	12/79	125C	N/R	8.06E 05	403	0	
					EM						403	0	
					OP CNST	LIFE	12/79	125C	N/R	2.15E 05	144	1	2329
					EM						143	0	
					OP CNST	LIFE	12/79	125C	N/R	1.13E 05	52	0	
					EM						52	0	
					OP CNST	LIFE	12/79	125C	N/R	1.47E 05	88	0	
					EM						88	0	
					OP CNST	LIFE	12/79	125C	N/R	9.81E 04	84	0	
					EM						84	0	
					OP CNST	LIFE	12/79	125C	N/R	1.18E 05	71	0	
					EM						71	0	

FAIRCHILD SEMI RAM

ECL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	REF #
100414	D	NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
100414		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	2.25E 05	150	0	
					EM						150	0	
					OP CNST	LIFE	12/79	125C	N/R	7.50E 04	150	0	
					EM						150	0	
10145		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	1.76E 05	89	1	
					EM						88	0	
10145		NHDIP	16	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	1	
								3X					
								60PSIG					
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
10145A		NHFPK	16	M	MECHSHK	ENV	8/79	.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

FAIRCHILD SEMI RAM

ECL BIPOLAR NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	IMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
10145A	D	NHFPK	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
10410		NHFPK	16	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					HERMETC						50	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					HERMETC						50	0	
10410		NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		7	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			7	0	
								10CY					
								10/10DT					
					HERMETC						7	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		7	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			7	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			7	0	
								1 MIN E					
					HERMETC						7	0	
					OP CNST	LIFE	5/77	125C	N/R	8.80E 04	44	0	
					EM						44	0	
					OP CNST	LIFE	5/77	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	8.80E 04	44	0	
					EM						44	0	
10410		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	4.18E 05	209	0	
					EM						209	0	
10410		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	1.40E 05	69	0	
					EM						69	0	

MOTOROLA SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10144	:D	:NHDIP	16	:1	: N/R	: FIELD	6/77	30C	GBC	5.50E 07	99999	8	
					: N/R			30C			10001	0	
:1037	:D-1	:HDIP	14	:C	: N/R	: FIELD	5/77	40C	GBC	8.80E 06	2472	1	
					: N/R	: FIELD	5/78	40C	GBC	8.05E 06	6192	1	
					: N/R	: FIELD	4/79	40C	GBC	8.66E 06	6660	0	
					: N/R	: FIELD	4/80	40C	GBC	4.33E 06	3330	1	

SIGNETICS — RAM

ECL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10145	:D	:NHDIP	16	:I	: OP DYN	: LIFE	11/77	125C	N/R	4.60E 04	46	0	
					: EM						46	1	
					: STGLIFE	: LIFE	11/77	150C	N/R	4.60E 04	46	0	
					: EM						46	0	

VARIOUS — RAM

ECL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:N/R	:X	:NHDIP	0	:N/R:	N/R	: FIELD	12/77	35C	GBC	2.40E 07	0	148	
:N/R	:	:NHDIP	0	:N/R:	N/R	: FIELD	12/77	35C	GBC	0.00E 07	0	49	

FAIRCHILD SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10415	:D	:NHFPK	16	:M	: TEMPCYC	: ENV	5/77	:-065C 150C	N/R		130	0	
								:10CY					
								:10/10DT					
					: CNSTACC			:30KG 6 AXES			130	0	
								:1 MIN E					
					: HERMETC						130	0	
					: MECHSHK	: ENV	5/77	:1.5KG .5MSEC	N/R		50	0	
								:6 AXES					
								:5 BLOS					
					: VBVRFQ			:20HZ 2KHZ			50	0	
								:20G					
								:3 AXES					
					: CNSTACC			:30KG 6 AXES			50	0	
								:1 MIN E					
					: HERMETC						50	0	

FAIRCHILD SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFR #
10415	D	NHFPK	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			50	0	
								98%RH					
					HERMETC						50	0	
					SALTATM	ENV	5/77	035C 25GMS	N/R		15	0	
								MSQ					
								24 HRS					
					VIS INS						15	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		35	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			35	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					HERMETC						35	0	
					TEMPCYC	ENV	5/77	-065C 150C	N/R		32	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			32	0	
								1 MIN E					
					HERMETC						32	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		35	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			35	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			35	0	
								98%RH					
					HERMETC						35	0	
					OP CNST	LIFE	5/79	125C	N/R	5.00E 04	25	0	
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		43	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			43	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			43	0	
								1 MIN E					
					FINE LK			HE 5.E-8			43	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			43	0	
								3X					
								60PSIG					
					EM						43	0	

FAIRCHILD SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10415	D	NHFPK	16	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		138	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			138	0	
								1 MIN E					
					FINE LK			HE 5.E-8			138	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			138	0	
								3X					
								60PSIG					
					EM						138	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		43	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			43	0	
								1 MIN E					
					FINE LK			HE 5.E-8			43	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			43	0	
								3X					
								60PSIG					
					EM						43	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		14	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			14	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			14	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			14	0	
								3X					
								60PSIG					
					EM						14	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		43	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			43	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI RAM

ECL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10415	D	NHFPK	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		43	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			43	0	
								3X					
								60PSIG					
					EM						43	0	
					OP CNST	LIFE	12/79	125C	N/R	1.90E 05	95	0	
					EM						95	0	
10415		NHDIP	16	M	TEMPCYC	ENV	5/77	-065C 150C	N/R		75	0	
								10CY					
								10/10DT					
					THRMSHK			-055C 125C			75	0	
								15CY					
								LIQUID					
					MECHSHK			1.5KG .5MSEC			75	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			75	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			75	0	
								1 MIN E					
					HFRMETC						75	0	
					OP CNST	LIFE	5/77	125C	N/R	9.80E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/77	125C	N/R	4.60E 04	23	0	
					EM						23	0	
					OP CNST	LIFE	5/79	125C	N/R	1.95E 05	98	1	
					EM						97	0	
					OP CNST	LIFE	5/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		22	0	
								1 MIN E					
					FINE LK			HE 5.E-8			22	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			22	0	
								3X					
								60PSIG					
					EM						22	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		37	0	
								1 MIN E					
					FINE LK			HE 5.E-8			37	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			36	0	
								3X					
								60PSIG					
					EM						36	0	
10415		NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	2.50E 05	125	0	
					EM						125	0	
					OP CNST	LIFE	5/77	125C	N/R	9.90E 04	99	0	
					EM						99	0	
					OP CNST	LIFE	5/79	125C	N/R	3.00E 05	150	0	
					EM						150	0	
10415		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP CNST	LIFE	5/79	125C	N/R	2.00E 05	100	0	
					EM						100	0	
					OP CNST	LIFE	5/79	125C	N/R	5.80E 04	29	0	
					EM						29	0	
					OP CNST	LIFE	5/79	125C	N/R	3.46E 05	86	1	
					EM						85	0	
					OP CNST	LIFE	5/79	125C	N/R	3.00E 04	20	0	
					EM						20	0	

FAIRCHILD SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10415	:D	:NHDIP	16	:M	MECHSHK	ENV	8/79	:1.5KG .5MSEC	N/R		50	0	
								:6 AXES					
								:5 BLOS					
					VBVRFQ			:20HZ 2KHZ			50	0	
								:20G					
								:3 AXES					
					CNSTACC			:30KG 6 AXES			50	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			50	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			50	0	
								:3X					
								:60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	:-065C 150C	N/R		100	0	
								:10CY					
								:10/10DT					
					CNSTACC			:30KG 6 AXES			100	0	
								:1 MIN E					
					FINE LK			:HE 5.E-8			100	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			100	1	
								:3X					
								:60PSIG					
					EM						99	0	
					THRMSHK	ENV	8/79	:-055C 125C	N/R		100	0	
								:15CY					
								:LIQUID					
					TEMPCYC			:-065C 150C			100	0	
								:10CY					
								:10/10DT					
					MOIST			:-010C 065C			100	0	
								:98%RH					
					FINE LK			:HE 5.E-8			100	0	
								:60 MIN					
								:30 MIN					
					GROSSLK			:FLUOR 125C			100	0	
								:3X					
								:60PSIG					
					EM						100	0	
					OP CNST	LIFE	12/79	125C	N/R	1.00E 04	20	0	
					EM						20	0	
					OP CNST	LIFE	12/79	125C	N/R	2.94E 05	147	0	
					EM						147	0	
					OP CNST	LIFE	12/79	125C	N/R	5.87E 04	28	1	2333
					EM						27	0	
					OP CNST	LIFE	12/79	125C	N/R	5.61E 04	48	0	
					EM						48	0	
:10415		:HDIP	16	:C	OP CNST	LIFE	5/79	100C	N/R	1.30E 05	65	0	
					EM						65	0	
					RHRB	LIFE	5/79	85C	N/R	7.00E 04	35	0	
					EM						35	0	

MOTOROLA SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10146	:D	:NHDIP	16	:C	S&D EM	LIFE	/77	25C	N/R		20	0	

MOTOROLA SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10146	D	NHDIP	16	C	OP DYN	LIFE	/77	70C	N/R	8.06E 04	20	0	
					S&D EM			25C			20	0	

FAIRCHILD SEMI — RAM

ECL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10470	D	NHDIP	18	M	OP CNST	LIFE	5/79	125C	N/R	3.30E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	12/79	125C	N/R	8.89E 04	41	0	
					EM						41	0	
					OP CNST	LIFE	12/79	125C	N/R	1.92E 05	164	0	
					EM						164	0	

FAIRCHILD SEMI — RAM

IIL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93481	D	NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	4.00E 04	20	0	
					EM						20	0	
					OP CNST	LIFE	5/77	125C	N/R	4.80E 04	48	0	
					EM						48	0	
93481	D-1	HDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	5.40E 04	27	0	
					EM						27	0	
93481	D	NHDIP	16	C	S&D EM	LIFE	/77	25C	N/R		24	0	
					OP DYN			70C		4.44E 04	24	0	
					S&D EM			25C			24	0	

VARIOUS — RAM

S/R TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	2.87E 05	21	0	
					N/R	FIELD	7/79	25C	GF	9.07E 04	21	0	
					N/R	FIELD	8/80	25C	GF	2.12E 05	21	0	

ADVANCED MICRO DEVICES — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
27S01	B-2	NHFPK	16	M	OPERATE	CHECK	3/78	025C	AIT	2.29E 04	364	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	1.29E 03	364	0	
					OPERATE	CHECK	3/78	025C	AIT	5.78E 04	364	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	6.29E 04	364	0	
27S03		NHDIP	16	M	REVBIAS	BRN	6/80	150C	N/R	1.68E 04	84	0	
					EM			150C			84	0	
					REVBIAS	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	0	
3101		NHDIP	16	M	OPERATE	RELDEM	12/77		AIU	2.24E 04	695	0	
54S189		NHFPK	16	M	OPERATE	CHECK	3/78	025C	AIT	6.98E 02	26	0	
					OPERATE	CHECK	3/78	025C	AIT	2.04E 04	325	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	4.82E 02	26	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	1.15E 03	325	0	
					OPERATE	CHECK	3/78	025C	AIT	4.74E 03	26	0	
					OPERATE	CHECK	3/78	025C	AIT	5.17E 04	325	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	4.75E 03	26	0	
					TCVPC	RELPRO	3/78	002C 045C 5CY 1.5G 79% 45HZ 22%	AIT	5.62E 04	325	0	

MONOLITHIC MEMORIES — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5531	B-2	NHDIP	16	M	OPERATE	RELDEM	12/77		AIU	1.27E 05	3930	0	

NATIONAL SEMI — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S206	D	NHDIP	16	C	OP DYN	LIFE	12/78	125C	N/R	3.02E 04	30	0	
					EM						30	0	

SIGNETICS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S06	D	NHDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	1.27E 05	63	0	

SIGNETICS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S06	D	NHDIP	16	C	EM	LIFE	11/77		N/R		63	2	
					OP DYN	LIFE	11/77	125C	N/R	2.90E 04	29	0	
					EM						29	1	
					OP DYN	LIFE	11/77	125C	N/R	1.29E 05	64	0	
					EM						64	2	
					STGLIFE	LIFE	11/77	150C	N/R	1.37E 05	68	0	
					EM						68	1	
					STGLIFE	LIFE	11/77	150C	N/R	1.37E 05	68	0	
					EM						68	1	
82S06		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	0	
					STGLIFE	LIFE	11/77	150C	N/R	9.00E 04	90	0	
					EM						90	0	
82S06	D-1	HDIP	16	N/R	OP DYN	LIFE	11/77	85C	N/R	4.50E 04	45	0	
					EM						45	0	
82S12	D	NHDIP	24	N/R	STGLIFE	LIFE	11/77	150C	N/R	4.50E 04	45	0	
					EM						45	0	
82S16		NHDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	7.80E 04	77	0	
					EM						77	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
82S25	S-2	NHDIP	16	M	N/R	FIELD	3/80		NS	1.41E 06	217	0	

VARIOUS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D-1	HDIP	16	C	OP DYN	LIFE	9/78	150C	N/R	3.00E 04	20	2	
					S&F EM			25C			20	1	
					OP DYN	LIFE	9/78	150C	N/R	4.00E 04	20	3	
					S&F EM			25C			20	12	
N/R	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	5.25E 06	384	0	
					N/R	FIELD	1/79	25C	GF	1.93E 07	1408	0	
					N/R	FIELD	1/79	25C	GF	1.19E 07	872	0	
					N/R	FIELD	1/79	25C	GF	6.57E 05	48	0	
					N/R	FIELD	7/79	25C	GF	2.07E 05	48	0	
					N/R	FIELD	7/79	25C	GF	1.66E 06	384	0	
					N/R	FIELD	7/79	25C	GF	6.08E 06	1408	0	
					N/R	FIELD	7/79	25C	GF	3.77E 06	872	0	
					N/R	FIELD	8/80	25C	GF	4.84E 05	48	0	
					N/R	FIELD	8/80	25C	GF	3.87E 06	384	0	
					N/R	FIELD	8/80	25C	GF	1.42E 07	1408	0	
					N/R	FIELD	8/80	25C	GF	8.79E 06	872	0	
3101	B-1	NHDIP	16	M	N/R	FIELD	9/78		AUF	1.50E 05	132	0	
					N/R	FIELD	9/79		AIU	4.75E 04	132	0	
3101	D	NHDIP	16	C	OP DYN	LIFE	9/78	150C	N/R	6.00E 04	20	1	
					FNCT EM			25C			20	0	
					ACCLFOD	LIFE	9/78	200C	N/R	6.00E 04	20	2	
					FNCT EM			25C			20	0	
3101	NONE		0	M	N/R	FIELD	4/79	25C	GB	1.5E 05	8	0	
					N/R	FIELD	4/79	25C	GB	3.18E 05	16	0	
3101A	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	3.48E 07	9960	14	
					N/R	FIELD	5/78	40C	GBC	2.51E 07	19333	10	
					N/R	FIELD	4/79	40C	GBC	1.52E 07	11662	1	
					N/R	FIELD	4/80	40C	GBC	9.69E 06	7452	6	
					N/R	FIELD	4/81	40C	GBC	1.42E 07	5456	3	
74S189		HDIP	16	C	N/R	FIELD	2/78	25C	GBC	9.22E 04	9	0	
					N/R	FIELD	2/78	25C	GBC	1.16E 05	21	0	
					N/R	FIELD	2/78	25C	GBC	4.03E 05	40	0	
					N/R	FIELD	6/78	25C	GBC	2.59E 04	9	0	

VARIOUS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74S189	D-1	HDIP	16	C	N/R	FIELD	6/78	25C	GBC	6.05E 04	21	0	
					N/R	FIELD	6/78	25C	GBC	1.15E 05	40	0	
8582/3107	NONE	DIP	16	C	N/R	FIELD	5/77	40C	GBC	2.65E 05	73	0	
					N/R	FIELD	5/78	40C	GBC	3.85E 05	296	0	
					N/R	FIELD	4/79	40C	GBC	4.98E 05	383	1	
					N/R	FIELD	4/80	40C	GBC	3.95E 05	304	0	
					N/R	FIELD	4/81	40C	GBC	1.51E 06	582	0	

SIGNETICS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 576

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S09	D	NHDIP	28	N/R	OP DYN	LIFE	11/77	125C	N/R	4.40E 04	44	0	
					EM						44	0	
					STGLIFE	LIFE	11/77	150C	N/R	1.01E 05	101	0	
					EM						101	0	

SIGNETICS — RAM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S10	D	NHDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	3	
					OP DYN	LIFE	11/77	125C	N/R	9.10E 04	45	0	
					EM						45	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
82S10		NHDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	2.01E 05	200	0	
					EM						200	0	
					REVBIAS	LIFE	11/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					REVBIAS	LIFE	11/77	125C	N/R	1.01E 05	100	0	
					EM						100	0	
					REVBIAS	LIFE	11/77	125C	N/R	1.01E 05	100	0	
					EM						100	1	
					REVBIAS	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	0	
					REVBIAS	LIFE	11/77	125C	N/R	6.60E 04	65	0	
					EM						65	0	
82S10	D-1	HDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	9.10E 04	45	0	
					EM						45	1	
82S11	D	NHDIP	16	C	REVBIAS	LIFE	11/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					REVBIAS	LIFE	11/77	125C	N/R	6.80E 04	67	0	
					EM						67	1	

FAIRCHILD SEMI — RAM

SCHOTTKY I IL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9410	D-1	HDIP	18	N/R	OP CNST	LIFE	5/78	100C	N/R	8.79E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/78	100C	N/R	4.80E 04	24	0	
					EM						24	0	
					THRMSHK	ENV	5/78	125C	N/R		41	0	
								15CY					
					TEMPCYC			-065C 150C			41	0	
								100CY					
					EM						41	1	
					THRMSHK	ENV	5/78	-055C 125C	N/R		25	0	
								15CY					
					TEMPCYC			-065C 150C			25	0	
								10CY					
					MOIST						25	0	
					EM						25	0	
					THRMSHK	ENV	5/78	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		21	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			21	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			21	0	
								3X					
								60PSIG					
					EM						21	0	

ADVANCED MICRO DEVICES — RAM

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
27LS00	B-2	NHDIP	16	M	REVBIAS	LIFE	6/80	125C	N/R	2.67E 05	267	0	
					EM			125C			267	1	

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L420	D	NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	7.90E 04	79	0	
					EM						79	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
93L420		NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	7.80E 04	78	0	
					EM						78	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		26	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	

NATIONAL SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74L89A	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	5.34E 05	143	1	
					N/R	FIELD	5/78	40C	GBC	2.29E 05	176	0	
					N/R	FIELD	4/79	40C	GBC	1.05E 05	81	0	
					N/R	FIELD	4/80	40C	GBC	3.38E 04	26	0	
86L99		HDIP	16	C	N/R	FIELD	5/77	40C	GBC	8.19E 04	126	2	
					N/R	FIELD	5/78	40C	GBC	1.72E 05	132	0	

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L412	D	NHDIP	22	M	OP CNST	LIFE	5/77	125C	N/R	1.52E 05	76	0	
					EM						76	0	
					OP CNST	LIFE	5/77	125C	N/R	7.90E 04	79	0	
					EM						79	0	
					OP CNST	LIFE	5/79	125C	N/R	1.52E 05	76	0	
					EM						76	0	

FAIRCHILD SEMI RAM

LOW POWER TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L412	D	NHDIP	22	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		26	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			26	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		14	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			14	0	
								1 MIN E					
					FINE LK			HE 5.E-8			14	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			14	0	
								3X					
								60PSIG					
					EM						14	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	7.70E 04	77	0	
					EM						77	0	
93L415	D-1	HDIP	16	C	RHRB	LIFE	5/77	85C	N/R	1.22E 05	61	0	
					EM						61	0	
					RHRB	LIFE	5/77	85C	N/R	3.20E 05	160	0	
					EM						160	0	
					RHRB	LIFE	5/77	85C	N/R	9.60E 04	48	0	
					EM						48	0	
					RHRB	LIFE	5/77	85C	N/R	2.00E 05	100	0	
					EM						100	0	
					RHRB	LIFE	5/77	85C	N/R	3.08E 05	308	0	
					EM						308	0	
					RHRB	LIFE	5/79	85C	N/R	1.08E 05	108	0	
					EM						108	0	
					RHRB	LIFE	5/79	85C	N/R	2.16E 05	108	0	
					EM						108	0	
					RHRB	LIFE	5/79	85C	N/R	1.08E 05	54	0	
					EM						54	0	
					RHRB	LIFE	5/79	85C	N/R	2.14E 05	108	1	
					EM						107	0	
					RHRB	LIFE	5/79	85C	N/R	1.08E 05	54	0	
					EM						54	0	
93L415	D	NHDIP	16	M	THRMSHK	ENV	5/77	-055C 125C	N/R		15	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L415	D	NHDIP	16	M	TEMPCYC	ENV	5/77	-065C 150C	N/R		15	0	
								10CY					
								10/10DT					
					HERMETC						15	0	
					SALTATM	ENV	5/77	035C 25GMS	N/R		15	0	
								MSQ					
								24 HRS					
					VIS INS						15	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		15	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			15	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			15	0	
								1 MIN E					
					HERMETC						15	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			20	0	
								98%RH					
					HERMETC						20	0	
					MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		20	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			20	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			20	0	
								1 MIN E					
					HERMETC						20	0	
					OP CNST	LIFE	5/77	125C	N/R	2.80E 05	140	0	
					EM						140	0	
					OP CNST	LIFE	5/77	125C	N/R	3.20E 04	16	0	
					EM						16	0	
					OP CNST	LIFE	5/77	125C	N/R	3.86E 05	193	0	
					EM						193	0	
					OP CNST	LIFE	5/77	125C	N/R	4.00E 05	200	0	
					EM						200	0	
					OP CNST	LIFE	5/77	125C	N/R	5.60E 05	280	0	
					EM						280	0	
					OP CNST	LIFE	5/77	125C	N/R	9.80E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/77	125C	N/R	5.02E 05	251	0	
					EM						251	1	
					OP CNST	LIFE	5/79	125C	N/R	9.82E 04	50	1	
					EM						50	0	
					OP CNST	LIFE	5/79	125C	N/R	1.80E 05	90	0	
					EM						90	0	
					OP CNST	LIFE	5/79	125C	N/R	2.14E 05	107	0	
					EM						107	0	
					OP CNST	LIFE	5/79	125C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP CNST	LIFE	5/79	125C	N/R	9.80E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/79	125C	N/R	4.50E 04	45	0	
					EM						45	0	
					OP CNST	LIFE	5/79	125C	N/R	2.80E 05	140	0	
					EM						140	0	
					OP CNST	LIFE	5/79	100C	N/R	3.20E 04	16	0	
					EM						16	0	
					OP CNST	LIFE	5/79	125C	N/R	3.86E 05	193	0	
					EM						193	0	
					OP CNST	LIFE	5/79	125C	N/R	4.00E 05	200	0	
					EM						200	0	

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LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEP #
93L415	D	NHDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	5.60E 05	280	0	
					EM						280	0	
					OP CNST	LIFE	5/79	125C	N/R	4.90E 04	49	0	
					EM						49	0	
					OP CNST	LIFE	5/79	125C	N/R	3.78E 05	189	0	
					EM						189	0	
					OP CNST	LIFE	5/79	125C	N/R	5.00E 05	251	1	
					EM						250	0	
					OP CNST	LIFE	5/79	125C	N/R	2.94E 05	148	1	
					EM						147	0	
					OP CNST	LIFE	5/79	125C	N/R	2.92E 05	146	0	
					EM						146	0	
					OP CNST	LIFE	5/79	125C	N/R	2.20E 05	111	1	
					EM						110	0	
					OP CNST	LIFE	5/79	125C	N/R	2.46E 05	123	0	
					EM						123	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93L415		NHDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	4.04E 05	202	0	
					EM						202	0	
					OP CNST	LIFE	5/77	125C	N/R	5.29E 05	529	0	
					EM						529	1	
					OP CNST	LIFE	5/79	125C	N/R	4.04E 05	202	0	
					EM						202	0	
					OP CNST	LIFE	5/79	125C	N/R	1.06E 06	529	1	
					EM						528	0	
					OP CNST	LIFE	5/79	125C	N/R	8.73E 05	291	0	
					EM						291	0	
					OP CNST	LIFE	5/79	125C	N/R	1.20E 05	60	0	
					EM						60	0	
					OP CNST	LIFE	5/79	125C	N/R	3.90E 05	195	0	
					EM						195	0	
					OP CNST	LIFE	5/79	125C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP CNST	LIFE	5/79	1C	N/R	5.00E 04	50	0	
					EM						50	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					

FAIRCHILD SEMI RAM

LOW POWER TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L415	D	NHDIP	16	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					OP CNST	LIFE	12/79	125C	N/R	5.00E 04	50	0	
					EM						50	0	
93L415	D-1	HDIP	16	C	OP CNST	LIFE	5/79	100C	N/R	6.60E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	5/79	100C	N/R	1.86E 05	93	0	
					EM						93	0	
					OP CNST	LIFE	5/79	100C	N/R	1.08E 05	54	0	
					EM						54	0	
	NONE				OP CNST	LIFE	5/79	100C	N/R	3.34E 05	167	0	
					EM						167	0	
					OP CNST	LIFE	5/79	100C	N/R	1.66E 05	83	0	
					EM						83	0	
					OP CNST	LIFE	5/79	100C	N/R	3.17E 05	159	1	
					EM						158	0	
	D-1				OP CNST	LIFE	5/79	100C	N/R	7.20E 04	48	0	
					EM						48	0	
93L422	D	NHDIP	22	M	MECHSHK	ENV	5/77	1.5KG .5MSEC	N/R		45	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			45	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			45	0	
								1 MIN E					
					HERMETC						45	0	
					THRMSHK	ENV	5/77	-055C 125C	N/R		45	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			45	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			45	0	
								98%RH					
					HERMETC						45	0	
					OP CNST	LIFE	5/79	125C	N/R	2.38E 04	10	0	

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LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHDIP	22	M	EM	LIFE	5/79		N/R		10	0	
					OP CNST	LIFE	5/79	125C	N/R	1.58E 05	79	0	
					EM						79	0	
					OP CNST	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/79	125C	N/R	9.60E 04	48	0	
					EM						48	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		48	0	
								1 MIN E					
					FINE LK			HE 5.E-8			48	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			48	0	
								3X					
								60PSIG					
					EM						48	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		32	0	
								1 MIN E					
					FINE LK			HE 5.E-8			32	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			32	0	
								3X					
								60PSIG					
					EM						32	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		24	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			24	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79		N/R		25	0	
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					

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LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
93L422	D	NHDIP	22	M	CNSTACC	ENV	8/79	30KG 6 AXES; 1 MIN E	N/R		25	0	
					FINE LK			HE 5.E-8; 60 MIN; 30 MIN			25	0	
					GROSSLK			FLUOR 125C; 3X; 60PSIG			25	0	
					EM			0			25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC; 6 AXES; 5 BLOS	N/R		21	0	
					VBVRFQ			20HZ 2KHZ; 20G; 3 AXES			21	0	
					CNSTACC			30KG 6 AXES; 1 MIN E			21	0	
					FINE LK			HE 5.E-8; 60 MIN; 30 MIN			21	0	
					GROSSLK			FLUOR 125C; 3X; 60PSIG			21	0	
					EM						21	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC; 6 AXES; 5 BLOS	N/R		29	0	
					VBVRFQ			20HZ 2KHZ; 20G; 3 AXES			29	0	
					CNSTACC			30KG 6 AXES; 1 MIN E			29	0	
					FINE LK			HE 5.E-8; 60 MIN; 30 MIN			29	0	
					GROSSLK			FLUOR 125C; 3X; 60PSIG			29	0	
					EM						29	0	
					TEMPCYC	ENV	8/79	-065C 150C; 10CY; 10/10DT	N/R		25	0	
					CNSTACC			30KG 6 AXES; 1 MIN E			25	0	
					FINE LK			HE 5.E-8; 60 MIN; 30 MIN			25	0	
					GROSSLK			FLUOR 125C; 3X; 60PSIG			25	0	
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C; 10CY; 10/10DT	N/R		25	0	
					CNSTACC			30KG 6 AXES; 1 MIN E			25	0	
					FINE LK			HE 5.E-8; 60 MIN; 30 MIN			25	1	
					GROSSLK			FLUOR 125C; 3X; 60PSIG			24	0	
					EM						24	0	
					TEMPCYC	ENV	8/79	-065C 150C; 10CY; 10/10DT	N/R		25	0	
					CNSTACC			30KG 6 AXES; 1 MIN E			25	0	

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LOW POWER TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHDIP	22	M	FINE LK	ENV	8/79	HE 5.E-8	N/R		25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		15	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			15	0	
								1 MIN E					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								60PSIG					
					EM						15	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								60PSIG					
					EM						35	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		26	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		49	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			49	0	
								1 MIN E					
					FINE LK			HE 5.E-8			49	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			49	0	
								3X					
								60PSIG					
					EM						49	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		32	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			32	0	
								1 MIN E					
					FINE LK			HE 5.E-8			32	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			32	0	
								3X					
								60PSIG					
					EM						32	0	

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LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHDIP	22	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		4	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			4	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			4	0	
								98%RH					
					FINE LK			HE 5.E-8			4	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			4	0	
								3X					
								60PSIG					
					EM						4	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		29	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			29	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			29	0	
								98%RH					
					FINE LK			HE 5.E-8			29	0	
								60 MIN					
								30 MIN					

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LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHDIP	22	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		29	0	
								3X					
								60PSIG					
					EM						29	0	
					OP CNST	LIFE	12/79	125C	N/R	5.00E 03	5	0	
					EM						5	0	
					OP CNST	LIFE	12/79	125C	N/R	7.70E 04	77	0	
					EM						77	0	
93L422		NHFPK	24	M	CNSTACC	ENV	8/79	30KG 2 AXES	N/R		24	0	
								1 MIN E					
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								60PSIG					
					EM						24	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		22	0	
								1 MIN E					
					FINE LK			HE 5.E-8			22	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			22	0	
								3X					
								60PSIG					
					EM						22	0	
					CNSTACC	ENV	8/79	30KG 2 AXES	N/R		89	0	
								1 MIN E					
					FINE LK			HE 5.E-8			89	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			89	1	
								3X					
								60PSIG					
					EM						88	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		30	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			30	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	1	
								3X					
								60PSIG					
					EM						29	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		28	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			28	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			28	0	
								1 MIN E					
					FINE LK			HE 5.E-8			28	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			28	0	
								3X					
								60PSIG					
					EM						28	1	
					THRMSHK	ENV	8/79	-055C 125C	N/R		30	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHFPK	24	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			30	0	
								98%RH					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		28	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			28	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			28	0	
								98%RH					
					FINE LK			HE 5.E-8			28	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			28	0	
								3X					
								60PSIG					
					EM						28	0	
93L422		NHDIP	22	M	OP CNST	LIFE	5/79	125C	N/R	7.20E 04	48	0	
					EM						48	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		32	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			32	0	
								1 MIN E					
					FINE LK			HE 5.E-8			32	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHDIP	22	M	GROSSLK	ENV	8/79	FLUOR 125C	N/R		32	0	
								3X					
								60PSIG					
					EM						32	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		20	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			20	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			20	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			20	0	
								3X					
								60PSIG					
					EM						20	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		50	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			50	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			50	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								60PSIG					
					EM						50	0	
					OP CNST	LIFE	12/79	125C	N/R	1.92E 05	96	0	
					EM						96	0	
					OP CNST	LIFE	12/79	125C	N/R	4.60E 04	46	0	
					EM						46	0	
93L422		NHFPK	22	M	THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	

FAIRCHILD SEMI RAM

LOW POWER TTL BIPOLAR NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHFPK	22	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		47	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			47	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			47	0	
								1 MIN E					
					FINE LK			HE 5.E-8			47	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			47	0	
								3X					
								60PSIG					
					EM						47	0	
					MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		48	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			48	0	
								1 MIN E					
					FINE LK			HE 5.E-8			48	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			48	0	
								3X					
								60PSIG					
					EM						48	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		40	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			40	0	
								1 MIN E					
					FINE LK			HE 5.E-8			40	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			40	0	
								3X					
								60PSIG					
					EM						40	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		22	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			22	0	
								1 MIN E					
					FINE LK			HE 5.E-8			22	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			22	0	
								3X					
								60PSIG					
					EM						22	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		40	0	
								15CY					
								LIQUID					

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L422	D	NHFPK	22	M	TEMPCYC	ENV	8/79	-065C 150C	N/R		40	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			40	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			40	0	
								3X					
								60PSIG					
					EM						40	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								60PSIG					
					EM						25	0	
93L425	D-1	HDIP	16	C	RHRB	LIFE	5/77	85C	N/R	9.40E 04	94	0	
					EM						94	0	
					OP CNST	LIFE	5/77	100C	N/R	2.86E 05	143	0	
					EM						143	1	
					OP CNST	LIFE	5/77	100C	N/R	6.60E 04	33	0	
					EM						33	0	
					OP CNST	LIFE	5/79	100C	N/R	3.20E 05	160	0	
					EM						160	0	
					OP CNST	LIFE	5/79	100C	N/R	1.16E 05	58	0	
					EM						58	0	
					OP CNST	LIFE	5/79	100C	N/R	2.84E 05	143	1	
					EM						142	0	
					OP CNST	LIFE	5/79	100C	N/R	7.40E 04	37	0	
					EM						34	0	
					RHRB	LIFE	5/79	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					AUTOCLV	ENV	8/79	15PSIG121C	N/R		134	0	
								500HRS					
					EM						134	0	
					OP CNST	LIFE	12/79	125C	N/R	2.07E 05	207	0	
					EM						207	0	
					OP CNST	LIFE	12/79	125C	N/R	1.20E 05	60	0	
					EM						60	0	
					RHRB	LIFE	12/79	85C	N/R	2.30E 05	230	0	
					EM						230	0	
					RHRB	LIFE	12/79	85C	N/R	1.30E 05	65	0	
					EM						65	0	
93L425	D	NHDIP	16	M	THRMSHK	ENV	5/77		N/R		20	0	
								500CY					
					HERMETC						20	0	
					OP CNST	LIFE	5/79	125C	N/R	1.32E 05	66	0	
					EM						66	0	
					OP CNST	LIFE	5/79	125C	N/R	1.48E 05	74	0	
					EM						74	0	
					OP CNST	LIFE	5/79	125C	N/R	2.40E 05	121	1	
					EM						120	0	
					OP CNST	LIFE	5/79	125C	N/R	8.50E 04	85	0	
					EM						85	0	
					OP CNST	LIFE	5/79	125C	N/R	2.64E 05	132	0	
					EM						132	0	
					OP CNST	LIFE	5/79	125C	N/R	6.00E 04	60	0	
					EM						60	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI | KAM

LOW POWER TTL | BIPOLAR | NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TYP ENG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	LELF #
93L425	B	MDIP	16	M	CNSTACC	ENV	8/79	30KG 6 AXES	N/R		30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		30	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			30	0	
								1 MIN E					
					FINE LK			HE 5.E-8			30	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			30	0	
								3X					
								60PSIG					
					EM						30	0	
93L425		MDIP	16	M	OP CNST	LIFE	5/77	125C	N/R	3.78E 05	189	0	
					EM						189	0	
					OP CNST	LIFE	5/79	125C	N/R	1.10E 05	55	0	
					EM						55	0	
93L425		MDIP	16	M	OP CNST	LIFE	5/79	125C	N/R	3.76E 05	188	0	
					EM						188	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		26	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			26	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			26	0	
								3X					
								60PSIG					
					EM						26	0	
					TEMPCYC	ENV	8/79	-065C 150C	N/R		28	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 6 AXES			26	0	
								1 MIN E					
					FINE LK			HE 5.E-8			28	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			28	0	
								3X					
								60PSIG					
					EM						28	0	
					OP CNST	LIFE	12/79	125C	N/R	4.70E 04	47	0	
					EM						47	0	
					OP CNST	LIFE	12/79	125C	N/R	4.60E 04	23	0	
					EM						23	0	
					OP CNST	LIFE	12/79	125C	N/R	4.90E 04	49	0	
					EM						49	0	
93L425		WHFPK	16	M	MECHSHK	ENV	8/79	1.5KG .5MSEC	N/R		27	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			27	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	0	
								60 MIN					
								30 MIN					

FAIRCHILD SEMI — RAM

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L425	D	NHFPK	16	M	GROSSLK	ENV	6/79	FLUOR 125C	N/I		27	0	
								3X					
								60PSIG					
					LM						27	0	

SIGNETICS — RAM

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2501	D-1	HDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	7.80E 04	78	0	
					EM						78	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — RAM

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D-1	HDIP	16	C	OP DYN	LIFE	9/78	150C	N/R	2.00E 04	20	0	
					S&F EM			25C			20	0	

MOSTEK — RAM

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4006	D	NHDIP	16	C	N/R	FIELD	6/77	30C	GBC	3.00E 07	31000	10	

NATIONAL SEMI — RAM

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4261	B-1	NHDIP	18	M	N/R	RELDEM	7/78	025C	GT	1.14E 05	324	0	

NO. AMER ROCKWELL INT. RAM

P-DYN MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	SELF #
10432	B	CERQIP	42	C	S&D IN	LIFE	/77	25C	N/R		41	0	
					OP DYN			125C		4.40E 05	41	0	
					S&D EN			25C			41	0	
1103A		CERDIP	18	C	S&D IN	LIFE	/77	25C	N/R		25	0	
					OP DYN			125C		2.49E 05	25	0	
					S&D EN			25C			17	0	

SIGNETICS RAM

P-DYN MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	SELF #
2103	D-1	CERDIP	18	C	OP DYN	LIFE	11/77	85C	N/R	7.10E 04	71	0	
					EN						71	0	
					OP DYN	LIFE	11/77	85C	N/R	8.00E 03	32	0	
					EN						32	0	
					OP DYN	LIFE	11/77	85C	N/R	4.00E 03	15	0	
					EN						15	0	
					OP DYN	LIFE	11/77	85C	N/R	4.00E 04	40	0	
					EN						40	2	
					OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EN						46	1	
					OP DYN	LIFE	11/77	85C	N/R	9.00E 04	45	0	
					EN						45	0	
					OP DYN	LIFE	11/77	85C	N/R	8.50E 04	43	0	
					EN						43	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.50E 04	45	0	
					EN						45	1	
					STGLIFE	LIFE	11/77	150C	N/R	1.20E 04	46	0	
					EN						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	9.10E 04	91	0	
					EN						91	0	
					STGLIFE	LIFE	11/77	150C	N/R	1.86E 05	46	0	
					EN						46	3	
					STGLIFE	LIFE	11/77	150C	N/R	1.71E 05	46	0	
					EN						46	4	
					OP DYN	BRN	11/77	85C	N/R	6.00E 03	36	0	
					EN						36	0	
1103	D	CERDIP	18	C	OP DYN	LIFE	11/77	85C	N/R	3.60E 04	36	0	
					EN						36	0	
					OP DYN	LIFE	11/77	85C	N/R	9.40E 04	48	0	
					EN						48	2	
					STGLIFE	LIFE	11/77	150C	N/R	1.00E 05	150	0	
					EN						150	0	
					REVBIAS	LIFE	11/77	-10C	N/R	5.60E 04	28	0	
					EN						28	0	
1103		CERDIP	18	C	OP DYN	LIFE	11/77	85C	N/R	9.40E 04	48	0	
					EN						48	2	
					STGLIFE	LIFE	11/77	150C	N/R	9.90E 04	150	0	
					EN						150	1	
					REVBIAS	LIFE	11/77	-10C	N/R	5.60E 04	28	0	
					EN						28	0	

ADVANCED MICRO DEVICES — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2102	:D-1	:HDIP	16	:C	OP CRST	BRN	5/80	125C	N/R	2.61E 05	1556	0	
					EM						1556	354	
:2102A	:C-1	:HDIP	16	:C	OP DYN	LIFE	3/77	50C	N/R	4.15E 06	816	3	
					OP DYN	LIFE	3/77	50C	N/R	1.63E 06	816	3	
					OP DYN	LIFE	3/77	50C	N/R	1.31E 06	816	0	
:2102A	:X	:HDIP	16	:C	OP DYN	LIFE	3/78	50C	N/R	1.81E 06	816	3	
					OP DYN	LIFE	3/78	50C	N/R	4.24E 05	816	1	
					OP DYN	LIFE	3/78	50C	N/R	9.56E 05	816	1	
	:D				OP DYN	BRN	3/78	50C	N/R	1.31E 05	816	7	
:9110A/B	:C-1	:HDIP	22	:M	OPERATE	CHECK	4/78	:125C	GT	6.95E 04	894	1	
:9102	:B-2	:HDIP	16	:M	PAR EXC	LIFE	6/80	125C	N/R	1.61E 05	161	0	
					EM			125C			161	1	
:9112		:HDIP	16	:M	PAR EXC	LIFE	6/80	125C	N/R	8.00E 04	80	0	
					EM			125C			80	0	

AMERICAN MICROSYSTEMS — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:4015	:D	:HDIP	16	:C	OP DYN	LIFE	7/77	125C	N/R	1.60E 06	800	0	
					EM						800	6	
					THRMSHK	ENV	7/77	:-055C 125C	N/R		220	0	
								:200CY					
								:LIQUID					
					EM						220	0	
:7001	:E-2	:HDIP	22	:M	OPERATE	RELDEM	12/77		AIU	1.62E 05	1008	0	

FAIRCHILD SEMI — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2102	:D-1	:HDIP	16	:C	N/R	FIELD	4/81	40C	GBC	2.93E 07	11267	10	

INTEL — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:N/R	:D-1	:HDIP	16	:C	N/R	FIELD	5/77	40C	GBC	2.25E 07	5743	0	
					N/R	FIELD	5/78	40C	GBC	1.62E 07	12483	0	
					N/R	FIELD	4/79	40C	GBC	2.18E 07	16768	1	
					N/R	FIELD	4/80	40C	GBC	1.32E 07	10167	1	
:M2115	:D	:HDIP	16	:M	BURN-IN	BRN	6/80	25C	N/R	8.00E 05	16658	0	

INTEL RAM

N-STAT MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2115	D	NHDIP	16	M	EM	BRN	6/80	25C	N/R		16658	16	2511
													2512
					REVBIAS	LIFE	6/80	150C	N/R	6.25E 04	125	0	
					EM			25C			125	0	
					REVBIAS			150C		6.25E 04	125	0	
					EM			25C			125	0	
					OP DYN	LIFE	6/80	125C	N/R	1.22E 06	7248	0	
					EM			25C			7248	2	2573
					OP DYN			125C		3.88E 05	1168	0	
					EM			25C			1168	1	2574
					OP DYN			125C		5.00E 05	1000	0	
					EM			25C			1000	0	
					OP DYN			125C		4.00E 05	400	0	
					EM			25C			400	0	
					BAKE	LIFE	6/80	250C	N/R	1.68E 04	350	0	
					EM			25C			350	0	
					BAKE			250C		4.20E 04	350	0	
					EM			25C			350	0	
					BAKE			250C		1.16E 05	350	0	
					EM			25C			350	0	
					OP DYN	LIFE	6/80	-10C	N/R	1.25E 04	25	0	
					EM			25C			25	0	
					OP DYN			-10C		1.25E 04	25	0	
					EM			25C			25	0	
M8111A	B-1	NHDIP	18	M	TEMPCYC	RELDEN	11/77	000C 050C 16CY	NSS	3.02E 03	4	0	
2102	D	NHDIP	16	C	S&D EM	LIFE	/77	25C	N/R		90	0	
					OP DYN			125C		9.72E 05	90	4	
					S&D EM			25C			86	0	
					S&D EM	LIFE	/77	25C	N/R		76	0	
					OP DYN			70C		8.27E 05	76	1	
					S&D EM			25C			75	0	
					S&D EM	LIFE	/77	25C	N/R		75	0	
					OP DYN			25C			75	0	
					S&D EM			25C			75	0	
2102	D-1	HDIP	16	C	OP CNST	BRN	5/80	125C	N/R	2.25E 05	1342	0	
					EM						1342	35	
2102A	D	NHDIP	16	C	OP DYN	LIFE	3/77	50C	N/R	6.84E 05	408	0	
					OP DYN	LIFE	3/77	50C	N/R	1.42E 06	816	3	
2102A	D-1	HDIP	16	C	N/R	FIELD	12/77	25C	GBC	9.98E 05	96	0	
					N/R	FIELD	12/77	25C	GBC	1.44E 05	16	0	
					N/R	FIELD	12/77	25C	GBC	2.58E 04	8	0	
2102A	D	NHDIP	16	C	OP DYN	LIFE	3/78	50C	N/R	7.76E 05	816	0	
					OP DYN	LIFE	3/78	50C	N/R	9.79E 05	816	0	
2115A	X	NHDIP	16	C	OP DYN	LIFE	3/77	125C	N/R	1.68E 05	168	0	
					EM						168	0	
	D				OP DYN	BRN	8/78	125C	N/R	2.34E 05	4874	0	
					EM						4874	5	1995
					OP DYN	LIFE	5/79	125C	N/R	8.40E 04	84	0	
					EM						84	0	
					OP DYN	LIFE	5/79	125C	N/R	4.20E 04	84	0	
					EM						84	0	
2115A/25A		NHDIP	16	M	BURN-IN	BRN	6/80	25C	N/R	2.90E 06	60389	0	
					EM			25C			60389	55	2513
													2514
													2515
													2516
													2517
					OP DYN	LIFE	6/80	125C	N/R	8.88E 05	5285	0	
					EM			25C			5285	7	
					OP DYN			125C		1.69E 06	5100	0	
					EM			25C			5100	2	
					OP DYN			125C		2.27E 06	4547	0	
					EM			25C			4547	1	
					OP DYN			125C		2.60E 05	260	0	
					EM			25C			260	0	
					REVBIAS	LIFE	6/80	150C	N/R	5.00E 04	100	0	
					EM			25C			100	0	
					REVBIAS			150C		5.00E 04	100	0	

INTEL — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2115A/25A	D	NHDIP	16	M	EM	LIFE	6/80	25C	N/R		100	0	
					BAKE	LIFE	6/80	250C	N/R	1.00E 05	2089	0	
					EM			25C			2089	1	2660
					BAKE			250C		2.16E 05	1799	0	
					EM			25C			1799	0	
					BAKE			250C		5.64E 05	1699	0	
					EM			25C			1699	1	
					TEMPCYC	ENV	6/80	-055C 125C 200 CYC	N/R		100	0	
					EM			025C			100	0	
2125	X	NHDIP	16	C	OP DYN	LIFE	8/77	125C	N/R	4.52E 05	452	0	
					EM			0C			452	0	
	D				OP DYN	BRN	2/79	125C	N/R	2.04E 05	4246	0	
					EM						4246	0	
					OP DYN	BRN	3/79	125C	N/R	1.34E 05	800	0	
					EM						800	0	
					OP DYN	LIFE	3/79	125C	N/R	3.50E 05	700	0	
					EM						700	0	
					OP DYN	LIFE	4/79	125C	N/R	4.84E 05	484	0	
					EM						484	0	
2125A	X	HDIP	16	C	OP DYN	LIFE	8/77	125C	N/R	1.32E 05	132	0	
					EM						132	0	
8102A-4	D-1	HDIP	16	C	N/R	FIELD	8/77	25C	GF	4.48E 06	5120	4	
8111A-4	D	NHDIP	18	C	OP DYN	BDLIFE	5/77	25C	N/R	1.97E 05	168	0	
					OP DYN	BDLIFE	5/77	55C	N/R	1.14E 05	168	0	
					OP DYN	BDLIFE	5/77	70C	N/R	1.60E 05	168	0	

MOTOROLA SEMI — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6810	D	NHDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	1.54E 05	153	0	
					SDF EM						153	0	
6810	D-1	HDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	7.56E 03	45	0	
					SDF EM						45	0	
6810	NONE	DIP	24	C	OP DYN	LIFE	11/77	125C	N/R	1.62E 05	198	0	
					EM						198	0	

NATIONAL SEMI — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2102A	D	NHDIP	16	C	OP DYN	LIFE	3/78	50C	N/R	2.45E 06	2448	0	
2102AD	X	NHDIP	16	C	OP DYN	LIFE	3/77	50C	N/R	2.14E 06	816	2	

NEC MICROCOMPUTERS — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
2102A	D-1	HDIP	16	C	N/R	FIELD	5/78	25C	GBC	7.54E 07	24000	0	

SIGNETICS — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
2102	D-1	HDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	2.28E 05	228	0	
					EM						228	0	
					OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	1	
					OP DYN	LIFE	11/77	85C	N/R	1.01E 06	128	0	
					EM						128	0	
					OP DYN	LIFE	11/77	125C	N/R	2.18E 05	44	0	
					EM						44	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.70E 04	47	0	
					EM						47	1	
					STGLIFE	LIFE	11/77	150C	N/R	8.06E 05	101	0	
					EM						101	2	
					STGLIFE	LIFE	11/77	150C	N/R	4.90E 04	49	0	
					EM						49	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					REVBIAS	LIFE	11/77	85C	N/R	4.90E 04	49	0	
					EM						49	2	
					REVBIAS	LIFE	11/77	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					REVBIAS	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	BRN	11/77	125C	N/R	9.00E 03	56	0	
					EM						56	0	
					BAKE	BRN	11/77	150C	N/R	9.00E 03	56	0	
					EM						56	0	
					OP CNST	BRN	5/80	125C	N/R	2.55E 06	15193	0	
					EM						15193	92	
2102	D	NHDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	2.70E 05	54	0	
					EM						54	0	
					STGLIFE	LIFE	11/77	150C	N/R	2.56E 05	52	0	
					EM						52	1	
					REVBIAS	LIFE	11/77	-10C	N/R	2.40E 04	24	0	
					EM						24	0	
2102		NHDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	2.53E 05	51	0	
					EM						51	1	
					OP DYN	LIFE	11/77	125C	N/R	1.58E 05	73	0	
					EM						73	1	
					OP DYN	LIFE	11/77	85C	N/R	4.50E 04	45	0	
					EM						45	1	
					OP DYN	LIFE	11/77	85C	N/R	5.00E 04	50	0	
					EM						50	2	
					OP DYN	LIFE	11/77	85C	N/R	4.70E 04	47	0	
					EM						47	0	
					OP DYN	LIFE	11/77	125C	N/R	2.31E 05	47	0	
					EM						47	1	
					OP DYN	LIFE	11/77	125C	N/R	6.70E 04	67	0	
					EM						67	1	
					STGLIFE	LIFE	11/77	150C	N/R	2.80E 05	56	0	
					EM						56	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.50E 04	45	0	
					EM						45	1	

SIGNETICS — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2102	D	HDIP	16	C	STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFL	LIFE	11/77	150C	N/R	4.90E 04	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	175C	N/R	4.90E 04	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	200C	N/R	4.90E 04	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	225C	N/R	4.90E 04	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	250C	N/R	4.90E 04	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	300C	N/R	4.90E 04	49	0	
					EM						49	2	
					STGLIFE	LIFE	11/77	150C	N/R	4.30E 04	43	0	
					EM						43	1	
					REVBIAS	LIFE	11/77	-10C	N/R	2.40E 04	24	0	
					EM						24	0	
					REVBIAS	LIFE	11/77	-25C	N/R	6.40E 04	205	0	
					EM						205	0	
					REVBIAS	LIFE	11/77	85C	N/R	4.90E 04	49	0	
					EM						49	0	
					REVBIAS	LIFE	11/77	125C	N/R	4.90E 04	49	0	
					EM						49	0	
					REVBIAS	LIFE	11/77	150C	N/R	4.90E 04	49	0	
					EM						49	0	
					REVBIAS	LIFE	11/77	-25C	N/R	1.56E 05	156	0	
					EM						156	0	
					REVBIAS	LIFE	11/77	125C	N/R	1.54E 05	154	0	
					EM						154	0	
2102A	D-1	HDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	5.50E 04	55	0	
					EM						55	0	
					STGLIFE	LIFE	11/77	150C	N/R	5.50E 04	55	0	
					EM						55	0	
					OP DYN	BRN	11/77	125C	N/R	9.00E 03	56	0	
					EM						56	0	
					BAKE	BRN	11/77	150C	N/R	9.00E 03	56	0	
					EM						56	0	
2112		HDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	125C	N/R	6.80E 04	58	0	
					EM						58	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	6.50E 04	56	0	
					EM						56	0	

SYNERTEK — RAM

N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2102	D-1	HDIP	16	C	OP CNST	BRN	5/80	125C	N/R	1.08E 06	6429	0	
					EM						6429	49	

VARIOUS RAM

N-STAT MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2101	D	NHDIP	22	C	VIS INS	EBRN	3/78		N/R		5895	0	
					TEMPCYC			-055C 125C			5895	0	
								10CY					
					REVBIAS			125C		9.43E 05	5895	0	
					S&F EM			070C			5895	77	2474
													2475
2101	D-1	HDIP	22	C	VIS INS	EBRN	3/78		N/R		800	0	
					TEMPCYC			-055C 125C			800	0	
								10CY					
					REVBIAS			125C		1.28E 05	800	0	
					S&F EM			070C			800	2	2484
													2485
2101A	D	NHDIP	22	C	VIS INS	EBRN	3/78		N/R		12741	0	
					TEMPCYC			-055C 125C			12741	0	
								10CY					
					REVBIAS			125C			12741	0	
					S&F EM			070C			12741	80	2476
													2477
													2478
2102	X	HDIP	16	C	N/R	FIELD	4/77	20C	GBC	6.10E 06	960	1	
					N/R	FIELD	9/78	20C	GBC	1.08E 07	960	6	
2102	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	1.40E 07	1024	2	
	B-2				OPERATE	RELDEM	12/77		AIU	1.65E 05	5110	0	
	JB/B1				N/R	FIELD	7/79	25C	GF	4.42E 06	1024	0	
					N/R	FIELD	8/80	25C	GF	1.03E 07	1024	0	
2102	X	NHDIP	16	C	ACCLFRB	LIFE	9/78	200C	N/R	1.00E 05	20	1	
					FNCT EM			25C			20	0	
	D				ACCLFOD	LIFE	9/78	200C	N/R	6.00E 04	20	0	
					FNCT EM			25C			20	0	
					OP DYN	LIFE	9/78	150C	N/R	1.20E 05	40	1	
					FNCT EM			25C			40	0	
					ACCLFOD	LIFE	9/78	200C	N/R	8.00E 04	20	0	
					FNCT EM			25C			20	0	
					ACCLFRB	LIFE	9/78	200C	N/R	8.00E 04	20	0	
					FNCT EM			25C			20	0	
					ACCLFOD	LIFE	9/78	200C	N/R	8.00E 04	20	3	
					FNCT EM			25C			20	3	
2102	D-1	HDIP	16	C	RHRB	LIFE	9/78	85C	N/R	4.00E 04	20	5	
					FNCT EM			25C			20	3	
2102	D	NHDIP	16	C	ACCLFOD	LIFE	9/78	200C	N/R	6.30E 04	14	0	
					FNCT EM			25C			14	3	
					ACCLFOD	LIFE	9/78	200C	N/R	2.00E 04	20	1	
					FNCT EM			25C			20	0	
					ACCLFOD	LIFE	9/78	200C	N/R	6.00E 04	20	0	
					ACCLFOD			25C			20	0	
2102A	B-2	NHDIP	16	C	N/R	FIELD	5/77		AIT	1.63E 04	48	0	
9102/2602		NHFPK	16	M	OPERATE	CHECK	3/78	025C	AIT	4.19E 03	156	0	
					OPERATE	CHECK	3/78	025C	AIT	2.21E 05	3523	9	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	2.89E 03	156	0	
					VBVRFQ	EQENV	3/78	10HZ 100HZ	AIT	1.25E 04	3523	1	
					OPERATE	CHECK	3/78	025C	AIT	2.84E 04	156	0	
					OPERATE	CHECK	3/78	025C	AIT	5.60E 05	3523	3	
					TCVPC	RELPRO	3/78	002C 045C	AIT	2.85E 04	156	0	
								5CY 1.5G 79%					
								45HZ 22%					
					TCVPC	RELPRO	3/78	002C 045C	AIT	6.09E 05	3523	0	
								5CY 1.5G 79%					
								45HZ 22%					

EMM RAM

N-STAT MOS NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3539	D	NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	4.80E 04	46	0	
					EM			25C			48	3	
3539	D-1	HDIP	22	C	OP DYN	LIFE	9/78	100C	N/R	1.92E 05	96	0	
					EM			25C			96	8	

INTEL RAM

N-STAT MOS NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8/55/56	D	NHDIP	40	C	BURN-IN	BRN	5/80		N/R	5.51E 04	1147	0	
					EM						1147	2	
					OP DYN	LIFE	5/80	125C	N/R	3.58E 05	359	1	3147
					EM						358	0	
8155/56	D-1	HDIP	40	C	BURN-IN	BRN	5/80		N/R	1.74E 05	3630	0	
					EM						3630	10	
					OP DYN	LIFE	5/80	125C	N/R	6.71E 05	671	1	3146
					EM						670	0	
					OP DYN	LIFE	5/80	125C	N/R	6.00E 04	120	0	
					EM						120	0	
8155/56	D	NHDIP	40	C	BURN-IN	BRN	5/80		N/R	1.08E 04	225	0	
					EM						225	3	
					OP DYN	LIFE	5/80	125C	N/R	5.90E 04	118	0	
					EM						118	0	
					OP DYN	LIFE	5/80	125C	N/R	1.01E 05	101	0	
					EM						101	0	

EMM RAM

N-STAT MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2114	D	NHDIP	18	C	OP DYN	LIFE	9/78	125C	N/R	3.62E 04	36	0	
					EM			25C			36	1	
2114	D-1	HDIP	18	C	OP DYN	LIFE	9/78	100C	N/R	5.81E 05	144	0	
					EM			25C			144	4	
4104	D	NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	7.73E 05	192	0	
					EM			25C			192	17	
4200		NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	1.77E 06	284	0	
					EM			25C			284	39	
4200		NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	7.72E 05	192	0	
					EM			25C			192	20	
4402		NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	1.22E 06	240	0	
					EM			25C			240	26	
4402		NHDIP	22	C	OP DYN	LIFE	9/78	125C	N/R	2.37E 06	336	0	
					EM			25C			336	24	
4801	D-1	HDIP	18	C	OP DYN	LIFE	9/78	100C	N/R	3.27E 05	108	0	
					EM			25C			108	4	
4804	D	NHDIP	18	C	OP DYN	LIFE	9/78	125C	N/R	3.62E 04	36	0	
					EM			25C			36	0	
4804	D-1	HDIP	18	C	OP DYN	LIFE	9/78	100C	N/R	5.81E 05	144	0	
					EM			25C			144	3	

INTEL RAM

N-STAT MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2114A	D	NHDIP	18	M	BURN-IN	BRN	6/80	25C	N/R	4.75E 05	9892	0	
					EM			25C			9892	5	
					OP DYN	LIFE	6/80	125C	N/R	1.51E 05	900	0	
					EM			25C			900	0	
					OP DYN			125C		2.66E 05	800	0	
					EM			25C			800	0	
					OP DYN			125C		3.50E 05	700	0	
					EM			25C			700	0	
					BAKE	LIFE	6/80	250C	N/R	2.04E 04	425	0	
					EM			25C			425	0	
					BAKE			250C		5.10E 04	425	0	
					EM			25C			425	0	
					BAKE			250C		1.25E 05	375	0	
					EM			25C			375	0	
2114A	D-1	HDIP	18	C	BURN-IN	BRN	6/80	25C	N/R	5.87E 05	12234	0	
					EM			25C			12234	22	
					OP DYN	LIFE	6/80	125C	N/R	2.02E 05	1200	0	
					EM			25C			1200	0	
					OP DYN			125C		3.32E 05	1000	0	
					EM			25C			1000	0	
					OP DYN			125C		4.50E 05	900	0	
					EM			25C			900	0	
					REVBIAS	LIFE	6/80	150C	N/R	3.75E 04	75	0	
					EM			25C			75	0	
					REVBIAS			150C		3.75E 04	75	0	
					EM			25C			75	0	
					BAKE	LIFE	6/80	160C	N/R	2.16E 04	450	0	
					EM			25C			450	0	
					BAKE			160C		4.80E 04	400	0	
					EM			25C			400	0	
					BAKE			160C		9.96E 04	300	0	
					EM			25C			300	0	
2141	X	HDIP	18	C	OP DYN	LIFE	12/77	125C	N/R	4.11E 05	411	0	
					EM						411	0	
					REVBIAS	LIFE	12/77	150C	N/R	7.50E 04	75	0	
					EM						75	0	
	D-1				OP DYN	BRN	4/78	125C	N/R	3.39E 05	7067	0	
					EM						7067	7	1996
					OP DYN	BRN	4/78	125C	N/R	4.76E 05	2835	0	
					EM						2835	1	1997
					OP DYN	LIFE	2/79	125C	N/R	5.00E 04	100	0	
					EM						100	0	
					OP DYN	LIFE	8/78	125C	N/R	2.00E 05	200	0	
					EM						200	0	
					REVBIAS	LIFE	11/78	150C	N/R	2.50E 04	25	0	
					EM						25	0	
					BURN-IN	BRN	6/80	25C	N/R	5.40E 05	11250	0	
					EM			25C			11250	17	
					OP DYN	LIFE	6/80	125C	N/R	7.78E 05	4632	0	
					EM			25C			4632	1	2589
					OP DYN			125C		3.03E 05	913	0	
					EM			25C			913	0	
					OP DYN			125C		3.57E 05	713	0	
					EM			25C			713	0	
					REVBIAS	LIFE	6/80	150C	N/R	3.75E 04	75	0	
					EM			25C			75	0	
					REVBIAS			150C		3.75E 04	75	0	
					EM			25C			75	0	
					BAKE	LIFE	6/80	160C	N/R		275	0	
					EM			25C			275	0	
					BAKE			160C			175	0	
					EM			25C			175	0	
					BAKE			160C			175	0	
					EM			25C			175	0	
					BAKE			160C		3.75E 04	75	0	
					EM			25C			75	0	
					TEMPCYC	ENV	6/80	-055C 125C 200 CYC	N/R		75	0	
					EM			025C			75	0	

INTEL RAM

N-STAT MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2141	X	NHDIP	18	C	OP DYN	LIFE	1/77	125C	N/R	8.70E 04	87	0	
					EM						87	0	
	D				OP DYN	BRN	6/78	125C	N/R	5.28E 04	1100	0	
					EM						1100	1	1998
					OP DYN	LIFE	7/78	125C	N/R	1.00E 05	100	0	
					EM						100	0	
2147	X	NHDIP	18	C	OP DYN	LIFE	6/77	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					OP DYN	LIFE	6/77	125C	N/R	6.00E 05	120	0	
					EM						120	1	
					OP DYN	LIFE	12/77	125C	N/R	1.01E 06	1012	0	
					EM						1012	0	
					REVBIAS	LIFE	10/77	150C	N/R	7.80E 04	78	0	
					EM						78	0	
					OP DYN	LIFE	10/77	70C	N/R	3.00E 05	300	0	
					EM						300	0	
					OP DYN	BRN	9/77	125C	N/R	3.30E 05	1962	0	
					EM						1962	0	
	D				REVBIAS	LIFE	11/78	150C	N/R	6.59E 05	659	1	2009
					EM						658	0	
2147		NHDIP	18	M	OP DYN	BRN	10/78	125C	N/R	1.77E 06	36851	0	
					EM						36851	73	1993
					OP DYN	LIFE	11/78	125C	N/R	2.00E 05	200	0	
					EM						200	0	
					OP DYN	BRN	2/79	125C	N/R	1.01E 05	600	0	
					EM						600	1	1994
					OP DYN	LIFE	2/79	125C	N/R	2.99E 05	597	0	
					EM						597	0	
					OP DYN	LIFE	4/79	125C	N/R	1.30E 06	1300	0	
					EM						1300	0	
					OP DYN	LIFE	6/80	125C	N/R	2.31E 06	13735	0	
					EM			25C			13735	9	2590
													2591
					OP DYN			125C		3.94E 06	11861	0	
					EM			25C			11861	9	2592
													2593
													2594
													2595
					OP DYN			125C		5.13E 06	10258	0	
					EM			25C			10258	4	2596
													2597
													2598
													2599
					OP DYN			125C		5.70E 05	570	0	
					EM			25C			570	2	2600
													2601
					REVBIAS	LIFE	6/80	150C	N/R	4.31E 05	862	0	
					EM			25C			862	3	2640
													2641
					REVBIAS			150C		4.30E 05	859	0	
					EM			25C			859	1	2642
					BURN-IN	BRN	6/80	25C	N/R	5.90E 06	122813	0	
					EM			25C			122813	243	2522
													2523
													2524
					BAKE	LIFE	6/80	250C	N/R	2.07E 05	4303	0	
					EM			25C			4303	5	2675
													2676
					BAKE			250C		5.19E 05	4324	0	
					EM			25C			4324	1	2677
					BAKE			250C		1.39E 06	4174	0	
					EM			25C			4174	2	2678
					OP DYN	LIFE	6/80	:- 10C	N/R	7.50E 04	150	0	
					EM			25C			150	0	
					OP DYN			:- 10C		7.50E 04	150	0	
					EM			25C			150	0	
					TEMPCYC	ENV	6/80	:-055C 125C	N/R		477	0	
								:200 CYC					
					EM			:025C			477	0	

INTEL — RAM

N-STAT — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFFF #
2147	D-1	HDIP	18	C	OP CNST	BRN	5/80	125C	N/R	2.88E 06	17161	0	
					EM						17161	67	

VARIOUS — RAM

N-STAT — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFFF #
N/R	D	NHDIP	18	C	OP DYN	LIFE	9/76	150C	N/R	3.00E 04	20	8	
					S&F EM			25C			20	0	

ZILOG — RAM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFFF #
6116	D	NHDIP	0	C	PAR EXC	LIFE	3/80	125C	N/R	3.10E 06	1551	0	
					FM						1551	3	2395
													2396
6116	D-1	HDIP	0	C	PAR EXC	LIFE	3/80	125C	N/R	4.46E 05	223	0	
					EM						223	1	

ADVANCED MICRO DEVICES — RAM

N-DYN — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFFF #
9050	D	NHDIP	18	C	N/R	FIELD	10/77	25C	GF	1.25E 07	1160	14	
9060	B-2	NHDIP	22	C	PAR EXC	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	0	

FAIRCHILD SEMI — RAM

N-DYN — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFFF #
4096	D	NHDIP	16	C	N/R	FIELD	10/77	25C	GF	9.07E 06	842	10	

INTEL RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2104A	D	NHDIP	16	M	OP DYN	LIFE	6/80	125C	N/R	5.90E 06	35113	0	
					EM			25C			35113	16	2563
													2564
													2565
													2566
					OP DYN			125C		7.08E 06	21334	0	
					EM			25C			21334	10	2567
													2568
													2569
					OP DYN			125C		9.42E 06	18842	0	
					EM			25C			18842	6	2570
													2571
													2572
					REVBIAS	LIFE	6/80	150C	N/R	1.41E 06	2812	0	
					EM			25C			2812	4	2635
					REVBIAS			150C		1.37E 06	2733	0	
					EM			25C			2733	2	2636
													2637
					BAKE	LIFE	6/80	250C	N/R	3.30E 05	6872	0	
					EM			25C			6872	8	2654
													2655
					BAKE			250C		7.13E 05	5945	0	
					EM			25C			5945	12	2656
													2657
													2658
					BAKE			250C		1.95E 06	5883	0	
					EM			25C			5883	5	2659
					BURN-IN	BRN	6/80	25C	N/R	6.59E 06	137268	0	
					EM			25C			137268	133	2507
													2508
													2509
													2510
					OP DYN	LIFE	6/80	:- 10C	N/R	5.78E 05	1156	0	
					EM			25C			1156	0	
					OP DYN			:- 10C		5.78E 05	1156	0	
					EM			25C			1156	0	
					TEMPCYC	ENV	6/80	:-055C 125C	N/R		893	0	
								:200 CYC					
					EM			:025C			893	0	
M2107C		NHDIP	22	M	BURN-IN	BRN	6/80	25C	N/R	2.44E 06	50763	0	
					EM			25C			50763	30	
					OP DYN	LIFE	6/80	125C	N/R	6.21E 05	3698	0	
					EM			25C			3698	2	
					OP DYN			125C		9.46E 05	2850	0	
					EM			25C			2850	0	
					OP DYN			125C		1.23E 06	2450	0	
					EM			25C			2450	0	
					REVBIAS	LIFE	6/80	150C	N/R	1.95E 05	390	0	
					EM			25C			390	1	2633
					REVBIAS			150C		1.95E 05	389	0	
					EM			25C			389	1	2634
					BAKE	LIFE	6/80	250C	N/R	8.59E 04	1790	0	
					EM			25C			1790	3	2650
													2651
					BAKE			250C		1.61E 05	1339	0	
					EM			25C			1339	2	2652
													2653
					BAKE			250C		4.44E 05	1337	0	
					EM			25C			1337	0	
					TEMPCYC	ENV	6/80	:-055C 125C	N/R		75	0	
								:200 CYC					
					EM			:025C			75	0	
2104	D-1	HDIP	16	C	OP CNST	BRN	5/80	125C	N/R	9.80E 05	5833	0	
					EM						5833	697	
2104A	D	NHDIP	16	C	OP DYN	LIFE	8/77	125C	N/R	3.50E 06	3500	0	
					EM						3500	0	
					OP DYN	BRN	8/77	125C	N/R	5.50E 05	3275	0	
					EM						3275	0	
					OP DYN	LIFE	8/77	70C	N/R	4.99E 05	499	0	

INTEL RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2104A	D	NHDIP	16	C	EM	LIFE	8/77		N/R		499	0	
					OP DYN	LIFE	8/77	70C	N/R	3.20E 04	64	0	
					EM						64	0	
					OP DYN	LIFE	8/77	125C	N/R	3.99E 05	400	3	
					EM						397	1	
					OP DYN	LIFE	8/77	125C	N/R	1.95E 04	39	0	
					EM						39	0	
					OP DYN	LIFE	8/77	-10C	N/R	1.16E 06	1157	0	
					EM						1157	0	
					REVBIAS	LIFE	8/77	150C	N/R	9.00E 05	900	0	
					EM						900	0	
					REVBIAS	LIFE	8/77	150C	N/R	1.29E 05	130	2	
					EM						128	1	
					STGLIFE	LIFE	8/77	250C	N/R	3.83E 04	40	2	
					EM						38	0	
					STGLIFE	LIFE	8/77	250C	N/R	5.97E 05	597	0	
					EM						597	0	
					STGLIFE	LIFE	8/77	160C	N/R	1.05E 05	105	0	
					EM						105	0	
					TEMPCYC	ENV	8/77	-055C 150C	N/R		658	0	
					EM						658	0	
2107B		NHDIP	22	C	OPERATE	CHECK	10/77	025C	GBC	1.36E 04	31	0	
	X				N/R	FIELD	9/77	25C	GBC	0.00E 07	99999	292	
					N/R					7.60E 07	93501	293	
2107C	D-1	HDIP	22	C	BURN-IN	BRN	6/80	25C	N/R	2.31E 06	48106	0	
					EM			25C			48106	29	
					OP DYN	LIFE	6/80	125C	N/R	1.32E 06	7868	0	
					EM			25C			7868	1	
					OP DYN			125C		1.70E 06	5111	0	
					EM			25C			5111	0	
					OP DYN			125C		2.51E 06	5011	0	
					EM			25C			5011	1	
					REVBIAS	LIFE	6/80	150C	N/R	3.38E 05	675	0	
					EM			25C			675	0	
					REVBIAS			150C		3.38E 05	675	0	
					EM			25C			675	0	
					BAKE	LIFE	6/80	160C	N/R	6.54E 04	1362	0	
					EM			25C			1362	0	
					BAKE			160C		1.45E 05	1212	0	
					EM			25C			1212	0	
					BAKE			160C		3.69E 05	1112	0	
					EM			25C			1112	0	
					TEMPCYC	ENV	6/80	-055C 125C	N/R		75	0	
								200 CYC					
					EM			025C			75	0	

MOSTEK RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4027	X	NHDIP	16	C	OP DYN	LIFE	3/77	25C	N/R	1.87E 05	136	1	
					EM						135	0	
					OP DYN	LIFE	3/77	25C	N/R	2.73E 05	204	0	
					EM						204	0	
					OP DYN	LIFE	3/77	25C	N/R	6.34E 05	476	0	
					EM						476	0	
					OP DYN	LIFE	3/77	25C	N/R	8.89E 04	68	0	
					EM						68	0	
					OP DYN	LIFE	3/77	25C	N/R	1.74E 05	136	0	
					EM						136	0	

MOSTEK RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4027	X	HDIP	16	C	OP DYN	LIFE	3/77	25C	N/R	1.[illegible]E 06	816	0	
					EM						816	0	
					OP DYN	LIFE	3/77	25C	N/R	1.68E 05	136	0	
					EM						136	0	
					OP DYN	LIFE	3/77	25C	N/R	6.00E 04	68	1	
					EM						67	0	
					OP DYN	LIFE	3/77	25C	N/R	7.81E 04	68	1	
					EM						67	0	
					OP DYN	LIFE	3/77	25C	N/R	7.45E 04	68	1	
					EM						67	0	
					OP DYN	LIFE	3/77	25C	N/R	1.27E 05	136	0	
					EM						136	0	
					OP DYN	LIFE	3/77	25C	N/R	6.23E 04	68	1	
					EM						67	0	
					OP DYN	LIFE	3/77	25C	N/R	5.85E 04	68	0	
					EM						68	0	
4027	D-1	HDIP	16	C	OP DYN	LIFE	6/78	125C	N/R	1.27E 06	1674	0	
					EM						1674	30	
4096	X	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	3.11E 06	336	4	
	D				N/R	FIELD	10/77	25C	GF	8.95E 06	831	1	
	X				N/R	FIELD	6/78	25C	GBC	9.66E 05	336	0	
4096		HDIP	16	C	N/R	FIELD	2/78	25C	GBC	6.35E 06	640	2	
	D-1				N/R	FIELD	10/77	25C	GF	9.61E 06	892	2	
4096	X	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	2.45E 06	160	2	
					N/R	FIELD	6/78	25C	GBC	4.61E 05	160	0	

MOTOROLA SEMI RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4027	D	NHDIP	16	C	OP DYN	LIFE	7/77	125C	N/R	8.85E 04	90	2	
					EM						88	0	
4027		NHDIP	16	C	OP DYN	LIFE	7/77	125C	N/R	6.25E 04	94	1	
					EM						93	0	
6604		NHDIP	16	C	N/R	FIELD	10/77	25C	GF	7.53E 06	699	4	
6605		NHDIP	22	C	OP DYN	LIFE	6/77	125C	N/R	7.00E 04	71	0	
					EM						71	9	
					N/R	FIELD	6/77	30C	GBC	0.00E 07	99999	174	
					N/R			30C			99999	0	
					N/R			30C			2	0	

NATIONAL CASH REGISTER RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4227	D	NHDIP	16	C	OP LIFE	LIFE	5/77	125C	N/R	3.20E 04	32	0	
					SDF EM						32	1	
					OP CNST	LIFE	5/77	125C	N/R	3.40E 04	34	0	
					SDF EM						34	0	
					STGLIFE	LIFE	5/77	125C	N/R	3.15E 04	32	1	
					SDF EM						31	0	

SIGNETICS RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2660	D	NHDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	8.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	11/77	0C	N/R	2.00E 04	40	0	
					EM						40	0	
					STGLIFE	LIFE	11/77	150C	N/R	9.00E 04	45	0	
					EM						45	2	
					REVBIAS	LIFE	11/77	150C	N/R	4.90E 04	49	0	
					EM						49	0	
2660		NHDIP	16	C	REVBIAS	BRN	11/77	150C	N/R	7.00E 03	46	0	
					EM						46	0	
2680		NHDIP	22	C	OP DYN	LIFE	11/77	125C	N/R	3.68E 05	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	85C	N/R	4.10E 04	41	0	
					EM						41	1	
					OP DYN	LIFE	11/77	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					STGLIFE	LIFE	11/77	150C	N/R	3.69E 05	49	0	
					EM						49	1	
					OP DYN	BRN	11/77	125C	N/R	9.00E 03	56	0	
					EM						56	1	
					BAKE	BRN	11/77	150C	N/R	9.00E 03	56	0	
					EM						56	0	
2680		NHDIP	22	C	OP DYN	LIFE	11/77	85C	N/R	4.30E 04	43	0	
					EM						43	1	
					OP DYN	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	2	

TEXAS INSTRUMENTS RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4050	D	NHDIP	18	C	N/R	FIELD	10/77	25C	GF	1.19E 07	1101	2	
4050		HDIP	18	C	N/R	FIELD	10/77	25C	GF	1.08E 07	1003	1	

VARIOUS RAM

N-DYN MOS NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	22	C	N/R	FIELD	2/78	25C	GBC	3.67E 07	35352	26	
N/R	X	NHDIP	22	N/R	N/R	FIELD	12/77	35C	GBC	0.00E 07	0	351	
N/R		DIP	16	N/R	N/R	FIELD	4/78	40C	GF	1.83E 07	68000	3	
N/R	D	NHDIP	22	C	ACCLFOD	LIFE	9/78	160C	N/R	1.36E 05	23	1	
					FNCT EM			25C			23	2	
					ACCLFOD	LIFE	9/78	200C	N/R	4.00E 04	20	4	
					FNCT EM			25C			20	1	
N/R		NHDIP	22	M	N/R	FIELD	5/79	25C	GBC	4.00E 07	97280	42	
2107/5280		NHDIP	22	C	VIS INS	EBRN	3/78		N/R		308104	0	
					TEMPCYC			-055C 125C			308104	0	
								10CY					
					OP DYN			125C		1.48E 07	308104	0	
					S&F EM			070C			308104	4545	2498

VARIOUS — RAM

N-DYN — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2107/5280	D	NHDIP	22	C	S&F EM	EBRN	3/78	070C	N/R		308104	4545	2499
													2500

INTEL — RAM

N-DYN — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8185	D	NHDIP	18	C	BURN-IN	BRN	6/80		N/R	4.11E 04	856	0	
					EM						856	1	3141
					OP DYN	BRN	6/80	125C	N/R	2.02E 04	120	0	
					EM						120	0	
					OP DYN	LIFE	6/80	125C	N/R	5.00E 02	1	0	
					EM						1	0	
					OP DYN	LIFE	6/80	125C	N/R	2.49E 05	249	0	
					EM						249	0	
8185	D-1	HDIP	18	C	BURN-IN	BRN	6/80		N/R	1.23E 05	2568	0	
					EM						2568	8	3142
													3143
													3144
													3145
					OP DYN	LIFE	6/80	125C	N/R	3.91E 05	391	0	
					EM						391	0	
8185	D	NHDIP	18	C	BURN-IN	BRN	6/80		N/R	3.84E 03	80	0	
					EM						80	0	
					OP DYN	LIFE	6/80	125C	N/R	8.00E 04	80	0	
					EM						80	0	

FUJITSU — RAM

N-DYN — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8116	D	NHDIP	16	C	N/R	FIELD	10/77	25C	GF	4.75E 05	132	0	
					MECHSHK	ENV	11/77	1.5KG .5MSEC	N/R		50	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			50	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			50	0	
								1 MIN E					
					EM						50	0	
					TEMPCYC	ENV	11/77	-065C 150C	N/R		50	0	
								10CY					
								10/10DT					
					EM						50	0	
					THRMSHK	ENV	11/77	000C 100C	N/R		50	0	
								15CY					
								LIQUID					
					EM						50	0	
					STGLIFE	LIFE	11/77	150C	N/R	2.54E 05	200	0	
					EM						200	0	

FUJITSU RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8116	D	NHDIP	16	C	STGLIFE	LIFE	11/77	200C	N/R	2.14E 05	200	0	
					EM						200	0	
					STGLIFE	LIFE	11/77	250C	N/R	1.01E 05	100	0	
					EM						100	1	
					REVBIAS	LIFE	11/77	150C	N/R	2.41E 05	200	0	
					EM						200	0	
					PAR EXC	LIFE	11/77	125C	N/R	1.17E 05	400	0	
					EM						400	1	

INTEL RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2118	D	NHDIP	16	M	BURN-IN	BRN	6/80	25C	N/R	1.67E 06	34711	0	
					EM			25C			34711	18	2518
													2519
													2520
													2521
					OP DYN	LIFE	6/80	125C	N/R	1.58E 06	9432	0	
					EM			25C			9432	0	
					OP DYN			125C		1.86E 06	5602	0	
					EM			25C			5602	0	
					OP DYN			125C		2.51E 06	5010	0	
					EM			25C			5010	0	
					OP DYN			125C		3.83E 05	383	0	
					EM			25C			383	0	
					REVBIAS	LIFE	6/80	150C	N/R	4.38E 05	875	0	
					EM			25C			875	0	
					REVBIAS			150C		2.09E 05	417	0	
					EM			25C			417	0	
					BAKE	LIFE	6/80	250C	N/R	9.79E 04	2039	0	
					EM			25C			2039	4	2671
													2672
					BAKE			250C		2.44E 05	2035	0	
					EM			25C			2035	2	2673
													2674
					BAKE			250C		6.41E 05	1931	0	
					EM			25C			1931	0	
					OP DYN	LIFE	6/80	:- 10C	N/R	4.70E 04	94	0	
					EM			25C			94	0	
					OP DYN			:- 10C		2.35E 04	47	0	
					EM			25C			47	0	
2116		NHDIP	16	C	OP DYN	LIFE	2/77	125C	N/R	1.41E 05	141	0	
					EM						141	0	
					OP DYN	LIFE	3/77	125C	N/R	4.04E 05	404	0	
					EM						404	1	
					OP DYN	LIFE	4/77	125C	N/R	3.77E 05	377	0	
					EM						377	0	
					OP DYN	LIFE	6/77	125C	N/R	1.51E 06	1506	0	
					EM						1506	1	
2117		NHDIP	16	C	N/R	FIELD	10/77	25C	GF	4.75E 05	149	0	
2117		NHDIP	16	M	OP DYN	BRN	1/79	125C	N/R	1.79E 06	10653	0	
					EM						10653	8	2010
					OP DYN	LIFE	2/79	125C	N/R	3.18E 06	3179	0	
					EM						3179	9	2011
					OP DYN	LIFE	4/79	125C	N/R	2.16E 06	723	4	2012
													2013
													2014
					EM						719	1	2015
					OP DYN	LIFE	4/79	125C	N/R	2.88E 06	960	0	

INTEL RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2117	D	NHDIP	16	M	EM	LIFE	4/79		N/R		960	0	
					OP DYN	LIFE	3/79	125C	N/R	3.07E 06	1029	6	2016
													2017
					EM						1026	0	
					OP DYN	LIFE	2/79	125C	N/R	6.64E 05	798	0	
					EM						798	0	
					OP DYN	LIFE	2/79	125C	N/R	4.51E 05	532	2	2018
					EM						532	0	
					OP DYN	LIFE	1/79	125C	N/R	8.27E 04	249	0	
					EM						249	0	
2117		NHDIP	16	M	OP DYN	BRN	1/79	125C	N/R	1.18E 05	703	0	
					EM						703	0	
					OP DYN	LIFE	3/79	125C	N/R	1.34E 05	67	0	
					EM						67	0	
					OP DYN	LIFE	6/80	125C	N/R	7.36E 06	43818	0	
					EM			25C			43818	33	2575
													2576
													2577
													2578
					OP DYN			125C		1.03E 07	31030	0	
					EM			25C			31030	17	2579
													2580
													2581
													2582
													2583
													2584
					OP DYN			125C		1.42E 07	28488	0	
					EM			25C			28488	18	2585
													2586
													2587
													2588
					OP DYN			125C		3.80E 06	3795	0	
					EM			25C			3795	3	
					REVBIAS	LIFE	6/80	150C	N/R	9.15E 05	1830	0	
					EM			25C			1830	5	2638
													2639
					REVBIAS			150C		8.25E 05	1650	0	
					EM			25C			1650	0	
					BURN-IN	BRN	6/80	25C	N/R	7.89E 06	164391	0	
					EM			25C			164391	0	
					BAKE	LIFE	6/80	250C	N/R	2.18E 05	4543	0	
					EM			25C			4543	13	2662
													2663
													2664
					BAKE			250C		5.44E 05	4530	0	
					EM			25C			4530	17	2665
													2666
					BAKE			250C		1.30E 06	3901	0	
					EM			25C			3901	7	2667
													2668
													2669
													2670
					OP DYN	LIFE	6/80	:- 10C	N/R	3.58E 05	715	0	
					EM			25C			715	1	
					OP DYN			:- 10C		3.57E 05	714	0	
					EM			25C			714	0	
					TEMPCYC	ENV	6/80	:-055C 125C	N/R		325	0	
								:200 CYC					
					EM			:025C			325	0	
2117	D-1	HDIP	16	C	OP CNST	BRN	5/80	125C	N/R	1.34E 04	80	0	
					EM						80	2	
2118		HDIP	16	C	OP DYN	LIFE	6/80	125C	N/R	1.17E 05	699	0	
					EM			25C			699	0	
					OP DYN			125C		2.32E 05	699	0	
					EM			25C			699	0	
					OP DYN			125C		3.50E 05	699	0	
					EM			25C			699	0	
					REVBIAS	LIFE	6/80	150C	N/R	6.25E 04	125	0	
					EM			25C			125	0	

INTEL RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2118	D-1	HDIP	16	C	REVBIAS	LIFE	6/80	150C	N/R	6.25E 04	125	0	
					EM			25C			125	0	
					BAKE	LIFE	6/80	160C	N/R	2.10E 04	125	0	
					EM			25C			125	0	
					BAKE			160C		4.15E 04	125	0	
					EM			25C			125	0	
					BAKE			160C		6.25E 04	125	0	
					EM			25C			125	0	

MOSTEK RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4116	D	NHDIP	16	C	OP DYN	LIFE	2/77	125C	N/R	1.46E 06	1405	98	
					EM						1307	0	
					N/R	FIELD	10/77	25C	GF	4.75E 05	149	0	

TEXAS INSTRUMENTS RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4116	D	NHDIP	16	C	N/R	FIELD	10/77	25C	GF	4.75E 05	149	0	

VARIOUS RAM

N-DYN MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	16	M	N/R	FIELD	5/79	25C	GBC	7.10E 07	53504	38	

NATIONAL SEMI — RAM

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74C89	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	3.87E 05	153	1	
					N/R	FIELD	5/78	40C	GBC	1.07E 06	826	0	
					N/R	FIELD	4/79	40C	GBC	1.41E 06	1084	0	
					N/R	FIELD	4/80	40C	GBC	1.47E 06	1130	0	
					N/R	FIELD	4/81	40C	GBC	2.82E 06	1086	0	

RCA — RAM

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4036A	S-1	NHFPK	24	M	STAT EM	EBRN	9/77	025C	N/R		43	2	
					BAKE			125C		1.97E 03	41	0	
					TEMPCYC			-065C 125C			41	0	
								10CY					
								15/15DT					
					HERMETC						41	0	
					STAT EM			025C			41	5	
					BURN-IN			125C		8.64E 03	36	0	
					DYN EM			025C			36	1	
					X-RAY						35	5	
					VIS INS						30	0	

VARIOUS — RAM

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D-1	HDIP	14	C	OP DYN	LIFE	9/78	150C	N/R	5.00E 04	20	0	
					FNCT EM			25C			20	0	

INTERSIL — RAM

CMOS — MOS — NUMBER OF BITS 768

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6512	D	NHDIP	18	I	OP CNST	LIFE	6/79	125C	N/R	3.50E 05	70	0	
					EM			25C			70	0	

HARRIS SEMI — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6508D/18D-5	C-2	NHDIP	0	C	OP DYN	LIFE	4/79	85C	N/R	6.10E 04	61	0	
6561/62		HDIP	0	N/R	OP DYN	LIFE	4/79	85C	N/R	4.00E 04	40	0	
					HUMLIFE	LIFE	4/79	85C	N/R	3.60E 04	36	0	

INTEL — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M5101	D	NHDIP	22	N	BURN-IN	BRN	6/80	25C	N/R	6.43E 05	13393	0	
					EM			25C			13393	2	2531
					OP DYN	LIFE	6/80	125C	N/R	2.18E 05	1300	0	
					EM			25C			1300	1	2608
					OP DYN			125C		3.98E 05	1199	0	
					EM			25C			1199	0	
					OP DYN			125C		5.50E 05	1099	0	
					EM			25C			1099	0	
					BAKE	LIFE	6/80	250C	N/R	3.12E 04	650	0	
					EM			25C			650	0	
					BAKE			250C		7.20E 04	600	0	
					EM			25C			600	1	2661
					BAKE			250C		1.99E 05	599	0	
					EM			25C			599	0	
	B-2				N/R	FIELD	5/77		AIT	2.04E 03	6	0	

INTERSIL — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6508	D	NHDIP	16	C	OP CNST	LIFE	6/79	125C	N/R	3.89E 06	1965	0	
					EM			25C			1965	42	
6518		NHDIP	18	I	OP CNST	LIFE	6/79	125C	N/R	1.04E 06	1039	0	
					EM			25C			1039	9	
6551		NHDIP	22	I	OP CNST	LIFE	6/79	125C	N/R	1.77E 05	177	0	
					EM			25C			177	1	
6561		NHDIP	18	I	OP CNST	LIFE	6/79	125C	N/R	2.96E 05	206	0	
					EM			25C			206	0	

RCA — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHCC	24	M	EM	EBRN	5/80	025C	N/R		25	0	

RCA RAM

CMOS MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
	D	NHCC	24	M	BAKE	EBRN	5/80	150C	N/R	6.00E 02	25	0	
					EM			025C			25	0	
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					EM			025C			25	0	
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					EM			025C			25	0	
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM			025C			25	0	
					MECHSHK			1.5KG .5MSEC			25	0	
								6 AXES					
								5 BLOS					
					EM			025C			25	0	
					THRMSHK			-055C 125C			25	0	
								15CY					
								LIQUID					
					EM			025C			25	0	
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					EM			025C			25	0	
	B-2				EM	EBRN	5/80	025C	N/R		25	0	
					BAKE			150C		6.00E 02	25	0	
					EM			025C			25	0	
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					EM			025C			25	0	
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					EM			025C			25	0	
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM			025C			25	0	
					MECHSHK			1.5KG .5MSEC			25	0	
								6 AXES					
								5 BLOS					
					EM			025C			25	0	
					THRMSHK			-055C 125C			25	0	
								15CY					
								LIQUID					
					EM			025C			25	0	
					CNSTACC			30KG 6 AXES			25	0	
								1 MIN E					
					EM			025C			25	2	3230
1821	D	NHDIP	0	M	OP DYN	LIFE	12/77	125C	N/R	4.07E 04	12	1	
					FNCT EM						11	0	
					OP DYN	LIFE	12/77	125C	N/R	5.96E 04	19	1	
					FNCT EM						18	0	
					OP DYN	LIFE	12/77	125C	N/R	6.52E 04	18	0	
					FNCT EM						18	0	
					OP DYN	LIFE	12/77	125C	N/R	8.09E 04	14	1	
					FNCT EM						13	0	
					OP DYN	LIFE	12/77	125C	N/R	4.36E 04	45	2	
					FNCT EM						43	0	
					OP DYN	LIFE	12/77	125C	N/R	3.08E 04	30	0	
					FNCT EM						30	20	
					OP DYN	LIFE	12/77	125C	N/R	5.79E 04	29	0	
					FNCT EM						29	1	
					OP DYN	LIFE	12/77	125C	N/R	6.96E 04	21	0	
					FNCT EM						21	0	
					OP DYN	LIFE	12/77	125C	N/R	5.11E 04	16	1	
					FNCT EM						15	0	

RCA — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1821	D	NHDIP	0	M	OP DYN	LIFE	12/77	125C	N/R	2.65E 04	8	0	
					FNCT EM						8	0	
					OP DYN	LIFE	12/77	125C	N/R	7.45E 04	13	0	
					FNCT EM						13	0	
					OP DYN	LIFE	12/77	125C	N/R	1.90E 04	30	1	
					FNCT EM						29	0	
					OP DYN	LIFE	12/77	125C	N/R	5.00E 04	30	1	
					FNCT EM						29	0	
5001		NHDIP	16	1	S&D EM	LIFE	/77	25C	N/R		8	0	
					OP DYN			125C		5.30E 04	8	1	
					S&D EM			25C			7	0	

VARIOUS — RAM

CMOS — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	16	C	ACCLFIN	LIFE	9/78	200C	N/R	3.60E 04	20	0	
					FNCT EM			25C			20	0	
N/R		NHDIP	16	C	ACCLFOD	LIFE	9/78	200C	N/R	5.00E 04	20	3	
					FNCT EM			25C			20	0	
					ACCLFOD	LIFE	9/78	200C	N/R	1.20E 04	8	2	
					FNCT EM			25C			8	1	
					OP DYN	LIFE	9/78	150C	N/R	6.00E 04	20	0	
					FNCT EM			25C			20	0	
1822S/5101		NHDIP	22	C	N/R	FIELD	6/78		GF	2.86E 05	28	0	
					N/R	FIELD	6/78		GF	4.08E 04	4	0	
					N/R	FIELD	3/80		GF	4.44E 05	28	0	
					N/R	FIELD	3/80		GF	6.34E 04	4	0	
5101/6501		NHDIP	22	C	ACCLFOD	LIFE	9/78	200C	N/R	1.20E 05	20	5	
					FNCT EM			25C			20	0	
					OP DYN	LIFE	9/78	150C	N/R	1.40E 05	20	0	
					FNCT EM			25C			20	1	
					ACCLFRB	LIFE	9/78	200C	N/R	2.60E 04	20	4	
					FNCT EM			25C			20	0	
					ACCLFRR	LIFE	9/78	200C	N/R	2.60E 04	20	0	
					FNCT EM			25C			20	0	
5101/6501	B-1	NHDIP	22	M	N/R	FIELD	10/80		AUT	3.40E 05	80	0	

HARRIS SEMI — RAM

CMOS — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6514	C-2	NHDIP	18	N/R	OP DYN	LIFE	4/79	125C	N/R	5.80E 04	58	0	

SIGNETICS — RAM

LOW POWER N-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
21L02	D-1	HDIP	16	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

INTEL — RAM

HIGH SPEED N-STAT — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M2147H	D	NHDIP	18	M	BURN-IN	BRN	6/80	25C	N/R	1.13E 06	23446	0	
					EM			25C			23446	42	2525
													2526
													2527
													2528
					OP DYN	LIFE	6/80	125C	N/R	1.15E 06	6872	0	
					EM			25C			6872	9	2602
													2603
					OP DYN			125C		9.45E 05	2846	0	
					EM			25C			2846	2	2604
													2605
					OP DYN			125C		1.15E 06	2294	0	
					EM			25C			2294	2	2606
					OP DYN			125C			466	0	
					EM			25C			466	0	
					REVBIAS	LIFE	6/80	150C	N/R	6.25E 04	125	0	
					EM			25C			125	0	
					REVBIAS			150C		5.60E 04	112	0	
					EM			25C			112	0	
					BAKE	LIFE	6/80	250C	N/R	2.76E 04	575	0	
					EM			25C			575	0	
					BAKE			250C		6.30E 04	525	0	
					EM			25C			525	1	2679
					BAKE			250C		1.57E 05	474	0	
					EM			25C			474	3	2680
M2148H/49H		NHDIP	18	M	BURN-IN	BRN	6/80	25C	N/R	2.24E 05	4659	0	
					EM			25C			4659	4	2529
													2530
					OP DYN	LIFE	6/80	125C	N/R	8.40E 04	500	0	
					EM			25C			500	0	
					OP DYN			125C		1.66E 05	500	0	
					EM			25C			500	0	
					OP DYN			125C		2.00E 05	400	0	
					EM			25C			400	2	2607
					BAKE	LIFE	6/80	250C	N/R	2.40E 03	50	0	
					EM			25C			50	0	
					BAKE			250C		6.00E 03	50	0	
					EM			25C			50	0	
					BAKE			250C		1.66E 04	50	0	
					EM			25C			50	0	

INTERSIL — RECEIVE/TRANSMIT

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6402	D	NHDIP	40	I	N/R	FIELD	6/78		GF	7.14E 04	7	0	
					N/R	FIELD	6/78		GF	1.02E 04	1	0	
					N/R	FIELD	3/80		GF	1.11E 05	7	0	
					N/R	FIELD	3/80		GF	1.58E 04	1	0	
					N/R	FIELD	4/80	40C	GBC	8.81E 05	678	0	
					N/R	FIELD	4/81	40C	GBC	1.65E 06	633	0	

NATIONAL SEMI — REGISTER

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
85S68	D	NHDIP	18	C	N/R	FIELD	5/78	40C	GBC	2.07E 05	159	0	
					N/R	FIELD	4/79	40C	GBC	6.94E 05	534	0	
85S68		NHDIP	18	C	N/R	FIELD	4/80	40C	GBC	1.35E 06	1035	0	

ADVANCED MICRO DEVICES — REGISTER

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2812A	D	NHDIP	28	M	STAT EM	EBRN	9/77	025C	N/R		15	0	
					BAKE			125C		7.20E 02	15	0	
					TEMPCYC			-065C 125C			15	0	
								10CY					
								15/15DT					
					HERMETC						15	0	
					STAT EM			025C			15	1	
					BURN-IN			125C		3.36E 03	14	0	
					DYN EM			025C			14	0	
					X-RAY						14	5	
					VIS INS						9	0	

VARIOUS — ROM

TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-1	NHDIP	24	M	N/R	FIELD	9/78		AUF	3.39E 05	297	0	
					N/R	FIELD	9/79		AIU	1.07E 05	297	0	

SIGNETICS — ROM

TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8205	D	NHDIP	24	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	125C	N/R	4.90E 04	49	0	
					EM						49	1	
					STGLIFE	LIFE	11/77	150C	N/R	9.10E 04	91	0	
					EM						91	0	
8228		NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	0	

MONOLITHIC MEMORIES — ROM

TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5280	D	NHDIP	24	N	PAR EXC	LIFE	10/81	125C	N/R	7.70E 04	77	1	3700

VARIOUS — ROM

TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-1	NHDIP	24	M	N/R	FIELD	9/78		AUF	4.14E 05	363	0	
					N/R	FIELD	9/79		AIU	1.31E 05	363	0	

SIGNETICS — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S226	D	NHDIP	16	N/R	OP DYN	LIFE	11/77	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

MONOLITHIC MEMORIES — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5205	D	NHDIP	16	M	OP DYN	LIFE	1/79	125C	N/R	7.70E 04	77	0	
					EM			25C			77	0	
6209	D-1	HDIP	20	C	PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	
6209	D	NHDIP	20	C	PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	

SIGNETICS — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S215	D	NHDIP	24	M/T	OP DYN	LIFE	11/77	125C	N/R	4.50E 04	45	0	
					EM						45	0	
					STDLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

FAIRCHILD SEMI — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93454	D	NHDIP	24	M	OP DYN	LIFE	5/77	125C	N/R	5.00E 04	25	0	
					EM						25	0	
93464		NHFPK	24	M	CNSTACC	ENV	8/79	30KG 2 AXES	N/R		27	0	
								1 MIN E					
					FINE LK			HE 5.E-8			27	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			27	0	
								3X					
								60PSIG					
					EM						27	0	

MONOLITHIC MEMORIES — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5282	D	NHDIP	24	M	OP DYN	LIFE	1/79	125C	N/R	1.56E 05	310	0	
					EM			25C			310	1	
6280		NHDIP	24	C	OP DYN	LIFE	1/79	125C	N/R	5.20E 04	52	0	
					EM			25C			52	0	
6282		NHDIP	24	C	PAR EXC	LIFE	10/81	125C	N/R	2.50E 04	25	0	

SIGNETICS — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
82S260	D	NHDIP	24	N/R	STDLIFE EN	LIFE	11/77	150C	N/R	4.60E 04	46 46	0 0	

MONOLITHIC MEMORIES — ROM

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5276	D	NHDIP	24	M	OP DYN EN	LIFE	1/79	125C 25C	N/R	1.90E 04	19 19	0 0	

SOLITRON DEVICES — ROM

P-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6525	JB/B1	NHDIP	24	M	TCVPC	CHECK	2/77	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	5.56E 04	936	0	
					TCVPC	CHECK	6/79	-054C 055C 14CY 2.2G50% 22HZ 17%	AI	1.56E 05	5736	0	
					TCVPC	CHECK	6/79	-054C 055C 14CY 2.2G50% 22HZ 17%	AI	2.91E 05	10515	0	
					TCVPC	CHECK	2/77	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	2.29E 05	3834	0	

NATIONAL SEMI — ROM

P-STAT — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
16A/521	X	NHDIP	24	C	N/R	FIELD	2/78		AIT	4.28E 05	38	0	
16A/522		NHDIP	24	C	N/R	FIELD	2/78		AIT	4.28E 05	38	0	

SIGNETICS — ROM

P-STAT — MOS — NUMBER OF BITS 3K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
2513	D-1	HDIP	24	C	STCLIFE	LIFE	11/77	150C	N/R	4.00E 04	40	0	
					EM						40	0	

NATIONAL SEMI — ROM

P-STAT — MOS — NUMBER OF BITS 4K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
5232	D-1	HDIP	24	C	OP CNST	LIFE	12/78	125C	N/R	2.23E 05	223	0	
					LM						223	6	2349

ELECTRONIC ARRAYS — ROM

P-STAT — MOS — NUMBER OF BITS 5K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
4000	B-1	NHDIP	24	M	N/R	FIELD	9/78		AUF	3.39E 05	297	0	
					N/R	FIELD	9/79		AUF	1.07E 05	297	0	

NO. AMER ROCKWELL INT. — ROM

P-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
05XX	D	NHQIP	42	C	S&D EM	LIFE	/77	25C	N/R		32	0	
					OP DYN			125C		8.44E 05	32	0	
					S&D EM			25C			32	0	

SIGNETICS — ROM

P-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
2580	D-1	HDIP	24	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	2	
2580	D	NHDIP	24	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	

SIGNETICS ROM

P-STAT MOS NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFLF #
2580	D	NHDIP	24	C	STGLIFL	LIFT	11/77	150C	N/R	1.00E 05	50	0	
					LM						50	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS ROM

P-STAT MOS NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	ACCLFOD	LIFE	9/78	200C	N/R	5.40E 04	20	0	
					S&F EM			25C			20	1	
					ACCLFOD	LIFE	9/78	200C	N/R	7.00E 04	20	1	
					FNCT EM			25C			20	0	
					OP DYN	LIFE	9/78	150C	N/R	2.00E 04	20	0	
					FNCT EM			25C			20	0	

VARIOUS ROM

P-STAT MOS NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	OP DYN	LIFE	9/78	150C	N/R	3.00E 04	10	0	
					FNCT EM			25C			10	0	
					OP DYN	LIFE	9/78	150C	N/R	1.50E 04	10	1	
					FNCT EM			25C			10	0	
					OP DYN	LIFE	9/78	150C	N/R	3.00E 04	15	5	
					FNCT EM			25C			15	4	
					OP DYN	LIFE	9/78	125C	N/R	1.40E 04	7	0	
					FNCT EM			25C			7	1	

ELECTRONIC ARRAYS ROM

N-STAT MOS NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8316F	D	NHDIP	24	N/R	OP DYN	LIFE	11/79	125C	N/R	3.12E 04	93	0	
					EM						93	0	

ELECTRONIC ARRAYS — ROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6306C	D-1	HDIP	24	C	OP DYN	LIFE	2/80	125C	N/R	8.53E 04	170	0	
					EM						170	0	

MOTOROLA SEMI — ROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6830	NONE	DIP	24	C	OP DYN	LIFE	11/77	125C	N/R	1.25E 05	126	0	
					EM						126	2	
6830A	D	NHDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	1.88E 05	235	0	
					SDF EM						235	4	
68308A		NHDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	1.00E 05	126	0	
					SDF EM						126	0	
68308A	D-1	HDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	4.87E 03	29	0	
					SDF EM						29	0	
68316E		HDIP	24	C	OP DYN	LIFE	4/78	125C	N/R	4.54E 04	90	0	
					SDF EM						90	0	

VARIOUS — ROM

N-STAT — MOS — NUMBER OF BITS 8K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2609/6570	D	NHDIP	24	C	VIS INS	EBRN	3/78		N/R		1791	0	
					TEMPCYC			-055C 125C			1791	0	
								10CY					
					RFVBIAS			125C		2.87E 05	1791	0	
					S&F EM			070C			1791	108	2465
													2466
													2467
2609/6570	D-1	HDIP	24	C	VIS INS	EBRN	3/78		N/R		1906	0	
					TEMPCYC			-055C 125C			1906	0	
								10CY					
					REVBIAS			125C		3.05E 05	1906	0	
					S&F EM			070C			1906	58	2479
													2480

ADVANCED MICRO DEVICES — ROM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9218	B-2	NHDIP	24	M	PAR EXC	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	0	

ELECTRONIC ARRAYS — ROM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8316E	D-1	HDIP	24	N/R	OP DYN	LIFE	6/78	100C	N/R	4.67E 05	303	0	
					EM						303	1	
8316E	D	NHDIP	24	N/R	OP DYN	LIFE	6/78	125C	N/R	9.70E 04	84	0	
					EM						84	0	
8316F	D-1	HDIP	24	N/R	OP DYN	LIFE	2/80	125C	N/R	1.07E 05	213	0	
					EM						213	0	

NATIONAL SEMI — ROM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
42116	D-1	HDIP	24	I	OP DYN	LIFE	12/78	125C	N/R	1.12E 05	112	0	
					EM						112	1	
					OP DYN	LIFE	12/78	125C	N/R	9.55E 04	154	0	
					EM						154	5	
					OP DYN	LIFE	12/78	125C	N/R	1.65E 04	33	0	
					EM						33	1	
42116	D	NHDIP	24	I	OP DYN	LIFE	12/78	125C	N/R	2.73E 04	44	0	
					EM						46	1	

SIGNETICS — ROM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2600	D	NHDIP	24	C	OP DYN	LIFE	11/77	125C	N/R	7.20E 04	72	0	
					EM						72	0	

VARIOUS — ROM

N-STAT — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	24	C	ACCLFOD	LIFE	9/78	200C	N/R	4.00E 04	10	1	
					FNCT EM			25C			10	0	
					OP DYN	LIFE	9/78	150C	N/R	8.00E 04	20	0	
					FNCT EM			25C			20	0	
4600	C-1	NHDIP	24	N/R	OPERATE	CHECK	4/78	125C	GT	2.08E 05	2682	2	
8316A	B-2	NHDIP	24	C	N/R	FIELD	5/77		AIT	8.15E 03	24	0	

ELECTRONIC ARRAYS — ROM

N-STAT — MOS — NUMBER OF BITS 32K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8332E	D-1	HDIP	24	C	OP DYN	LIFE	5/79	100C	N/R	2.43E 04	74	0	
					EM						74	0	
					OP DYN	LIFE	5/79	125C	N/R	1.79E 05	240	0	
					EM						240	0	
8332E	D	NHDIP	24	C	OP DYN	LIFE	2/80	125C	N/R	8.88E 04	78	0	
					EM						78	0	

NATIONAL SEMI — ROM

N-STAT — MOS — NUMBER OF BITS 64K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4235	D-1	HDIP	28	N/R	OP DYN	LIFE	12/78	125C	N/R	1.10E 04	11	0	
					EM						11	0	

INTEL — ROM

N-DYN — MOS — NUMBER OF BITS 16K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8355	D	NHDIP	40	C	BURN-IN	BRN	6/80		N/R	3.90E 04	812	0	
					EM						812	3	3128
													3129
					OP DYN	LIFE	6/80	125C	N/R	2.66E 05	532	0	
					EM						532	0	
					OP DYN	BRN	6/80	125C	N/R	1.68E 04	100	0	
					EM						100	1	
					OP DYN	LIFE	6/80	125C	N/R	2.87E 05	287	0	
					EM						287	0	
8355		HDIP	40	C	BURN-IN	BRN	6/80		N/R	1.68E 04	350	0	
					EM						350	0	
	D-1				OP DYN	BRN	6/80	125C	N/R	4.03E 04	240	0	
					EM						240	0	
					OP DYN	LIFE	6/80	125C	N/R	2.20E 05	110	0	
					EM						110	0	
					N/R	FIELD	4/81	40C	GBC	1.09E 06	421	0	
8355		NHDIP	40	C	BURN-IN	BRN	6/80		N/R	1.61E 04	335	0	
					EM						335	0	
	D				OP DYN	LIFE	6/80	125C	N/R	9.50E 04	190	0	
					EM						190	0	
					OP DYN	BRN	6/80	125C	N/R	9.91E 03	59	0	
					EM						59	0	

RCA ROM

CMOS MOS NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHCC	24	M	EM	EBRN	5/80	025C	N/R		75	0	
					BAKE			150C		1.80E 03	75	0	
					EM			025C			75	0	
					TEMPCYC			-065C 150C			75	0	
								10CY					
								10/10DT					
					EM			025C			75	0	
					FINE LK			HE 5.E-8			75	0	
								60 MIN					
								30 MIN					
					EM			025C			75	0	
					GROSSLK			FLUOR 125C			75	0	
								3X					
								90PSIG					
					EM			025C			75	0	
					MECHSHK			1.5KG .5MSEC			75	0	
								6 AXES					
								5 BLOS					
					EM			025C			75	0	
					THRMSHK			-055C 125C			75	0	
								15CY					
								LIQUID					
					EM			025C			75	0	
					CNSTACC			30KG 6 AXES			75	0	
								1 MIN E					
					EM			025C			75	0	
					EM	EBRN	5/80	025C	N/R		35	0	
					BAKE			150C		8.40E 02	35	0	
					EM			025C			35	0	
					TEMPCYC			-065C 150C			35	0	
								10CY					
								10/10DT					
					EM			025C			35	0	
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					EM			025C			35	0	
					GROSSLK			FLUOR 125C			35	0	
								3X					
								90PSIG					
					EM			025C			35	0	
					EM	EBRN	5/80	025C	N/R		75	0	
					BAKE			150C		1.80E 03	75	0	
					EM			025C			75	0	
					TEMPCYC			-065C 150C			75	0	
								10CY					
								10/10DT					
					EM			025C			75	0	
					FINE LK			HE 5.E-8			75	0	
								60 MIN					
								30 MIN					
					EM			025C			75	2	3231
					GROSSLK			FLUOR 125C			73	0	
								3X					
								90PSIG					
					EM			025C			73	0	
					MECHSHK			1.5KG .5MSEC			73	0	
								6 AXES					
								5 BLOS					
					EM			025C			73	0	
					THRMSHK			-055C 125C			73	0	
								15CY					
								LIQUID					
					EM			025C			73	0	
					CNSTACC			30 KG 6 AXES			73	0	
								1 MIN E					
					EM			025C			73	8	3232

INTERSIL — ROM

CMOS — MOS — NUMBER OF BITS 12K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6312	D	NHDIP	18	I	OP CHST	LIFE	6/79	125C	N/R	2.09E 05	• 211	0	
					EM			25C			211	1	

HARRIS SEMI — ROM

HIGH SPEED CMOS — MOS — NUMBER OF BITS 12K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6312	C-2	NHDIP	18	N/R	OP DYN	LIFE	4/79	125C	N/R	4.10E 04	41	1	
					OP DYN	LIFE	4/79	125C	N/R	2.00E 04	20	0	

INTEL — SENSE AMP

SCHOTTKY TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3208A	D-1	NDIP	16	C	N/R	FIELD	5/77	40C	GBC	5.23E 06	1050	0	

ADVANCED MICRO DEVICES — SHIFT REG

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2504	B-2	NHDIP	24	M	OPERATE	RELDEM	12/77		AIU	1.29E 03	40	0	

VARIOUS — SHIFT REG

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9328	D	NHFPK	16	M	TCVPC	RELPRO	1/77	-054C 071C	AUF	6.25E 04	486	0	
								17CY 1.3G50%					
								23HZ 8.3%					
9328	C-1	NHFPK	16	M	N/R	FIELD	9/78		AUF	9.14E 06	8019	8	2211
													2212
													2213
					N/R	FIELD	9/79		AIU	2.89E 06	8019	0	

VARIOUS — SHIFT REG

TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9328	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.43E 07	3471	0	
					N/R	FIELD	5/78	40C	GBC	5.23E 06	4020	0	
					N/R	FIELD	4/79	40C	GBC	6.55E 05	504	0	
					N/R	FIELD	4/80	40C	GBC	2.34E 05	180	0	
9328	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	3.56E 06	260	0	
					N/R	FIELD	1/79	25C	GF	5.75E 05	42	0	
	B-2				OPERATE	RELDEM	12/77		AIU	1.29E 03	40	0	
	JB/B1				N/R	FIELD	7/79	25C	GF	1.12E 06	260	0	
					N/R	FIELD	7/79	25C	GF	1.81E 05	42	0	
					N/R	FIELD	8/80	25C	GF	2.62E 06	260	0	
					N/R	FIELD	8/80	25C	GF	4.23E 05	42	0	
9328	J-B	NHDIP	16	M	N/R	FIELD	9/79		AUF	2.48E 05	165	0	

TEXAS INSTRUMENTS — SHIFT REG

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS673	D-1	HDIP	24	C	N/R	FIELD	4/81	40C	GBC	5.02E 05	193	0	

VARIOUS — SHIFT REG

LOW POWER TTL — BIPOLAR — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L28	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.68E 07	4382	11	
					N/R	FIELD	5/78	40C	GBC	1.46E 07	11260	2	
					N/R	FIELD	4/79	40C	GBC	2.32E 07	17850	0	
					N/R	FIELD	4/80	40C	GBC	2.42E 07	18610	2	
					N/R	FIELD	4/81	40C	GBC	4.77E 07	18365	3	

GENERAL INSTRUMENTS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2064	D	NHFPK	14	M	TCVPC	RELPRO	1/77	-054C 071C 17CY 1.3G50% 23HZ 8.3%	AUF	1.03E 05	804	0	

NATIONAL SEMI — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5052	D	NHCAN	8	C	N/R	FIELD	5/77	40C	GBC	1.23E 06	256	0	

SIGNETICS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2510	D-1	HDIP	14	C	OP DYN	LIFE	11/77	85C	N/R	1.47E 05	49	0	
					EM						49	0	
					STGLIFE	LIFE	11/77	150C	N/R	1.44E 05	48	0	
					EM						48	0	
2518		HDIP	16	C	OP DYN	LIFE	11/77	125C	N/R	3.70E 04	37	0	
					EM						37	1	
					OP DYN	LIFE	11/77	125C	N/R	7.30E 04	73	0	
					EM						73	2	
					STGLIFE	LIFE	11/77	150C	N/R	3.40E 04	34	0	
					EM						34	0	
					STGLIFE	LIFE	11/77	150C	N/R	7.40E 04	74	0	
					EM						74	1	
2521		HDIP	8	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	1	
					OP DYN	LIFE	11/77	85C	N/R	1.00E 05	50	0	
					EM						50	0	
					OP DYN	LIFE	11/77	85C	N/R	9.90E 04	50	0	
					EM						50	1	
					OP DYN	LIFE	11/77	85C	N/R	8.80E 04	88	0	
					EM						88	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	5.30E 04	53	0	
					EM						53	0	

VARIOUS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	C-1	NHFPK	14	M	N/R	FIELD	9/78		AUF	1.51E 07	13266	45	
					N/R	FIELD	9/79		AIU	4.78E 06	13266	1	2502

SIGNETICS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 320

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2532	:D	:NHDIP	16	:C	OP DYN	LIFE	11/77	85C	N/R	7.10E 04	71	0	
					EM						71	1	
					OP DYN	LIFE	11/77	85C	N/R	2.36E 05	34	0	
					EM						34	0	
					OP DYN	LIFE	11/77	125C	N/R	2.48E 05	36	0	
					EM						36	1	
					STGLIFE	LIFE	11/77	150C	N/R	3.86E 05	50	0	
					EM						50	1	
:2532		:NHDIP	16	:C	OP DYN	LIFE	11/77	85C	N/R	7.10E 04	71	0	
					EM						71	0	
					OP DYN	LIFE	11/77	85C	N/R	2.43E 05	35	0	
					EM						35	0	
					OP DYN	LIFE	11/77	125C	N/R	2.27E 05	36	0	
					EM						36	3	
					STGLIFE	LIFE	11/77	150C	N/R	3.74E 05	50	0	
					EM						50	1	
:2532	:D-1	:HDIP	16	:C	OP DYN	LIFE	11/77	125C	N/P	2.46E 05	123	0	
					EM						123	2	
					OP DYN	LIFE	11/77	125C	N/R	7.20E 04	72	0	
					EM						72	0	
					STGLIFE	LIFE	11/77	150C	N/R	2.57E 05	130	0	
					EM						130	0	
					STGLIFE	LIFE	11/77	150C	N/R	5.20E 04	52	0	
					EM						52	1	

VARIOUS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 320

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS..	#TEST	#FAIL	MFEF #
:N/R	:D-1	:HDIP	16	:I	N/R	FIELD	5/77	40C	GBC	2.68E 05	81	0	

SIGNETICS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 480

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2527	:D-1	:HDIP	8	:C	OP DYN	BRN	11/77	85C	N/R	1.20E 04	49	0	
					EM						49	1	
					BAKE	BRN	11/77	150C	N/R	1.20E 04	50	0	
					EM						50	0	

SIGNETICS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2533	D-1	HDIP	8	C	OP DYN	LIFE	11/77	85C	N/P	4.60E 04	46	0	
					FM						46	2	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — SHIFT REG

P-STAT — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2533/5050	D-1	HDIP	8	C	N/R	FIELD	5/77	40C	GBC	3.90E 03	6	0	
					N/R	FIELD	5/78	40C	GBC	7.15E 04	55	0	

ELECTRONIC ARRAYS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1202	C-1	NHDIP	14	I	N/R	FIELD	12/79	25C	NS	1.82E 05	36	0	

NATIONAL SEMI — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
406	C-1	NHCAN	8	M	N/E	FIELD	12/79	25C	NS	3.03E 05	60	0	
5006A	D	NHCAN	8	C	N/R	FIELD	5/77	40C	GBC	9.83E 05	260	0	
					N/R	FIELD	5/78	40C	GBC	6.08E 05	468	0	
					N/R	FIELD	4/79	40C	GBC	4.37E 05	336	0	
					N/R	FIELD	4/80	40C	GBC	4.52E 05	348	0	
					N/R	FIELD	4/81	40C	GBC	4.99E 05	192	0	

SIGNETICS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2506	B-1	HDIP	8	C	OP DYN	LIFE	11/77	85C	N/R	5.80E 04	58	0	
					EM						58	1	
2507		LDIP	8	C	OP DYN	LIFE	11/77	125C	N/R	3.90E 04	39	0	
					EM						39	0	
					OP DYN	LIFE	11/77	85C	N/R	3.90E 04	39	0	
					EM						39	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	40	0	
					EM						40	0	
2517		HDIP	8	C	OP DYN	LIFE	11/77	125C	N/R	5.10E 04	51	0	
					EM						51	0	

VARIOUS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-1	NHCAN	8	C	N/R	FIELD	5/77	25C	GF	5.97E 05	42	0	
					N/R	FIELD	5/77	25C	GF	1.39E 06	98	0	

SIGNETICS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 512

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2505	D	NHCAN	10	C	OP DYN	LIFE	11/77	85C	N/R	5.60E 04	56	0	
					EM						56	0	
					OP DYN	LIFE	11/77	85C	N/R	7.90E 04	79	0	
					EM						79	2	

ADVANCED MICRO DEVICES — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1402A	B-2	NHDIP	16	M	PAR EXC	LIFE	6/80	125C	N/R	8.40F 04	84	0	
					EM			125C			84	1	3227
1404A		NHCAN	8	M	PAR EXC	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	1	3228

INTEL — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1402A	D	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.17E 06	339	0	
					N/R	FIELD	5/78	40C	GBC	1.65E 06	1272	0	
					N/R	FIELD	4/79	40C	GBC	3.20E 06	2520	0	

SIGNETICS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2503	D	NHCAN	8	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
2504		NHCAN	8	C	OP DYN	LIFE	11/77	85C	N/R	3.80E 04	38	0	
					EM						38	1	
					OP DYN	LIFE	11/77	85C	N/R	4.70E 04	47	0	
					EM						47	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	BRN	11/77	125C	N/R	1.00E 04	62	0	
					EM						62	0	
					BAKE	BRN	11/77	150C	N/R	9.00E 03	56	0	
					EM						56	0	
2504	D-1	HDIP	8	C	OP DYN	LIFE	11/77	85C	N/R	4.50E 04	45	0	
					EM						45	0	
2525		HDIP	8	C	OP DYN	LIFE	11/77	125C	N/R	4.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	11/77	85C	N/R	1.38E 05	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	1.50E 05	50	0	
					EM						50	2	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1402A	NONE		0	C	N/R	FIELD	4/80	40C	GBC	4.80E 06	3696	0	
	N/R				N/R	FIELD	4/81	40C	GBC	9.21E 06	3544	0	
1404A	D	NHCAN	8	C	N/R	FIELD	4/79	25C	GB	5.23E 07	2720	36	
					N/R	FIELD	4/79	25C	GB	0.81E 07	5440	11	
2802	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	7.20E 06	526	1	
					N/R	FIELD	7/79	25C	GF	2.27E 06	526	0	
					N/R	FIELD	8/80	25C	GF	5.30E 06	526	0	
2803/1403A	D	NHCAN	8	C	N/R	FIELD	5/77	40C	GBC	5.10E 06	1693	2	

HUGHES — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP REQ	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2048	B-2	HHFPK	14	N	OPERATE	CHECK	3/78	025C	AIT	1.68E 05	6240	15	
					VERIFY	EQUIV	3/78	100HZ 100KHZ	AIT	1.16E 05	6240	6	
					OPERATE	CHECK	3/78	025C	AIT	1.14E 06	6240	16	
					TOTAL	DELPRO	3/78	002C 045C	AIT	1.14E 06	6240	6	
								5CY 1.5G 79%					
								45HZ 22%					

VARIOUS — SHIFT REG

N-DYN — MOS — NUMBER OF BITS 2K

PART NO.	SCR. CLS	PKG	#PINS	TMP REQ	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2401	NONE	DIP	16	C	N/P	FIELD	5/77	40C	GBC	2.29E 06	797	1	

MOTOROLA SEMI — SHIFT REG

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP REQ	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14490V	D-1	LDIP	16	I	N/R	FIELD	4/79	40C	GBC	5.20E 06	4000	0	
					N/R	FIELD	4/80	40C	GBC	1.32E 07	10148	2	
					N/R	FIELD	4/81	40C	GBC	2.49E 07	9584	0	
14557		LDIP	16	I	N/R	FIELD	4/81	40C	GBC	5.02F 05	193	0	

PCA — SHIFT REG

CMOS — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP REQ	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4006A	D	NHFPK	14	N	STAT EM	EBRN	9/77	025C	N/R		30	1	
					BAKE			125C		1.39E 03	29	0	
					TEMPCYC			-065C 125C			29	0	
								10CY					
								15/15DT					
					HERMETC						29	0	
					STAT EM			025C			29	1	
					BURN-IN			125C		6.72E 03	28	0	
					DYN EM			025C			28	3	
					X-RAY						25	1	
					VIS INS						24	0	
	S-1				STAT EM	EBRN	9/77	025C	N/R		55	4	
					BAKE			125C		2.45E 03	51	0	
					TEMPCYC			-065C 125C			51	0	
								10CY					
								15/15DT					

INTEL — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1402A	D	CDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.17E 06	339	0	
					N/R	FIELD	5/78	40C	GBC	1.65E 06	1272	0	
					N/R	FIELD	4/79	40C	GBC	3.20E 06	2520	0	

SIGNETICS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2503	D	NHCAN	8	C	OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
2504		NHCAN	8	C	OP DYN	LIFE	11/77	85C	N/R	3.80E 04	38	0	
					EM						38	1	
					OP DYN	LIFE	11/77	85C	N/R	4.70E 04	47	0	
					EM						47	0	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP DYN	BRN	11/77	125C	N/R	1.00E 04	62	0	
					EM						62	0	
					BAKE	BRN	11/77	150C	N/R	9.00E 03	56	0	
					EM						56	0	
2504	D-1	NDIP	8	C	OP DYN	LIFE	11/77	85C	N/R	4.50E 04	45	0	
					EM						45	0	
2525		NDIP	8	C	OP DYN	LIFE	11/77	125C	N/R	4.00E 04	40	0	
					EM						40	0	
					OP DYN	LIFE	11/77	85C	N/R	1.38E 05	46	0	
					EM						46	0	
					OP DYN	LIFE	11/77	85C	N/R	4.60E 04	46	0	
					EM						46	0	
					STGLIFE	LIFE	11/77	150C	N/R	1.50E 05	50	0	
					EM						50	2	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

VARIOUS — SHIFT REG

P-DYN — MOS — NUMBER OF BITS 1K

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1402A	NONE		0	C	N/R	FIELD	4/80	40C	GBC	4.80E 06	3696	0	
	N/R				N/R	FIELD	4/81	40C	GBC	9.21E 06	3544	0	
1404A	D	NHCAN	8	C	N/R	FIELD	4/79	25C	GB	5.23E 07	2720	36	
					N/R	FIELD	4/79	25C	GB	0.81E 07	5440	11	
2802	JB/B1	NHDIP	16	M	N/R	FIELD	1/79	25C	GF	7.20E 06	526	1	
					N/R	FIELD	7/79	25C	GF	2.27E 06	526	0	
					N/R	FIELD	8/80	25C	GF	5.30E 06	526	0	
2803/1403A	D	NHCAN	8	C	N/R	FIELD	5/77	40C	GBC	5.10E 06	1693	2	

RCA SHIFT REG

CMOS MOS NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
4006A	S-1	HFFPK	14	M	HERMETC	EBRN	9/77		N/R		51	0	
					STAT EM			025C			51	3	
					BURN-IN			125C		1.15E 04	48	0	
					DYN EM			025C			48	1	
					X-RAY						47	3	
					VIS INS						44	0	
4031A	D-1	HDIP	16	N	N/R	FIELD	4/79	40C	GBC	1.69E 04	13	0	
					N/R	FIELD	4/80	40C	GBC	3.64E 04	28	0	
					N/R	FIELD	4/81	40C	GBC	9.10E 04	35	0	
4031A	D	HFFPK	16	M	STAT EM	EBRN	9/77	025C	N/R		46	0	
					BAKE			125C		2.21E 03	46	0	
					TEMPCYC			-065C 125C			46	0	
								10CY					
								15/15DT					
					HERMETC						46	0	
					STAT EM			025C			46	0	
					BURN-IN			125C		1.10E 04	46	0	
					DYN EM			025C			46	3	
					X-RAY						43	3	
					VIS INS						40	4	
					STAT EM	EBRN	9/77	025C	N/R		62	0	
					BAKE			125C		2.96E 03	62	0	
					TEMPCYC			-065C 125C			62	0	
								10CY					
								15/15DT					
					HERMETC						62	0	
					STAT EM			025C			62	0	
					BURN-IN			125C		1.63L 04	62	0	
					DYN EM			025C			62	1	
					X-RAY						61	4	
					VIS INS						57	0	
	S-1				STAT EM	EBRN	9/77	025C	N/P		106	0	
					BAKE			125C		5.09E 03	106	0	
					TEMPCYC			-065C 125C			106	0	
								10CY					
								15/15DT					
					HERMETC						106	0	
					STAT EM			025C			106	1	
					BURN-IN			125C		2.52E 04	105	0	
					DYN EM			025C			105	0	
					X-RAY						105	5	
					VIS INS						100	4	
	J-S				STAT EM	EBRN	9/77	025C	N/R		83	1	
					BAKE			125C		3.94E 03	82	0	
					TEMPCYC			-065C 125C			82	0	
								10CY					
								15/15DT					
					HERMETC						82	0	
					STAT EM			025C			82	0	
					BURN-IN			125C		1.97E 04	82	0	
					DYN EM			025C			82	0	
					X-RAY						82	0	
					VIS INS						82	6	
	S-2				STAT EM	EBRN	9/77	025C	N/R		44	0	
					BAKE			125C		2.11E 03	44	0	
					TEMPCYC			-065C 125C			44	0	
								10CY					
								15/15DT					
					HERMETC						44	0	
					STAT EM			025C			44	0	
					BURN-IN			125C		1.06E 04	44	0	
					DYN EM			025C			44	0	
					X-RAY						44	3	
					VIS INS						41	0	

NATIONAL SEMI — TIME PIECE

P-DYN — MOS — NUMBER OF BITS 0-256

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5315	D-1	HDIP	28	C	N/R	FIELD	5/78	40C	GBC	1.69E 04	13	0	
					N/R	FIELD	4/79	40C	GBC	2.15E 05	165	0	
					N/R	FIELD	4/80	40C	GBC	2.91E 05	224	0	
					N/R	FIELD	4/81	40C	GBC	7.31E 05	281	0	
5371		HDIP	28	C	N/R	FIELD	5/78	40C	GBC	1.69E 04	13	0	
					N/R	FIELD	4/79	40C	GBC	2.15E 05	165	0	
					N/R	FIELD	4/80	40C	GBC	2.91E 05	224	2	
					N/R	FIELD	4/81	40C	GBC	7.31E 05	281	2	

ADVANCED MICRO DEVICES — ADDER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 108

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
25LS15	X	HDIP	20	C	N/R	FIELD	4/78	25C	GBC	2.16E 06	500	0	

COLLINS RADIO — ADDER

P-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9503	B-1	NHFPK	34	I	TCVPC	RELDEM	8/75	-054C 071C 545CY1.6G62% 30HZ 10%	A1F	5.45E 03	2	0	

MOTOROLA SEMI — ADDRESS

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7849	X	NHFPK	42	C	PAR EXC EM	LIFE	2/75	125C	N/R	4.64E 04	9 7	2 0	

NATIONAL SEMI — ARITHMETIC

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7853	X	NHFPK	42	C	PAR EXC EM	LIFE	2/75	125C	N/R	1.00E 04	10 10	0 0	

MOTOROLA SEMI — ARITHMETIC

ECL — BIPOLAR — NUMBER OF GATES 350

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10800	D	NHQIP	48	I	S&D EM OP DYN	LIFE	/77	25C 70C	N/R	7.39E 03	4 4	0 0	

MOTOROLA SEMI — ARITHMETIC

ECL — BIPOLAR — NUMBER OF GATES 350

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:10800	:D	:NHQIP	48	:I	: S&D EM	: LIFE	/77	: 25C	: N/R		4	0	

NITRON — ARITHMETIC

P-STAT — MOS — NUMBER OF GATES 900

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:N/R	:D	:NHDIP	40	:N/R	: BAKE	: EBRN	8/77	:150C	: N/R	: 5.13E 04	2139	0	
					: TEMPCYC			:-065C 150C			2139	0	
								:10CY					
								:10/10DT					
					: CNSTACC			:20KG 1 AXIS			2139	0	
								:1 MIN E					
					: FINE LK			:HE 5.E-7			2139	8	1915
								:60 MIN					
								:30 MIN					
					: GROSSLK			:FLUOR 125C			2139	15	1916
								:3X					
								:90PSIG					
					: FNCT EM			:085C			2116	519	
	:B-1				: REVBIAS	: BRN	2/78	: 125C	: N/R	: 3.28E 05	1950	0	
					: S&F EM			: 85C			1950	14	
					: STAT EM			:- 35C			1950	5	
					: FNCT EM			: 25C			1950	28	
					: VIS INS						1950	14	
	:JB/B1				: N/R	: FIELD	1/79	: 25C	: GF	: 1.37E 04	1	0	
	:C-1				: OPERATE	: CHECK	4/78	:125C	: GT	: 3.47E 04	447	0	

NATIONAL SEMI — ARITHMETIC

P-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TFST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:00A/520	:X	:NHDIP	24	:C	: N/R	: FIELD	2/78	:	: AIT	: 1.71E 06	152	0	

RCA — ARITHMETIC

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:4057A	:D	:NHFPK	28	:M	. STAT EM	: EBRN	9/77	:025C	: N/R		14	0	
					: BAKE			:125C		: 6.72E 02	14	0	
					: TEMPCYC			:-065C 125C			14	0	
								:10CY					
								:15/15DT					

RCA — ARITHMETIC

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4057A	D	NHFPK	28	M	HERMETC	EBRN	9/77		N/R		14	0	
					STAT EM			025C			14	0	
					BURN-IN			125C		3.36E 03	14	0	
					DYN EM			025C			14	0	
					X-RAY						14	0	
								N					
					VIS INS						14	0	
					STAT EM	EBRN	9/77	025C	N/R		5	0	
					BAKE			125C		2.40E 02	5	0	
					TEMPCYC			-065C 125C			5	0	
								10CY					
								15/15DT					
					HERMETC						5	0	
					STAT EM			025C			5	0	
					BURN-IN			125C		1.20E 03	5	0	
					DYN EM			025C			5	0	
					X-RAY						5	0	
					VIS INS						5	0	

MOTOROLA SEMI — A/D CONVERTER

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14433	D	NHDIP	24	I	N/R	FIELD	4/79	40C	GBC	8.19E 04	63	0	
					N/R	FIELD	4/80	40C	GBC	3.20E 06	2465	5	
					N/R	FIELD	4/81	40C	GBC	8.29E 06	3187	7	

RCA — BINARY

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4040B	D	NHDIP	16	M	TEMPCYC	RELDEM	11/77	000C 050C	NSS	1.51E 03	2	0	
								16CY					

SOLID STATE SCIENTIFIC — BINARY

CMOS — MOS — NUMBER OF GATES 81

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4024A	B-1	NHDIP	14	M	TCVPC	RELDEM	12/75	-054C 055C	AI	1.17E 03	2	0	
								140CY2.2G70%:					
								22HZ 17%:					

SOLID STATE SCIENTIFIC — BINARY

CMOS — MOS — NUMBER OF GATES 81

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4024A	B-1	NHDIP	14	M	TCVPC	CHECK	1/76	-054C 055C 15CY 2.2G70% 22HZ 17%	AI	1.41E 04	162	0	
					TCVPC	RELPRO	1/76	-054C 055C 16CY 2.2G70% 22HZ 17%	AI	1.14E 04	169	0	
					TCVPC	CHECK	1/76	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	9.68E 03	144	0	
					TCVPC	RELPRO	1/76	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	7.88E 03	122	0	
					TCVPC	RELDEM	12/75	-054C 055C 140CY2.2G70% 22HZ 17%	AI	4.70E 03	8	0	
	JB/B1				TCVPC	CHECK	2/77	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	3.71E 04	624	0	
					TCVPC	CHECK	2/77	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	1.53E 05	2556	0	
					TCVPC	CHECK	2/77	-054C 055C 11CY 2.2G70% 22HZ 17%	AI	1.77E 05	2825	0	
					TCVPC	CHECK	6/79	-054C 055C 14CY 2.2G50% 22HZ 17%	AI	1.04E 05	3824	0	
					TCVPC	CHECK	6/79	-054C 055C 14CY 2.2G50% 22HZ 17%	AI	1.94E 05	7010	0	
					TCVPC	CHECK	6/79	-054C 055C 14CY 2.2G50% 22HZ 17%	AI	1.84E 05	6749	0	

MOTOROLA SEMI — BINARY

CMOS — MOS — NUMBER OF GATES 132

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14020	C-2	NHDIP	16	I	OPERATE	CHECK	4/76	025C	GP	0.60E 01	6	0	
					OPERATE			000C		0.60E 01	6	0	
					OPERATE			050C		0.60E 01	6	0	
14020B	D-1	HDIP	16	C	N/R	FIELD	4/80	40C	GBC	6.26E 06	4818	6	

RCA — BINARY

CMOS — MOS — NUMBER OF GATES 132

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4020A	D-1	HDIP	16	I	N/R	FIELD	5/77	40C	GBC	4.54E 06	1151	0	
					N/R	FIELD	5/78	40C	GBC	2.29E 06	1765	0	
					N/R	FIELD	4/79	40C	GBC	5.61E 06	4313	0	
4020A	S-1	NHFPK	16	M	STAT EM	EBRN	9/77	025C	N/R		41	0	

RCA — BINARY

CMOS — MOS — NUMBER OF GATES 132

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4020A	S-1	NHFPK	16	M	BAKE	EBRN	9/77	125C	N/R	1.97E 03	41	0	
					TEMPCYC			-065C 125C			41	0	
								10CY					
								15/15DT					
					HERMETC						41	0	
					STAT EM			025C			41	0	
					BURN-IN			125C		9.84E 03	41	0	
					DYN EM			025C			41	0	
					X-RAY						41	0	
					VIS INS						41	0	

NITRON — BUFFER

P-STAT — MOS — NUMBER OF GATES 784

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	6.54E 04	2724	0	
					TEMPCYC			-065C 150C			2724	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			2724	0	
								1 MIN E					
					FINE LK			HE 5.E-7			2724	12	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			2724	8	
								3X					
								90PSIG					
					FNCT EM			085C			2704	434	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.61E 05	1553	0	
					S&F EM			85C			1553	12	
					STAT EM			- 35C			1553	5	
					FNCT EM			25C			1553	20	
					VIS INS						1553	16	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	1	

INTEL — BUS DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8218	D	DIP	28	C	BURN-IN	BRN	1/80		N/R	2.30E 04	480	0	
					EM						480	0	
					OP DYN	LIFE	1/80	125C	N/R	4.80E 05	480	0	
					EM						480	1	3179
8218/19		NHDIP	28	C	BURN-IN	BRN	6/80		N/R	1.75E 05	3638	0	
					EM						3638	7	3135
													3136
													3137
													3138
													3139
					OP DYN	BRN	6/80	125C	N/R	1.73E 04	103	0	
					EM						103	1	3177

INTEL — BUS DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8218/19	D	NHDIP	28	C	OP DYN	LIFE	6/80	125C	N/R	7.84E 05	784	0	
					EM						784	1	3178

INTEL — CLOCK DRIVER

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8284	D	NHDIP	18	C	BURN-IN	BRN	6/80		N/R	1.14E 04	238	0	
					EM						238	0	
					OP DYN	LIFE	6/80	125C	N/R	2.38E 05	238	0	
					EM						238	0	
					BAKE	BRN	6/80	250C	N/R	3.36E 03	20	0	
					EM						20	0	
					TEMPCYC	ENV	6/80	-055C 125C 200 CY	N/R		20	0	
					EM						20	0	
8284	D-1	HDIP	18	C	BURN-IN	BRN	6/80		N/R	2.41E 04	502	0	
					EM						502	4	
					OP DYN	LIFE	6/80	125C	N/R	3.29E 05	341	25	
					EM						316	0	
					BAKE	BRN	6/80	160C	N/R	3.36E 03	20	0	
					EM						20	0	
					TEMPCYC	ENV	6/80	-055C 125C 200 CY	N/R		20	0	
					EM						20	0	

NITRON — CONTROL

P-STAT — MOS — NUMBER OF GATES 435

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	1.96E 05	8183	0	
					TEMPCYC			-065C 150C 10CY			8183	0	
								10/10DT					
					CNSTACC			20KG 1 AXIS 1 MIN E			8183	0	
					FINE LK			HE 5.E-7 60 MIN			8183	53	
								30 MIN					
					GROSSLK			FLUOR 125C 3X 90PSIG			8183	23	
					FNCT EM			085C			8107	999	
					N/R						0	28	
	B-1				REVBIAS	BRN	2/78	125C	N/R	1.31E 06	7816	0	
					S&F EM			85C			7816	59	
					STAT EM			-35C			7816	20	
					FNCT EM			25C			7816	145	
					VIS INS						7816	44	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	8	

NITRON — CONTROL

P-STAT — MOS — NUMBER OF GATES 707

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	4.99E 04	208	0	
					TEMPCYC			-065C 150C			2081	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			2081	0	
								1 MIN E					
					FINE LK			HE 5.E-7			2081	7	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			2081	2	
								3X					
								90PSIG					
					FNCT EM			085C			2072	144	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.32E 05	1378	0	
					S&F EM			85C			1337	29	
					STAT EM			- 35C			1337	25	
					FNCT EM			25C			1337	15	
					VIS INS						1337	9	
					REVBIAS	BRN	2/78	125C	N/R	7.22E 03	43	0	
					S&F EM			85C			43	0	
					STAT EM			- 35C			43	0	
					FNCT EM			25C			43	0	
					VIS INS						43	0	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	0	

MOTOROLA SEMI — CONVERTER

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7854	X	NHFPK	42	C	PAR EXC	LIFE	2/75	125C	N/R	5.03E 04	10	0	
					EM						10	0	
					PAR EXC	LIFE	2/75	125C	N/R	3.02E 04	10	0	
					EM						10	0	

NATIONAL SEMI — COUNTER

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7843	X	NHFPK	42	C	PAR EXC	LIFE	2/75	125C	N/R	2.01E 04	10	0	
					EM						10	0	

MOSTEK — COUNTER

P-DYN — MOS — NUMBER OF GATES 1333

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5009	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	4.82E 06	1421	3	
					N/R	FIELD	5/78	40C	GBC	5.95E 06	4574	3	
					N/R	FIELD	4/79	40C	GBC	9.30E 06	7154	6	
					N/R	FIELD	4/80	40C	GBC	7.89E 06	6068	5	
					N/R	FIELD	4/81	40C	GBC	1.46E 07	5598	5	
5009	D	NHDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.22E 07	3142	16	
					N/R	FIELD	5/78	40C	GBC	7.40E 06	5689	9	
					N/R	FIELD	4/79	40C	GBC	8.76E 06	6739	3	
					N/R	FIELD	4/79	40C	GBC	3.72E 05	286	0	
					N/R	FIELD	4/80	40C	GBC	9.36E 06	7201	9	
					N/R	FIELD	4/81	40C	GBC	1.63E 07	6256	13	

INTERSIL — COUNTER

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7226A	D	NHDIP	40	I	N/R	FIELD	4/79	40C	GBC	4.67E 05	359	1	
					N/R	FIELD	4/80	40C	GBC	5.20E 06	4001	12	
					N/R	FIELD	4/81	40C	GBC	1.15E 07	4404	16	

NITRON — CUSTOM

P-STAT — MOS — NUMBER OF GATES 282

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	8.72E 04	3632	0	
					TEMPCYC			-065C 150C			3632	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			3632	0	
								1 MIN E					
					FINE LK			HE 5.E-7			3632	15	1894
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			3632	11	1895
								3X					
								90PSIG					
					FNCT EM			085C			3606	177	
	B-1				REVBIAS	BRN	2/78	125C	N/R	4.74E 05	2820	0	
					S&F EM			85C			2820	24	
					STAT EM			- 35C			2820	17	
					FNCT EM			25C			2820	21	
					VIS INS						2820	2	

NITRON — CUSTOM

P-STAT — MOS — NUMBER OF GATES 826

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	3.07E 05	12809	0	
					TEMPCYC			-065C 150C			12809	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			12809	0	
								1 MIN E					
					FINE LK			HE 5.E-7			12809	93	1892
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			12809	47	1893
								3X					
								90PSIG					
					FNCT EM			085C			12669	999	
					N/R						0	67	
	B-1				REVBIAS	BRN	2/78	125C	N/R	4.41E 06	26265	0	
					S&F EM			85C			26265	82	
					STAT EM			- 35C			26265	30	
					FNCT EM			25C			26265	153	
					VIS INS						26265	67	
					REVBIAS	BRN	2/78	125C	N/R	2.30E 04	137	0	
					S&F EM			85C			137	4	
					STAT EM			- 35C			137	1	
					FNCT EM			25C			137	3	
					VIS INS						137	2	
	C-1				OPERATE	CHECK	4/78	125C	GT	6.95E 04	894	1	

HUGHES — CUSTOM

P-DYN — MOS — NUMBER OF GATES 105

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHDIP	14	C	N/R	FIELD	12/75	45C	AIT	2.22E 04	0	36	

HUGHES — CUSTOM

P-DYN — MOS — NUMBER OF GATES 200

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHDIP	32	C	N/R	FIELD	12/75	45C	AIT	2.22E 04	0	45	
N/R		NHFPK	28	M	N/R	FIELD	3/78	32C	AIT	4.68E 05	18	1	

MOSTEK — DECADE

P-DYN — MOS — NUMBER OF GATES 2000

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
5007	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.98E 07	5846	28	
					N/R	FIELD	5/78	40C	GBC	2.02E 07	15522	38	
					N/R	FIELD	4/79	40C	GBC	2.17E 07	16658	48	
5007	D	NHDIP	16	C	N/R	FIELD	4/80	40C	GBC	1.53E 07	11749	20	
					N/R	FIELD	4/81	40C	GBC	2.46E 07	9468	21	

HUGHES — DECODER

P-DYN — MOS — NUMBER OF GATES 150

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHDIP	18	C	N/R	FIELD	12/75	45C	AIT	2.22E 04	0	106	

MOTOROLA SEMI — DECODER/DEMULTIPLX

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7814	X	NHFPK	40	C	PAR EXC	LIFE	2/75	125C	N/R	7.78E 05	72	5	
					EM						67	0	

MOSTEK — DECODER/DRIVER

P-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
50399	D-1	HDIP	28	N/R	N/R	FIELD	4/80	40C	GBC	5.07E 04	39	0	
					N/R	FIELD	4/81	40C	GBC	4.95E 06	1904	0	

HUGHES — ENCODER

P-DYN — MOS — NUMBER OF GATES 265

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHDIP	24	C	N/R	FIELD	12/75	45C	AIT	2.22E 04	0	105	

MOTOROLA SEMI | GENERATOR

SCHOTTKY RTL | BIPOLAR | NUMBER OF GATES 160

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8503	D-1	HDIP	14	C	TEMPCYC	ENV	2/75	-065C 150C	N/R		20	0	
								8500CY					
					EM						20	0	
					THRMSHK	ENV	2/75	-065C 150C	N/R		23	0	
								6500CY					
					EM						23	0	
					REVBIAS	LIFE	2/75	125C	N/R	2.22E 04	22	0	
					EM						22	0	
8503	D	NHDIP	14	C	VIS INS	ENV	2/75	10X	N/R		148	0	
								20X					
					SOLDER	ENV	2/75	260C 95%	N/R		390	1	
								5 SEC					
					EM						389	0	
					LEADFTG	ENV	2/75	8 OZ 90DEGS	N/R		191	0	
								3 ARCS					
					FINE LK			HE 5.E-8			191	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			191	0	
								3X					
								90PSIG					
					THRMSHK	ENV	2/75	-055C 125C	N/R		141	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			141	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			141	0	
								98%RH					
					FINE LK			HE 5.E-8			141	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			141	0	
								3X					
								90PSIG					
					EM						141	0	
					MECHSHK	ENV	2/75	1.5KG .5MSEC	N/R		141	0	
								6 AXES					
								5 BLOS					
					VIBVRFQ			20HZ 2KHZ			141	0	
								20G					
								3 AXES					
					CNSTACC			30KG 6 AXES			141	0	
								1 MIN E					
					FINE LK			HE 5.E-8			141	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			141	0	
								3X					
								90PSIG					
					EM						141	0	
					SALTATM	ENV	2/75	035C 25GMS	N/R		92	0	
								MSQ					
								24 HRS					
					EM						92	0	
					THRMSHK	ENV	2/75	-055C 125C	N/R		50	0	
								10CY					
								LIQUID					
					FINE LK			HE 5.E-8			50	2	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			50	0	
								3X					
								90PSIG					

NATIONAL SEMI — GENERATOR

SCHOTTKY RTL — BIPOLAR — NUMBER OF GATES 160

PART NO.	SCR. CLS	PKG	#PIN	TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFER #
8503	D	NHD1P	16	AS INS	ENV	2/75	10X	N/R		38	0	
							20X					
				SOLDER	ENV	2/75	260C 95%	N/R		22	0	
							5 SEC					
				EM						22	0	
				LEADFTG	ENV	2/75	8 OZ 90DEGS	N/R		38	0	
							3 ARCS					
				FINE LK			HE 5.E-8			38	0	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			38	0	
							3X					
							90PSIG					
				THRMSHK	ENV	2/75	-055C 125C	N/R		38	0	
							15CY					
							LIQUID					
				TEMPCYC			-055C 150C			38	0	
							10CY					
							10/10DT					
				MOIST			-010C 065C			38	0	
							98%RH					
				FINE LK			HE 5.E-8			38	0	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			38	0	
							3X					
							90PSIG					
				EM						38	0	
				MECHSHK	ENV	2/75	1.5KG .5MSEC	N/R		38	0	
							6 AXES					
							5 BLOS					
				VBVRFQ			20HZ 2KHZ			38	0	
							20G					
							3 AXES					
				CNSTACC			30KG 6 AXES			38	0	
							1 MIN E					
				FINE LK			HE 5.E-8			38	1	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			38	0	
							3X					
							90PSIG					
				EM						38	0	
				SALTATM	ENV	2/75	035C 25GMS	N/R		38	0	
							MSQ					
							24 HRS					
				EM						38	0	
				THRMSHK	ENV	2/75	-055C 125C	N/R		38	0	
							3000CY					
							LIQUID					
				FINE LK			HE 5.E-8			38	0	
							60 MIN					
							30 MIN					
				GROSSLK			FLUOR 125C			38	0	
							3X					
							90PSIG					

FAIRCHILD SEMI — GENERATOR

SCHOTTKY I IL — BIPOLAR — NUMBER OF GATES 114

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9401	D-1	HDIP	14	N/R	OP CNST	LIFE	12/76	125C	N/R	4.60E 04	46	0	
					EM						46	0	
					OP CNST	BRN	12/76	100C	N/R	8.06E 03	48	0	
					EM						48	0	
					VIS INS	EBRN	9/76		N/R		50	0	
					S&F EM			025C 070C			50	0	
					THRMSHK			000C 100C			50	0	
								15CY					
								LIQUID					
					REVBIAS			125C		8.40E 03	50	0	
					S&F EM			070C			50	0	
					VIS INS	EBRN	10/76		N/R		150	0	
					S&F EM			025C 070C			150	0	
					THRMSHK			000C 100C			150	0	
								15CY					
								LIQUID					
					REVBIAS			125C		2.52E 04	150	0	
					S&F EM			070C			150	1	
					VIS INS	EBRN	12/76		N/R		150	0	
					S&F EM			025C 070C			150	0	
					THRMSHK			000C 100C			150	0	
								15CY					
								LIQUID					
					REVBIAS			125C		2.52E 04	150	0	
					S&F EM			070C			150	0	
					OP CNST	LIFE	5/79	100C	N/R	7.50E 04	75	0	
					EM						75	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		40	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			40	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			40	0	
								98%RH					
					FINE LK			HE 5.E-8			40	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			40	0	
								3X					
								60PSIG					
					EM						40	0	
					THRMSHK	ENV	8/79	-055C 125C	N/R		40	0	
								1000CY					
								LIQUID					
					FINE LK			HE 5.E-8			40	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			40	0	
								3X					
								60PSIG					
					EM						40	0	
					OP CNST	LIFE	12/79	100C	N/R	7.50E 04	75	0	
					EM						75	0	
					OP CNST	LIFE	12/79	100C	N/R	1.46E 05	97	0	
					EM						97	0	
					VIS INS	EBRN	3/78		N/R		3296	0	
					TEMPCYC			-055C 125C			3296	0	
								10CY					
					REVBIAS			125C		5.27E 05	3296	0	
					S&F EM			070C			3296	87	2486
													2487
9401	D	NHDIP	14	N/R	OP CNST	LIFE	5/78	125C	N/R	4.80E 04	48	0	
					EM						48	0	
					OP CNST	LIFE	5/78	125C	N/R	8.00E 04	80	0	
					EM						80	0	
					TEMPCYC	ENV	5/78	-065C 150C	N/R		29	0	
								10CY					
								10/10DT					

FAIRCHILD SEMI — GENERATOR

SCHOTTKY IIL — BIPOLAR — NUMBER OF GATES 114

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	NREF #
9401	D	NHDIP	14	N/R	CNSTACC	ENV	5/78	30KG 1 AXIS	N/R		29	0	
								1 MIN E					
					FINE LK			HE 5.E-8			29	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			28	0	
								3X					
								90PSIG					
					EM						28	0	
					TEMPCYC	ENV	5/78	-065C 150C	N/R		35	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 1 AXIS			35	0	
								1 MIN E					
					FINE LK			HE 5.E-8			35	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			35	0	
								3X					
								90PSIG					
					EM						35	0	
					TEMPCYC	ENV	5/78	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					CNSTACC			30KG 1 AXIS			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM						25	0	
					MECHSHK	ENV	5/78	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXIS					
					CNSTACC			30KG 1 AXIS			25	0	
								1 MIN E					
					FINE LK			HE 5.E-8			25	1	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			24	0	
								3X					
								90PSIG					
					EM						24	0	
					THRMSHK	ENV	5/78	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM						25	0	
					OP CNST	LIFE	5/79	125C	N/R	4.80E 04	48	0	
					EM						48	0	

NITRON — GENERATOR

P-STAT — MOS — NUMBER OF GATES 1079

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	7.72E 04	3217	0	
					TEMPCYC			-065C 150C			3217	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			3217	0	
								1 MIN E					
					FINE LK			HE 5.E-7			3217	6	1907
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			3217	15	1908
								3X					
								90PSIG					
					FNCT EM			085C			3196	243	
	B-1				REVBIAS	BRN	2/78	125C	N/R	4.29E 05	2553	0	
					S&F EM			85C			2553	25	
					STAT EM			- 35C			2553	18	
					FNCT EM			25C			2553	27	
					VIS INS						2553	12	
	C-1				OPERATE	CHECK	4/78	125C	GT	6.95E 04	894	0	

RCA — GENERATOR

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
6993	B-2	NHDIP	24	N/R	TCVPC	RELDEM	6/79	-065C 160C	AIF		8	0	
								126CY					

FAIRCHILD SEMI — IMAGE SENSING

CCD — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
221	D-1	HDIP	22	N/R	TCVPC	RELDEM	6/79	-065C 160C	AIF	3.90E 03	0	11	3182
								126CY					

MOTOROLA SEMI — LATCH

CMOS — MOS — NUMBER OF GATES 102

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MTBF #
14515	D-1	HDIP	24	I	N/R	FIELD	5/77	40C	GBC	3.76E 05	89	0	
					N/R	FIELD	4/79	40C	GBC	1.17E 04	9	0	
					N/R	FIELD	4/80	40C	GBC	8.06E 04	62	0	
					N/R	FIELD	4/81	40C	GBC	4.65E 05	179	0	

RCA — LATCH

CMOS — MOS — NUMBER OF GATES 102

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4515B	D	NHFPK	24	M	STAT EM	EBRN	9/77	025C	N/R		3	0	
					BAKE			125C		1.44E 02	3	0	
					TEMPCYC			-065C 125C			3	0	
								10CY					
								15/15DT					
					HERMETC						3	0	
					STAT EM			025C			3	0	
					BURN-IN			125C		7.20E 02	3	0	
					DYN EM			025C			3	0	
					X-RAY						3	0	
					VIS INS						3	0	
	S-1				STAT EM	EBRN	9/77	025C	N/R		5	0	
					BAKE			125C		2.40E 02	5	0	
					TEMPCYC			-065C 125C			5	0	
								10CY					
								15/15DT					
					HERMETC						5	0	
					STAT EM			025C			5	0	
					BURN-IN			125C		1.20E 03	5	0	
					DYN EM			025C			5	0	
					X-RAY						5	0	
					VIS INS						5	0	
	S-2				STAT EM	EBRN	9/77	025C	N/R		10	0	
					BAKE			125C		4.80E 02	10	0	
					TEMPCYC			-065C 125C			10	0	
								10CY					
								15/15DT					
					HERMETC						10	0	
					STAT EM			025C			10	0	
					BURN-IN			125C		2.40E 03	10	0	
					DYN EM			025C			10	0	
					X-RAY						10	4	
					VIS INS						6	1	

MOTOROLA SEMI — LATCH

CMOS — MOS — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
14515B	D	NHDIP	24	I	N/R	FIELD	6/78		GF		14	0	
					N/R	FIELD	6/78		GF	2.04E 04	2	0	

WESTERN DIGITAL — LINE RECEIVER

P-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1472	D-1	HDIP	40	C	VIS INS	EBRN	12/76		N/R		54	0	
					S&F EM			025C 070C			54	0	
					THRMSHK			000C 100C			54	0	
								15CY					
								LIQUID					
					REVBIAS			125C		9.07E 03	54	0	

WESTERN DIGITAL — LINE RECEIVER

P-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1472	D-1	HDIP	40	C	S&F EM	EBRN	12/76	070C	N/R		54	1	

MONOLITHIC MEMORIES — LOGIC ARRAY

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 121

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
HAL16R4	D	NHDIP	20	C	PAR EXC	LIFE	10/81	125C	N/R	1.35E 05	135	0	
HAL16R4	D-1	HDIP	20	N/R	PAR EXC	LIFE	10/81	125C	N/R	1.15E 05	90	0	

SIGNETICS — MICROPROCESSOR

TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3002	D-1	HDIP	28	C	OP DYN	LIFE	11/77	85C	N/R	6.40E 04	63	0	
					EM						63	1	
					STGLIFE	LIFE	11/77	150C	N/R	4.60E 04	46	0	
					EM						46	0	

TEXAS INSTRUMENTS — MICROPROCESSOR

IIL — BIPOLAR — NUMBER OF GATES 3100

PART NO.	SCR. CLS	PKG	#PINS	TMP:RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9900	D	NHDIP	64	I	OP LIFE	LIFE	6/77	125C	N/R	2.00E 04	20	0	
					EM						20	0	
					OP LIFE	LIFE	6/77	85C	N/R	1.00E 04	10	0	
					EM						10	0	
					STGLIFE	LIFE	6/77	150C	N/R	2.20E 04	22	0	
					EM						22	0	
					OP LIFE	LIFE	6/78	125C	N/R	1.18E 05	59	1	
					EM						58	0	
					STGLIFE	LIFE	6/78	150C	N/R	8.80E 04	44	1	
					EM						43	1	

ADVANCED MICRO DEVICES — MICROPROCESSOR

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 542

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2901A	X	NHDIP	40	N	OP DYN	LIFE	3/78	- 55C	N/R	2.00E 03	4	0	
					OP DYN	LIFE	3/78	125C	N/R	2.00E 03	4	0	
	B-2				REVBIAS	LIFE	6/80	125C	N/R	2.52E 05	252	0	
					EN			125C			252	0	

INTEL — MICROPROCESSOR

P-DYN — NOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8008	B-1	NHDIP	18	N/R	OPERATE	RELDEM	9/75	004C 051C 18CY 95%	GT	2.94E 03	7	0	
					OPERATE	RELDEM	10/75	004C 051C 16CY 95%	GT	2.71E 03	7	0	
					OPERATE	RELDEM	10/75	004C 051C 24CY 95%	GT	5.66E 02	1	0	
					OPERATE	RELDEM	10/75	004C 051C 24CY 95%	GT	1.13E 03	2	0	
					OPERATE	RELDEM	9/75	004C 051C 18CY 95%	GT	8.40E 02	2	0	
					N/R	FIELD	7/76	25C	GT	4.07E 04	7	0	
					N/R	FIELD	7/76	25C	GT	6.25E 03	1	0	
					N/R	FIELD	7/76	25C	GT	3.30E 04	9	0	
					N/R	FIELD	7/76	25C	GT	7.26E 03	2	0	
					N/R	FIELD	7/76	25C	GT	8.15E 03	2	0	
					N/R	RELDEM	7/78	025C	GT	1.06E 03	3	0	
8008	D	NHDIP	18	C	OP DYN	LIFE	1/75	70C	N/R	9.30E 05	930	1	
8008		NHDIP	18	N/R	OP DYN	LIFE	5/75	125C	N/R	2.20E 04	22	0	
					STAT EN						22	0	
					OP CNST	LIFE	5/75	125C	N/R	2.20E 04	22	1	
					STAT EM						21	0	
					FINE LK	ENV	5/75		N/R		21	0	
					GROSSLK						21	1	
					MECHSHK						21	0	
					VBVRFQ						21	0	
					VIB FTG						21	0	
					FINE LK						21	0	
					GROSSLK						21	1	
					FINE LK	ENV	5/75		N/R		21	0	
					GROSSLK						21	0	
					TEMPCYC						21	0	
					THRMSHK						21	0	
					FINE LK						21	0	
					GROSSLK						21	0	
8008	NONE	DIP	18	C	N/R	FIELD	10/77	30C	GF	5.00E 05	0	0	
8008-1	D	NHDIP	18	C	N/R	FIELD	5/77	40C	GBC	1.09E 05	37	0	
					N/R	FIELD	5/78	40C	GBC	1.76E 05	135	0	
					N/R	FIELD	4/79	40C	GBC	2.39E 05	184	0	
					N/R	FIELD	4/80	40C	GBC	2.64E 05	203	0	
					N/R	FIELD	4/81	40C	GBC	7.25E 05	279	0	

INTEL — MICROPROCESSOR

P-DYN — MOS — NUMBER OF GATES 759

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4004	D	NHDIP	16	C	OP DYN	LIFE	1/75	70C	N/R	9.30E 05	930	1	
					N/R	FIELD	1/77	25C	GF	1.75E 07	1200	13	
					N/R	FIELD	6/77	25C	GF	8.00E 04	13	1	
	NONE				N/R	FIELD	6/77	25C	GF	1.75E 07	1200	12	
					N/R	FIELD	12/77	25C	GF	3.31E 07	2400	21	
4004		DIP	16	N/R	N/R	FIELD	6/77	25C	GF	1.47E 06	1350	4	

MOSTEK — MICROPROCESSOR

N-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3872	D-1	HDIP	40	C	N/R	FIELD	4/81	40C	GBC	2.11E 05	81	0	

ADVANCED MICRO DEVICES — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9080	B-2	NHDIP	40	M	PAR EXC	LIFE	6/80	125C	N/R	1.50E 04	15	0	
					EN			125C			15	0	

GENERAL INSTRUMENTS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1600	D	NHDIP	40	C	OP CNST	LIFE	8/77	110C	N/R	1.21E 04	18	0	
					S&F EM						18	0	

INTEL — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8035L	D-1	HDIP	40	C	N/R	FIELD	4/80	40C	GBC	5.07E 04	39	0	
					N/R	FIELD	4/81	40C	GBC	1.74E 06	670	0	

INTEL

MICROPROCESSOR

N-DYN

MOS

NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8039	D-1	HDIP	40	C	N/R	FIELD	4/81	40C	GBC	6.01E 05	231	0	
8086	D	NHDIP	40	C	BURN-IN	BRN	6/80		N/R	4.39E 05	9136	0	
					EM						9136	20	3120
					OP DYN	LIFE	6/80	125C	N/R		311	2	3148
													3149
					EM						309	0	
					OP DYN	LIFE	6/80	125C	N/R	4.83E 05	242	1	3150
					EM						241	0	
					BAKE	BRN	6/80	250C	N/R	1.51E 04	90	0	
					EM						90	0	
					BAKE	BRN	6/80	250C	N/R	1.49E 03	31	0	
					EM						31	0	
					TEMPCYC	ENV	6/80	-055C 150C 200 CY	N/R		175	0	
					EM						175	1	
8088		NHDIP	40	C	BURN-IN	BRN	6/79		N/R	5.44E 04	1134	0	
					EM						1134	4	
					OP DYN	LIFE	6/79	125C	N/R	3.50E 04	35	0	
					EM						35	1	
					OP DYN	LIFE	6/79	125C	N/R	2.23E 04	46	2	
					EM						44	0	
8748		NHDIP	40	I	BURN-IN	BRN	2/80		N/R	1.13E 05	2352	0	
					EM						2352	6	3124
													3125
													3126
													3127
					OP DYN	LIFE	2/80	125C	N/R	3.79E 05	379	1	3155
					EM						378	1	3156
					OP DYN	BRN	2/80	125C	N/R	1.36E 05	812	0	3157
					EM						812	3	3158
													3159
8748		NHDIP	40	I	BURN-IN	BRN	2/80		N/R	6.29E 03	131	0	
					EM						131	0	
					OP DYN	LIFE	2/80	125C	N/R	1.31E 05	131	0	
					EM						131	0	

MOS TECHNOLOGY

MICROPROCESSOR

N-DYN

MOS

NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6502	D	NHDIP	40	C	OP DYN	BRN	3/76	125C	N/R	1.44E 02	6	0	
					OP DYN	BRN	3/76	125C	N/R	3.84E 02	16	1	

MOSTEK

MICROPROCESSOR

N-DYN

MOS

NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3870	D	NHDIP	40	C	N/R	FIELD	4/79	25C	GB	2.39E 05	12	0	
					OP DYN	LIFE	4/79	125C	N/R	3.26E 05	558	5	
					EM						119	0	

MOSTEK — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:3870	:D	:NHDIP	40	:C	: THRMSHK	: ENV	: 4/79	:-055C 125C	: N/R	:	: 40	: 0	:
								:100CY					
								:LIQUID					
					: EM			:			: 40	: 0	:
					: STGLIFE	: ENV	: 4/79	:150C	: N/R	: 9.60E 03	: 100	: 0	:
					: EM			:			: 100	: 0	:
					: TEMPCYC	: ENV	: 4/79	:-065C 150C	: N/R	:	: 50	: 1	:
								:1000CYC					
								:10/10DT					
					: EM			:			: 49	: 1	:
:3870	:D-1	:HDIP	40	:C	: OP DYN	: LIFE	: 4/79	: 125C	: N/R	: 2.78E 05	: 524	: 6	:
					: EM			:			: 120	: 0	:
					: N/R	: FIELD	: 4/80	: 40C	: GBC	: 1.09E 06	: 842	: 1	:
					: N/R	: FIELD	: 4/81	: 40C	: GBC	: 6.29E 05	: 242	: 0	:

MOTOROLA SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:3870	:D-1	:HDIP	40	:C	: N/R	: FIELD	: 4/79	: 40C	: GBC	: 7.18E 05	: 552	: 1	:
:6801	:	:HDIP	40	:C	: N/R	: FIELD	: 4/81	: 40C	: GBC	: 1.48E 06	: 568	: 1	:

SIGNETICS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2650	:D	:NHDIP	40	:C	: OP DYN	: LIFE	: 2/76	: 85C	: N/R	: 9.00E 04	: 45	: 0	:
					: OP DYN	: LIFE	: 11/77	: 85C	: N/R	: 9.00E 04	: 45	: 0	:
					: EM			:			: 45	: 0	:
					: OP DYN	: LIFE	: 11/77	: 125C	: N/R	: 3.49E 05	: 45	: 0	:
					: EM			:			: 45	: 4	:
					: OP DYN	: LIFE	: 11/77	: 125C	: N/R	: 4.50E 04	: 45	: 0	:
					: EM			:			: 45	: 1	:

VARIOUS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:3850/3851	:D-1	:HDIP	4	:C	: N/R	: FIELD	: 11/77	: 25C	: GF	: 9.00E 04	: 6	: 0	:
:3870	:	:HDIP	40	:C	: N/R	: FIELD	: 4/79	: 40C	: GBC	: 8.29E 05	: 638	: 0	:
					: N/R	: FIELD	: 4/80	: 40C	: GBC	: 6.53E 06	: 5020	: 12	:
					: N/R	: FIELD	: 4/81	: 40C	: GBC	: 2.12E 07	: 8147	: 12	:

VARIOUS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6800	D	NHDIP	40	C	N/R	FIELD	4/80	40C	GBC	1.16E 07	8909	2	
					N/R	FIELD	4/81	40C	GBC	2.72E 07	10459	8	
8080		NHDIP	40	C	VIS INS	EBRN	11/76		N/R		90	0	
					S&F EM			025C 070C			90	0	
					TEMPCYC			-055C 125C			90	0	
								5CY					
								10/10DT					
					REVBIAS			125C		1.51E 04	90	0	
					S&F EM			070C			90	0	
					VIS INS	EBRN	3/78		N/R		3576	0	
					TEMPCYC			-055C 125C			3576	0	
								10CY					
					REVBIAS			125C		5.72E 05	3576	0	
					S&F EM			025C			3576	71	2496
													2497
	B-2				N/R	FIELD	5/77		AIT	1.02E 03	3	0	
9900	D	NHDIP	64	C	N/R	FIELD	4/80	40C	GBC	1.14E 05	88	0	
					N/R	FIELD	4/81	40C	GBC	2.67E 06	1028	0	

ZILOG — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8002	NONE	DIP	40	C	OP CNST	LIFE	7/80	125C	N/R	7.60E 04	38	0	
					OP CNST	LIFE	7/80	125C	N/R	6.00E 04	40	0	

ADVANCED MICRO DEVICES — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9080A	D	NHDIP	40	C	N/R	FIELD	5/78	40C	GBC	5.98E 04	46	0	
					N/R	FIELD	4/79	40C	GBC	1.43E 06	1102	0	
					N/R	FIELD	4/80	40C	GBC	2.51E 06	1934	1	
					N/R	FIELD	4/81	40C	GBC	4.63E 06	1781	3	
9080A	B-1	NHDIP	40	M	OP LIFE	LIFE	10/80	125C	N/R	3.00E 04	30	0	
					EM			25C			30	0	
					VIS INS	ENV	10/80	80X	N/R		1	0	
					VIS INS						3	0	
					BONDSTR			5GMS 2BDS			10	0	
					SOLDER			260C 95%			3	0	
								5 SEC					
					OP LIFE	LIFE	10/80	125C	N/R	7.70E 04	77	0	
					EM			25C			77	0	
					TEMPCYC	ENV	10/80	-065C 150C	N/R		25	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					

ADVANCED MICRO DEVICES — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9080A	B-1	NHDIP	40	M	GROSSLK	ENV	10/80	FLUOR 125C	N/R		25	0	
								3X					
								90PSIG					
					VIS INS			3X			25	0	
								10X					
					EM			025C			25	1	3469
					LEADFTG	ENV	10/80	8 OZ 90DEGS	N/R		15	0	
								3 ARCS					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								90PSIG					
					THRMSHK	ENV	10/80	-055C 125C	N/R		25	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			25	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			25	0	
								98%RH					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM			025C			25	5	3470
					MECHSHK	ENV	10/80	1.5KG .5MSEC	N/R		25	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			25	0	
								20G					
								3 AXES					
					FINE LK			HE 5.E-8			25	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			25	0	
								3X					
								90PSIG					
					EM			025C			25	0	
	NONE				CNSTACC	LIFE	10/80		N/R		263	0	
					FINE LK						263	0	
					GROSSLK						263	2	3472
					FNCT EM			25C			261	2	3473
					STAT EM			25C			259	0	
					DYN EM			25C			259	0	
					REVBIAS			125C		4.35E 04	259	0	
					S&F EM			25C			259	0	
					S&F EM			125C			259	0	
					S&F EM			-55C			259	0	
					DYN EM			25C			259	0	
					DYN EM			125C			259	0	

NATIONAL SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	B-1	NHDIP	40	C	OP LIFE	LIFE	10/80	125C	N/R	3.00E 04	30	0	

NATIONAL SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	B-1	NHDIP	[illegible]	[illegible]C	[illegible]	LIFE	10/80	25C	N/R		30	0	

SIGNETICS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	B-1	NHDIP	40	C	OP LIFE	LIFE	10/80	125C	N/R	3.00E 04	30	0	
					EM			25C			30	0	

TEXAS INSTRUMENTS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	B-1	NHDIP	40	C	OP LIFE	LIFE	10/80	125C	N/R	3.00E 04	30	0	
					EM			25C			30	0	

VARIOUS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080/9080	D-1	HDIP	40	C	N/R	FIELD	5/77	40C	GBC	1.50E 05	109	1	
					N/R	FIELD	5/78	40C	GBC	1.43E 06	1103	2	
					N/R	FIELD	4/79	40C	GBC	6.53E 06	5022	6	
					N/R	FIELD	4/80	40C	GBC	9.85E 06	7574	21	
					N/R	FIELD	4/81	40C	GBC	1.48E 07	5708	8	

MOTOROLA SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1300

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
MC6800/A00/B:D		NHDIP	40	C	OP DYN	LIFE	3/75	137C	N/R	5.62E 03	0	0	
					OP DYN	LIFE	3/75	124C	N/R	1.87E 04	0	1	
					OPERATE	CHECK	2/77	025C	N/R	4.00E 03	2	0	

MOTOROLA SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1300

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
MC6800/A00/B	D	NHDIP	40	C	OPERATE	CHECK	2/77	025C	N/R	3.20E 04	4	0	
					OPERATE	CHECK	2/77	025C	N/R	1.50E 03	1	0	
					N/R	FIELD	6/77	30C	GBC	6.60E 06	13200	3	
					N/R	FIELD	5/77	40C	GBC	1.11E 06	293	0	
					S&D EM	LIFE	/77	25C	N/R		15	0	
					OP DYN			70C		3.42E 04	15	0	
					S&D EM			25C			15	0	
					OP DYN	LIFE	4/78	125C	N/R	2.48E 05	257	0	
					SDF EM						257	2	
					N/R	FIELD	5/76	40C	GBC	9.05E 05	696	3	
					N/R	FIELD	4/79	40C	GBC	6.80E 06	5231	7	
					N/R	FIELD	4/80	40C	GBC	1.62E 04	14	0	
					N/R	FIELD	4/81	40C	GBC	1.18E 06	455	0	
6800/A00/B00	D-1	HDIP	40	C	OP DYN	LIFE	4/78	125C	N/R	1.62E 05	195	0	
					SDF EM						195	0	
					N/R	FIELD	5/78	40C	GBC	1.04E 04	8	0	
					N/R	FIELD	4/79	40C	GBC	4.95E 05	381	0	
					N/R	FIELD	4/80	40C	GBC	1.17E 06	901	0	
					N/R	FIELD	4/81	40C	GBC	3.79E 06	1456	0	
					N/R	FIELD	4/81	40C	GBC	1.85E 05	71	0	
6800/A00/B00	NONE	DIP	40	C	OP DYN	LIFE	11/77	125C	N/R	3.68E 05	411	0	
					EM						411	2	

INTEL — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1500

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
M8080A	B-1	NHDIP	40	M	TEMPCYC	RELDEM	11/77	000C 050C 16CY	NSS	1.51E 03	2	0	
8080A	D	NHDIP	40	C	OP DYN	LIFE	1/75	125C	N/R	9.80E 04	98	1	
					OP DYN	LIFE	1/75	125C	N/R	2.22E 05	74	0	
					OP DYN	LIFE	1/75	125C	N/R	2.68E 05	268	0	
					OP DYN	BRN	1/75	125C	N/R	2.40E 03	50	0	
					OP DYN	BRN	1/75	125C	N/R	1.15E 03	24	0	
					OP DYN	BRN	1/75	125C	N/R	1.15E 03	24	0	
					OP DYN	BRN	1/75	125C	N/R	8.16E 03	170	0	
					OP DYN	BRN	1/75	125C	N/R	1.15E 03	24	0	
					OP DYN	BRN	1/75	125C	N/R	1.16E 04	241	0	
					FNCT EM						241	1	
					OP DYN	BRN	1/75	125C	N/R	1.34E 04	280	0	
					FNCT EM						280	1	
					OP DYN	BRN	1/75	125C	N/R	8.59E 03	179	0	
					OP DYN	BRN	1/75	125C	N/R	1.15E 03	24	0	
					OP DYN	BRN	1/75	125C	N/R	1.34E 04	280	0	
					OP DYN	BRN	1/75	125C	N/R	1.34E 04	280	0	
					N/R	FIELD	6/77	25C	GF	6.60E 03	8	0	
					N/R	FIELD	12/77	25C	GBC	1.04E 04	1	0	
					N/R	FIELD	12/77	25C	GBC	8.98E 03	1	0	
					N/R	FIELD	12/77	25C	GBC	3.22E 03	1	0	
					OP DYN	BDLIFE	5/77	25C	N/R	2.47E 04	21	0	
					OP DYN	BDLIFE	5/77	55C	N/R	1.43E 04	21	0	
					OP DYN	BDLIFE	5/77	70C	N/R	2.00E 04	21	0	
8080A	NONE	DIP	40	C	N/R	FIELD	3/77	30C	GF	4.40E 06	1000	0	
					N/R	FIELD	8/77	25C	GF	1.40E 06	160	2	
8080A	D-1	HDIP	40	C	BURN-IN	BRN	6/80		N/R	2.92E 05	6073	0	
					EM						6073	13	
					OP DYN	LIFE	6/80	125C	N/R	9.07E 05	909	3	3153
													3154
					EM						906	0	
8080A	D	NHDIP	40	C	BURN-IN	BRN	6/80		N/R	4.75E 05	9892	0	

INTEL MICROPROCESSOR

N-DYN MOS NUMBER OF GATES 1500

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	D	MHDIP	40	C	EM	BRN	6/80		N/R		9892	11	
					OP DYN	LIFE	6/80	125C	N/R	1.24E 05	124	0	
					EM						124	0	
8080A		MHDIP	40	M	REVBIAS	LIFE	5/77	70C	N/R	5.06E 06	156	0	
					EM						156	4	
	B-1				OP LIFE	LIFE	10/80	125C	N/R	2.95E 04	30	1	3467
					EM			25C			29	0	
					VIS INS	LIFE	10/80		N/R		1	0	
					VIS INS						3	0	
					BONDSTR						10	0	
					SOLDER			260C			3	0	
					OP LIFE	LIFE	10/80	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
					TEMPCYC	ENV	10/80	-065C 150C	N/R		15	0	
								10CY					
								10/10DT					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								90PSIG					
					VIS INS			3X			15	0	
								10X					
					EM			025C			15	0	
					LEADFTG	ENV	10/80	8 OZ 90DEGS	N/R		15	0	
								3 ARCS					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								90PSIG					
					THRMSHK	ENV	10/80	-055C 125C	N/R		15	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			15	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			15	0	
								98%RH					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								90PSIG					
					EM			025C			15	0	
					MECHSHK	ENV	10/80	1.5KG .5MSEC	N/R		15	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			15	0	
								20G					
								3 AXES					
					FINE LK			HE 5.E-8			15	0	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			15	0	
								3X					
								90PSIG					
					EM			025C			15	0	
	NONE				CNSTACC	LIFE	10/80		N/R		93	0	
					FINE LK						93	0	
					GROSSLK						93	5	3477
					FNCT EM			25C			88	0	
					STAT EM			25C			88	0	
					DYN EM			25C			88	0	
					REVBIAS			125C		1.48E 04	88	0	
					S&F EM			25C			88	1	3478

INTEL — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 1500

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8080A	883C	CHDIP	40	M	S&F EN	LIFE	10/80	125C	N/R		87	0	
					S&F EN			-55C			87	0	
					DYN EN			25C			87	0	
					DYN EN			125C			87	0	
					DYN EN			-55C			87	0	
					VIS INS						87	0	

ADVANCED MICRO DEVICES — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 2067

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8085	B-2	CHDIP	40	M	PAR EXC	LIFE	6/80	125C	N/R	7.70E 04	77	0	
					EN			125C			77	0	

INTEL — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 2067

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8085	D	CHDIP	40	C	BURN-IN	BRN	6/80		N/R	3.14E 04	650	0	
					EN						650	0	
					OP DYN	LIFE	6/80	125C	N/R	8.30E 05	831	1	3151
					EN						830	0	
8085A	D-1	CHDIP	40	C	N/R	FIELD	4/79	40C	GBC	5.33E 0[illegible]	41	0	
					N/R	FIELD	4/80	40C	GBC	2.70E 06	2078	5	
					BURN-IN	BRN	6/80		N/R	2.27E 05	4732	0	
					EN						4732	3	3121
													3122
					OP DYN	LIFE	6/80	125C	N/R	1.30E 06	1305	1	3152
					EN						1304	0	
					N/R	FIELD	4/81	40C	GBC	1.27E 07	4870	6	

MOSTEK — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 2833

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3880	D	CHDIP	40	C	OP DYN	LIFE	2/77	125C	N/R	7.03E 04	142	1	
					EM						141	0	
					OP CNST	LIFE	2/77	125C	N/R	5.08E 04	30	2	
					EM						28	0	

VARIOUS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 2833

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3880/Z80CPU	D-1	HDIP	40	C	N/R	FIELD	4/80	40C	GBC	6.50E 04	50	0	
					N/R	FIELD	4/81	40C	GBC	6.92E 05	242	0	
					N/R	FIELD	4/81	40C	GBC	9.91E 05	381	2	

ZILOG — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 2833

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80CPU	D-1	HDIP	40	C	N/R	FIELD	5/78	25C	GBC	4.71E 06	1500	6	
Z80CPU	D	NHDIP	40	C	PAR EXC	LIFE	12/78	125C	N/R	1.95E 05	100	3	
					STAT EM			25C			97	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.52E 05	79	4	
					STAT EM			25C			75	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.26E 05	63	0	
					STAT EM			25C			63	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.36E 05	71	3	
					STAT EM			25C			68	0	
					PAR EXC	LIFE	12/78	125C	N/R	7.05E 04	37	4	
					STAT EM			25C			33	1	
					PAR EXC	LIFE	12/78	125C	N/R	1.00E 03	1	0	
					STAT EM			25C			1	0	
					PAR EXC	LIFE	12/78	125C	N/R	7.40E 04	37	0	
					STAT EM			25C			37	0	
					PAR EXC	LIFE	12/78	125C	N/R	5.02E 04	26	1	
					STAT EM			25C			25	0	
					PAR EXC	LIFE	12/78	125C	N/R	5.22E 04	26	1	
					STAT EM			25C			25	0	
					PAR EXC	LIFE	3/80	125C	N/R	1.10E 06	548	0	
					EM						548	3	2397
Z80CPU	D-1	HDIP	40	C	PAR EXC	LIFE	12/78	125C	N/R	9.57E 04	51	4	
					STAT EM			25C			47	0	
					PAR EXC	LIFE	12/78	125C	N/R	2.00E 03	2	0	
					STAT EM			25C			2	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.95E 05	100	3	
					STAT EM			25C			97	0	
					PAR EXC	LIFE	12/78	125C	N/R	5.02E 04	26	1	
					STAT EM			25C			25	0	
					PAR EXC	LIFE	12/78	125C	N/R	6.00E 03	12	0	
					STAT EM			25C			12	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.80E 04	98	0	
					STAT EM			25C			98	3	

MOTOROLA SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 3000

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6802	D	NHDIP	40	C	OP DYN	LIFE	4/78	125C	N/R	6.43E 04	94	0	
					SDF EM						94	2	
					N/R	FIELD	4/79	40C	GBC	2.44E 05	188	2	
					N/R	FIELD	4/80	40C	GBC	1.01E 06	774	1	
					N/R	FIELD	4/81	40C	GBC	2.35E 06	903	2	

MOTOROLA SEMI — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 3000

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:6802	:D-1	:HDIP	40	:C	OP DYN	LIFE	4/78	125C	N/R	7.90E 04	111	0	
					SDF EM						111	1	
					N/R	FIELD	4/80	40C	GBC	1.30E 03	1	0	
					N/R	FIELD	4/81	40C	GBC	4.01E 06	1544	7	

MOSTEK — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 3530

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:3850	:D	:NHDIP	40	:C	OP DYN	LIFE	2/77	125C	N/R	7.30E 04	107	2	
					EM						105	0	
					OP CNST	LIFE	2/77	125C	N/R	6.55E 03	40	0	
					EM						40	0	

VARIOUS — MICROPROCESSOR

N-DYN — MOS — NUMBER OF GATES 3530

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:3850	:D	:NHDIP	40	:C	N/R	FIELD	5/78	40C	GBC	6.15E 05	473	1	
					N/R	FIELD	4/79	40C	GBC	2.42E 06	1864	0	
					N/R	FIELD	4/80	40C	GBC	2.98E 06	2293	4	
					N/R	FIELD	4/81	40C	GBC	1.14E 07	4376	5	

HARRIS SEMI — MICROPROCESSOR

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:6100	:C-2	:NHDIP	40	:C	OP DYN	LIFE	9/76	70C	N/R	2.30E 04	23	1	
					OP DYN	LIFE	4/79	125C	N/R	2.20E 04	22	0	
:6100		:NHDIP	40	:M	OP DYN	BRN	7/79	125C	N/R	4.03E 03	24	0	
					EM						24	0	
					OP DYN	LIFE	7/79	125C	N/R	2.23E 04	12	0	
					EM						12	0	
					OP CNST	LIFE	7/79	70C	N/R	6.00E 04	60	0	
					EM						60	0	
:6100A		:NHDIP	40	:M	OP DYN	LIFE	9/76	125C	N/R	5.40E 04	34	0	

INTERSIL MICROPROCESSOR

CMOS MOS NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6100	D	MBDIP	40	N/R	OP CNST	LIFE	1/76	125C	N/R	5.04E 03	30	0	
					LM			25C			30	1	
					OP CNST			125C		9.63E 03	29	0	
					EM			25C			29	0	
					OP CNST			125C		1.45E 04	29	0	
					EM			25C			29	0	
					OP CNST			125C		2.90E 04	29	0	
					EM			25C			29	1	
					OP CNST	LIFE	6/79	125C	N/R	2.64E 05	73	0	
					EM			25C			73	1	

RCA MICROPROCESSOR

CMOS MOS NUMBER OF GATES 1375

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1802	D	NHDIP	40	M	OP DYN	LIFE	12/77	125C	N/R	7.08E 03	11	4	
					FNCT EM						7	6	
					OP DYN	LIFE	12/77	125C	N/R	5.91E 03	13	11	
					FNCT EM						2	2	
					OP DYN	LIFE	12/77	125C	N/R	7.96E 03	10	3	
					FNCT EM						7	4	
					OP DYN	LIFE	12/77	125C	N/R	9.36E 03	9	0	
					FNCT EM						9	0	
	B-2				OP DYN	BRN	12/77	125C	N/R	4.56E 03	24	0	
					FNCT EM						24	17	
					OP DYN	BRN	12/77	125C	N/R	3.76E 03	21	0	
					FNCT EM						21	8	
					OP DYN	BRN	12/77	125C	N/R	8.40E 02	5	0	
					FNCT EM						5	1	
					OP DYN	BRN	12/77	125C	N/R	1.85E 03	11	0	
					FNCT EM						11	11	
					OP DYN	BRN	12/77	125C	N/R	8.02E 03	48	0	
					FNCT EM						48	14	
					OP DYN	BRN	12/77	125C	N/R	1.12E 04	48	0	
					FNCT EM						48	13	
					OP DYN	BRN	12/77	125C	N/R	3.84E 03	24	0	
					FNCT EM						24	5	
					OP DYN	BRN	12/77	125C	N/R	3.02E 03	18	0	
					FNCT EM						18	3	
					OP DYN	BRN	12/77	125C	N/R	3.34E 03	20	0	
					FNCT EM						20	4	
					OP DYN	BRN	12/77	125C	N/R	5.68E 03	34	0	
					FNCT EM						34	20	
					OP DYN	BRN	12/77	125C	N/R	2.86E 03	17	0	
					FNCT EM						17	9	
					OP DYN	LIFE	12/77	125C	N/R	1.33E 05	38	20	
					FNCT EM						18	16	
					OP DYN	LIFE	12/77	125C	N/R	6.05E 03	18	1	
					FNCT EM						17	8	
1802	D	NHDIP	40	M	OP DYN	LIFE	12/77	125C	N/R	4.53E 04	23	0	
					FNCT EM						23	0	
					OP DYN	LIFE	12/77	125C	N/R	1.78E 04	13	0	
					FNCT EM						13	0	
					OP DYN	LIFE	12/77	125C	N/R	5.62E 03	12	0	
					FNCT EM						12	0	
					OP DYN	LIFE	12/77	125C	N/R	1.62E 04	14	0	
					FNCT EM						14	0	
					OP DYN	LIFE	12/77	125C	N/R	2.85E 04	12	0	
					FNCT EM						12	0	
					OP DYN	LIFE	12/77	125C	N/R	3.86E 04	15	0	

RCA | MICROPROCESSOR

CMOS | MOS | NUMBER OF GATES 1375

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1802	D	NHDIP	40	M	FNCT EM	LIFE	12/77		N/R		15	0	
					OP DYN	LIFE	12/77	125C	N/R	4.84E 04	29	0	
					FNCT EM						29	1	
					OP DYN	BRN	12/77	125C	N/R	3.86E 03	23	0	
					FNCT EM						23	0	
					OP DYN	BRN	12/77	125C	N/R	2.35E 03	14	0	
					FNCT EM						14	1	
					OP DYN	BRN	12/77	125C	N/R	2.52E 03	15	0	
					FNCT EM						15	3	
					OP DYN	BRN	12/77	125C	N/R	3.27E 03	15	0	
					FNCT EM						15	1	
					OP DYN	BRN	12/77	125C	N/R	1.44E 04	90	0	
					FNCT EM						90	6	
					OP DYN	BRN	12/77	125C	N/R	2.40E 03	15	0	
					FNCT EM						15	3	
					OP DYN	BRN	12/77	125C	N/R	2.40E 03	15	0	
					FNCT EM						15	0	
					OP DYN	BRN	12/77	125C	N/R	5.55E 03	30	0	
					FNCT EM						30	1	
					N/R	FIELD	6/78		GF	7.14E 04	7	0	
					N/R	FIELD	6/78		GF	1.02E 04	1	0	
					N/R	FIELD	3/80		GF	1.11E 05	7	0	
					N/R	FIELD	3/80		GF	1.58E 04	1	0	
1802	B-2	NHCC	40	M	EM	EBRN	5/80	025C	N/R		24	0	
					BAKL			150C		5.76E 02	24	0	
					EM			025C			24	0	
					TEMPCYC			-065C 150C			24	0	
								10CY					
								10/10DT					
					EM			025C			24	0	
					FINE LK			HE 5.E-8			24	0	
								60 MIN					
								30 MIN					
					EM			025C			24	0	
					GROSSLK			FLUOR 125C			24	0	
								3X					
								90PSIG					
					EM			025C			24	0	
					MECHSHK			1.5KG .5MSEC			24	0	
								6 AXES					
								5 BLOS					
					EM			025C			24	0	
					THRMSHK			-055C 125C			24	0	
								15CY					
								LIQUID					
					EM			025C			24	0	
					CNSTACC			30KG 6 AXES			24	0	
								1 MIN E					
					EM			025C			24	3	3237
													3238
													3239

MOTOROLA SEMI | MODEM

N-DYN | MOS | NUMBER OF GATES 652

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6860	D	NHDIP	24	C	OP DYN	LIFE	3/75	76C	N/R	5.48E 04	0	1	
6860	D-1	HDIP	24	C	OP DYN	LIFE	3/75	75C	N/R	5.46E 03	0	0	

MOTOROLA SEMI — MODULATOR

N-DYN — MOS — NUMBER OF GATES 406

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6862	NONE	DIP	24	C	OP DYN	LIFE	11/77	125C	N/R	1.60E 05	170	0	
					EM						170	7	

HUGHES — MULTIPLEXER

P-DYN — MOS — NUMBER OF GATES 107

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHFPK	24	M	N/R	FIELD	3/78	32C	AIT	3.74E 06	144	2	

HUGHES — MULTIPLEXER

P-DYN — MOS — NUMBER OF GATES 170

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-2	NHFPK	32	M	N/R	FIELD	3/78	32C	AIT	4.68E 05	18	0	

MONOLITHIC MEMORIES — MULTIPLIER

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
57558	D	NHDIP	40	M	OP DYN	LIFE	1/79	125C	N/R	1.00E 05	50	0	
					EM			25C			50	0	
67558		NHDIP	40	C	OP DYN	LIFE	1/79	125C	N/R	4.50E 04	45	0	
					EM			25C			45	0	
					PAR EXC	LIFE	10/81	125C	N/R	8.70E 04	87	0	

TRW — MULTIPLIER

RAD HARDEN TTL — BIPOLAR — NUMBER OF GATES 295

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8AJ	D	NHDIP	40	C	ACCLFOD	LIFE	5/77	320C	N/R	7.85E 02	5	2	
					FNCT EM			25C			3	1	
					ACCLFOD	LIFE	5/77	290C	N/R	3.91E 03	12	4	
					FNCT EM			25C			8	2	

ADVANCED MICRO DEVICES — PERIPHERAL

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2909	B-2	NHFPK	28	M	REVBIAS	LIFE	6/80	125C	N/R	4.00E 04	40	0	
					EM			125C			40	0	

INTEL — PERIPHERAL

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8288	D	NHDIP	20	C	BURN-IN	BRN	7/80		N/R	2.94E 04	613	0	
					EM						613	2	3132
					OP DYN	LIFE	7/80	125C	N/R	6.11E 05	611	0	
					EM						611	1	3163
8289		NHDIP	20	C	BURN-IN	BRN	6/80		N/R	1.22E 05	2547	0	
					EM						2547	7	
					OP DYN	LIFE	6/80	125C	N/R	5.45E 04	109	0	
					EM						109	0	
					OP DYN	LIFE	6/80	125C	N/R	1.05E 05	105	0	
					EM						105	0	
8289	D-1	HDIP	20	C	BURN-IN	BRN	6/80		N/R	3.02E 04	630	0	
					EM						630	0	
					OP DYN	LIFE	6/80	125C	N/R	3.33E 05	334	2	3161
													3162
					EM						332	0	
					BAKE	LIFE	6/80	160C	N/R	1.00E 05	100	0	
					EM						100	0	
					TEMPCYC	ENV	6/80	-055C 150C 200 CY	N/R		100	0	
					EM						100	1	3180

VARIOUS — PERIPHERAL

N-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8243	D-1	HDIP	24	C	N/R	FIELD	4/81	40C	GBC	6.01E 05	231	0	

VARIOUS — PERIPHERAL

N-STAT — MOS — NUMBER OF GATES 1550

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3853	D-1	HDIP	40	C	N/R	FIELD	11/77	25C	GF	1.50E 04	3	0	
					N/R	FIELD	4/79	40C	GBC	1.77E 06	1364	0	
					N/R	FIELD	4/80	40C	GBC	4.02E 06	3091	1	
					N/R	FIELD	4/81	40C	GBC	1.47E 07	5655	1	

INTEL PERIPHERAL

N-DYN MOS NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
MD255	B-1	NHDIP	40	M	TEMPCYC	RELDLH	11/77	000C 050C 16CY	NSS	9.07E 03	12	0	
MD255A	D	NHDIP	40	M	OPERATE	CHECK	10/77	025C	GBC	8.80E 02	2	0	
					OP DYN	BDLIFE	5/77	25C	N/R	4.93E 04	42	0	
					OP DYN	BDLIFE	5/77	55C	N/R	2.86E 04	42	0	
					OP DYN	BDLIFE	5/77	70C	N/R	4.00E 04	42	0	
8255A		NHDIP	40	C	OP DYN	LIFE	6/80	125C	N/R	4.75E 04	48	1	3175
					EM						47	0	
					OP DYN	LIFE	6/80	125C	N/R	2.40E 04	48	0	
					EM						48	0	
8255A		NHDIP	40	C	BURN-IN	BRN	6/80		N/R	1.62E 04	337	0	
					EM						337	2	
					OP DYN	LIFE	6/80	125C	N/R	5.06E 05	506	0	
					EM						506	0	
8279		NHDIP	40	C	OP DYN	LIFE	2/80	125C	N/R	4.50E 04	90	0	
					EM						90	9	3166
					OP DYN	LIFE	2/80	125C	N/R	1.44E 05	144	0	
					EM						144	0	
					N/R	FIELD	4/81	40C	GBC	2.31E 05	89	0	
8279	D-1	HDIP	40	C	BURN-IN	BRN	2/80		N/R	1.01E 04	210	0	
					EM						210	0	
					OP DYN	LIFE	2/80	125C	N/R	4.34E 05	434	0	
					EM						434	1	3167

VARIOUS PERIPHERAL

N-DYN MOS NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3881/Z80PIO	D-1	HDIP	40	C	N/R	FIELD	4/80	40C	GBC	6.50E 04	50	0	
					N/R	FIELD	4/81	40C	GBC	6.29E 05	242	0	
6821	D	NHDIP	40	C	N/R	FIELD	4/80	40C	GBC	9.58E 06	7369	2	
					N/R	FIELD	4/81	40C	GBC	3.42E 07	13160	10	
8255		NHDIP	40	C	N/R	FIELD	5/78	40C	GBC	1.79E 05	138	0	
					N/R	FIELD	4/79	40C	GBC	4.30E 06	3306	0	
					N/R	FIELD	4/80	40C	GBC	5.26E 06	4047	5	
					N/R	FIELD	4/81	40C	GBC	1.06E 07	4058	0	

MOTOROLA SEMI PERIPHERAL

N-DYN MOS NUMBER OF GATES 350

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6820	D	NHDIP	40	C	OP DYN	LIFE	3/75	139C	N/R	5.38E 04	0	0	
					N/R	FIELD	5/77	40C	GBC	1.11E 06	293	1	
					OP DYN	LIFE	4/78	125C	N/R	9.31E 04	134	0	
					SDF EM						134	0	
					N/R	FIELD	5/78	40C	GBC	4.43E 05	341	1	
6820	NONE	DIP	40	C	OP DYN	LIFE	11/77	125C	N/R	1.09E 05	254	0	
					EM						254	2	

MOTOROLA SEMI — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 652

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6520	D-1	HDIP	40	C	OP DYN	LIFE	4/78	125C	N/R	3.09E 04	120	0	
					SDF EM						120	0	

ZILOG — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 900

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80PIO	D	NHDIP	40	C	PAR EXC	LIFE	12/78	125C	N/R	9.00E 04	45	0	
					STAT EM			25C			45	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.53E 04	50	3	
					STAT EM			25C			47	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.63E 04	50	2	
					STAT EM			25C			48	0	
					PAR EXC	LIFE	12/78	125C	N/R	3.80E 04	38	0	
					STAT EM			25C			38	0	
					PAR EXC	LIFE	3/80	125C	N/R	9.00E 04	45	0	
					EM						45	0	
Z80PIO	D-1	HDIP	40	C	PAR EXC	LIFE	12/78	125C	N/R	1.93E 05	100	4	
					STAT EM			25C			96	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.20E 04	47	1	
					STAT EM			25C			46	0	
					PAR EXC	LIFE	3/80	125C	N/R	8.95E 04	45	0	
					EM						45	0	

ZILOG — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 1400

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80CTC	D	NHDIP	28	C	PAR EXC	LIFE	12/78	125C	N/R	9.05E 04	46	1	
					STAT EM			25C			45	0	
					PAR EXC	LIFE	12/78	125C	N/R	5.04E 02	3	0	
					STAT EM			25C			3	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.00E 03	1	0	
					STAT EM			25C			1	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.43E 04	49	2	
					STAT EM			25C			47	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.00E 03	1	0	
					STAT EM			25C			1	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.98E 05	99	0	
					STAT EM			25C			99	0	
					PAR EXC	LIFE	12/78	125C	N/R	5.00E 02	1	0	
					STAT EM			25C			1	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.08E 05	55	2	
					STAT EM			25C			53	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.70E 04	49	1	
					STAT EM			25C			48	0	
					PAR EXC	LIFE	12/78	125C	N/R	7.60E 04	38	0	
					STAT EM			25C			38	0	
					PAR EXC	LIFE	3/80	125C	N/R	1.57E 05	79	0	
					EM						79	0	
Z80CTC	D-1	HDIP	28	C	PAR EXC	LIFE	12/78	125C	N/R	7.50E 04	41	4	

ZILOG — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 1400

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80CTC	D-1	HDIP	28	C	STAT EM	LIFE	12/78	25C	N/R		37	0	
					PAR EXC	LIFE	12/78	125C	N/R	1.68E 02	1	0	
					STAT EM			25C			1	0	
					PAR EXC	LIFE	12/78	125C	N/R	3.00E 03	6	0	
					STAT EM			25C			6	0	
					PAR EXC	LIFE	12/78	125C	N/R	2.00E 03	2	0	
					STAT EM			25C			2	0	
					PAR EXC	LIFE	12/78	125C	N/R	9.06E 04	48	3	
					STAT EM			25C			45	3	
					PAR EXC	LIFE	12/78	125C	N/R	1.00E 03	1	0	
					STAT EM			25C			1	0	

VARIOUS — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 1423

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3861	D-1	HDIP	4	C	N/R	FIELD	11/77	25C	GF	1.50E 04	3	0	
					N/R	FIELD	4/79	40C	GBC	1.43E 04	11	0	
					N/R	FIELD	4/80	40C	GBC	4.32E 05	332	0	
					N/R	FIELD	4/81	40C	GBC	4.06E 06	1562	0	

ZILOG — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 3300

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
Z80SIO	D	NHDIP	40	C	PAR EXC	LIFE	3/80	125C	N/R	4.64E 05	233	0	
					EM						233	1	2398

MOTOROLA SEMI — PERIPHERAL

N-DYN — MOS — NUMBER OF GATES 5500

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6846	D	NHDIP	40	C	OP DYN	LIFE	4/78	125C	N/R	1.14E 05	114	0	
					SDF EM						114	2	

FAIRCHILD SEMI — PROCESSING UNIT

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3850/3851	B-1	NDIP	40	C	OP CNST	BBRN	7/77	25C	GP	8.64E 04	1800	0	
					EM						1800	67	
	X				N/R	FIELD	7/77		GP	4.27E 07	99999	462	
					N/R						20001	0	

MOSTEK — PROGRAM

N-DYN — MOS — NUMBER OF GATES 1623

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3851	D	NHDIP	40	C	OP DYN	LIFE	2/77	125C	N/R	2.52E 04	52	5	
					EM						47	0	
					OP CNST	LIFE	2/77	125C	N/R	6.38E 03	38	0	
					EM						38	0	

MONOLITHIC MEMORIES — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
10L8	D	NHDIP	20	C	OP DYN	LIFE	1/79	125C	N/R	4.80E 04	48	0	
					EM			25C			48	0	
					PAR EXC	LIFE	10/81	125C	N/R	2.29E 05	162	0	
16L8		NHDIP	20	N/R	PAR EXC	LIFE	10/81	125C	N/R	7.60E 04	76	0	
16R4		NHDIP	20	N/R	OP DYN	LIFE	1/79	125C	N/R	6.00E 04	60	0	
					EM			25C			60	0	
					PAR EXC	LIFE	10/81	125C	N/R	3.80E 04	38	0	
16R6		NHDIP	20	N/R	OP DYN	LIFE	1/79	125C	N/R	4.60E 04	23	0	
					EM			25C			23	0	

MONOLITHIC MEMORIES — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 114

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
PAL20X4	D	NHDIP	24	M	PAR EXC	LIFE	10/81	125C	N/R	4.40E 04	44	0	

VARIOUS — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 121

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
PAL16R4	NONE	DIP	20	N/R	N/R	FIELD	4/81	40C	GBC	9.91E 05	381	0	

MONOLITHIC MEMORIES — PROGRAMMABLE

SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 146

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
PAL16R6	D-1	HDIP	20	N/R	TEMPCYC	ENV	10/81	000C +100C 100CY	N/R		38	0	
					HIPRESS	LIFE	10/81	0C	N/R	6.38E 03	38	0	
PAL16R8	D	NHDIP	20	M	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	0	
PAL16R8		NHDIP	20	C	PAR EXC	LIFE	10/81	125C	N/R	4.50E 04	45	1	3694

INTEL — PROGRAMMABLE

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8237	D-1	HDIP	40	C	BURN-IN	BRN	6/80		N/R	3.65E 04	761	0	
					EM						761	2	
					OP DYN	LIFE	6/80	125C	N/R	1.75E 05	175	0	
					EM						175	0	
					OP DYN	LIFE	7/80	125C	N/R	2.21E 05	221	0	
					EM						221	0	
8237	D	NHDIP	40	C	BURN-IN	BRN	6/80		N/R	6.27E 04	1306	0	
					EM						1306	5	
					OP DYN	LIFE	6/80	125C	N/R	9.65E 04	97	1	3176
					EM						96	0	
8251A		NHDIP	28	C	BURN-IN	BRN	6/80		N/R	6.10E 04	1270	0	
					EM						1270	2	
8251A	D-1	HDIP	28	C	BURN-IN	BRN	6/80		N/R	2.96E 05	6177	0	
					EM						6177	12	
					OP DYN	LIFE	6/80	125C	N/R	4.78E 05	478	0	
					EM						478	0	
					OP DYN	BRN	6/80	125C	N/R	4.54E 03	27	0	
					EM						27	0	
					OP DYN	LIFE	6/80	125C	N/R	9.55E 04	191	0	
					EM						191	0	
8253	D	NHDIP	24	C	OP DYN	LIFE	2/80	125C	N/R	8.93E 04	180	2	
					EM						178	0	
					OP DYN	LIFE	2/80	125C	N/R	6.59E 05	665	10	
					EM						655	2	
8253	D-1	HDIP	24	C	N/R	FIELD	5/78	40C	GBC	5.98E 04	46	0	
					N/R	FIELD	4/79	40C	GBC	1.43E 06	1102	0	
					OP DYN	LIFE	2/80	125C	N/R	1.79E 05	181	3	
					EM						178	2	
8253	D	NHDIP	24	C	N/R	FIELD	4/80	40C	GBC	2.40E 06	1845	0	
					BURN-IN	BRN	2/80		N/R	9.22E 03	192	0	
					EM						192	0	
					OP DYN	LIFE	2/80	125C	N/R	9.60E 04	96	0	
					EM						96	0	
					OP DYN	LIFE	2/80	125C	N/R	4.80E 04	96	0	
					EM						96	0	

INTEL — PROGRAMMABLE

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:8253	:D	:NHDIP	24	:C	N/R	FIELD	4/81	40C	GBC	5.74E 06	2208	1	
:8257	:	:NHDIP	40	:C	BURN-IN	BRN	2/80		N/R	4.32E 03	90	0	
:	:	:	:	:	EM	:	:		:	:	90	2	3134
:	:	:	:	:	OP DYN	LIFE	2/80	125C	N/R	3.60E 04	72	0	
:	:	:	:	:	EM	:	:		:	:	72	0	
:	:	:	:	:	OP DYN	LIFE	2/80	125C	N/R	8.80E 04	88	0	
:	:	:	:	:	EM	:	:		:	:	88	0	
:8257	:D-1	:HDIP	40	:C	OP DYN	LIFE	2/80	125C	N/R	4.20E 04	84	0	
:	:	:	:	:	EM	:	:		:	:	84	0	
:	:	:	:	:	N/R	FIELD	4/81	40C	GBC	5.02E 05	193	0	
:6259A	:	:HDIP	28	:I	BURN-IN	BRN	2/80		N/R	2.19E 04	456	0	
:	:	:	:	:	EM	:	:		:	:	456	0	
:	:	:	:	:	OP DYN	LIFE	2/80	125C	N/R	5.00E 04	100	0	
:	:	:	:	:	EM	:	:		:	:	100	0	
:	:	:	:	:	BAKE	BRN	2/80	160C	N/R	3.36E 03	20	0	
:	:	:	:	:	FM	:	:		:	:	20	0	
:	:	:	:	:	TEMPCYC	ENV	2/80	:-055C 125C	N/R	:	40	0	
:	:	:	:	:	:	:	:	:200 CY	:	:	:	:	
:	:	:	:	:	EM	:	:		:	:	40	1	
:	:	:	:	:	OP DYN	LIFE	2/80	125C	N/R	3.56E 05	356	0	
:	:	:	:	:	EM	:	:		:	:	356	1	3174
:8273	:	:HDIP	40	:C	BURN-IN	BRN	6/80		N/R	1.30E 04	270	0	
:	:	:	:	:	EM	:	:		:	:	270	0	
:	:	:	:	:	OP DYN	LIFE	6/80	125C	N/R	2.69E 05	270	1	3171
:	:	:	:	:	EM	:	:		:	:	269	1	3172
:8273	:D	:NHDIP	40	:C	BURN-IN	BRN	6/80		N/R	2.78E 04	580	0	
:	:	:	:	:	EM	:	:		:	:	580	1	3133
:	:	:	:	:	OP DYN	LIFE	6/80	125C	N/R	2.20E 05	220	0	
:	:	:	:	:	EM	:	:		:	:	220	6	3173
:8275	:	:NHDIP	40	:C	BURN-IN	BRN	7/80		N/R	9.98E 03	208	0	
:	:	:	:	:	EM	:	:		:	:	208	0	
:	:	:	:	:	OP DYN	LIFE	7/80	125C	N/R	4.03E 05	403	0	
:	:	:	:	:	EM	:	:		:	:	403	1	3168
:	:	:	:	:	OP DYN	BRN	7/80	125C	N/R	1.51E 04	90	0	
:	:	:	:	:	EM	:	:		:	:	90	1	3169
:8275	:D-1	:HDIP	40	:C	BURN-IN	BRN	7/80		N/R	2.18E 04	454	0	
:	:	:	:	:	EM	:	:		:	:	454	0	
:	:	:	:	:	OP DYN	LIFE	7/80	125C	N/R	7.80E 05	781	1	3170
:	:	:	:	:	EM	:	:		:	:	780	0	
:8275	:D	:NHDIP	40	:C	N/R	FIELD	4/80	40C	GBC	1.34E 05	103	0	
:	:	:	:	:	N/R	FIELD	4/81	40C	GBC	1.99E 06	765	5	

MOTOROLA SEMI — PROGRAMMABLE

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:14536B	:D-1	:HDIP	16	:I	N/R	FIELD	4/81	40C	GBC	4.21E 05	162	0	

INTEL — RAM

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:8202	:D	:NHDIP	40	:C	BURN-IN	BRN	2/80		N/R	5.97E 04	1243	0	
					EM						1243	3	
					OP DYN	LIFE	2/80	125C	N/R	3.07E 05	307	0	
					EM						307	1	

VARIOUS — RECEIVE/TRANSMIT

P-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:N/R	:D	:NHDIP	40	:C	N/R	FIELD	7/76	25C	GF	1.79E 07	4810	22	

VARIOUS — RECEIVE/TRANSMIT

P-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:N/R	:D	:NHDIP	40	:C	N/R	FIELD	5/77	40C	GBC	2.02E 04	13	0	
					N/R	FIELD	5/78	40C	GBC	7.07E 05	544	0	
					N/R	FIELD	4/79	40C	GBC	1.20E 06	922	0	
					N/R	FIELD	4/80	40C	GBC	1.71E 06	1312	0	
					N/R	FIELD	4/81	40C	GBC	2.50E 05	96	0	
:N/R	:D-1	:HDIP	40	:C	N/R	FIELD	4/79	40C	GBC	1.43E 06	1103	10	
					N/R	FIELD	4/80	40C	GBC	4.14E 06	3185	22	
	:NONE				N/R	FIELD	1/81	44C	GF	3.28E 06	636	6	3460
													3461
													3462
													3505
													3506
	:D-1				N/R	FIELD	4/81	40C	GBC	1.43E 07	5483	40	

GENERAL INSTRUMENTS — RECEIVE/TRANSMIT

P-DYN — MOS — NUMBER OF GATES 525

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:1013	:D	:NHDIP	40	:C	N/R	FIELD	6/77	30C	GBC	1.00E 07	11000	9	
:1013	:D-1	:HDIP	40	:C	N/R	FIELD	10/77	30C	GBC	1.02E 07	2250	26	
:1013A	:X	:HDIP	40	:C	N/R	FIELD	2/78	25C	GBC	1.91E 05	17	2	
					N/R	FIELD	6/78	25C	GBC	4.90E 04	17	0	

AMERICAN MICROSYSTEMS — RECEIVE/TRANSMIT

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:2350	:D-1	:HDIP	40	:C	VIS INS	EBRN	3/78		N/R		198	0	
					TEMPCYC			:-055C 125C			198	0	
								:10CY					
					REVBIAS			:125C		3.17E 04	198	0	
					S&F EM			:070C			198	0	
:2350	:D	:NHDIP	40	:C	VIS INS	EBRN	3/78		N/R		1469	0	
					TEMPCYC			:-055C 125C			1469	0	
								:10CY					
					REVBIAS			:125C		2.35E 05	1469	0	
					S&F EM			:070C			1469	29	2493
													2494

INTEL — RECEIVE/TRANSMIT

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:M8251	:D	:NHDIP	28	:M	OPERATE	CHECK	10/77	:025C	GBC	4.40E 02	1	0	
					OP DYN	BDLIFE	5/77	25C	N/R	2.47E 04	21	0	
					OP DYN	BDLIFE	5/77	55C	N/R	1.43E 04	21	0	
					OP DYN	BDLIFE	5/77	70C	N/R	2.00E 04	21	0	
					N/R	FIELD	5/77	40C	GBC	7.15E 03	11	0	
					N/R	FIELD	5/78	40C	GBC	1.20E 05	92	0	
					N/R	FIELD	4/79	40C	GBC	2.87E 06	2204	1	
:8251A		:NHDIP	28	:C	N/R	FIELD	4/80	40C	GBC	4.93E 06	3793	2	
					N/R	FIELD	4/81	40C	GBC	0.00E 06	3846	5	
:8291		:NHDIP	40	:C	BURN-IN	BRN	2/80		N/R	1.51E 04	314	0	
					EM						314	2	3130
					OP DYN	LIFE	2/80	125C	N/R	3.12E 05	312	1	3160
					EM						311	0	
					N/R	FIELD	4/81	40C	GBC	1.01E 06	390	0	
:8291	:D-1	:HDIP	40	:C	BURN-IN	BRN	2/80		N/R	5.18E 03	108	0	
					EM						108	1	3131
					OP DYN	LIFE	2/80	125C	N/R	1.07E 05	107	0	
					EM						107	0	

MOTOROLA SEMI — RECEIVE/TRANSMIT

N-DYN — MOS — NUMBER OF GATES 650

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:6852	:NONE	:DIP	24	:C	OP DYN	LIFE	11/77	125C	N/R	6.03E 04	154	0	
					EM						154	5	

HARRIS SEMI — RECEIVE/TRANSMIT

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6402	C-2	DIP	40	N/R	OP DYN	LIFE	4/79	125C	N/R	4.40E 04	22	0	

INTERSIL — RECEIVE/TRANSMIT

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
6402	D-1	HDIP	40	1	OP CNST	LIFE	6/79	125C	N/R	2.34E 05	78	0	
					EM			25C			78	0	
					OP CNST	LIFE	6/79	125C	N/R	2.48E 05	248	0	
					EM			25C			248	5	

ADVANCED MICRO DEVICES — REGISTER

TTL — BIPOLAR — NUMBER OF GATES 187

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2502	B-2	NHFPK	16	M	REVBIAS	LIFE	6/80	125C	N/R	2.70E 04	27	0	
					EM			125C			27	0	

VARIOUS — REGISTER

TTL — BIPOLAR — NUMBER OF GATES 260

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2504	D-1	HDIP	24	C	N/R	FIELD	5/77	40C	GBC	1.20E 05	49	0	
					N/R	FIELD	5/78	40C	GBC	1.12E 06	865	0	
					N/R	FIELD	4/79	40C	GBC	3.74E 06	2875	0	
					N/R	FIELD	4/80	40C	GBC	6.67E 06	5133	6	
					N/R	FIELD	4/81	40C	GBC	1.10E 07	4229	9	

MOTOROLA SEMI — REGISTER

SCHOTTKY RTL — BIPOLAR — NUMBER OF GATES 160

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8501	D-1	HDIP	16	C	REVBIAS	LIFE	2/75	125C	N/R	1.92E 04	19	0	

MOTOROLA SEMI — REGISTER

SCHOTTKY RTL — BIPOLAR — NUMBER OF GATES 160

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
8501	D-1	HDIP	16	C	EM	LIFE	2/75		N/R		19	0	
8502		HDIP	24	C	REVBIAS	LIFE	2/75	125C	N/R	2.77E 04	28	2	
					EM						26	0	

ADVANCED MICRO DEVICES — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 104

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS299	D-1	HDIP	20	C	N/R	FIELD	5/78	40C	GBC	6.89E 04	53	0	
					N/R	FIELD	4/79	40C	GBC	2.31E 05	178	0	

VARIOUS — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 144

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
54LS670	B-2	NHDIP	16	M	N/R	FIELD	5/77		AIT	2.04E 03	6	0	
					N/R	FIELD	5/77		AIT	1.94E 04	57	0	

TEXAS INSTRUMENTS — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 145

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS170	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	1.58E 05	243	0	
					N/R	FIELD	5/78	40C	GBC	5.20E 06	3999	0	
					N/R	FIELD	4/79	40C	GBC	1.01E 07	7798	1	
					N/R	FIELD	4/80	40C	GBC	2.10E 07	16134	1	
					N/R	FIELD	4/81	40C	GBC	4.43E 07	17043	4	

TEXAS INSTRUMENTS — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 146

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS670	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.08E 04	32	0	

TEXAS INSTRUMENTS — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 146

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS670	D-1	HDIP	16	C	N/R	FIELD	5/78	40C	GBC	2.67E 06	2051	1	
					N/R	FIELD	4/79	40C	GBC	8.06E 06	6201	1	
					N/R	FIELD	4/80	40C	GBC	1.45E 07	11117	5	
					N/R	FIELD	4/81	40C	GBC	2.93E 07	11269	0	

VARIOUS — REGISTER

LOW POWER/SCHOTTKYTTL — BIPOLAR — NUMBER OF GATES 146

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS670	D-1	HDIP	16	C	N/R	FIELD	2/78	25C	GBC	9.52E 05	93	2	
					N/R	FIELD	2/78	25C	GBC	3.33E 04	6	0	
					N/R	FIELD	2/78	25C	GBC	1.01E 06	100	0	
					N/R	FIELD	6/78	25C	GBC	2.68E 05	93	0	
					N/R	FIELD	6/78	25C	GBC	1.73E 04	6	0	
					N/R	FIELD	6/78	25C	GBC	2.88E 05	100	0	

NITRON — REGISTER

P-STAT — MOS — NUMBER OF GATES 489

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	4.75E 04	1980	0	
					TEMPCYC			-065C 150C			1980	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			1980	0	
								1 MIN E					
					FINE LK			HE 5.E-7			1980	10	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			1980	4	
								3X					
								90PSIG					
					FNCT EM			085C			1966	100	
	B-1				REVBIAS	BRN	2/78	125C	N/R	3.22E 05	1917	0	
					S&F EM			85C			1917	5	
					STAT EM			- 35C			1917	3	
					FNCT EM			25C			1917	23	
					VIS INS						1917	5	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	0	

RCA REGISTER

CMOS MOS NUMBER OF GATES 142

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4034	D	HDIP	24	I	OP CNST	BRN	5/80	125C	N/R	6.87E 04	409	0	
					EM						409	8	

TEXAS INSTRUMENTS SHIFT REG

TTL BIPOLAR NUMBER OF GATES 100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74166	D-1	HDIP	16	C	N/R	FIELD	5/77	40C	GBC	2.91E 05	125	0	
					N/R	FIELD	5/78	40C	GBC	1.57E 06	1204	0	
					N/R	FIELD	4/79	40C	GBC	3.96E 06	3043	0	
					N/R	FIELD	4/80	40C	GBC	3.96E 06	3046	0	
					N/R	FIELD	4/81	40C	GBC	3.38E 06	1301	0	

VARIOUS SHIFT REG

TTL BIPOLAR NUMBER OF GATES 100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
54166	B-1	NHDIP	16	M	TCVPC	RELPRO	6/75	-054C 071C	AUF	1.99E 04	12	0	
								368CY 1G 56%					
								20HZ 10%					

VARIOUS SHIFT REG

TTL BIPOLAR NUMBER OF GATES 101

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
54199	C-1	NHDIP	24	M	OPERATE	RELDEM	7/76	020C	GT	7.26E 04	108	0	
74199	D-1	HDIP	24	C	N/R	FIELD	5/77	40C	GBC	3.28E 06	883	0	
					N/R	FIELD	5/78	40C	GBC	3.31E 06	2544	0	
					N/R	FIELD	4/79	40C	GBC	5.39E 06	4149	0	
					N/R	FIELD	4/80	40C	GBC	3.71E 06	2850	0	
					N/R	FIELD	4/81	40C	GBC	7.29E 06	2802	5	

VARIOUS — SHIFT REG

TTL — BIPOLAR — NUMBER OF GATES 105

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:8274	:D-1	:HDIP	16	:C	VIS INS	EBRN	5/76		N/R		100	0	
					S&F EM			:025C 070C			100	0	
					THRMSHK			:000C 100C			100	0	
								:15CY					
								:LIQUID					
					REVBIAS			:125C		1.68E 04	100	0	
					S&F EM			:070C			100	3	1747

SIGNETICS — SHIFT REG

TTL — BIPOLAR — NUMBER OF GATES 111

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:54198	:D	:NHFPK	24	:M	STGLIFE	LIFE	11/77	150C	N/R	4.50E 04	45	0	
					EM						45	0	

TEXAS INSTRUMENTS — SHIFT REG

TTL — BIPOLAR — NUMBER OF GATES 111

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:74198	:D-1	:HDIP	24	:C	SDF EM	EBRN	11/75	:025C	N/R		28	0	
					THRMSHK			:000C 100C			28	0	
								:5CY					
								:LIQUID					
					REVBIAS			:100C		4.70E 03	28	0	
					SDF EM			:025C			28	0	
:74198		:HDIP	24	:C	N/R	FIELD	5/77	40C	GBC	5.20E 04	12	0	
					N/R	FIELD	5/78	40C	GBC	4.09E 06	3147	4	
					N/R	FIELD	5/78	40C	GBC	5.20E 05	400	0	
					N/R	FIELD	4/79	40C	GBC	4.29E 06	3298	0	
					N/R	FIELD	4/80	40C	GBC	8.50E 06	6535	0	
					N/R	FIELD	4/81	40C	GBC	1.92E 07	7378	0	

MOTOROLA SEMI — SHIFT REG

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
:7844	:X	:NHFPK	42	:C	PAR EXC	LIFE	2/75	125C	N/R	3.02E 04	10	0	
					EM						10	0	
					PAR EXC	LIFE	2/75	125C	N/R	2.01E 04	10	0	
					EM						10	0	

ADVANCED MICRO DEVICES — SHIFT REG

TTL — BIPOLAR — NUMBER OF GATES 187

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
2503	B-2	NHDIP	16	N	REVBIAS	LIFE	6/80	125C	N/R	8.40E 04	84	0	
					EM			125C			84	0	

TEXAS INSTRUMENTS — SHIFT REG

LOW POWER/SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 100

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS166	D-1	HDIP	16	C	N/R	FIELD	5/78	40C	GBC	2.08E 04	16	0	
					N/R	FIELD	4/79	40C	GBC	4.29E 06	3300	1	
					N/R	FIELD	4/80	40C	GBC	1.01E 07	7756	1	

ADVANCED MICRO DEVICES — SHIFT REG

LOW POWER/SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 104

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
25LS299	X	HDIP	20	C	N/R	FIELD	4/78	25C	GBC	2.16E 06	500	0	

TEXAS INSTRUMENTS — SHIFT REG

LOW POWER/SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 104

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS299	D-1	HDIP	20	C	N/R	FIELD	4/80	40C	GBC	4.49E 05	345	0	

VARIOUS — SHIFT REG

LOW POWER/SCHOTTKY TTL — BIPOLAR — NUMBER OF GATES 104

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
74LS299	D-1	HDIP	20	C	N/R	FIELD	4/81	40C	GBC	1.11E 06	428	0	

ADVANCED MICRO DEVICES — SHIFT REG

LOW POWER TTL — BIPOLAR — NUMBER OF GATES 139

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
93L28	B-2	NHDIP	16	M	REVBIAS	LIFE	6/80	125C	N/R	1.61E 05	161	0	
					EM			125C			161	0	

FAIRCHILD SEMI — SHIFT REG

LOW POWER TTL — BIPOLAR — NUMBER OF GATES 144

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
9228	D	NHDIP	16	M	THRMSHK	ENV	1/75	000C 100C	N/R		42	0	
								15CY					
								LIQUID					
					TEMPCYC			-065C 150C			42	0	
								10CY					
								10/10DT					
					MOIST			-010C 065C			42	0	
								98%RH					
					FINE LK			RADIS 5.E-8			42	0	
								12 MIN					
								5 ATMO					
					GROSSLK			MINOIL			42	0	
					EM						42	0	
					MECHSHK	ENV	1/75	1.5KG .5MSEC	N/R		42	0	
								6 AXES					
								5 BLOS					
					VBVRFQ			20HZ 2KHZ			42	0	
								50G					
								3 AXES					
					CNSTACC			30KG 6 AXES			42	0	
								1 MIN E					
					FINE LK			RADIS 5.E-8			42	0	
								12 MIN					
								5 ATMO					
					GROSSLK			MINOIL			42	0	
					EM						42	2	

ADVANCED MICRO DEVICES — SHIFT REG

LOW POWER TTL — BIPOLAR — NUMBER OF GATES 263

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
25L04	D-1	HDIP	24	C	N/R	FIELD	5/78	40C	GBC	5.33E 04	41	0	
					N/R	FIELD	4/79	40C	GBC	9.93E 05	764	0	
					N/R	FIELD	4/80	40C	GBC	8.07E 05	621	0	
					N/R	FIELD	4/81	40C	GBC	1.92E 06	737	0	
25L04	D	NHFPK	24	M	STAT EM	EBRN	9/77	025C	N/R		8	0	
					BAKE			125C		3.84E 02	8	0	
					TEMPCYC			-065C 125C			8	0	
								10CY					
								15/15DT					
					HERMETC						8	0	
					STAT EM			025C			8	0	
					BURN-IN			125C		2.30E 03	8	0	
					DYN EM			025C			8	0	

ADVANCED MICRO DEVICES — SHIFT REG

LOW POWER TTL — BIPOLAR — NUMBER OF GATES 263

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
25L04	D	NHFPK	24	M	X-RAY	EBRN	9/77		N/R		8	1	
					VIS INS						7	0	

TEXAS INSTRUMENTS — SHIFT REG

P-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
3002	D	NHCAN	10	I	N/R	FIELD	4/80	40C	GBC	1.64E 05	126	4	

VARIOUS — SHIFT REG

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4557B	B-2	NHDIP	16	M	TCVPC	RELDEM	6/79	-065C 160C 126CY	AIF	7.81E 03	16	0	

NATIONAL SEMI — SHIFT REG

CMOS — MOS — NUMBER OF GATES 109

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4006C	D-1	HDIP	14	I	N/R	FIELD	4/79	40C	GBC	2.29E 06	1758	0	
					N/R	FIELD	4/80	40C	GBC	2.61E 06	2005	0	
					N/R	FIELD	4/81	40C	GBC	4.89E 06	1881	0	

VARIOUS — SHIFT REG

CMOS — MOS — NUMBER OF GATES 119

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4094B	D-1	HDIP	16	I	N/R	FIELD	4/81	40C	GBC	6.28E 06	2415	1	

NITRON — STORAGE UNIT

P-DYN — MOS — NUMBER OF GATES 569

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	1.33E 05	5526	0	
					TEMPCYC			-065C 150C			5526	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			5526	0	
								1 MIN E					
					FINE LK			HE 5.E-7			5526	21	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			5526	28	
								3X					
								90PSIG					
					FNCT EM			085C			5477	999	
					N/R						0	42	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.25E 06	13365	0	
					S&F EM			85C			13365	65	
					STAT EM			- 35C			13365	64	
					FNCT EM			25C			13365	93	
					VIS INS						13365	7	
					REVBIAS	BRN	2/78	125C	N/R	2.47E 04	147	0	
					S&F EM			85C			147	2	
					STAT EM			- 35C			147	0	
					FNCT EM			25C			147	0	
					VIS INS						147	2	

NATIONAL SEMI — SUBSYSTEM

N/R — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
48142	D-1	HDIP	24	C	OP CNST	LIFE	12/78	125C	N/R	4.50E 04	45	0	
					EM						45	2	
					OP DYN	LIFE	12/78	125C	N/R	1.36E 05	136	0	
					EM						136	5	

NITRON — SUBSYSTEM

P-STAT — MOS — NUMBER OF GATES 348

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	1.86E 05	7740	0	
					TEMPCYC			-065C 150C			7740	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			7740	0	
								1 MIN E					
					FINE LK			HE 5.E-7			7740	31	1911
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			7740	29	1912
								3X					
								90PSIG					
					FNCT EM			085C			7680	567	

NITRON — SUBSYSTEM

P-STAT — MOS — NUMBER OF GATES 348

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-1	NHDIP	40	N/R	REVBIAS	BRN	2/78	125C	N/R	1.16E 06	6894	0	
					S&F EM			85C			6894	104	
					STAT EM			-35C			6894	22	
					FNCT EM			25C			6894	131	
					VIS INS						6894	11	

NITRON — SUBSYSTEM

P-STAT — MOS — NUMBER OF GATES 564

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	5.35E 04	2229	0	
					TEMPCYC			-065C 150C			2229	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			2229	0	
								1 MIN E					
					FINE LK			HE 5.E-7			2229	7	1913
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			2229	6	1914
								3X					
								90PSIG					
					FNCT EM			085C			2216	216	
	B-1				REVBIAS	BRN	2/78	125C	N/R	2.51E 05	1496	0	
					S&F EM			85C			1496	3	
					STAT EM			-35C			1496	1	
					FNCT EM			25C			1496	5	
					VIS INS						1496	7	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	0	

NITRON — SUBSYSTEM

P-STAT — MOS — NUMBER OF GATES 776

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	2.78E 05	11599	0	
					TEMPCYC			-065C 150C			11599	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			11599	0	
								1 MIN E					
					FINE LK			HE 5.E-7			11599	85	1909
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			11599	123	1910
								3X					
								90PSIG					
					FNCT EM			085C			11391	999	
					N/R						0	215	
	B-1				REVBIAS	BRN	2/78	125C	N/R	1.66E 06	9906	0	
					S&F EM			85C			9906	61	
					STAT EM			-35C			9906	18	

NITRON — SUBSYSTEM

P-STAT — MOS — NUMBER OF GATES 776

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	B-1	NHDIP	40	N/R	FNCT EM	BRN	2/78	25C	N/R		9906	187	
					VIS INS						9906	75	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	4	

SILICONIX — SUBSYSTEM

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
320D	B-2	NHDIP	18	I	REVBIAS	LIFE	12/79	125C	N/R	9.60E 04	96	0	
					EM			25C			96	1	
					HERMETC						96	0	

MOTOROLA SEMI — SWITCH

TTL — BIPOLAR — NUMBER OF GATES 112

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
7846	X	NHFPK	42	C	PAR EXC	LIFE	2/75	125C	N/R	2.01E 04	10	0	
					EM						10	0	

NITRON — SWITCH

P-STAT — MOS — NUMBER OF GATES 499

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	NHDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	2.14E 05	8926	0	
					TEMPCYC			-065C 150C			8926	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			8926	0	
								1 MIN E					
					FINE LK			HE 5.E-7			8926	77	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			8926	66	
								3X					
								90PSIG					
					FNCT EM			085C			8783	999	
					N/R						0	112	
	B-1				REVBIAS	BRN	2/78	125C	N/R	1.36E 06	8088	0	
					S&F EM			85C			8088	23	
					STAT EM			-35C			8088	20	
					FNCT EM			25C			8088	62	
					VIS INS						8088	52	

NITRON — SWITCH

P-STAT — MOS — NUMBER OF GATES 499

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	C-1	HDIP	40	N/R	OPERATE	CHECK	4/78	125C	GT	1.39E 05	1788	0	

NITRON — TIME PIECE

P-STAT — MOS — NUMBER OF GATES 629

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
N/R	D	HDIP	40	N/R	BAKE	EBRN	8/77	150C	N/R	5.44E 04	2265	0	
					TEMPCYC			-065C 150C			2265	0	
								10CY					
								10/10DT					
					CNSTACC			20KG 1 AXIS			2265	0	
								1 MIN E					
					FINE LK			HE 5.E-7			2265	7	
								60 MIN					
								30 MIN					
					GROSSLK			FLUOR 125C			2265	3	
								3X					
								90PSIG					
					FNCT EM			085C			2255	324	
	B-1				REVBIAS	BRN	2/78	125C	N/R	3.57E 05	2127	0	
					S&F EM			85C			2127	28	
					STAT EM			35C			2127	30	
					FNCT EM			25C			2127	20	
					VIS INS						2127	0	
	C-1				OPERATE	CHECK	4/78	125C	GT	3.47E 04	447	0	

NATIONAL SEMI — TIME PIECE

P-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
53110	D-1	HDIP	22	I	OP DYN	LIFE	12/78	125C	N/R	4.70E 04	47	0	
					EM						47	0	
5387AA		HDIP	40	I	OP DYN	LIFE	12/78	125C	N/R	2.20E 04	22	0	
					EM						22	0	

NATIONAL SEMI — TIME PIECE

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4402	D-1	HDIP	40	N/R	OP DYN	LIFE	12/78	125C	N/R	1.67E 05	167	0	
					EM						167	5	
					OP DYN	LIFE	12/78	125C	N/R	3.05E 05	531	0	

NATIONAL SEMI — TIME PIECE

N-DYN — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
4402	D-1	HDIP	40	N/R	EM	LIFE	12/78		N/R		531	4	

NATIONAL SEMI — TIME PIECE

CMOS — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
48115	D	NHDIP	40	C	OP CNST	LIFE	12/78	125C	N/R	3.50E 04	35	0	
					EM						35	0	

WESTERN DIGITAL — TRANSMITTER

P-STAT — MOS — NUMBER OF GATES N/R

PART NO.	SCR. CLS	PKG	#PINS	TMP RNG	TEST TYPE	SOURCE	TEST DATE	STRESS LEVEL	ENV	PART HRS.	#TEST	#FAIL	MFEF #
1482	D-1	HDIP	40	C	VIS INS	EERN	12/76		N/R		81	0	
					S&F EM			025C 070C			81	0	
					THRMSHK			000C 100C			81	0	
								15CY					
								LIQUID					
					REVBIAS			125C		1.36E 04	81	0	
					S&F EM			070C			81	2	

MICROCIRCUIT DEVICE RELIABILITY
MEMORY/DIGITAL LSI DATA

Section 4

FAILURE ANALYSIS DATA SUMMARY

INTRODUCTION

This section presents summaries of the detailed failure event data of Section 5 in tabular form. The data was arranged in a number of different tables so that the effects of various functional groups, circuit types, etc., may be evaluated. For each table, the relative distribution of a number of factors (or descriptors) which influence failure is presented. Thus the tables in this section provide quantitative information about the frequency of failure modes, effects (indicators), causes, stresses, and defects. Exact definitions of all these terms and hierarchical structure relating to them is given in Appendix A.

The column then contains information at up to four levels of detail, although only three levels appear in the example. The full range of entries at each level are defined in Appendix A.

Column 2 is headed "Quantity Totals," and the entries in that column are simply the numbers falling into each category at each level. These quantities sum as indicated by the arrows, in nested fashion. The third level may not always be represented, depending on the quality of the data.

Column 3 expresses the quantity totals as percentages. Again, the entries are nested and sum, as before, percentagewise.

Column 4 is headed "Normalized Quantity" and is basically the quantity totals (Column 2) with the unknowns removed from levels 2, 3 and 4. This allows comparisons to be made without the added complication of unknowns. Since the term "unknown" applies only to one level at a time, the normalized quantities are not always additive to the next level. Rather, the normalized quantity at each level represents the sum of the knowns on the next lowest level. The dotted arrows clarify.

Column 5 is headed "Normalized Percent" and represents the normalized quantities as percentages. The entries then sum percentagewise as before, and the level 1 entries sum down the page to 100%.

Format

The data is first separated broadly by functional group into either memory or digital/LSI devices. Tables 3-1 through 3-210 are memory data; tables 3-211 through 3-264 are digital devices. Next, for each functional group, the data is tabulated by up to five descriptors. The five descriptors are:

(1) Failure indicator
(2) Failure mode(s)
(3) Defect
(4) Cause
(5) Stress

Full definitions are given in Appendix A. Depending on the amount of data available, it may not be possible to consider all five descriptors. Only one or two are possible in many cases. The descriptor used is indicated at the head of each table.

Again, for each functional group the data is then summarized by circuit type. For example, memory data may be split into ROMs, RAMs, PROMs, etc. Each circuit type (within each functional group) is then tabulated by the five descriptors as before. Since this produces a large number of subgroups, there is often not enough data to print a table. Indeed, there is seldom enough to go further than the first two descriptors. This is due to the nested nature of the data, each descriptor providing more detailed information than the last.

Figure 18 gives an example of a page of summary tables. The tables consist of essentially five columns.

Column 1 is headed by the descriptor; in the example the descriptor is "failure indicator."

FUNCTIONAL GROUP: MEMORY/DIGITAL LSI

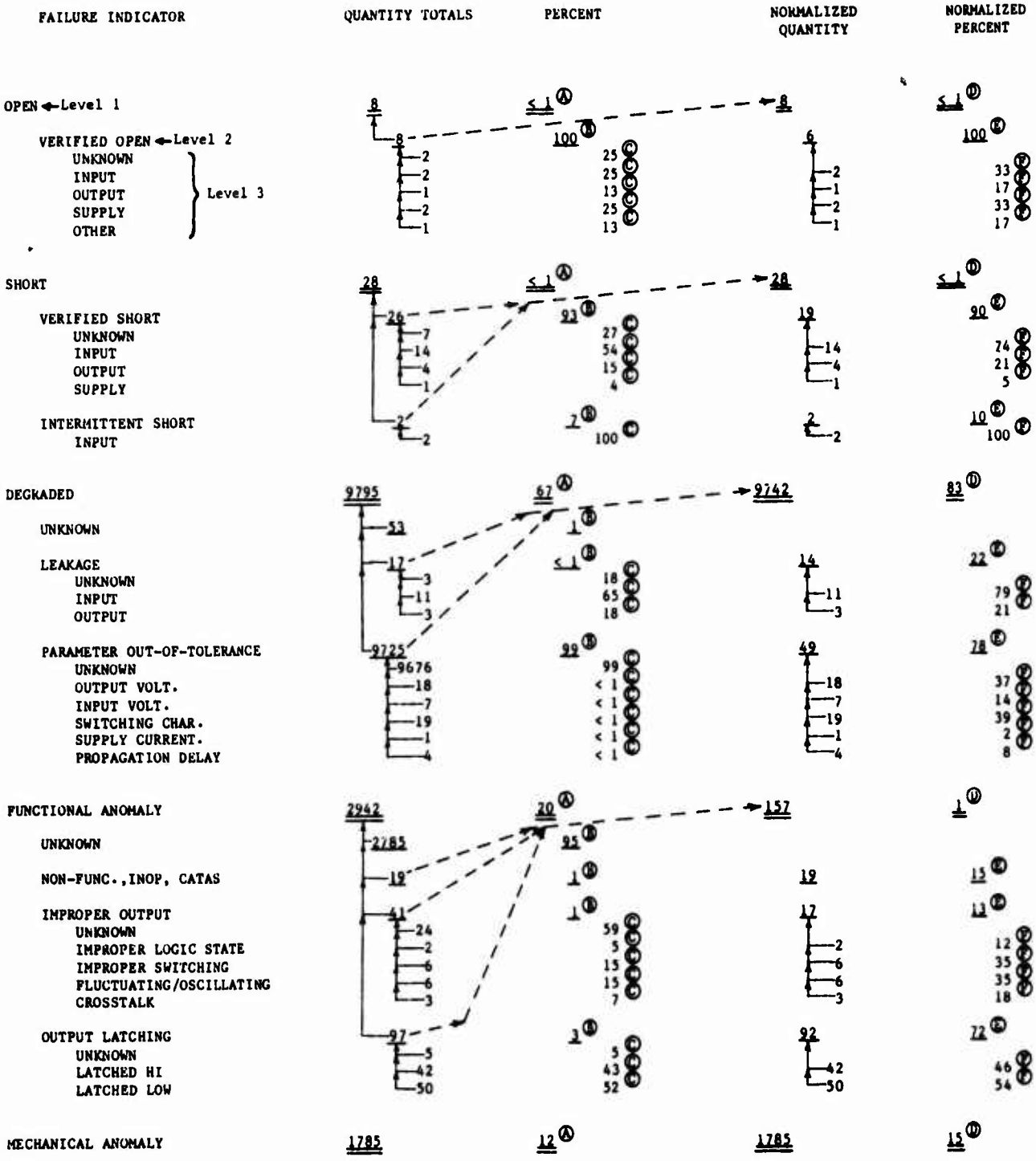

FIGURE 18: Illustration of Failure Analysis Table

TABLE 13: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

FAILURE INDICATOR	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
OPEN	[9]	(1)	[9]	(2)
VERIFIED OPEN	9	100		
UNKNOWN	9	100		
SHORT	[12]	(1)	[12]	(2)
VERIFIED SHORT	12	100	3	100
UNKNOWN	9	75		
INPUT	1	8	1	33
OUTPUT	1	8	1	33
SUPPLY	1	8	1	33
DEGRADED	[560]	(62)	[438]	(79)
UNKNOWN	122	22		
LEAKAGE	22	4	14	3
UNKNOWN	8	36		
INPUT	9	41	9	64
OTHER	5	23	5	36
PARAMETER OUT-OF-TOLERANCE	416	74	412	97
UNKNOWN	4	1		
OUTPUT VOLT.	1	< 1	1	< 1
SWITCHING CHAR.	2	< 1	2	< 1
SUPPLY CURRENT.	1	< 1	1	< 1
PROPAGATION DELAY	26	6	26	6
DYNAMIC CHAR.	356	86	356	86
HIGH LVL. INPUT CURRENT	1	< 1	1	< 1
COMBINATION	25	6	25	6
FUNCTIONAL ANOMALY	[323]	(36)	[89]	(16)
UNKNOWN	234	72		
NON-FUNC.,INOP, CATAS	53	16	53	74
IMPROPER OUTPUT	19	6	2	3
UNKNOWN	17	89		
MEMORY DATA LOSS	1	5	1	50
FLUCTUATING/OSCILLATING	1	5	1	50
OUTPUT LATCHING	17	5	17	24
LATCHED HI	7	41	7	41
LATCHED LOW	10	59	10	59
MECHANICAL ANOMALY	[5]	(1)	[5]	(1)

TABLE 14: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

FAILURE MODES	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DIE	[14]	(74)	[14]	(74)
BULK ASPECTS	1	7	1	100
JUNCTION	1	100	1	100
METALIZATION	11	79		
UNKNOWN	11	100		
OXIDE/DIELECTRIC	2	14		
UNKNOWN	2	100		
INTERCONNECTS	[4]	(21)	[4]	(21)
WIRE	4	100	4	100
PACKAGE	[1]	(5)	[1]	(5)
DIE ATTACH BOND	1	100	1	100

TABLE 15: DEFECT DESCRIPTION
FUNCTIONAL GROUP: DIGITAL LSI

DEFECT DESCRIPTION	QUANTITY TOTALS	PERCENT
LIFTED	1	6
OPEN (NOC)	9	56
PARTICLE BRIDGE	5	31
ZAPPED-EVAPORATED	1	6

TABLE 16: DEFECT CAUSE DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

DEFECT CAUSE	QUANTITY TOTALS	PERCENT
CONTAMINATION	18	64
DENDRITE GROWTH	5	18
WORKMANSHIP	5	18

TABLE 17: ACTIVATING STRESS-A DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

ACTIVATING STRESS-A	QUANTITY TOTALS	PERCENT
ELECTRICAL OVERSTRESS	5	26
ELECTROSTATIC DISCHARGE	2	11
CURRENT STRESS	4	21
HUMIDITY	5	26
TEMPERATURE	3	16

TABLE 18: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

MICROPROCESSORS

FAILURE INDICATOR	QUANTITY TOTALS		PERCENT		NORMALIZED QUANTITY		NORMALIZED PERCENT	
OPEN	[5]		(29)		[5]		(45)	
VERIFIED OPEN	5		100					
UNKNOWN	5		100					
DEGRADED	[6]		(35)		[5]		(45)	
UNKNOWN	1		17					
LEAKAGE	2		33					
UNKNOWN	2		100					
PARAMETER OUT-OF-TOLERANCE	3		50		3		100	
OUTPUT VOLT.	2		67		2		67	
SWITCHING CHAR.	1		33		1		33	
FUNCTIONAL ANOMALY	[5]		(29)					
UNKNOWN	5		100					
MECHANICAL ANOMALY	[1]		(6)		[1]		(9)	

TABLE 19: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: DIGITAL LSI

MICROPROCESSORS

FAILURE MODES	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DIE	[9]	(90)	[9]	(90)
BULK ASPECTS	1	11	1	100
JUNCTION	1	100	1	100
METALIZATION	6	67		
UNKNOWN	6	100		
OXIDE/DIELECTRIC	2	22		
UNKNOWN	2	100		
PACKAGE	[1]	(10)	[1]	(10)
DIE ATTACH BOND	1	100	1	100

TABLE 20: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

FAILURE INDICATOR	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
OPEN	[9]	(14)	[9]	(25)
VERIFIED OPEN	9	100	4	100
UNKNOWN	5	56		
SUPPLY	4	44	4	100
DEGRADED	[36]	(56)	[18]	(50)
UNKNOWN	18	50		
LEAKAGE	8	22	1	13
UNKNOWN	7	88		
OTHER	1	13	1	100
PARAMETER OUT-OF-TOLERANCE	10	28	7	88
UNKNOWN	3	30		
OUTPUT VOLT.	5	50	5	71
SWITCHING CHAR.	2	20	2	29
FUNCTIONAL ANOMALY	[18]	(28)	[8]	(22)
UNKNOWN	10	56		
NON-FUNC., INOP, CATAS	8	44	8	100
MECHANICAL ANOMALY	[1]	(2)	[1]	(3)

TABLE 21: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

FAILURE MODES	QUANTITY TOTALS		PERCENT		NORMALIZED QUANTITY		NORMALIZED PERCENT	
DIE	[337]		(89)		[173]		(83)	
UNKNOWN	164		49					
BULK ASPECTS	1		< 1		1		1	
CRYSTAL		1		100		1		100
METALIZATION	131		39		73		72	
UNKNOWN		58		44				
OXIDE STEP/CUTOUT		60		46		60		82
PROM FUSE		2		2		2		3
CONTACT WINDOW		1		1		1		1
POLYSILICON CONDUCTOR		3		2		3		4
BOND PAD		7		5		7		10
OXIDE/DIELECTRIC	35		10		22		22	
UNKNOWN		13		37				
GATE OXIDE/DIELECTRIC		19		54		19		86
FIELD OXIDE/DIELECTRIC		1		3		1		5
CAPACITOR DIELECTRIC		2		6		2		9
GLASSIVATION	3		1		3		3	
SURFACE	3		1		3		3	
INTERCONNECTS	[17]		(5)		[15]		(7)	
UNKNOWN	2		12					
WIRE	4		24		4		31	
WIREBOND	11		65		9		69	
UNKNOWN		2		18				
WIREBOND AT DIE PAD		8		73				
UNKNOWN			8	100				
WIREBOND AT LEAD FRAME		1		9				
UNKNOWN			1	100				
PACKAGE	[23]		(6)		[20]		(10)	
UNKNOWN	3		13					
PACKAGE BODY	2		9		2		10	
LEAD FRAME/EXTERNAL LEADS	7		30		7		35	
DIE ATTACH BOND	11		48		11		55	

TABLE 22: DEFECT DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

DEFECT DESCRIPTION	QUANTITY TOTALS	PERCENT
BROKEN	4	4
CRACKED	6	6
IMPURITIES	8	8
LIFTED	19	19
MASK FAULT	9	9
OPEN (NOC)	1	1
PINHOLE	21	21
SHORT (NOC)	6	6
FAULT (NOC)	12	12
CORRODED	8	8
MELTED-FUSED	2	2
HOLE	4	4
EXTRANEOUS PARTICLE	1	1

TABLE 23: DEFECT CAUSE DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

DEFECT CAUSE	QUANTITY TOTALS	PERCENT
CONTAMINATION	108	47
CORROSION	3	1
DIELECTRIC BREAKDOWN	2	1
ELECTROMIGRATION	43	19
GROWBACK	2	1
INTERMETALLIC FORMATION	10	4
WORKMANSHIP	1	< 1
PROCESS FLAW	52	23
INDUCED (NOC)	4	2
IMPROPER HANDLING	6	3

TABLE 24: ACTIVATING STRESS-A DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

ACTIVATING STRESS-A	QUANTITY TOTALS	PERCENT
ELECTRICAL OVERSTRESS	26	25
ELECTROSTATIC DISCHARGE	12	11
HUMIDITY	3	3
MECHANICAL STRESS	2	2
TEMPERATURE	62	59

TABLE 25: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

ROMS

FAILURE INDICATOR	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DEGRADED	[1]	(50)		
UNKNOWN	1	100		
MECHANICAL ANOMALY	[1]	(50)	[1]	(100)

TABLE 26: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

ROMS

FAILURE MODES	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DIE	[2]	(100)	[2]	(100)
OXIDE/DIELECTRIC	1	50	1	50
FIELD OXIDE/DIELECTRIC	1	100	1	100
SURFACE	1	50	1	50

TABLE 27: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

RAMS

FAILURE INDICATOR	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
OPEN	[1]	(< 1)	[1]	(1)
VERIFIED OPEN	1	100		
UNKNOWN	1	100		
SHORT	[7]	(2)	[7]	(6)
VERIFIED SHORT	7	100	3	100
UNKNOWN	4	57		
INPUT	1	14	1	33
OUTPUT	1	14	1	33
SUPPLY	1	14	1	33
DEGRADED	[126]	(32)	[65]	(58)
UNKNOWN	61	48		
LEAKAGE	10	8	8	13
UNKNOWN	2	20		
INPUT	8	80	8	100
PARAMETER OUT-OF-TOLERANCE	55	44	53	87
UNKNOWN	2	4		
OUTPUT VOLT.	1	2	1	2
SUPPLY CURRENT.	1	2	1	2
PROPAGATION DELAY	26	47	26	49
HIGH LVL. INPUT CURRENT	1	2	1	2
COMBINATION	24	44	24	45
FUNCTIONAL ANOMALY	[255]	(66)	[40]	(35)
UNKNOWN	215	84		
NON-FUNC.,INOP, CATAS	23	9	23	58
IMPROPER OUTPUT	1	< 1	1	3
MEMORY DATA LOSS	1	100	1	100
OUTPUT LATCHING	16	6	16	40
LATCHED HI	6	38	6	38
LATCHED LOW	10	63	10	63

TABLE 28: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

RAMS

FAILURE MODES	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DIE	[289]	(91)	[134]	(83)
UNKNOWN	155	54		
METALIZATION	122	42	66	88
UNKNOWN	56	46		
OXIDE STEP/CUTOUT	56	46	56	85
CONTACT WINDOW	1	1	1	2
POLYSILICON CONDUCTOR	3	2	3	5
BOND PAD	6	5	6	9
OXIDE/DIELECTRIC	9	3	6	8
UNKNOWN	3	33		
GATE OXIDE/DIELECTRIC	6	67	6	100
GLASSIVATION	3	1	3	4
INTERCONNECTS	[12]	(4)	[12]	(7)
WIRE	1	8	1	10
WIREBOND	11	92	9	90
UNKNOWN	2	18		
WIREBOND AT DIE PAD	8	73		
UNKNOWN	8	100		
WIREBOND AT LEAD FRAME	1	9		
UNKNOWN	1	100		
PACKAGE	[18]	(6)	[16]	(10)
UNKNOWN	2	11		
PACKAGE BODY	2	11	2	13
LEAD FRAME/EXTERNAL LEADS	4	22	4	25
DIE ATTACH BOND	10	56	10	63

TABLE 29: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

PROMS

FAILURE INDICATOR	QUANTITY TOTALS		PERCENT		NORMALIZED QUANTITY		NORMALIZED PERCENT	
OPEN	[8]		(2)		[8]		(2)	
VERIFIED OPEN	8		100					
UNKNOWN		8		100				
SHORT	3]		(1)		[3]		(1)	
VERIFIED SHORT	3		100					
UNKNOWN		3		100				
DEGRADED	[428]		(87)		[370]		(89)	
UNKNOWN	58		14					
LEAKAGE	12		3		6		2	
UNKNOWN		6		50				
INPUT		1		8		1		17
OTHER		5		42		5		83
PARAMETER OUT-OF-TOLERANCE	358		84		356		98	
UNKNOWN		2		1				
DYNAMIC CHAR.		356		99		356		100
FUNCTIONAL ANOMALY	[50]		(10)		[32]		(8)	
UNKNOWN	18		36					
NON-FUNC., INOP, CATAS	28		56		28		97	
IMPROPER OUTPUT	3		6					
UNKNOWN		3		100				
OUTPUT LATCHING	1		2		1		3	
LATCHED HI		1		100		1		100
MECHANICAL ANOMALY	[4]		(1)		[4]		(1)	

TABLE 30: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

PROMS

FAILURE MODES	QUANTITY TOTALS		PERCENT		NORMALIZED QUANTITY		NORMALIZED PERCENT	
DIE	[23]		(82)		[15]		(79)	
UNKNOWN	8		35					
BULK ASPECTS	1		4		1		13	
CRYSTAL		1		100		1		100
METALIZATION	7		30		6		75	
UNKNOWN		1		14				
OXIDE STEP/CUTOUT		3		43		3		50
PROM FUSE		2		29		2		33
BOND PAD		1		14		1		17
OXIDE/DIELECTRIC	6		26					
UNKNOWN		6		100				
SURFACE	1		4		1		13	
INTERCONNECTS	[3]		(11)		[3]		(16)	
WIRE	3		100		3		100	
PACKAGE	[2]		(7)		[1]		(5)	
UNKNOWN	1		50					
DIE ATTACH BOND	1		50		1		100	

TABLE 31: FAILURE INDICATOR DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

SHIFT REGISTERS

FAILURE INDICATOR	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
SHORT	[1]	(5)	[1]	(5)
VERIFIED SHORT	1	100		
UNKNOWN	1	100		
DEGRADED	[2]	(10)	[2]	(10)
PARAMETER OUT-OF-TOLERANCE	2	100	2	100
SWITCHING CHAR.	2	100	2	100
FUNCTIONAL ANOMALY	[17]	(85)	[17]	(85)
NON-FUNC.,INOP, CATAS	2	12	2	67
IMPROPER OUTPUT	15	88	1	33
UNKNOWN	14	93		
FLUCTUATING/OSCILLATING	1	7	1	100

TABLE 32: FAILURE MODES DISTRIBUTION
FUNCTIONAL GROUP: MEMORY

SHIFT REGISTERS

FAILURE MODES	QUANTITY TOTALS	PERCENT	NORMALIZED QUANTITY	NORMALIZED PERCENT
DIE	[18]	(100)	[18]	(100)
METALIZATION	1	6	1	6
OXIDE STEP/CUTOUT	1	100	1	100
OXIDE/DIELECTRIC	17	94	15	94
UNKNOWN	2	12		
GATE OXIDE/DIELECTRIC	13	76	13	87
CAPACITOR DIELECTRIC	2	12	2	13

MICROCIRCUIT DEVICE RELIABILITY
MEMORY/DIGITAL LSI DATA

Section 5

FAILURE EVENT DATA - DETAILED LISTINGS

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INTRODUCTION

This section contains computerized listings of detailed information on failures. The computer file from which the information is taken is called the Microcircuit Failure Event File. The numbers of specific records in this file have already been referenced where applicable in the last column of the tables of Section 3. Note that Section 4 is a summary of all the data in this section.

Each failure event record contains specific information regarding individual device characteristics, environmental and test conditions at the time of failure, and the exact nature of failure.

The nature of each failure has been categorized to follow a structured hierarchy of failure descriptors. Each condition defined in Appendix A is outlined below.

Failure Indicator -	How microcircuit failed within circuit prior to destructive analysis (i.e., output locked high)
Failure Mode -	Physical location of failure within the microcircuit (i.e., metalization, oxide, package seal, etc.)
Failure Defect -	Description of physical condition existing at the appropriate failure modes (i.e., melted, evaporated, voids, etc.)
Failure Defect Cause -	The physical phenomenon which caused the occurrence of the failure defect (i.e., electromigration, workmanship, manufacturing process, etc.)

Failure Activating Stress - The electrical/environmental parameter which may have introduced and/or accelerated the failure defect cause (i.e., humidity, temperature cycling, mecharical shock, voltage stress, etc.)

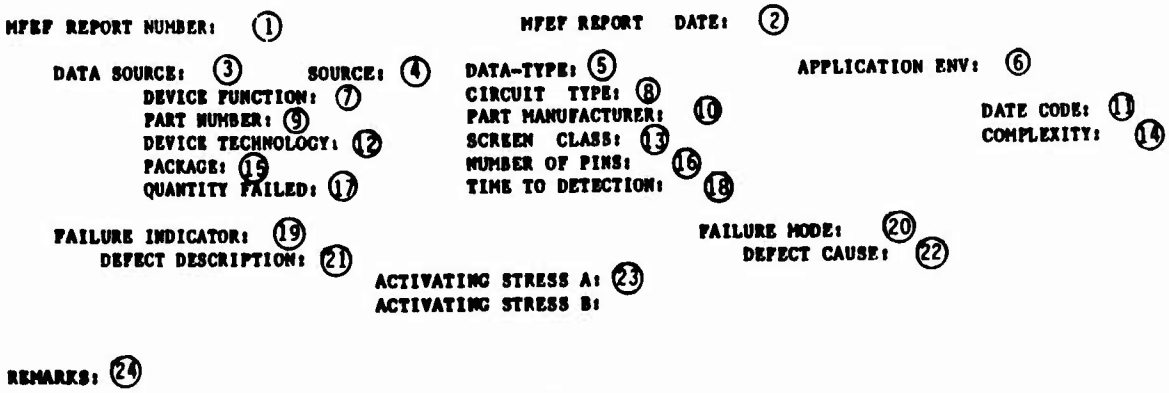
In addition, each failure event record may contain remarks which will further elaborate on device, test, environment or failure information which may not appear elsewhere in the record. Hence, it is possible to correlate actual device test and field experience with its associated failure analysis results for large numbers and broad categories of microelectronic devices, enabling a clearer understanding of cause and effect of failures.

Those wishing a more extensive overview of failure mode or failure indicator distributions may contact the Reliability Analysis Center directly.

USER GUIDE

The description given below applies to the computer listings of this section. The circled numbers on the tabulation form below refer to the explanatory text which follows.

EXAMPLE



① MFEF REPORT NUMBER. Failure events are listed sequentially by MFEF Report Number. Each unique failure event is assigned its own number, where a failure event is defined as a detailed description of the physical/electrical failure attributes of a specific part number, including the failure indicator, failure mode, failure defect, failure defect cause, and failure activating stress(es), where such information is reported. This is the number which corresponds to the MFEF number given in the Device Data-Detailed Listings.

② MFEF REPORT DATE. This date is reported in the format of year/month (e.g., 7804) and is assigned according to the following order of priority: A.) Date device failed; or B.) Date device was reported as failed; or C.) Date that failure report was submitted/written.

③ DATA SOURCE. Indicates the unique data source from which each failure event was reported. The alphabetic characters of the code represent the intended/applied environment of the appropriate device/equipment. The final four integers of the code are assigned sequentially within each coded environment to maintain the identity of the data source. Data source prefixes are defined as follows:

AF Airborne, Fighter (Environment Unknown)
AI Airborne, Inhabited (Aircraft Type Unknown)
AT Airborne, Transport (Environment Unknown)
AU Airborne, Uninhabited (Aircraft Type Unknown)
FE Failure Data (Only Equipment Level)
FP Failure Data (Only Part Level)
GB Ground, Benign
GF Ground, Fixed
GM Ground, Mobile
GP Ground, Portable
GT Ground, Transport
ML Missile, Launch
NS Naval, Sheltered
NSS Naval, Sheltered, Submarine
NU Naval, Unsheltered
PA Part-Level, Government Agency Tested
PI Part-Level, Independent Test Lab Tested
PM Part-Level, Part Manufacturer Tested
PQ Part-Level, Government Qualification
PU Part-Level, Part User Tested
SF Space, Flight
SL Satellite, Launch

④ SOURCE. Indicates the test environment to which the component/board/equipment was subjected. Categories are listed as follows:

BURN-IN	Device Burn-In (< 250 hrs.)
CHECKOUT	Equipment Check
DEVICE EVALUATION	Non-Stress Evaluation
ENVIRONMENTAL	Environmental Test
FIELD	Field Experience
LIFE	Device Laboratory Life (> 250 hrs.)
REL DEMO	Equipment Reliability Demonstration
REL PROD DEMO	Reliability Production Demonstration

NOTE: For DEVICE EVALUATION tests, quantity failed is indicated as zero, since no stress tests have been applied to verify the failure. These results, therefore, are excluded from the summary tables.

⑤ DATA TYPE. Identifies the data source level at which the failure(s) was reported, i.e., component level, board level, or equipment level.

⑥ APPLICATION ENV. The actual or intended environment from which the failure data was reported. The definitions used here are identical to the conventions defined in item 3 , except that the part-level codes (PA, PI, PM, PQ, PU) do not constitute an operational environment and, hence, are not included within this category.

⑦ DEVICE FUNCTION. The device function represents the basic circuit function/classification of the device which failed under test.

⑧ CIRCUIT TYPE. The circuit type further identifies the specialized characteristics of a given device function.

⑨ PART NUMBER. Represents the full manufacturer's commercial part number for the failed device including any stated prefix or suffix designations.

⑩ PART MANUFACTURER. Manufacturer of the failed device, indicated by the part number.

⑪ DATE CODE. This date is reported in the format of year/week (e.g., 7848) and is assigned by the device manufacturer to indicate the date of fabrication.

⑫ DEVICE TECHNOLOGY. Represents the fabrication technology applied in the implementation of the failed device.

⑬ SCREEN CLASS. Indicates the screen class of the failed device(s). The appropriate definitions are included below:

JS	38510, Class S
S-1	883 Method 5004, Screen Class S
JB	38510, Class B
B-1	883 Method 5004, Screen Class B
B-2	Class B, vendor or user equivalent
JC	38510, Class C
C-1	883 Method 5004, Screen Class C
C-2	Class C, vendor or user equivalent
D	Hermetic pkg., no screening beyond normal Q.C.
D-1	Plastic pkg., no screening beyond normal Q.C.
S/R	See Remarks. Device quality defined in item 24 REMARKS
JAN	38510, Screen Class not reported
883	883, probably Method 5004, Screen Class not reported

⑭ COMPLEXITY. Represents the complexity of the failed device in terms of the number of gates (G), the number of bits (B), or the number of transistors (T).

⑮ PACKAGE. Indicates the materials used for package enclosure and the type of construction used in the package design, as follows:

PACKAGE ENCLOSURES:

NONHERMETIC	HERMETIC
EPOXY	CERAMIC
SILICONE	METAL
PHENOLIC	CERAMIC/METAL
	METAL/GLASS
	GLASS/GLASS

PACKAGE CONSTRUCTION:

DIP	Dual In-Line Package
CAN	Can Package
FPK	Flatpack
QIP	Quad In-Line Package
LLP	Leadless Package
CC	Chip Carrier
INL	In-Line Package

⑯ NUMBER OF PINS. Represents the number of pins as applied to the package construction.

⑰ QUANTITY FAILED. The quantity of failures of identical parts exhibiting the exact failure description and occurring within the same failure event (meaning identical data source, test and device information, failure analysis description, time-to-detection, etc.).

⑱ TIME-TO-DETECTION. This value, expressed in hours, represents the reported or calculated time of the device under test before a) a verified failure actually occurs or b) a verified failure is finally detected.

⑲ FAILURE INDICATOR. Is the first externally detectable effect of a part failure.

⑳ FAILURE MODE. Specifies the internal location of the defect.

㉑ FAILURE DEFECT DESCRIPTION. The failure defect is the actual flaw which causes the component to fail.

㉒ FAILURE DEFECT CAUSE. Failure cause is the condition which activates or leads to the defect.

㉓ ACTIVATING STRESS "A" OR "B". Is usually an environmental stress which influences the rate of defect formation.

㉔ REMARKS. Contains additional comments which describe in detail the conditions or activities which lead to the occurrence of a failure event. This section may also contain information about device screen class levels not defined sufficiently in item ⑬ .

MFEF REPORT NUMBER: 45 MFEF REPORT DATE: 7810

DATA SOURCE: FE-0001 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: REGISTER CIRCUIT TYPE: N/R
PART NUMBER: AM25LS22DMB PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7744
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 8 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 20
QUANTITY FAILED: 4 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN SUPPLY FAILURE MODE: WIRE
DEFECT DESCRIPTION: OPEN (NOC) DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: CURRENT STRESS
ACTIVATING STRESS B: ELECTRICAL OVERSTRESS

REMARKS: VCC LEAD WIRES BLOWN OPEN ON ALL DEVICES DUE TO OVERSTRESS >1 AMP,POSSIBLY REVERSAL OF VCC AND GND DUE TO MISMOUNTING.

MFEF REPORT NUMBER: 57 MFEF REPORT DATE: 7806

DATA SOURCE: FE-0001 SOURCE: ENVIRONMENTAL DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: REGISTER LOGIC UNIT CIRCUIT TYPE: CALCULATOR
PART NUMBER: PART MANUFACTURER: DATE CODE: 7801
DEVICE TECHNOLOGY: N/R SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: DIE BULK NOC
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: N/R
ACTIVATING STRESS A: MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: DIE BROKEN FROM HEADER. SILICON FRACTURE INDICATES GOOD EUTECTIC BOND. MANY LEADS BROKEN DUE TO LATERAL DISPLACEMENT.

MFEF REPORT NUMBER: 294 MFEF REPORT DATE: 7607

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: COUNTER CIRCUIT TYPE: BINARY
PART NUMBER: CD4020AK PART MANUFACTURER: RCA DATE CODE: 7535
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: N/R COMPLEXITY: 132 G
PACKAGE: CERAMIC/METAL FPK NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: ZAPPED-EVAPORATED DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: N/R

REMARKS: STATIC ZAPP.

MFEF REPORT NUMBER: 611 MFEF REPORT DATE: 7808

DATA SOURCE: FE-0005 SOURCE: DEV EVALUATION DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: COUNTER CIRCUIT TYPE: BINARY
PART NUMBER: PART MANUFACTURER: DATE CODE: 7710
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: J-B COMPLEXITY: 132 G
PACKAGE: CERAMIC FPK NUMBER OF PINS: 16
QUANTITY FAILED: 0 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE BODY
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: AMBIENT LIGHT PERMEATS TRANSLUCENT PACKAGE, GENERATES PHOTOELECTRIC CURRENT POSSIBLY > LEAKAGE CURRENT (REVERSE I DIR.).

MFEF REPORT NUMBER: 682 MFEF REPORT DATE: 7805

DATA SOURCE: FH-0001 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: COUNTER CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: 9406 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 64 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: WIRE
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: N/R
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: THERMAL SHOCK/TEMPERATURE CYCLE SEQUENCE.

MFEF REPORT NUMBER: 704 MFEF REPORT DATE: 7502

DATA SOURCE: SF-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: SF
DEVICE FUNCTION: ADDER CIRCUIT TYPE: N/R
PART NUMBER: 69690100 PART MANUFACTURER: CONTROL DATA DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: S-1 COMPLEXITY: 770 T
PACKAGE: METAL/CLASS FPK NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 200

FAILURE INDICATOR: N/R FAILURE MODE: PACKAGE LEAD FRAME/EXTERNAL LEADS
DEFECT DESCRIPTION: DISLOCATION DEFECT CAUSE: N/R
ACTIVATING STRESS A: MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: FAILED EQUIP. Y-AXIS RANDOM VIBR. TEST. PINS 26-35 SEPARATED FROM PKG AT EMERGENCE POINT. LEADS TWISTED, BENT, NICKED.

MFEF REPORT NUMBER: 1892 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CUSTOM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 826 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 93 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1893 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CUSTOM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 826 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 47 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1894 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CUSTOM CIRCUIT TYPE: N/R
PART NUMBER PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 282 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 15 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1895 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CUSTOM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 282 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 11 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER 1907 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: GENERATOR CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 1079 C
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 6 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1908 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: GENERATOR CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 1079 C
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 15 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1909 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 776 C
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 85 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1910 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 776 C
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 123 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1911 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 348 C
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 31 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1912 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 348 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 29 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1913 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 564 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 7 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1914 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 564 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 6 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1915 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: ARITHMETIC
PART NUMBER: PART MANUFACTURER NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 900 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 8 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 1916 MFEF REPORT DATE: 7708

DATA SOURCE: PU-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SUB SYSTEM CIRCUIT TYPE: ARITHMETIC
PART NUMBER: PART MANUFACTURER NITRON DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 900 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 15 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PACKAGE SEAL IS NON-HERMETIC.

MFEF REPORT NUMBER: 2397 MFEF REPORT DATE: 0

DATA SOURCE: PH-0008 SOURCE: LIFE DATA-TYPE: COMPONENT APPLICATION ENV: GB
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CE
PART NUMBER: Z80CPU PART MANUFACTURER: MC DATE CODE: 0
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: J COMPLEXITY: 2833 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: LOT NUM E032-17

MFEF REPORT NUMBER: 2493 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: S2350 PART MANUFACTURER: AMERICAN MICROSYSTEMS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 8 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2494 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: S2350 PART MANUFACTURER: AMERICAN MICROSYSTEMS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 21 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2496 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 8080 PART MANUFACTURER VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 8 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2497 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 8080 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 60 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER 2902 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: COUNTER CIRCUIT TYPE: BINARY
PART NUMBER: CD4020AE PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: B-1 COMPLEXITY: 132 C
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#3425

MFEF REPORT NUMBER 3120 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8086 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B COMPLEXITY: 16 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER 3121 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B COMPLEXITY: 8 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3122 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B COMPLEXITY: 8 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3124 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: CR74B PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B COMPLEXITY: 8 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3125 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3126 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIREBOND NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3127 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: IMPROPER LOGIC STATE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: DATA RETENTION

MFEF REPORT NUMBER: 3130 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: D8291 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GPIB TALKER/LISTENER

MFEF REPORT NUMBER: 3131 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: P8291 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GPIB TALKER/LISTENER

MFEF REPORT NUMBER: 3132 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: D8288 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 20
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BUS CONTROLLER

MFEF REPORT NUMBER: 3133 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: D8273 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE HDLC/SDLC PROTOCOL CONTROLLER

MFEF REPORT NUMBER: 3134 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: D8257 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE DMA CONTROLLER

MFEF REPORT NUMBER: 3135 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3136 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3137 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3138 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3139 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3148 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8086 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 15 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3149 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8086 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3150 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8086 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: SWITCHING CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3151 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: D8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3152 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: P8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3153 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: P8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3154 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: P8085A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3155 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3156 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3157 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: VERIFIED SHORT SUPPLY FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3158 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3159 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: C8748 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: B B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: IMPROPER LOGIC STATE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: DATA RETENTION

MFEF REPORT NUMBER: 3160 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: D8291 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GPIB TALKER/LISTENER

MFEF REPORT NUMBER: 3161 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: P8289 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 20
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BUS ARBITER

MFEF REPORT NUMBER: 3162 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: P8289 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 20
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BUS ARBITER

MFEF REPORT NUMBER: 3163 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: D8288 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 20
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: SWITCHING CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BUS CONTROLLER

MFEF REPORT NUMBER: 3166 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: D8279 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 9 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE KEYBOARD DISPLAY INTERFACE

MFEF REPORT NUMBER: 3167 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: INTERFACE
PART NUMBER: P8279
DEVICE TECHNOLOGY: NMOS
PACKAGE: EPOXY DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: PERIPHERAL
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D-1 COMPLEXITY: 0
NUMBER OF PINS: 40
TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE KEYBOARD DISPLAY INTERFACE

MFEF REPORT NUMBER: 3168 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: CONTROL
PART NUMBER: C8275
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC/METAL DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: PROGRAMMABLE
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 0
NUMBER OF PINS: 40
TIME TO DETECTION: 1000

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE CRT CONTROLLER

MFEF REPORT NUMBER: 3169 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: BURN-IN
DEVICE FUNCTION: CONTROL
PART NUMBER: C8275
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC/METAL DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: PROGRAMMABLE
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 0
NUMBER OF PINS: 40
TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE CRT CONTROLLER

MFEF REPORT NUMBER: 3170 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: CONTROL
PART NUMBER: P8275
DEVICE TECHNOLOGY: NMOS
PACKAGE: EPOXY DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: PROGRAMMABLE
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D-1 COMPLEXITY: 0
NUMBER OF PINS: 40
TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE CRT CONTROLLER

MFEF REPORT NUMBER: 3171 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: CONTROL
PART NUMBER: P8273
DEVICE TECHNOLOGY: NMOS
PACKAGE: EPOXY DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: PROGRAMMABLE
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D-1 COMPLEXITY: 0
NUMBER OF PINS: 40
TIME TO DETECTION: 168

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE HDLC/SDLC PROTOCOL CONTROLLER

MEEF REPORT NUMBER: 3172 MEEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: D8273 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE HDLC/SDLC PROTOCOL CONTROLLER

MEEF REPORT NUMBER: 3173 MEEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: D8273 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 6 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE HDLC/SDLC PROTOCOL CONTROLLER

MEEF REPORT NUMBER: 3174 MEEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: P8259A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE INTERUPT CONTROLLER

MEEF REPORT NUMBER: 3175 MEEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: CR255A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE PERIPHERAL INTERFACE

MEEF REPORT NUMBER: 3176 MEEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: D8237 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PROGRAMMABLE DMA CONTROLLER

MFEF REPORT NUMBER: 3177 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3178 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: D8218/19 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3179 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: CONTROL CIRCUIT TYPE: BUS DRIVER
PART NUMBER: 8218 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: N/R DIP NUMBER OF PINS: 28
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3180 MFEF REPORT DATE: 0

DATA SOURCE: PH-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: P8289 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 0
PACKAGE: EPOXY DIP NUMBER OF PINS: 20
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CORROSION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BUS ARBITER

MFEF REPORT NUMBER: 3182 MFEF REPORT DATE: 7906

DATA SOURCE: AI-0027 SOURCE: REL PROD DEMO DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: AIF
DEVICE FUNCTION: ARRAY CIRCUIT TYPE: IMAGE SENSING
PART NUMBER: CCD221 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 0
DEVICE TECHNOLOGY: CCD SCREEN CLASS: NONE COMPLEXITY: 185440 B
PACKAGE: CERAMIC/WINDOWDIP NUMBER OF PINS: 22
QUANTITY FAILED: 5 TIME TO DETECTION: 0

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: PARTICLE BRIDGE DEFECT CAUSE: DENDRITE GROWTH
ACTIVATING STRESS A: HUMIDITY
ACTIVATING STRESS B: N/R

REMARKS: WHISKER GROWTH ALONG AND BETWEEN THE VOLTAGE LINES

MEEF REPORT NUMBER: 3237 MEEF REPORT DATE: 8007

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER 1802 PART MANUFACTURER: RCA DATE CODE: 8020
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: B-2 COMPLEXITY: 1375 G
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: BOND WIRES LIFTED ON CHIP PAD OR BALL SIDE OF BONDING WIRE. PACKAGE PINS WERE 7 AND 8

MEEF REPORT NUMBER: 3238 MEEF REPORT DATE: 8007

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 1802 PART MANUFACTURER: RCA DATE CODE: 8020
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: B-2 COMPLEXITY: 1375 G
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: BOND WIRE LIFTED ON CHIP PAD OR BALL SIDE OF BONDING WIRE. PACKAGE PIN WAS 5

MEEF REPORT NUMBER: 3239 MEEF REPORT DATE: 8007

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 1802 PART MANUFACTURER: RCA DATE CODE: 8020
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: B-2 COMPLEXITY: 1375 G
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: N/R
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: BOND WIRE BROKEN CHIP PAD O R BALL SIDE OF BONDING WIRE. PACKAGE PIN WAS 6

MEEF REPORT NUMBER: 3460 MEEF REPORT DATE: 8008

DATA SOURCE: GF-0013 SOURCE: FIELD DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: GF
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: 1012/1883 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: NONE COMPLEXITY: 0 0
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: N/R

REMARKS: UAR/T

MEEF REPORT NUMBER: 3461 MEEF REPORT DATE: 8007

DATA SOURCE: GF-0013 SOURCE: FIELD DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: GF
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: 1012/1883 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: NONE COMPLEXITY: 0 0
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/P

REMARKS: UAR/T

MFEF REPORT NUMBER: 3462 MFEF REPORT DATE: 8011

DATA SOURCE: GF-0013 SOURCE: FIELD DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: GF
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: 1012/1PR3 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: NONE COMPLEXITY: 0 0
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: UAR/T

MFEF REPORT NUMBER: 3467 MFEF REPORT DATE: 7905

DATA SOURCE: PQ-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/P
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: MD8080A PART MANUFACTURER: INTEL DATE CODE: 7833
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B-1 COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: DIE JUNCTION
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3469 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: AM9080A-2DM PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7813
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B-1 COMPLEXITY: 1100 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3470 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/P
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: AM9080A-2DM PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7813
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B-1 COMPLEXITY: 1100 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 5 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: OPEN (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3472 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: AM9080A-2DM PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7813
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1100 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GROSS LEAK TEST

MFEF REPORT NUMBER: 3473 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: AM9080A-2DM PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7813
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1100 G
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3474 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 38510/42001 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 6 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: FINE LEAK TEST

MFEF REPORT NUMBER: 3475 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 38510/42001 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 15 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GROSS LEAK TEST

MFEF REPORT NUMBER: 3476 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: 38510/42001 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3477 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: MD8080A PART MANUFACTURER: INTEL DATE CODE: 7833
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 5 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE SEAL
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: GROSS LEAK TEST

MFEF REPORT NUMBER: 3478 MFEF REPORT DATE: 8101

DATA SOURCE: PQ-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: PROCESSING UNIT CIRCUIT TYPE: CENTRAL
PART NUMBER: MD8080A PART MANUFACTURER: INTEL DATE CODE: 7833
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: NONE COMPLEXITY: 1500 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3506 MFEF REPORT DATE: 8008

DATA SOURCE: GF-0013 SOURCE: FIELD DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: GF
DEVICE FUNCTION: N/R CIRCUIT TYPE: RECEIVE/TRANSMIT
PART NUMBER: 1012/1883 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: NONE COMPLEXITY: 0 0
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: UAR/T

MFEF REPORT NUMBER: 3694 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: LOGIC ARRAY CIRCUIT TYPE: PROGRAMMABLE
PART NUMBER: PAL16R8J PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8121
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 145 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 20
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OTHER LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: DIODE

MFEF REPORT NUMBER: 3 MFEF REPORT DATE: 7510

DATA SOURCE: FE-0001 SOURCE: CHECKOUT DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: GF
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: DM76L70J/883 PART MANUFACTURER: NATIONAL SEMI DATE CODE: 7436
DEVICE TECHNOLOGY: LTTL SCREEN CLASS: B-2 COMPLEXITY: 8 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 14
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: NON-FUNCT,I+-OP,CATAS FAILURE MODE: CAPACITOR DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: DIELECTRIC BREAKDOWN
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BIT 3 INOPERATIVE. METAL SHORT TO ISOLATION TUB THRU OXIDE PINHOLE. SECOND UNIT BIT 8 INOPERATIVE.

MFEF REPORT NUMBER: 162 MFEF REPORT DATE: 7604

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 2048-2B PART MANUFACTURER: HARRIS SEMI DATE CODE: 7335
DEVICE TECHNOLOGY: TTL SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: INTERMETALLIC FORMATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: ALL INPUTS DRAW IIL -8 TO -12MA. GND-TO-DIE HEADER BOND DESTROYED BY AU-AL INTERMETALLICS DUE TO EXCESSIVE BOND TEMP.

MFEF REPORT NUMBER: 163 MFEF REPORT DATE: 7607

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7438
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: OXIDE
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SINGLE CELL STUCK AT ZERO. STRIPPING OF METAL REVEALED OXIDE DEFECT IN "WORD 0" CELL,CAUSING EXCESS GATE LEAKAGE IN CELL

MFEF REPORT NUMBER: 164 MFEF REPORT DATE: 7502

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM5508 PART MANUFACTURER: INTERSIL DATE CODE: 7410
DEVICE TECHNOLOGY: TTL SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: INTERMETALLIC FORMATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: INSUFFICIENT BOND CONNECTIONS DUE TO INTERMETALLICS.

MFEF REPORT NUMBER: 165 MFEF REPORT DATE: 7506

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7336
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: OPEN WHERE POLYSILICON RUN PASSES OVER OXIDE STEP INTO CONTACT WINDOW, PROBABLY CAUSED BY A MASKING DEFECT.

MFEF REPORT NUMBER: 166 MFEF REPORT DATE: 0

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/K
PART NUMBER: PART MANUFACTURER: DATE CODE: 7333
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/K COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE OF 1 TRANSISTOR.

MFEF REPORT NUMBER: 167 MFEF REPORT DATE: 7409

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/K
PART NUMBER: PART MANUFACTURER: DATE CODE: 7337
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/K COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 168 MFEF REPORT DATE: 7510

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/K
PART NUMBER: PART MANUFACTURER: DATE CODE: 7340
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/K COMPLEXITY: 0
PACKAGE: N/K N/K NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR

MFEF REPORT NUMBER: 169 MFEF REPORT DATE: 7334

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/K
PART NUMBER: PART MANUFACTURER: DATE CODE: 7326
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/K COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 170 MFEF REPORT DATE: 7333

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/K
PART NUMBER: PART MANUFACTURER: DATE CODE: 7325
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/K COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 171 MFEF REPORT DATE: 7337

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7328
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: ONE TRANSISTOR CELL HAD GATE-TO-DRAIN SHORT DUE TO PINHOLE IN THE OXIDE.

MFEF REPORT NUMBER: 172 MFEF REPORT DATE: 7426

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7345
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 173 MFEF REPORT DATE: 7401

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7330
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 174 MFEF REPORT DATE: 7446

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7346
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 175 MFEF REPORT DATE: 7541

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7406
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 176 MFEF REPORT DATE: 7152

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7132
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 177 MFEF REPORT DATE: 7526

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7407
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 178 MFEF REPORT DATE: 7446

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: PART MANUFACTURER: DATE CODE: 7347
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN GATE OXIDE OF 1 CELL TRANSISTOR.

MFEF REPORT NUMBER: 219 MFEF REPORT DATE: 7504

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: PART MANUFACTURER: DATE CODE: 7343
DEVICE TECHNOLOGY: STTL SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: C-B SHORT IN DRIVER OUTPUT TRANSISTOR FOR ROW 62 OF THE MATRIX.

MFEF REPORT NUMBER: 225 MFEF REPORT DATE: 7507

DATA SOURCE: FE-0003 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3601 PART MANUFACTURER: INTEL DATE CODE: 7503
DEVICE TECHNOLOGY: STTL SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL PROM FUSE
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: GROWBACK
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: POLYSILICON FUSE REGROWTH.

MFEF REPORT NUMBER: 272 MFEF REPORT DATE: 7604

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 5306E PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 7524
DEVICE TECHNOLOGY: TTL SCREEN CLASS: N/K COMPLEXITY: 2048 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: METAL PROM FUSE
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: GROWBACK
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: REGROWTh.

MFEF REPORT NUMBER: 289 MFEF REPORT DATE: 7606

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 91L02 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7536
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: WIRE
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: BROKEN BONDING WIRE CAUSING OPEN INPUT PIN.

MFEF REPORT NUMBER: 290 MFEF REPORT DATE: 7606

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 91L02 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7536
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE BODY
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: N/K
ACTIVATING STRESS A: MECHANICAL STRESS
ACTIVATING STRESS B: N/K

REMARKS: CRACKED PACKAGE CAUSING OPEN INPUT PIN.

MFEF REPORT NUMBER: 292 MFEF REPORT DATE: 7607

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 91L02 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7536
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: WIREBOND LEAD FRAME NOC
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: BROKEN BONDING WIRE AT PACKAGE LEAD FRAME.

MFEF REPORT NUMBER: 293 MFEF REPORT DATE: 7607

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 91L02 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7536
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE BODY
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: N/K
ACTIVATING STRESS A: MECHANICAL STRESS
ACTIVATING STRESS B: N/K

REMARKS: CRACKED PACKAGE CAUSED OPEN LEADFRAME AT PIN 1.

MFEF REPORT NUMBER: 309 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2102 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7608
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: N/K

REMARKS: INPUT PROTECTION DIODE/RESISTOR HAD SOFT BREAKDOWN [TYPICALLY CAUSED BY STATIC DISCHARGE].

MFEF REPORT NUMBER: 310 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 9102 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7551
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K N/K NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: N/K

REMARKS: HIGH CURRENT DUE TO ABNORMAL SOFT BREAKDOWN IN PROTECTION NETWORK DUE TO STATIC ELECTRICITY.

MFEF REPORT NUMBER: 354 MFEF REPORT DATE: 7602

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 7552 PART MANUFACTURER: INTERSIL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 12 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: ROW DRIVER CAUSED FROM 1 TO 5 CELLS ON EACH DEVICE TO BE "STUCK-AT". DATE CODES 7438,7442,7445,7450.

MFEF REPORT NUMBER: 355 MFEF REPORT DATE: 7610

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL POLYSILICON CONDUCTOR
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PARALLEL POLYSILICON RUNS SHORTED DUE TO MASK DEFECT. DATE CODES 7435,7440,7442.

MFEF REPORT NUMBER: 356 MFEF REPORT DATE: 7605

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7438
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED HI FAILURE MODE: N/K
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: SINGLE CELL STUCK AT 1 DUE TO MASKING DEFECT.

MFEF REPORT NUMBER: 357 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7439
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: WIREBOND NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: INTERMETALLIC FORMATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: GOLD-ALUMINUM INTERMETALLICS DUE TO BONDING PROCESS DEFECTS.

MFEF REPORT NUMBER: 358 MFEF REPORT DATE: 7605

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED HI FAILURE MODE: N/K
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: ROW DRIVER INOPERATIVE DUE TO MANUFACTURING DEFECT.

MFEF REPORT NUMBER: 359 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7450
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED HI FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE DUE TO MASKING DEFECT.

MFEF REPORT NUMBER: 360 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7520
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: PINHOLE IN GATE OXIDE DUE TO MASKING DEFECT.

MFEF REPORT NUMBER: 361 MFEF REPORT DATE: 7611

DATA SOURCE: FE-0003 SOURCE: N/K DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: IM7552 PART MANUFACTURER: INTERSIL DATE CODE: 7520
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/K COMPLEXITY: 1024 B
PACKAGE: N/K DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: SINGLE CELL STUCK AT [1] DUE TO A GATE OXIDE DEFECT.

MFEF REPORT NUMBER: 393 MFEF REPORT DATE: 7602

DATA SOURCE: FE-0003 SOURCE: N/K
DEVICE FUNCTION: MEMORY
PART NUMBER:
DEVICE TECHNOLOGY: STTL
PACKAGE: N/K N/K
QUANTITY FAILED: 1
DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
CIRCUIT TYPE: PROM
PART MANUFACTURER:
SCREEN CLASS: N/K
NUMBER OF PINS: 0
TIME TO DETECTION: 0
DATE CODE: 7335
COMPLEXITY: 0

FAILURE INDICATOR: OUTPUT LATCHED HI
DEFECT DESCRIPTION: FAULT (NOC)
FAILURE MODE: DIE CRYSTAL
DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: BASE-TO-SUBSTRATE LEAKAGE ON SUBSTRATE PNP DUE TO IMPROPER PROCESSING.

MFEF REPORT NUMBER: 394 MFEF REPORT DATE: 7602

DATA SOURCE: FE-0003 SOURCE: N/K
DEVICE FUNCTION: MEMORY
PART NUMBER: 2048-2B
DEVICE TECHNOLOGY: STTL
PACKAGE: N/K N/K
QUANTITY FAILED: 1
DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
CIRCUIT TYPE: PROM
PART MANUFACTURER: HARRIS SEMI
SCREEN CLASS: N/K
NUMBER OF PINS: 0
TIME TO DETECTION: 0
DATE CODE: 7335
COMPLEXITY: 0

FAILURE INDICATOR: DYN CHAR OUT OF TOL
DEFECT DESCRIPTION: FAULT (NOC)
FAILURE MODE: METALIZATION NOC
DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: DEFECT IN GROUND METALIZATION.

MFEF REPORT NUMBER: 415 MFEF REPORT DATE: 7605

DATA SOURCE: FE-0003 SOURCE: N/K
DEVICE FUNCTION: MEMORY
PART NUMBER: F93421
DEVICE TECHNOLOGY: TTL
PACKAGE: N/K N/K
QUANTITY FAILED: 1
DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/K
CIRCUIT TYPE: RAM
PART MANUFACTURER: FAIRCHILD SEMI
SCREEN CLASS: N/K
NUMBER OF PINS: 16
TIME TO DETECTION: 0
DATE CODE: 7436
COMPLEXITY: 256 B

FAILURE INDICATOR: OUTPUT LATCHED LOW
DEFECT DESCRIPTION: FAULT (NOC)
FAILURE MODE: N/K
DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: SINGLE CELL STUCK AT ZERO.

MFEF REPORT NUMBER: 416 MFEF REPORT DATE: 7410

DATA SOURCE: FE-0003 SOURCE: N/K
DEVICE FUNCTION: MEMORY
PART NUMBER: 5531
DEVICE TECHNOLOGY: LSTTL
PACKAGE: N/K N/K
QUANTITY FAILED: 3
DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
CIRCUIT TYPE: RAM
PART MANUFACTURER: MONOLITHIC MEMORIES
SCREEN CLASS: N/K
NUMBER OF PINS: 16
TIME TO DETECTION: 0
DATE CODE: 0
COMPLEXITY: 256 B

FAILURE INDICATOR: OUTPUT LATCHED LOW
DEFECT DESCRIPTION: FAULT (NOC)
FAILURE MODE: METALIZATION NOC
DEFECT CAUSE: N/K
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/K

REMARKS: THREE DEVICES HAD VCC METAL FAULTS.

MFEF REPORT NUMBER: 417 MFEF REPORT DATE: 7406

DATA SOURCE: FE-0003 SOURCE: N/K
DEVICE FUNCTION: MEMORY
PART NUMBER: MM5531D
DEVICE TECHNOLOGY: LSTTL
PACKAGE: N/K N/K
QUANTITY FAILED: 2
DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: NSS
CIRCUIT TYPE: RAM
PART MANUFACTURER: MONOLITHIC MEMORIES
SCREEN CLASS: N/K
NUMBER OF PINS: 16
TIME TO DETECTION: 0
DATE CODE: 7316
COMPLEXITY: 256 B

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC
DEFECT DESCRIPTION: MELTED-FUSED
FAILURE MODE: METALIZATION NOC
DEFECT CAUSE: N/K
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/K

REMARKS: MELTED INPUT METALIZATION.

MFEF REPORT NUMBER: 418 MFEF REPORT DATE: 7606

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 5306-1 PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 7551
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: N/R COMPLEXITY: 2048 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: IMPROPER DESIGN ALLOWS EXCESSIVE TRI-STATE LEAKAGE CURRENTS.

MFEF REPORT NUMBER: 419 MFEF REPORT DATE: 7606

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 5306-1 PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 7551
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: N/R COMPLEXITY: 2048 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: EXTRA PROGRAMMING IN ONE ROW DUE TO A MASKING DEFECT IN THE 1 OF 64 DECODER.

MFEF REPORT NUMBER: 440 MFEF REPORT DATE: 7607

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: PART MANUFACTURER: DATE CODE: 0
DEVICE TECHNOLOGY: TTL SCREEN CLASS: N/R COMPLEXITY: 0
PACKAGE: N/R N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: FIELD OXIDE/DIELECTRIC
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PINHOLE IN THERMAL OXIDE BENEATH THE INPUT METALIZATION.

MFEF REPORT NUMBER: 573 MFEF REPORT DATE: 7701

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 7552 PART MANUFACTURER: INTERSIL DATE CODE: 7451
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: N/R N/R NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT INPUT FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: N/R

REMARKS: INPUT 11 TRANSISTOR S-G SHORT. SUSPECT ESD RESULTED IN GATE OXIDE BREAKDOWN IN FAILING TRANSISTOR. NOT CONFIRMED.

MFEF REPORT NUMBER: 574 MFEF REPORT DATE: 7701

DATA SOURCE: FE-0003 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: AM9102 PART MANUFACTURER: ADVANCED MICRO DEVICES DATE CODE: 7540
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: N/R N/R NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: PACKAGE LEAD FRAME/EXTERNAL LEADS
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: BLACK FOREIGN MATERIAL [AU,NI,CR,SN,AL] ATTACHED AT PIN 9,10,11 LD FRAMES [SHORT]. GOLD PLATING AT P10 LOOSE,PROTRUDE UP

MFEF REPORT NUMBER: 575 MFEF REPORT DATE: 0

DATA SOURCE: FE-0003 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 7552
DEVICE TECHNOLOGY: NMOS
PACKAGE: N/R N/R
QUANTITY FAILED: 1

DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTERSIL DATE CODE: 7436
SCREEN CLASS: N/R COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: 32 ADDRESS LOCATIONS OF 1 ROW FAILED. DEFECT IN ISOLATING GLASS BETW AL METAL OF DEFECTIVE ROW & POLY. LINE. MASK DEFECT

MFEF REPORT NUMBER: 576 MFEF REPORT DATE: 0

DATA SOURCE: FE-0003 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 7552
DEVICE TECHNOLOGY: NMOS
PACKAGE: N/R N/R
QUANTITY FAILED: 7

DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTERSIL DATE CODE: 7400
SCREEN CLASS: N/R COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: INTERMETALLIC FORMATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHLORINE RESIDUE COVERS DEFECTIVE BOND PADS, CAUSING INTERMETALLICS BETWEEN GOLD BALL BONDS & AL BOND PADS. 4 DATE CODES

MFEF REPORT NUMBER: 577 MFEF REPORT DATE: 0

DATA SOURCE: FE-0003 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 7552
DEVICE TECHNOLOGY: NMOS
PACKAGE: N/R N/R
QUANTITY FAILED: 1

DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTERSIL DATE CODE: 7451
SCREEN CLASS: N/R COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: NUMEROUS ADDRESSES "STUCK LOW" AT 125C. SUSPECT DEFECT DUE TO IMPROPER CONTROLS DURING GATE OXIDE APPL., LOWERS THRESHLD

MFEF REPORT NUMBER: 578 MFEF REPORT DATE: 0

DATA SOURCE: FE-0003 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 7552
DEVICE TECHNOLOGY: NMOS
PACKAGE: N/R N/R
QUANTITY FAILED: 1

DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTERSIL DATE CODE: 7451
SCREEN CLASS: N/R COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED HI FAILURE MODE: GATE OXIDE/DIELECTRIC
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: NUMEROUS ADDRESSES "STUCK HI" AT 100C. SUSPECT DEFECT DUE TO IMPROPER CONTROLS DURING GATE OXIDE APPL., LOWERS THRESHOLD

MFEF REPORT NUMBER: 594 MFEF REPORT DATE: 0

DATA SOURCE: FE-0004 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 7552
DEVICE TECHNOLOGY: NMOS
PACKAGE: N/R N/R
QUANTITY FAILED: 1

DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTERSIL DATE CODE: 7450
SCREEN CLASS: N/R COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: FAILURE MODE/DEFECT COULD NOT BE DETERMINED. SUSPECT LEAKY TRANSISTOR WITHIN CELL 465, BUT LEAKAGE PATH NOT ISOLATED.

MFEF REPORT NUMBER: 619 MFEF REPORT DATE: 7810

DATA SOURCE: FE-0005 SOURCE: DEV EVALUATION DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: PART MANUFACTURER: DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: N/R COMPLEXITY: 256 B
PACKAGE: METAL FPK NUMBER OF PINS: 16
QUANTITY FAILED: 13 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT COMB FAILURE MODE: WIREBOND DIE PAD NOC
DEFECT DESCRIPTION: MISALIGNED/MISPLACED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: MISPLACED BONDS CAUSED VARIOUS PIN-TO-VCC AND PIN-TO-GND SHORTS, DUE TO CLOSE SPACING BETWEEN BOND PADS AND METALIZATION

MFEF REPORT NUMBER: 620 MFEF REPORT DATE: 7810

DATA SOURCE: FE-0005 SOURCE: DEV EVALUATION DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: PART MANUFACTURER: DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: N/R COMPLEXITY: 256 B
PACKAGE: METAL FPK NUMBER OF PINS: 16
QUANTITY FAILED: 0 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: WIREBOND LEAD FRAME NOC
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: POST-ANNEAL BOND-PULL TESTS REVEALED 0 GM LIFTED BONDS DUE TO DEFECTIVE GOLD PLATING AT PKG POST. PLATING ALSO LIFTED.

MFEF REPORT NUMBER: 621 MFEF REPORT DATE: 7810

DATA SOURCE: FE-0005 SOURCE: DEV EVALUATION DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: PART MANUFACTURER: DATE CODE: 0
DEVICE TECHNOLOGY: STTL SCREEN CLASS: N/R COMPLEXITY: 2048 B
PACKAGE: METAL FPK NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: WIREBOND LEAD FRAME NOC
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: 4 BONDS LIFTED AT PACKAGE POST DUE TO PLATING PROCESS DEFECTS. GOLD PLATING WAS LIFTING FROM POST WITH THE BOND.

MFEF REPORT NUMBER: 1747 MFEF REPORT DATE: 7605

DATA SOURCE: PI-0002 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/A
PART NUMBER: 8274 PART MANUFACTURER: VARIOUS DATE CODE: 7546
DEVICE TECHNOLOGY: TTL SCREEN CLASS: D-1 COMPLEXITY: 105 G
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1993 MFEF REPORT DATE: 7801

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: DD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 73 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1994 MFEF REPORT DATE: 7902

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: DD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1995 MFEF REPORT DATE: 7806

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: DD2115A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1996 MFEF REPORT DATE: 7804

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: PE2141 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 4096 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 7 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1997 MFEF REPORT DATE: 7804

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: PE2141 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 4096 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1998 MFEF REPORT DATE: 7806

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: DD2141 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 1999 MFEF REPORT DATE: 7905

DATA SOURCE: PM-00 E: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE F ORY CIRCUIT TYPE: PROM
PART PART MANUFACTURER: INTEL DATE CODE: 0
DEVI S SCREEN CLASS: D COMPLEXITY: 16384 B
PAC DIP NUMBER OF PINS: 24
QUANTI 5 TIME TO DETECTION: 48

FAILURE INDICA NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESC N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2000 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2002 MFEF REPORT DATE: 7906

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2003 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2004 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATO NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DE CRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2005 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 10 TIME TO DETECTION: 166

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2006 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 6 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2007 MFEF REPORT DATE: 7906

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2008 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2009 MFEF REPORT DATE: 7810

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CL2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2010 MFEF REPORT DATE: 7901

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 8 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2011 MFEF REPORT DATE: 7902

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 9 TIME TO DETECTION: 1000

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2012 MFEF REPORT DATE: 7901

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2013 MFEF REPORT DATE: 7902

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2014 MFEF REPORT DATE: 7903

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2015 MFEF REPORT DATE: 7904

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2016 MFEF REPORT DATE: 7901

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2017 MFEF REPORT DATE: 7902

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 1000

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2018 MFEF REPORT DATE: 7901

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CC2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: NON-FUNCT,IN-OP,CATAS FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2329 MFEF REPORT DATE: 7905

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 7T93471 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7832
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 160

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2330 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 6D93415 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7843
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 1024 B
16 PACKAGE: HERMETIC DIP NUMBER OF PINS:
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE NOC
DEFECT DESCRIPTION: HOLE DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2331 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 6D93425 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7911
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2332 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 9B93415 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7920
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE NOC
DEFECT DESCRIPTION: HOLE DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2333 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 6D10415 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7904
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2334 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 7L93L451 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7912
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2341 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: AM27LS00DM PART MANUFACTURER: DATE CODE: 7744
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 4000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2342 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: AM27LS00DM PART MANUFACTURER: DATE CODE: 7744
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 9 TIME TO DETECTION: 4000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: PIN NO. FAILED WERE 6 AND 12.

MFEF REPORT NUMBER: 2343 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 4000

FAILURE INDICATOR: HI LVL INPUT CUR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: PIN NO. FAILED 14.

MFEF REPORT NUMBER: 2344 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 32

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL. WERE IIL,IIH AND BIIH. PIN 13 FAILED. DEVICE FAILED AT 32HRS BUT LEFT ON TEST TO 3000HRS

MFEF REPORT NUMBER: 2345 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO. FAILED WERE 6 AND 12.

MFEF REPORT NUMBER: 2346 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO. FAILED WERE 6 AND 12.

MFEF REPORT NUMBER: 2347 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 4000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO. FAILED WERE 6 AND 12.

MFEF REPORT NUMBER: 2349 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 64

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO. FAILED WERE 6 AND 12. DEVICE TTD AT 64HRS BUT LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION WAS SEEN.

MFEF REPORT NUMBER: 2350 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 128

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL WERE PROPAGATION DELAY&IIH PIN NO FAILED WERE 1,6&12 DEVICE LEFT ON TEST TO 3000HRS THEN EMIG SEEN

MFEF REPORT NUMBER: 2351 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 128

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE IIL,IIH&PROP-DELAY PIN NO FAILED ARE 6,12&15 DEVICE LEFT ON TEST TO 3000HRS WHERE EMIG SEEN

MFEF REPORT NUMBER: 2352 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 126

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12 DEVICE LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION WAS SEEN.

MFEF REPORT NUMBER: 2353 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 128

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE IIL,IIH,BIIH&PROP-DELAY PIN NO FAILED ARE 4,6&12 DEVICE LEFT ON TEST TO 3000HRS WHEN EMIG SEEN

MFEF REPORT NUMBER: 2354 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 250

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12 DEVICE LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION WAS SEEN.

MFEF REPORT NUMBER: 2355 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED 6&12 DEVICE LEFT ON TEST TO 3000 HRS AT WHICH TIME ELECTROMIGRATION WAS SEEN.

MFEF REPORT NUMBER: 2356 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 2000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS&PROP-DELAY PIN NO FAILED ARE 6,7,9&12.

MFEF REPORT NUMBER: 2357 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12

MFEF REPORT NUMBER: 2358 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12

MFEF REPORT NUMBER: 2359 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS&PROP-DELAY PIN NO FAILED ARE 6,7,9&12

MFEF REPORT NUMBER: 2360 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IOS&PROP-DELAY PIN NO FAILED ARE 6&12

MFEF REPORT NUMBER: 2361 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IOS,IZL&PROP-DELAY PIN NO FAILED ARE 6&12.

MFEF REPORT NUMBER: 2362 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE IIL,IIH&BIIH PIN NO FAILED IS 7.

MFEF REPORT NUMBER: 2363 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETER OUT OF TOL IS IOS PIN NO FAILED 6&12.

MFEF REPORT NUMBER: 2364 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL IS VOH PN NO FAILED IS 6.

MFEF REPORT NUMBER: 2365 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH&IOS PIN NO FAILED IS 6.

MFEF REPORT NUMBER: 2372 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: AM27LS000M PART MANUFACTURER: DATE CODE: 7744
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 32

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12.

MFEF REPORT NUMBER: 2373 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 32

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH&IOS PIN NO FAILED IS 6 DEVICE LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION SEEN.

MFEF REPORT NUMBER: 2374 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 64

FAILURE INDICATOR: SUPPLY CUR OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED IS 16 DEVICE LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION SEEN.

MFEF REPORT NUMBER: 2375 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 64

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL&IIL PIN NO FAILED ARE 2-7,9,11,13-15 DEVICE LEFT ON TEST TO 3000HRS THEN EMIG NOTED.

MFEF REPORT NUMBER: 2376 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 128

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12 DEVICE LEFT ON TEST TO 3000HRS AT WHICH TIME ELECTROMIGRATION SEEN.

MFEF REPORT NUMBER: 2377 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH&IOS PIN NO FAILED IS 6.

MFEF REPORT NUMBER: 2378 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 2000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12.

MFEF REPORT NUMBER: 2379 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS&PROP-DELAY PIN NO FAILED ARE 6,7,9,10,11&12.

MFEF REPORT NUMBER: 2380 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS&PROP-DELAY PIN NO FAILED ARE 6,7,9&12.

MFEF REPORT NUMBER: 2381 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 3000

FAILURE INDICATOR: PROPGN DELAY OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PIN NO FAILED ARE 6&12.

MFEF REPORT NUMBER: 2382 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH&IOS PIN NO FAILED IS 6.

MFEF REPORT NUMBER: 2383 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0000 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML53[illegible] PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LS[illegible] SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOL,VIC&I2L PIN NO FAILED ARE ALL

MFEF REPORT NUMBER: 2384 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS,VIC&PROP-DELAY PIN NO FAILED ARE ALL

MFEF REPORT NUMBER: 2385 MFEF REPORT DATE: 0

DATA SOURCE: PQ-0005 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MML5531D PART MANUFACTURER: DATE CODE: 7626
DEVICE TECHNOLOGY: LSTTL SCREEN CLASS: B-1 COMPLEXITY: 256 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 3000

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: ELECTROMIGRATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: VOLTAGE AND CURRENT STRESS

REMARKS: PARAMETERS OUT OF TOL ARE VOH,VOL,IIL,IOS&PROP-DELAY PIN NO FAILED ARE 6,7,9&12

MFEF REPORT NUMBER: 2386 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 9U9403A PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7916
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D-1 COMPLEXITY: 64 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2387 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 7L9343C PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7905
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIRE
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2388 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 7L93L451 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7912
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2389 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 7L93438 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7917
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: HERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: IMPURITIES DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2390 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 9N93438 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7914
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D-1 COMPLEXITY: 4096 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: IMP OPEN OUTPUT NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2391 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 9B93427 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7917
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE NOC
DEFECT DESCRIPTION: HOLE DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2392 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/K APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 9B93446 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7919
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D-1 COMPLEXITY: 2048 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIRE
DEFECT DESCRIPTION: BROKEN DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2393 MFEF REPORT DATE: 7912

DATA SOURCE: PM-0001 SOURCE: LIFE DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 9B93436 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7924
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: B-1 COMPLEXITY: 2048 B
PACKAGE: NONHERMETIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: WIRE
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2395 MFEF REPORT DATE: 0

DATA SOURCE: PM-0008 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: Z6116 PART MANUFACTURER: ZILOG DATE CODE: 7828
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 0
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2396 MFEF REPORT DATE: 0

DATA SOURCE: PM-0008 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: Z6116 PART MANUFACTURER: ZILOG DATE CODE: 7815
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B COMPLEXITY: 16384 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT OUTPUT FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: DATA OUT SHORTED TO GND

MFEF REPORT NUMBER: 2398 MFEF REPORT DATE: 0

DATA SOURCE: PM-0008 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: Z80SIO PART MANUFACTURER: ZILOG DATE CODE: 7908
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B COMPLEXITY: 3300 G
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: PINHOLE DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2399 MFEF REPORT DATE: 0

DATA SOURCE: PM-0008 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: INTERFACE CIRCUIT TYPE: PERIPHERAL
PART NUMBER: Z80SIO PART MANUFACTURER: ZILOG DATE CODE: 7816
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: B-1 COMPLEXITY: 3300 G
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: OPEN (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2465 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: 2609/6570 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2466 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: 2609/6570 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 33 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2467 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: 2609/6570 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 70 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2468 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2841/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 10 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2469 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2841/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 25 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2470 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2841/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 256 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 53 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2471 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 3604/82S140 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: TTL SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2472 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 3604/82S140 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: TTL SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2473 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: 3604/82S140 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: TTL SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2474 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2475 MFEF REPORT DATE: 7803

DATA SOURCE: FU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 75 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2476 MFEF REPORT DATE: 7803

DATA SOURCE: FU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101A PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 17 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2477 MFEF REPORT DATE: 7803

DATA SOURCE: FU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101A PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2478 MFEF REPORT DATE: 7803

DATA SOURCE: FU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101A PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 62 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2479 MFEF REPORT DATE: 7803

DATA SOURCE: FU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: 2609/6570 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2480 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: 2609/6570 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 24
QUANTITY FAILED: 56 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2481 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2041/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D-1 COMPLEXITY: 256 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2482 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2041/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D-1 COMPLEXITY: 256 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2483 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: N/R
PART NUMBER: 2841/3341 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D-1 COMPLEXITY: 256 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 10 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2484 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2485 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2101 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 1024 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2498 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2107/5280 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 560 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2499 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2107/5280 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 2668 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2500 MFEF REPORT DATE: 7803

DATA SOURCE: PU-0003 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: GB
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2107/5280 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1317 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2502 MFEF REPORT DATE: 0

DATA SOURCE: AU-0005 SOURCE: FIELD DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: AUF
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: SL-6-2064 PART MANUFACTURER: VARIOUS DATE CODE: 0
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: C-1 COMPLEXITY: 128 B
PACKAGE: HERMETIC FPK NUMBER OF PINS: 14
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2507 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 23 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2508 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 69 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2509 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 37 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2510 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2511 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2512 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 11 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2513 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 21 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2514 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 15 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2515 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 14 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2516 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2517 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2518 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 10 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2519 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2520 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2521 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2522 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 86 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2523 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 76 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2524 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 81 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2525 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 7 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2526 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 30 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2527 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: LOOSE DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2528 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2529 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2148H/49H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2530 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2148H/49H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2531 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD5101 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: MASK FAULT DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2532 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2533 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2534 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: SLOW ACCESS TIME

MFEF REPORT NUMBER: 2535 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: FAIL AC

MFEF REPORT NUMBER: 2536 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2537 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 100 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2538 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 9 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2539 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 43 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SPEED

MFEF REPORT NUMBER: 2540 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 24 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2541 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 19 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2542 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 8 TIME TO DETECTION: 48

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2543 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: OUTPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2544 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2545 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 10 TIME TO DETECTION: 48

FAILURE INDICATOR: OUTPUT VOLT OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2546 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2547 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 21 TIME TO DETECTION: 48

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: TACC

MFEF REPORT NUMBER: 2548 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: SPEED

MFEF REPORT NUMBER: 2549 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: ROW FAILURE

MFEF REPORT NUMBER: 2550 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 42 TIME TO DETECTION: 48

FAILURE INDICATOR: IMPROPER LOGIC STATE FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2551 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 N
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 131 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2552 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2553 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 6 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2554 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0001 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2555 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 8 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2556 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: OUTPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2557 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: VERIFIED SHORT SUPPLY FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2558 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: OPEN PIN

MFEF REPORT NUMBER: 2559 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 4 TIME TO DETECTION: 48

FAILURE INDICATOR: MEMORY DATA LOSS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2560 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: IMPROPER LOGIC STATE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHANGE GAIN

MFEF REPORT NUMBER: 2561 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2562 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 4 TIME TO DETECTION: 48

FAILURE INDICATOR: MEMORY DATA LOSS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2563 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 8 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2564 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2565 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: ISOLATION

MFEF REPORT NUMBER: 2566 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2567 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2568 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2569 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2570 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2571 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2572 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2573 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115M PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2574 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115M PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2575 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 17 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2576 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2577 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 8 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2578 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2579 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2580 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2581 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2582 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2583 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2584 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL BOND PAD
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2585 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 8 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2586 MFEF REPORT DATE: 8003

DATA SOURCE: FM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 8 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2587 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2588 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2589 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: CP2141 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 4096 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2590 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2591 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 6 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2592 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2593 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2594 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2595 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: GLASSIVATION
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2596 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B N/R

REMARKS:

MFEF REPORT NUMBER: 2597 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2598 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: GLASSIVATION
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2599 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2600 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2601 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 2000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2602 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEV APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2603 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 5 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2604 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2605 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2606 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2607 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2148H/49H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2608 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD5101 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2609 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M3605A/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2610 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD3628A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL BOND PAD
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2611 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 10 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2612 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2613 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2614 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 168

FAILURE INDICATOR: OTHER LEAKAGE FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2615 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 11 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2616 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2617 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2618 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SPEED

MFEF REPORT NUMBER: 2619 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2620 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2621 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 10 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2622 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 25 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2623 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 18 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2624 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 6 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2625 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2626 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2627 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2628 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2629 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2630 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2631 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2632 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2633 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2634 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2635 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2636 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2637 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 1000

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2638 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2639 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2640 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2641 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2642 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2643 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2644 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2645 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2646 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2647 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2648 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CONTAMINATION

MFEF REPORT NUMBER: 2649 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: ENVIRONMENTAL DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CONTAMINATION

MFEF REPORT NUMBER: 2650 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2651 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2652 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL OXIDE STEP/CUTOUT
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2653 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2107C PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2654 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2655 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2656 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 7 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2657 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 4 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2658 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2659 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2104A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 5 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2660 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2661 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2115/25A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2662 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 6 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2663 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 6 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2664 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL BOND PAD
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2665 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 6 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2666 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 2117 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 11 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2667 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: MEMORY
PART NUMBER: 2117
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 16
TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2667 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: MEMORY
PART NUMBER: 2117
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 16
TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2668 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: MEMORY
PART NUMBER: 2117
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC DIP
QUANTITY FAILED: 2

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 16
TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL BOND PAD
DEFECT DESCRIPTION: LIFTED DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2669 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: MEMORY
PART NUMBER: 2117
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC DIP
QUANTITY FAILED: 3

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 16
TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2670 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE
DEVICE FUNCTION: MEMORY
PART NUMBER: 2117
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 16
TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METAL BOND PAD
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2671 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2672 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2673 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2674 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2118 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2675 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 4 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2676 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: METALIZATION NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2677 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2678 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2679 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2680 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147H PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 3 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2681 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD5101 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2682 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 8 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2683 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: NON-FUNCT, IN-OP, CATAS FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2684 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 83 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2685 MFEF REPORT DATE: 8003

DATA SOURCE: PH-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2686 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: FROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2687 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: FROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 168

FAILURE INDICATOR: IMPROPER OUTPUT NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2688 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: FROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 29 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2689 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: FROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 500

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2690 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: FROM
PART NUMBER: MD2708 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: LIGHT SENSITIVE

MFEF REPORT NUMBER: 2691 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 44 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2692 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: DECODER FAILURE

MFEF REPORT NUMBER: 2693 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: EDGE BIT CHARGE LOSS NO FAILURE ANALYSIS

MFEF REPORT NUMBER: 2694 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2695 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SPEED

MFEF REPORT NUMBER: 2696 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 57 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2697 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2698 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SPEED

MFEF REPORT NUMBER: 2699 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 58 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2700 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: ROW FAILURE

MFEF REPORT NUMBER: 2701 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 2702 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE GAIN

MFEF REPORT NUMBER: 2703 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: SPEED

MFEF REPORT NUMBER: 2704 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: M2716 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 1000

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE LOSS

MFEF REPORT NUMBER: 2705 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2706 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 5 TIME TO DETECTION: 168

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2707 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 8 TIME TO DETECTION: 48

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2708 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 4 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2709 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: N/K DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS:

MFEF REPORT NUMBER: 2710 MFEF REPORT DATE: 8003

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MD2732A PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 32768 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: DYN CHAR OUT OF TOL FAILURE MODE: N/K
DEFECT DESCRIPTION: N/K DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/K

REMARKS: CHARGE RETENTION

MFEF REPORT NUMBER: 2751 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MULTIPLEXER CIRCUIT TYPE: N/R
PART NUMBER: HI506A PART MANUFACTURER: HARRIS SEMI DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 52 G
PACKAGE: HERMETIC N/R NUMBER OF PINS: 0
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: COMB PARAMETERS OUT OF TOL FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#4145

MFEF REPORT NUMBER: 2752 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MULTIPLEXER CIRCUIT TYPE: N/R
PART NUMBER: HI506A PART MANUFACTURER: HARRIS SEMI DATE CODE: 7552
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 52 G
PACKAGE: HERMETIC N/R NUMBER OF PINS: 0
QUANTITY FAILED: 7 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: [illegible]ICAL OVERSTRESS
ACTIVATING STRESS B: [illegible]

REMARKS: TR#5663-5587-5588-5589-5590-5591

MFEF REPORT NUMBER: 2792 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: MEM3050 PART MANUFACTURER: GENERAL INSTRUMENTS DATE CODE: 0
DEVICE TECHNOLOGY: PMOS SCREEN CLASS: D COMPLEXITY: 50 B
PACKAGE: METAL CAN NUMBER OF PINS: 10
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FLUCT/OSC OUTPUT FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#2820

MFEF REPORT NUMBER: 2864 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MULTIPLEXER CIRCUIT TYPE: N/R
PART NUMBER: AY6-4016 PART MANUFACTURER: GENERAL INSTRUMENTS DATE CODE: 7409
DEVICE TECHNOLOGY: MOS (NOC) SCREEN CLASS: D COMPLEXITY: 0
PACKAGE: HERMETIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: SURFACE
DEFECT DESCRIPTION: EXTRANEOUS PARTICLE DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#5926

MFEF REPORT NUMBER: 2938 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: 4031 PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 64 B
PACKAGE: HERMETIC N/R NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: SWITCHING CHAR OUT OF TOL FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#4492

MFEF REPORT NUMBER: 2939 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: SHIFT REGISTER CIRCUIT TYPE: N/R
PART NUMBER: CD4031A PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 64 B
PACKAGE: HERMETIC N/R NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: HOLE DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TR#3181

MFEF REPORT NUMBER: 2983 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: TMS4060JL PART MANUFACTURER: TEXAS INSTRUMENTS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 22
QUANTITY FAILED: 3 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TR#5079

MFEF REPORT NUMBER: 2984 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: TMS4060 PART MANUFACTURER: TEXAS INSTRUMENTS DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: N/R COMPLEXITY: 4096 B
PACKAGE: N/R DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED OPEN NOC FAILURE MODE: WIREBOND NOC
DEFECT DESCRIPTION: FAULT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#4428

MFEF REPORT NUMBER: 2985 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: TMS4060JL PART MANUFACTURER: TEXAS INSTRUMENTS DATE CODE: 7620
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT SUPPLY FAILURE MODE: N/R
DEFECT DESCRIPTION: SHORT (NOC) DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TR#5740

MFEF REPORT NUMBER: 2986 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: SNC4060JR PART MANUFACTURER: TEXAS INSTRUMENTS DATE CODE: 7620
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 4096 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 22
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: METAL CONTACT WINDOW
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TR#5465

MFEF REPORT NUMBER: 2987 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: TMS4060JL
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC/METAL DIP
QUANTITY FAILED: 2

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: TEXAS INSTRUMENTS DATE CODE: 7521
SCREEN CLASS: D COMPLEXITY: 4096 B
NUMBER OF PINS: 22
TIME TO DETECTION: 0

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TM#5229

MFEF REPORT NUMBER: 3083 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: MWS5501D
DEVICE TECHNOLOGY: CMOS/SOS
PACKAGE: CERAMIC/METAL DIP
QUANTITY FAILED: 3

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: RCA DATE CODE: 640
SCREEN CLASS: D COMPLEXITY: 1024 B
NUMBER OF PINS: 16
TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: PACKAGE LEAD FRAME/EXTERNAL LEADS
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TM#5940

MFEF REPORT NUMBER: 3103 MFEF REPORT DATE: 0

DATA SOURCE: FP-0001 SOURCE: N/R
DEVICE FUNCTION: MEMORY
PART NUMBER: 93L422
DEVICE TECHNOLOGY: TTL
PACKAGE: HERMETIC N/R
QUANTITY FAILED: 4

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 1024 B
NUMBER OF PINS: 24
TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: INDUCED (NOC)
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS: TM#6115

MFEF REPORT NUMBER: 3123 MFEF REPORT DATE: 0

DATA SOURCE: FM-0007 SOURCE: BURN-IN
DEVICE FUNCTION: MEMORY
PART NUMBER: D3636
DEVICE TECHNOLOGY: TTL
PACKAGE: EPOXY DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: RAM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 2048 B
NUMBER OF PINS: 40
TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3128 MFEF REPORT DATE: 0

DATA SOURCE: FM-0007 SOURCE: BURN-IN
DEVICE FUNCTION: MEMORY
PART NUMBER: CH355
DEVICE TECHNOLOGY: NMOS
PACKAGE: CERAMIC/METAL DIP
QUANTITY FAILED: 1

DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
CIRCUIT TYPE: ROM
PART MANUFACTURER: INTEL DATE CODE: 0
SCREEN CLASS: D COMPLEXITY: 16384 B
NUMBER OF PINS: 40
TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3129 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: C8355 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3141 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: C8185 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: OXIDE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3142 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: P8185 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: IONIC DRIFT
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3143 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: P8185 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 3 TIME TO DETECTION: 48

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3144 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: P8185 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 2 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: WORKMANSHIP
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3145 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: BURN-IN DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: P8185 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 8192 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 48

FAILURE INDICATOR: DEGRADED NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3146 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: P8155/56 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D-1 COMPLEXITY: 2048 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3147 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: D8155/56 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: D COMPLEXITY: 2048 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 40
QUANTITY FAILED: 1 TIME TO DETECTION: 168

FAILURE INDICATOR: LEAKAGE NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3181 MFEF REPORT DATE: 0

DATA SOURCE: PM-0007 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: D3636 PART MANUFACTURER: INTEL DATE CODE: 0
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: D COMPLEXITY: 16384 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 500

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3230 MFEF REPORT DATE: 7905

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: TA10669 PART MANUFACTURER: RCA DATE CODE: 7910
DEVICE TECHNOLOGY: CMOS/SOS SCREEN CLASS: B-2 COMPLEXITY: 1024 B
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: VERIFIED SHORT NOC FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: DISLOCATION DEFECT CAUSE: FATIGUE
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: DEVICES FAILED DUE TO EPOXY BOND DISLOCATING CAUSING LEADS SHORTING TO PKG LID STRESS WAS CNST ACC,MECH SHK AND THRM SHK

MFEF REPORT NUMBER: 3231 MFEF REPORT DATE: 0

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: TA10670 PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS/SOS SCREEN CLASS: B-2 COMPLEXITY: 1024 B
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: LEAKY
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: PRESSURE
ACTIVATING STRESS B: N/R

REMARKS: DEVICES FAILED HERMETICITY TEST (FINE LEAK)

MFEF REPORT NUMBER: 3232 MFEF REPORT DATE: 7903

DATA SOURCE: PA-0007 SOURCE: SCREENING DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: TA10670 PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS/SOS SCREEN CLASS: B-2 COMPLEXITY: 1024 B
PACKAGE: CERAMIC/METAL CC NUMBER OF PINS: 24
QUANTITY FAILED: 8 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: PACKAGE DIE ATTACH BOND
DEFECT DESCRIPTION: DISLOCATION DEFECT CAUSE: FATIGUE
ACTIVATING STRESS A: THERMO-MECHANICAL STRESS
ACTIVATING STRESS B: N/R

REMARKS: DEVICES FAILED DUE TO EPOXY FATIGUE STRESS WAS CNST ACC,MECH SHK AND THRM SHK DATE CODE ARE 7901V,7901X,7902B AND 7901W

MFEF REPORT NUMBER: 3270 MFEF REPORT DATE: 7605

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: REGISTER CIRCUIT TYPE: N/R
PART NUMBER: 4034 PART MANUFACTURER: RCA DATE CODE: 412
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: NONE COMPLEXITY: 56 G
PACKAGE: N/R N/R NUMBER OF PINS: 24
QUANTITY FAILED: 3 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: PACKAGE LEAD FRAME/EXTERNAL LEADS
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/K
ACTIVATING STRESS A: N/K
ACTIVATING STRESS B: N/R

REMARKS: TR#5070 EXTRANEOUS GOLD AND SILVER COATINGS ON EXTERNAL LEADS

MFEF REPORT NUMBER: 3299 MFEF REPORT DATE: 8004

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PERIPHERAL
PART NUMBER: CDP1852D PART MANUFACTURER: RCA DATE CODE: 0
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 8 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: INTERCONNECTS NOC
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TR#6428

MFEF REPORT NUMBER: 3300 MFEF REPORT DATE: 8004

DATA SOURCE: FP-0001 SOURCE: N/R DATA-TYPE: N/R APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PERIPHERAL
PART NUMBER: CDP1852D PART MANUFACTURER: RCA DATE CODE: 728
DEVICE TECHNOLOGY: CMOS SCREEN CLASS: D COMPLEXITY: 8 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 24
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS: TR#6358

MFEF REPORT NUMBER: 3479 MFEF REPORT DATE: 7705

DATA SOURCE: FP-0002 SOURCE: N/R DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: 93L415 PART MANUFACTURER: FAIRCHILD SEMI DATE CODE: 7648
DEVICE TECHNOLOGY: BIPOLAR (NOC) SCREEN CLASS: N/R COMPLEXITY: 1024 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 16
QUANTITY FAILED: 6 TIME TO DETECTION: 0

FAILURE INDICATOR: INPUT LEAKAGE FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: IMPROPER HANDLING
ACTIVATING STRESS A: ELECTROSTATIC DISCHARGE
ACTIVATING STRESS B: ELECTRICAL OVERSTRESS

REMARKS: A FOLLOW UP FUNCTIONAL EM TEST WAS PERFORMED IN WHICH ONLY ONE FAILED DUE TO A SHORTED GLITCH DIODE AT INPUT PIN S&X

MFEF REPORT NUMBER: 3688 MFEF REPORT DATE: 8107

DATA SOURCE: FE-0005 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147/B PART MANUFACTURER: INTEL DATE CODE: 8021
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: FUNCTIONAL ANOMALY NOC FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: GIDEP REPORT NO. GD-A-81-05

MFEF REPORT NUMBER: 3689 MFEF REPORT DATE: 8107

DATA SOURCE: FE-0005 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147/B PART MANUFACTURER: INTEL DATE CODE: 8021
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED HI FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: GIDEP REPORT NO. GD-A-81-05

MFEF REPORT NUMBER: 3690 MFEF REPORT DATE: 8107

DATA SOURCE: FE-0005 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147/B PART MANUFACTURER: INTEL DATE CODE: 8021
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MEMORY DATA LOSS FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: GIDEP REPORT NO. GD-A-81-05

MFEF REPORT NUMBER: 3691 MFEF REPORT DATE: 8107

DATA SOURCE: FE-0005 SOURCE: N/R DATA-TYPE: EQUIPMENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: RAM
PART NUMBER: MD2147/B PART MANUFACTURER: INTEL DATE CODE: 8021
DEVICE TECHNOLOGY: NMOS SCREEN CLASS: B-1 COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: OUTPUT LATCHED LOW FAILURE MODE: DIE NOC
DEFECT DESCRIPTION: CRACKED DEFECT CAUSE: PROCESS FLAW
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: GIDEP REPORT NO. GD-A-81-05

MFEF REPORT NUMBER: 3695 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/K
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM5353D PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 7940
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 18
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3697 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM6341J PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8048
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 4096 B
PACKAGE: CERAMIC DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: SURFACE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: IONIC

MFEF REPORT NUMBER: 3698 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM63S241N PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8046
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 2048 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: PARAMETER OUT OF TOL NOC FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: ELECTRICAL OVERSTRESS
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3700 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: ROM
PART NUMBER: MM5280D PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8051
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D COMPLEXITY: 8192 B
PACKAGE: CERAMIC/METAL DIP NUMBER OF PINS: 24
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: SURFACE
DEFECT DESCRIPTION: N/R DEFECT CAUSE: CONTAMINATION
ACTIVATING STRESS A: TEMPERATURE
ACTIVATING STRESS B: N/R

REMARKS: IONIC

MFEF REPORT NUMBER: 3703 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM63S140N PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8115
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: CORROSION
ACTIVATING STRESS A: HUMIDITY
ACTIVATING STRESS B: TEMPERATURE

REMARKS: METAL

MFEF REPORT NUMBER: 3705 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM53S140N PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8039
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 1 TIME TO DETECTION: 0

FAILURE INDICATOR: N/R FAILURE MODE: N/R
DEFECT DESCRIPTION: N/R DEFECT CAUSE: N/R
ACTIVATING STRESS A: N/R
ACTIVATING STRESS B: N/R

REMARKS:

MFEF REPORT NUMBER: 3706 MFEF REPORT DATE: 8110

DATA SOURCE: PM-0010 SOURCE: LIFE DATA-TYPE: COMPONENT LEVEL APPLICATION ENV: N/R
DEVICE FUNCTION: MEMORY CIRCUIT TYPE: PROM
PART NUMBER: MM63S140N PART MANUFACTURER: MONOLITHIC MEMORIES DATE CODE: 8047
DEVICE TECHNOLOGY: STTL SCREEN CLASS: D-1 COMPLEXITY: 1024 B
PACKAGE: EPOXY DIP NUMBER OF PINS: 16
QUANTITY FAILED: 2 TIME TO DETECTION: 0

FAILURE INDICATOR: MECHANICAL ANOMALY FAILURE MODE: N/R
DEFECT DESCRIPTION: CORRODED DEFECT CAUSE: CORROSION
ACTIVATING STRESS A: HUMIDITY
ACTIVATING STRESS B: TEMPERATURE

REMARKS: METAL

REFERENCES

1. Hald, A. Statistical Theory with Engineering Applications, Wiley, 1952.

2. Mann, N.R., R.E. Schafer and N.D. Singpurwalla, Methods for Statistical Analysis of Reliability and Life Data, Wiley, 1974.

3. Dey, K.A. "Correlation of Field Data with Reliability Prediction Models," RADC-TR-. to be published, early 1982.

4. MIL-HDBK-217C, "Reliability Prediction of Electronic Equipment," with Notice 1. 1 May 1980.

APPENDIX A

FAILURE EVENT RECORD STRUCTURE AND DEFINITIONS

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APPENDIX A
Definitions of the Five Major Failure Descriptor Categories

(1) Failure Indicator - Is the first externally detectable effect of a part failure

Example:

Indicator: Open

(2) Failure Mode - Specifies the internal location of the defect

Example:

Mode: Die

(3) Failure Defect Description - Is the actual flaw which causes the component to fail

Example:

Defect: Cracked

(4) Failure Defect Cause - Is the condition which activates or leads to the defect

Example:

Cause: Process Flaw

(5) Activating Stress "A" or "B" -Is usually an environmental stress which influences the rate of defect formation

Example:

Activating Stress "A": Thermo-Mechanical

Below each of the definitions for each of the five major failure descriptors is an example of each of the descriptors. These descriptors

would be the type of attributes which would be retrieved from a typical detailed part failure analysis, therefore providing an accurate overview of the failure occurrence from the initial failure indicator down to the activating stress for that particular failure. This link between each of the major failure descriptors can be seen in the example.

APPENDIX A

ILLUSTRATION OF FAILURE EVENT RECORD STRUCTURE

Failure Indicators

- Open
  - Verified Open
    - Unknown
    - Input
    - Output
    - Supply
    - Combination
    - Other
  - Intermittent Open
    - Unknown
    - Input
    - Output
    - Supply
    - Combination
    - Other
- Short
  - Verified Short
    - Unknown
    - Input
    - Output
    - Supply
    - Combination
    - Other
  - Intermittent Short
    - Unknown
    - Input
    - Output
    - Supply
    - Combination
    - Other
- Degraded
  - Unknown
  - Leakage
    - Unknown
    - Input
    - Output
    - Supply
    - Combination
    - Other
  - Parameter Out-of-Tolerance
    - Unknown
    - Output Voltage

Failure Modes

- Die
  - Unknown
  - Bulk Aspects
    - Unknown
    - Junction
    - Diffusion
    - Expitaxial Layer
    - Crystal
  - Metalization
    - Unknown
    - Oxide Step
    - PROM Fuze
    - Contact Window
    - Polysilicon Conductor
    - Multi-Level Interface
    - Multi-Layer Interface
    - Bond Pad
  - Oxide/Dielectric
    - Unknown
    - Gate Oxide/Dielectric
    - Field Oxide/Dielectric
    - Capacitor Dielectric
    - Crossover Dielectric
  - Glassivation
  - Surface
- Interconnects
  - Unknown
  - Wire
  - Wirebond
    - Unknown
    - Wirebond at Die Pad
      - Unknown
      - Die Pad Heel
      - Die Pad Neck
    - Wirebond at Lead Frame
      - Unknown
      - Lead Frame Heel
      - Lead Frame Neck
    - Beam Lead
      - Unknown
      - Die Pad
      - Lead Frame
    - Bump

APPENDIX A

ILLUSTRATION OF FAILURE EVENT RECORD STRUCTURE (Cont'd)

Failure Indicators (Cont'd)

Degraded (Cont'd)

- Input Voltage
- Input Offset Voltage
- Switching Characteristics
- Supply Current
- Propagation Delay
- Input Offset Current
- Gain Characteristics
- Dynamic Characteristics

Functional Anomaly

- Unknown
- Non-Func., Inoper., Catastrophic
- Improper Output
  - Unknown
  - Improper Logic State
  - Memory Data Loss
  - Improper Output Switching
  - Fluct./Oscillating Output
  - Distorted/Clipped Output
  - Crosstalk
- Output Latching
  - Unknown
  - Output Latched High
  - Output Latched Low

Mechanical Anomaly

Defect Description

- Brittle
- Broken
- Channel
- Chipout
- Cracked
- Crazed
- Delaminated
- Dislocation
- Etch Fault
- Etch Pit
- Extraneous Wire
- Flaking
- Fracture
- Hillock
- Impurities

Failure Modes (Cont'd)

Package

- Unknown
- Package Seal
- Package Lid
- Package Body
- Package Lead
- Die Attach Bond
- Package Encapsulant

Defect Cause

- Contamination
- Corrosion
- Dendrite Growth
- Dielectric Breakdown
- Electrolysis
- Electromigration
- Fatigue
- Growback
- Intermetallic Formation
- Ionic Drift
- Microplasma
- Oxidation
- Thermal Diffusion
- Workmanship
- Process Flaw
- Troubleshooting

Failure Activating Stress

- Electrical Overstress
- Electrostatic Discharge
- Current Stress
- Humidity
- Mechanical Stress
- Pressure
- Radiation-Nuclear
- Radiation-Electromagnetic
- Radiation-X-ray
- Temperature
- Thermo-Mechanical Stress
- Voltage Stress
- Voltage and Current Stress

APPENDIX A

ILLUSTRATION OF FAILURE EVENT RECORD STRUCTURE (Cont'd)

Defect Description (Cont'd)

Lifted
Loose
Mask Fault
Misaligned/Misplaced
Missing
Necked Down
Ohmic
Open (NOC)
Particle Bridge
Peeling
Pinhole
Pipe
Scratch
Short (NOC)
Smear
Spike
Stacking Fault
Voids
Zapped-Evaporated
Fault (NOC)
Flashover-Arc
Punch Through
Poor Plating
Discolored
Corroded
Melted-Fused
Diffusion Fault
Reversed
Deformed
Hole
Tunneled
Inadequate
Exposed
Mismarked
Swollen

APPENDIX B

ADDITIONAL RAC SERVICES

ADDITIONAL RAC SERVICES

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Retrospective Searches are conducted at a flat fee of $125 per search. If no references are identified, a $50 service charge will be made in lieu of the above. For best results, please call or write for assistance in formulating your search question. An extra charge, based on engineering time and costs, will be made for evaluating, extracting or summarizing information from the cited references.

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Consulting Service fees are determined by the costs incurred in the conduct of the designed work, including staff time and overhead, materials and other expenses. Work will be initiated upon receipt of a signed purchase order. We will be pleased to prepare firm cost proposals.

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Place orders or obtain additional information directly from the Reliability Analysis Center. Clearly specify the publications and services desired. Except for blanket purchase orders, prepayment is required. All foreign orders must be accompanied by a check drawn on a U.S. bank. Please make checks payable to IITRI/RAC.

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January 1982

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